ISSN 0022-0248

JOURNAL OF CRYSTAL GROWTH

VOLUME 170

MASTER INDEX

Volumes 161–170

EDITORS:

M. SCHIEBER (Principal Editor),
Hebrew University

R.S. FEIGELSON, Stanford University

D.T.J. HURLE, University of Bristol

R. KERN, Université Aix–Marseille

T. NISHINAGA, University of Tokyo

G.B. STRINGFELLOW, University of Utah

Last Issue of this Volume

CO-FOUNDERS: N. CABRERA, B. CHALMERS, F.C. FRANK
ADVISOR: R.A. LAUDISE

North-Holland

http://www.elsevier.nl

JCRGAE 161–170 (MI) 837–910 (1997)

Journal of Crystal Growth

EDITORIAL BOARD

M. SCHIEBER (Principal Editor)
Dept. Mater. Sci., School Appl. Sci. & Technol.
Hebrew University, Jerusalem 91904, Israel
Telefax: +972-2-5666 804

R. KERN
CRMC², CNRS, Campus Luminy, Case 913
F-13288 Marseille Cedex 9, France
Telefax: +33-91-418 916

R.S. FEIGELSON
Ctr. Materials Res., 105 McCullough Bldg.
Stanford Univ., Stanford, CA 94305-4045, USA
Telefax: +1-415-723 3044

T. NISHINAGA
Dept. Electron. Eng., Univ. of Tokyo
7-3-1, Hongo, Bunkyo-ku, Tokyo 113, Japan
Telefax: +81-3-5684-3974

D.T.J. HURLE
H.H. Wills Phys. Lab., Univ. Bristol
Tyndall Avenue
Bristol BS8 1TL, UK

G.B. STRINGFELLOW
Dept. Mater. Sci., 304 EMRO, Univ. of Utah
Salt Lake City, UT 84112, USA
Telefax: +1-801-581 4816

ASSOCIATE EDITORS

A. BARONNET (*Industrial, Biological, Molecular Crystals*)
CRMC², CNRS, Campus Luminy, Case 913
F-13288 Marseille Cedex 9, France
Telefax: +33-91-418 916

K.W. BENZ (*Microgravity, Electronic Materials*)
Kristallographisches Inst., Universität
Hebelstr. 25, D-79104 Freiburg, Germany
Telefax: +49-761-203 4369

A.A. CHERNOV (*Kinetics of Crystallization, Protein Crystallization*)
Inst. Crystallography, Acad. of Sciences
Leninskii Prosp., Moscow 117333, Russian Fed.
Telefax: +7-095-135 1011

A.Y. CHO (*Molecular Beam Epitaxy*)
Room 1C-323, AT&T Bell Laboratories
Murray Hill, NJ 07974-2070, USA
Telefax: +1-908-582 2043

B. COCKAYNE (*IOCG News*)
School of Metallurgy and Mater.
Univ. Birmingham, P.O. Box 363, Edgbaston, Birmingham
B15 2TT, UK
Telefax: +44-121-471 2207

S.R. CORIELL (*Theory*)
A153 Mater. Natl. Inst. of Standards & Technol.
Gaithersburgh, MD 20899-0001, USA
Telefax: +1-301-975 4553

M.E. GLICKSMAN (*Solidification*)
School of Eng., Mater. Eng. Dept., Rensselaer Polytechnic
Inst., Troy, NY 12180-3590, USA
Telefax: +1-518-276 8554

M.A.G. HALLIWELL (*X-ray Diffraction*)
Philips Analytical X-ray, Lelyweg 1
7602 EA Almelo, The Netherlands

T. HIBIYA (*Oxides, Melt Thermophysical Properties, Microgravity*)
Fundamental Res. Labs., NEC CORPORATION
34, Miyukigaoka, Tsukuba 305, Japan
Telefax: +81-298-566 136

H. KOMATSU (*Proteins Molecular Crystallization, Growth from Solutions*)
Inst. Mater. Res., Tohoku Univ.
Katahira 2-1-1, Sendai 980, Japan
Telefax: +81-22-215 2011

T.F. KUECH (*Thin Films and Electronic and Optical Devices*)
Dept. Chem. Eng., Univ. Wisconsin-Madison
Madison, WI 53706, USA
Telefax: +1-608-265 3782

A. McPHERSON (*Protein Growth*)
Dept. Biochemistry, Univ. of California
Riverside, CA 92521, USA
Telefax: +1-909-787 3790

P.A. MORRIS HOTSENPILLER (*Electrooptical Crystals, Book Reviews, Oxide Thin Films*)
E.I. du Pont de Nemours & Co., Exp. Station
Wilmington, DE 19888-0358, USA
Telefax: +1-302-695 1664

J.B. MULLIN (*Semiconductors*)
EMC, "The Hoo", Brockhill Road
West Malvern, Worcs., WR14 4DL, UK
Telefax: +44-1684-575 591

K. NAKAJIMA (*Liquid and Vapor Phase Epitaxy*)
Integrated Mater. Lab., Fujitsu Labs. Ltd.
Morinosato-Wakamiya 10-1, Atsugi 243-01, Japan
Telefax: +81-462-48 3473

H. OHNO (*Epitaxy*)
Research Inst. of Electrical Commun.
Tohoku Univ., Sendai 980 77, Japan
Telefax: +81-22-217 5553

K. PLOOG (*Molecular Beam Epitaxy*)
Paul-Drude-Inst. für Festkörperelektronik
Hausvogteiplatz 5–7, D-10117 Berlin, Germany
Telefax: +49-30-203 77201

F. ROSENBERGER (*Protein Crystallization, Fluid Dynamics*)
Center for Microgravity and Materials Research
Univ. Alabama, Huntsville, AL 35899, USA
Telefax: +1-205-890 6791

R.W. ROUSSEAU (*Solution Growth, Industrial Crystallization*)
School of Chem. Eng., Georgia Inst. of Technol.
Atlanta, GA 30332-0100, USA
Telefax: +1-404-894 2866

K. SATO (*Biocrystallization and Organic Crystals*)
Fac. Appl. Biol. Sci., Hiroshima Univ.
Higashi-Hiroshima 724, Japan
Telefax: +81-824-227 062

L.F. SCHNEEMEYER (*Superconductivity, Oxides, Novel Materials*)
Room 1A-363, AT&T Bell Labs.
Murray Hill, NJ 07974-2070, USA
Telefax: +1-908-582 2521

D.W. SHAW (*Semiconductors, Epitaxy, Devices*)
Texas Instruments Inc., P.O. Box 655936, MS 147
Dallas, TX 75265, USA
Telefax: +1-214-995 7785

I. SUNAGAWA (*Minerals*)
3-54-2 Kashiwa-cho, Tachikawa-shi
Tokyo 190, Japan
Telefax: +81-425-35 3637

G. VAN TENDELOO (*Electron Microscopy, Fullerenes, Superconductivity*)
University of Antwerp, RUCA
Groenenborgerlaan 171, B-2020 Antwerp, Belgium
Telefax: +32-3-2180 217

A.F. WITT (*Semiconductor Crystals*)
Dept. of Metall. & Mater. Sci., Massachusetts
Inst. of Technol., Cambridge, MA 02139, USA
Telefax: +1-617-253 5827

A. ZANGWILL (*Theory (Epitaxy)*)
School of Physics, Georgia Inst. of Technol.
Atlanta, GA 30332, USA
Telefax: +1-404-894 9958

Scope of the Journal
Experimental and theoretical contributions are invited in the following fields: Theory of nucleation and growth, molecular kinetics and transport phenomena, crystallization in viscous media such as polymers and glasses. Crystal growth of metals, minerals, semiconductors, magnetics, inorganic, organic and biological substances in bulk or as thin films. Apparatus, instrumentation and techniques for crystal growth, and purification methods. Characterization of single crystals by physical and chemical methods.

Abstracted/Indexed in:
Aluminium Industry Abstracts; Chemical Abstracts; Current Contents: Physical, Chemical and Earth Sciences; EI Compendex Plus; Engineered Materials Abstracts; Engineering Index; INSPEC; Metals Abstracts.

Subscription Information 1997
Volumes 170–181 of Journal of Crystal Growth (ISSN 0022-0248) are scheduled for publication. (Frequency: semimonthly.) Prices are available from the publishers upon request. Subscriptions are accepted on a prepaid basis only. Issues are sent by SAL (Surface Air Lifted) mail wherever this service is available. Airmail rates are available upon request. Please address all enquiries regarding orders and subscriptions to:

Elsevier Science B.V., Order Fulfilment Department
P.O. Box 211, 1000 AE Amsterdam, The Netherlands
Tel: +31 20 485 3642; Fax: +31 20 485 3598

Claims for issues not received should be made within six months of our publication (mailing) date.

US mailing notice – *Journal of Crystal Growth* (ISSN 0022-0248) is published semimonthly by Elsevier Science B.V., Molenwerf 1, P.O. Box 211, 1000 AE Amsterdam, The Netherlands. Annual subscription price in the USA is US $7081 (valid in North, Central and South America only), including air speed delivery. Periodicals postage paid at Jamaica NY 11431. US postmasters: Send address changes to Journal of Crystal Growth, Publications Expediting, Inc., 200 Meacham Avenue, Elmont NY 11003. Airfreight and mailing in the USA by Publications Expediting.

∞ The paper used in this publication meets the requirements of ANSI/NISO Z39.48-1992 (Permanence of Paper)

PRINTED IN THE NETHERLANDS

North-Holland, an imprint of Elsevier Science

ELSEVIER

Journal of Crystal Growth 161–170 (1997) 837–895

JOURNAL OF CRYSTAL GROWTH

Author index to volumes 161–170

Aarik, J., A. Aidla, V. Sammelselg, H. Siimon and T. Uustare, Control of thin film structure by reactant pressure in atomic layer deposition of TiO_2 169 (1996) 496

Abbaschian, R., see Saghir, M.Z. 169 (1996) 110

Abbona, F. and A. Baronnet, A XRD and TEM study on the transformation of amorphous calcium phosphate in the presence of magnesium 165 (1996) 98

Abell, J.S., see Bi, Y.J. 166 (1996) 298

Abell, J.S., see Yang, G. 166 (1996) 820

Abernathy, C.R., see Mackenzie 164 (1996) 143

Abernathy, C.R., see Santana 164 (1996) 248

Abernathy, C.R., see Antonell 164 (1996) 420

Abraham, R., see Wang, X.L. 167 (1996) 93

Abrosimov, N.V., S.N. Rossolenko, V. Alex, A. Gerhardt and W. Schröder, Single crystal growth of $Si_{1-x}Ge_x$ by the Czochralski technique 166 (1996) 657

Achiba, Y., see Tachibana, M. 166 (1996) 883

Adachi, H., see Nitanai, Y. 168 (1996) 280

Adam, D., see Ortion, J.M. 170 (1997) 674

Adam, J.D., see Singh, N.B. 166 (1996) 364

Adamik, M., see Hashimoto, M. 166 (1996) 792

Addadi, L., see Tunik, L. 167 (1996) 748

Adinolfi, S., see Sica, F. 168 (1996) 192

Adler, F., see Geiger, M. 170 (1997) 558

Aevarsson, A., see Garber, M. 168 (1996) 301

Aggarwal, M.D., W.S. Wang, J. Choi, T. Myers, R.D. Clark, B.G. Penn, D.O. Frazier and M. Sanghadasa, Modified Bridgman–Stockbarger growth of a novel NLO organic crystal (2-methoxyphenyl)–methylene–propanedinitrile 166 (1996) 542

Agmon, I., see Thygesen, J. 168 (1996) 308

Aguiar, M.R. and R. Caram, Directional solidification of a Sn–Se eutectic alloy using the Bridgman–Stockbarger method 166 (1996) 398

Aguiló, M., see Solé, R. 166 (1996) 402

Aguiló, M., see Solé, R. 167 (1996) 681

Aguiló, M., see Solé, R. 169 (1996) 600

Ahern, B.S., see Weyburne, D.W. 170 (1997) 77

Åhman, J., see Bolt, R. 166 (1996) 537

Ahmed, M.U., E.D. Jones, J.B. Mullin and N.M. Stewart, Two stream diffusion of Hg into CdTe 161 (1996) 223

Ahuja, M.N., see Sabharwal, S.C. 169 (1996) 304

Aidla, A., see Aarik, J. 169 (1996) 496

Aiga, M., see Takiguchi, T. 170 (1997) 705

Ailey, S.K., see Davis 164 (1996) 132

Aina, L., see Thompson, A.G. 170 (1997) 92

Ainger, F.W., see Galambos, L. 167 (1996) 660

Ainger, F.W., see Erdei, S. 167 (1996) 670

Akane, T., M. Umekawa, S. Matsumoto and H. Higuchi, Heteroepitaxial melt-regrowth of $Si_{1-x}Ge_x/Si(100)$ formed by laser melt mixing of photochemically deposited Ge films and Si substrate 167 (1996) 32

Akao, M., see Ito 163 (1996) 311

Akasaki, I. and H. Amano, Crystal growth of column-III nitride semiconductors and their electrical and optical properties 163 (1996) 86

Aksenova, L.L., see Givargizov 162 (1996) 73

Al-Allak, H.M., see Loginov 161 (1996) 159

Albrecht, M., see Kühnle 163 (1996) 470

Albrecht, M., see Voigt, A. 166 (1996) 694

Albrecht, M., S. Christiansen, J. Michler, H.P. Strunk, P.O. Hansson and E. Bauser, Locally varying chemical potential and growth surface profile: a case study on solution grown Si(Ge)/Si 167 (1996) 24

Albrecht, P., see Künzel 164 (1996) 449

Alex, V., see Abrosimov, N.V. 166 (1996) 657

Alexander, J.I.D., see Garandet 165 (1996) 471

Alexander, W.B., see Wickenden, A.E. 170 (1997) 367

Alexandre, F., see Legay 164 (1996) 314

Alexandru, H.V., C. Berbecaru, A. Grancea and V. Iov, KDP prismatic faces: kinetics and the mechanism of their growth from solutions 166 (1996) 162

Alexandru, H.V., Growth kinetic of prismatic faces of ammonium dihydrogen phosphate crystal in solutions 169 (1996) 347
Alexeev, A.N. and S.Yu. Karpov, Conditions of excess liquid phase formation during molecular beam epitaxy of III–V ternary compounds 162 (1996) 15
Alexeev, A.N., S.Yu. Karpov, Yu.V. Pogorelsky and I.A. Sokolov, RHEED study of $c(4\times4)\rightarrow(2\times4)$ transition on GaAs(001) surface 166 (1996) 72
Alexeev, A.N., S.Yu. Karpov, M.A. Maiorov, V.E. Myachin, Yu.V. Pogorelsky and I.A. Sokolov, Thermal etching of binary and ternary III–V compounds under vacuum conditions 166 (1996) 167
Alford, T.L., see Barbero 165 (1996) 57
Algra, E., see Werner 164 (1996) 223
Al-Karadaghi, S., see Garber, M. 168 (1996) 301
Alkemade, P., see Werner 164 (1996) 223
Allegrini, M., see Gennari, S. 166 (1996) 309
Allen, S.J., see Sadwick 164 (1996) 285
Allovon, M., see Legay 164 (1996) 314
Almgren, J., see Bolt, R. 166 (1996) 537
Althaus, M., K. Sonnenberg, E. Küssel and R. Naeven, Some new design features for vertical Bridgman furnaces and the investigation of small angle grain boundaries developed during VB growth of GaAs 166 (1996) 566
Alvarez, J.C., see Harada 163 (1996) 31
Alvarez, J.C., see Sokolov, N.S. 169 (1996) 40
Alves, E., see Sochinskii 161 (1996) 195
Amano, C., A. Rudra, P. Grunberg, J.F. Carlin and M. Ilegems, Growth temperature dependence of the interfacet migration in chemical beam epitaxy of InP on non-planar substrates 164 (1996) 321
Amano, H., see Akasaki 163 (1996) 86
Ambacher, O., R. Dimitrov, D. Lentz, T. Metzger, W. Rieger and M. Stutzmann, Growth of GaN/AlN by low-pressure MOCVD using triethylgallium and tritertbutylaluminium 167 (1996) 1
Ambacher, O., see Fischer, R.A. 170 (1997) 139
Ambacher, O., R. Dimitrov, D. Lentz, T. Metzger, W. Rieger and M. Stutzmann, Growth of GaN/AlN and AlGaN by MOCVD using triethylgallium and tritertiarybutylaluminium 170 (1997) 335
Amemiya, M., see Okajima 165 (1996) 37
Amon, J., D. Zemke, B. Hoffmann and G. Müller, Growth of 2″ InP and GaAs crystals by the vertical gradient freeze (VGF) technique and characterization 166 (1996) 646
Anagnostopoulos, K., see Thygesen, J. 168 (1996) 308
Anan, T., see Shimomura 162 (1996) 121
Anand, S., see Carlsson, N. 170 (1997) 127
Ancilotti, M., see Benchimol 164 (1996) 22
Anders, M.J., see Hageman, P.R. 170 (1997) 270
Anders, M.J., see Bastos, P.L. 170 (1997) 710
Anderson, D.M., M.G. Worster and S.H. Davis, The case for a dynamic contact angle in containerless solidification 163 (1996) 329
Anderson, T.J., see Burgess, D.R. 166 (1996) 763
Ando, H., S. Yamaura and T. Fujii, Recent progress in the multi-wafer CBE system 164 (1996) 1
Ando, H., see Kinoshita, K. 166 (1996) 266
Ando, H., Recent progress in multi-wafer CBE systems 170 (1997) 16
Ando, H., see Ando, S. 170 (1997) 719
Ando, M., see Ozawa, T. 166 (1996) 463
Ando, S., N. Kobayashi, H. Ando and Y. Horikoshi, Hexagonal facet laser with optical waveguides grown by flow-rate modulation epitaxy 170 (1997) 719
Ando, Y., M. Ohkohchi and M. Wang, Regrowth of carbon nanotubes and nanoparticles 166 (1996) 888
Andrieu, S., see Snoeck, E. 167 (1996) 143
Androussi, Y., A. Lefebvre, T. Benabbas, P. François, C. Delamarre, J.Y. Laval and A. Dubon, Dislocation introduction in the initial stages of MBE growth of highly strained $In_{0.30}Ga_{0.70}As/GaAs$ structures 169 (1996) 209
Ang, H.M., see Chan, V.A. 166 (1996) 1009
Anilkumar, A.V., see Shen 165 (1996) 438
Ansari, R.R., K.I. Suh, A. Arabshahi, W.W. Wilson, T.L. Bray and L.J. DeLucas, A fiber optic probe for monitoring protein aggregation, nucleation and crystallization 168 (1996) 216
Anselmo, A., J. Koziol and V. Prasad, Full-scale experiments on solid-pellets feed continuous Czochralski growth of silicon crystals 163 (1996) 359
Antonell, M.J., C.R. Abernathy and R.W. Gedridge, Tellurium doping of InP using triisopropylindium–diisopropyltellurium (TIPIn–DIPTe) 164 (1996) 420
Anzawa, S., see Kinoshita, K. 166 (1996) 266
Aogaki, R., see Tadano, A. 166 (1996) 1111
Aoki, H., see Ito 163 (1996) 311
Aoki, M., see Suzuki, M. 170 (1997) 661
Aoki, S., see Funato, M. 170 (1997) 276
Aoudia, A., see Martel 161 (1996) 250
Aoudia, A., see Zerrai 161 (1996) 264
Aoudia, A., see Rzepka 161 (1996) 286
Aoyagi, Y., see Zhang 164 (1996) 28
Aoyagi, Y., see Tanaka, S. 170 (1997) 329
Aoyama, K., 2D-crystallization of *Rhodococcus* 20S proteasome at the liquid–liquid interface 168 (1996) 198
Arabshahi, A., see Ansari, R.R. 168 (1996) 216
Arai, K., see Shishiguchi, S. 166 (1996) 689

Arai, K., see Shimizu, T. 166 (1996) 841
Arai, T., J. Hidaka, H. Tokunaga and K. Matsumoto, Highly uniform growth in a low-pressure MOVPE multiple wafer system 170 (1997) 88
Arai, Y., see Kinoshita, K. 166 (1996) 266
Arakawa, Y., see Kitamura, M. 170 (1997) 563
Arakcheeva, A., see Leonyuk, L. 167 (1996) 102
Araki, T., see Inoue 164 (1996) 88
Araki, T., see Fujiwara, S. 167 (1996) 357
Arata, Y., see Mizutani, R. 168 (1996) 253
Ardoino, M., see Zeng, L. 166 (1996) 528
Arès, R., S.P. Watkins and C.A. Tran, Breakdown of self-limiting behaviour in InAs/GaAs heterostructures grown by atomic layer epitaxy 170 (1997) 574
Arès, R., see Watkins, S.P. 170 (1997) 788
Arias, J.M., see González-Muñoz 163 (1996) 434
Arima, Y., see Irisawa 163 (1996) 22
Armour, E., see Thompson, A.G. 170 (1997) 92
Arnold, E., see Schall 165 (1996) 293
Arnold, E., see Schall 165 (1996) 299
Artymowicz, D.M., B.M. Lairson and B.M. Clemens, Formation of ordered tetragonal PtCo from epitaxial Pt/Co multilayers 169 (1996) 83
Asahi, H., see Yamamoto 164 (1996) 117
Asahi, T., O. Oda, Y. Taniguchi and A. Koyama, Growth and characterization of 100 mm diameter CdZnTe single crystals by the vertical gradient freezing method 161 (1996) 20
Asai, S., see Okajima 165 (1996) 37
Asami, K., see Yamamoto 164 (1996) 117
Asanuma, M., see Tadano, A. 166 (1996) 1111
Ashwin, M.J., see Sato 165 (1996) 345
Aspar, B., see Prieur, E. 166 (1996) 329
Aspnes, D.E., see Kamiya 163 (1996) 67
Aspnes, D.E., see Dietz 164 (1996) 34
Astier, J.P., see Veesler, S. 168 (1996) 124
Ataka, M., see Tanaka, S. 168 (1996) 44
Ataka, M., see Izumi, K. 168 (1996) 106
Ataka, M., see Kudo, N. 168 (1996) 118
Attolini, G., see Gennari, S. 166 (1996) 309
Ausloos, M., see Stassen, S. 166 (1996) 281
Ausloos, M., see Cloots, R. 166 (1996) 816
Ausloos, M., see Vandewalle, N. 169 (1996) 79
Ayers, J.E., see Gokhale 165 (1996) 25
Ayers, J.E., see Bao, K.X. 170 (1997) 497
Azzi, A., see Zhou, M. 168 (1996) 142
Azzi, A., see Zhu, D.-W. 168 (1996) 275

Baalbaki, B., see Vuillard, L. 168 (1996) 150
Babanin, A., see Dmitriev, V. 166 (1996) 601
Babonas, G.-J., see Leonyuk, L. 167 (1996) 102
Bach, H., see Brinkmann 163 (1996) 369
Bach, H., see Stauche, P. 166 (1996) 390
Bachem, K.H., see Davidson 164 (1996) 396
Bachmann, K.J., see Dietz 164 (1996) 34
Badaljan, E., see Pfeifer, J. 169 (1996) 727
Badescu, V. and M. Momirlan, Statistics of TiO_2 crystal growth in air on a metallic surface heated at temperatures in the range of 900–1100°C 169 (1996) 309
Bähr, G., see Helmers 165 (1996) 381
Baker, J.E., see Islam, M.R. 170 (1997) 413
Baker, M. and M.B. Baker, A model for the ice–vapor interface at equilibrium 169 (1996) 393
Baker, M.B., see Baker, M. 169 (1996) 393
Balakrishna, V., see Singh 163 (1996) 398
Balbashov, A.M., S.G. Karabashev, Ya.M. Mukovskiy and S.A. Zverkov, Growth and giant magnetoresistance effect in La–Ca–Mn–O and La–Sr–Mn–O single crystals 167 (1996) 365
Baldochi, S.L., A.M.E. Santo, E. Martins, M. Duarte, M.M.F. Vieira, N.D. Vieira Jr. and S.P. Morato, Growth and characterization of $BaLiF_3$:TM (Ni^{2+}, Co^{2+}) for laser applications 166 (1996) 375
Baldochi, S.L., see Ranieri, I.M. 166 (1996) 423
Baldock, P., V. Mills and P.S. Stewart, A comparison of microbatch and vapour diffusion for initial screening of crystallization conditions 168 (1996) 170
Balibar, S., see Rolley, E. 166 (1996) 55
Balitskaya, L.V., see Balitsky 162 (1996) 142
Balitsky, V.S., T.M. Bublikova, L.V. Balitskaya and A.G. Kalinichev, Growth of high temperature β-quartz from supercritical aqueous fluids 162 (1996) 142
Ban, D., see Kaito, C. 167 (1996) 580
Banhart, F., see Zwanger 163 (1996) 445
Banhart, F., see Konuma, M. 166 (1996) 234
Banhart, F., see Silier, I. 166 (1996) 727
Bao, K.X., see Gokhale 165 (1996) 25
Bao, K.X., R. Mo, X.G. Zhang, S. Kalisetty, M. Gokhale, J. Robinson, G. Zhao, J.E. Ayers and F.C. Jain, Compositional control of $Cd_xZn_{1-x}Se$ grown by photoassisted organometallic vapor phase epitaxy 170 (1997) 497
Baranowski, J.M., see Leszczynski, M. 169 (1996) 235
Barashov, L.V., see Terada, Y. 167 (1996) 369
Barata, P.A. and M.L. Serrano, Salting-out precipitation of potassium dihydrogen phosphate (KDP). II. Influence of agitation intensity 163 (1996) 426
Barber, D.B., see Mass 165 (1996) 250
Barbero, C.J., C. Deng, T.W. Sigmon, S.W. Russell and T.L. Alford, The fabrication of nickel and chromium silicide using an XeCl excimer laser 165 (1996) 57
Barna, A., see Hashimoto, M. 166 (1996) 792
Barna, P.B., see Hashimoto, M. 166 (1996) 792
Baronnet, A., see Abbona 165 (1996) 98
Baronnet, A. and B. Devouard, Topology and crystal growth of natural chrysotile and polygonal serpentine 166 (1996) 952

Bartels, H., see Thygesen, J. 168 (1996) 308
Baruchel, J., see Prieur, E. 166 (1996) 329
Basilavecchia, M., see Gurskii, A.L. 170 (1997) 533
Baskar, K., see Soga, T. 170 (1997) 447
Baskaran, S., see Noever, D. 167 (1996) 221
Basmaji, P., see González-Borrero, P.P. 169 (1996) 424
Bastos, P.L., M.J. Anders, M.M.G. Bongers, P.R. Hageman and L.J. Giling, Temperature dependence on the emerging crystal habit of GaInP deposited on nonplanar {001}GaAs substrates 170 (1997) 710
Bates, J.R., see Miles 161 (1996) 148
Bauknecht, A., see Geiger, M. 170 (1997) 558
Baumeister, H., see Veuhoff 164 (1996) 402
Baumeister, H., see Keidler, M. 170 (1997) 161
Baumgartl, J., see Friedrich, J. 167 (1996) 45
Baumgartl, J. and G. Müller, The use of magnetic fields for damping the action of gravity fluctuations (g-jitter) during crystal growth under microgravity 169 (1996) 582
Bauser, E., see Konuma, M. 166 (1996) 234
Bauser, E., see Silier, I. 166 (1996) 727
Bauser, E., see Albrecht, M. 167 (1996) 24
Beam III, E.A. and H.F. Chau, The use of CBr_4 and $SiBr_4$ doping in MOMBE and application to InP-based heterojunction bipolar transistor structures 164 (1996) 389
Beanland, R., see Boyd 164 (1996) 51
Beatty, K.M., see Jackson 163 (1996) 461
Beaumont, B., M. Vaille, T. Boufaden, B. el Jani and P. Gibart, High quality GaN grown by MOVPE 170 (1997) 316
Beccard, R., G. Lengeling, D. Schmitz, Y. Gigase and H. Jürgensen, Replacement of hydrides by TBAs and TBP for the growth of various III–V materials in production scale MOVPE reactors 170 (1997) 97
Becht, M., F. Wang, J.G. Wen and T. Morishita, Evolution of the microstructure of oxide thin films 170 (1997) 799
Becker, R.A., see Tanneberger, U. 166 (1996) 1074
Beckham, C., see Thompson, A.G. 170 (1997) 92
Behet, M., P. Schneider, D. Moulin, K. Heime, J. Woitok, J. Tümmler, J. Hermans and J. Geurts, Low pressure metalorganic vapor phase epitaxy and characterization of (Al,Ga)Sb/GaSb heterostructures 167 (1996) 415
Behet, M., see Tümmler, J. 170 (1997) 772
Behet, M., see von Eichel-Streiber, C. 170 (1997) 783
Behr, G., see Werner 165 (1996) 258
Behrend, J., M. Wassermeier and K.H. Ploog, Virtual-surfactant mediated epitaxy of InAs on GaAs(001) studied by scanning tunneling microscopy 167 (1996) 440
Behres, A., H. Werner, A. Kohl and K. Heime, InP growth on ion-implanted InP substrate: a new method to achieve selective area MOVPE 170 (1997) 655
Behres, A., see Lakner, H. 170 (1997) 732
Behrsing, R., see Earnest, T. 168 (1996) 248
Benabbas, T., see Androussi, Y. 169 (1996) 209
Ben Amar, G., see Horowitz, A. 167 (1996) 183
Benchimol, J.L. and M. Ancilotti, Simple high conductance gas line for high growth rate and low transient 164 (1996) 22
Benchimol, J.L., see Lamare 164 (1996) 122
Benchimol, J.L., see Legay 164 (1996) 314
Ben Hadid, H. and D. Henry, Numerical simulation of convective three-dimensional flows in a horizontal cylinder under the action of a constant magnetic field 166 (1996) 436
Benndorf, G., see Kirpal, G. 170 (1997) 167
Bennema, P., On the crystallographic and statistical mechanical foundations of the forty-year old Hartman–Perdok theory 166 (1996) 17
Bennema, P., see Liu, X.Y. 166 (1996) 112
Bennema, P., see Liu, X.Y. 166 (1996) 117
Bennett, W.S., see Thygesen, J. 168 (1996) 308
Ben Omar, N., see González-Muñoz 163 (1996) 434
Benory, E., see Weiss, E. 166 (1996) 745
Bensaoula, A., see Taferner 164 (1996) 167
Bensaoula, A., W.T. Taferner, E. Kim and A. Bousetta, The nitridation of GaAs and GaN deposition on GaAs examined by in situ time-of-flight low energy ion scattering and RHEED 164 (1996) 185
Bensaoula, A. and A. Freundlich, Strain balanced GaP/GaAs/InP/GaAs superlattices: structural and electronic properties 164 (1996) 271
Bensaoula, A., see Vilela 164 (1996) 465
Benz, K.W., see Laasch 161 (1996) 34
Benz, K.W., see Christmann 161 (1996) 259
Benz, K.W., see Eiche 161 (1996) 271
Benz, K.W., see Cröll, A. 166 (1996) 239
Benz, K.W., see Eiche, C. 166 (1996) 245
Benz, K.W., see Fiederle, M. 166 (1996) 256
Benz, K.W., see Kloess, G. 166 (1996) 319
Benz, K.W., see Tegetmeier, A. 166 (1996) 651
Berbecaru, C., see Alexandru, H.V. 166 (1996) 162
Beregi, E., see Hartmann, E. 166 (1996) 109
Berends, E.M., see Domingo, C. 166 (1996) 989
Berglund, K.A., see Uusi-Penttilä, M. 166 (1996) 967
Bergmann, R., see Kühnle 163 (1996) 470
Bergmann, R.B., Optical in situ monitoring of solid phase crystallization of amorphous silicon 165 (1996) 341
Bergunde, T., M. Dauelsberg, L. Kadinski, Yu.N. Makarov, M. Weyers, D. Schmitz, G. Strauch and H. Jürgensen, Heat transfer and mass transport in a multiwafer MOVPE reactor: modelling and experimental studies 170 (1997) 66
Bergunde, T., see Kurpas, P. 170 (1997) 203

Berkovitch-Yellin, Z., see Thygesen, J. 168 (1996) 308
Berkstresser, G.W., see Fratello, V.J. 166 (1996) 878
Berlouis, L.E.A., see Gupta 165 (1996) 19
Bermúdez, V., P.S. Dutta, M.D. Serrano and E. Diéguez, In situ poling of $LiNbO_3$ bulk crystal below the Curie temperature by application of electric field after growth 169 (1996) 409
Bernard, Y., see Lefaucheux 165 (1996) 90
Bernard, Y., see Vidal, O. 168 (1996) 40
Bernardi, S., see Sochinskii 161 (1996) 195
Berretta, J.R., see Ranieri, I.M. 166 (1996) 423
Bersano, G., see Marmo, L. 166 (1996) 1027
Bert, N., see Dmitriev, V. 166 (1996) 601
Bertone, D., A. Bricconi, R.Y. Fang, L. Greborio, G. Magnetti, M. Meliga and R. Paoletti, MOCVD regrowth of semi-insulating InP and p–n junction blocking layers around laser active stripes 170 (1997) 715
Bertram, F., see Heinrichsdorff, F. 170 (1997) 568
Bevan, M.J., H.D. Shih, H.Y. Liu, A.J. Syllaios and W.M. Duncan, Growth of high quality ZnSe on closely lattice-matched InGaAs substrates by metal organic chemical vapor deposition 170 (1997) 467
Beyer, R., see Prösch, G. 170 (1997) 537
Bharuth-Ram, K., see Restle 161 (1996) 168
Bharuth-Ram, K., see Jahn 161 (1996) 172
Bhat, I.B., see Dakshina Murthy, S. 170 (1997) 193
Bhattacharya, A., see Mawst, L.J. 170 (1997) 383
Bi, R.-C., see Pan, J.-S. 168 (1996) 227
Bi, W.G., X.B. Mei and C.W. Tu, Growth studies of GaP on Si by gas-source molecular beam epitaxy 164 (1996) 256
Bi, W.G. and C.W. Tu, Highly strained $In_yGa_{1-y}P/GaP$ quantum wells grown on GaP and on an $In_{x/2}Ga_{1-x/2}P$ buffer layer by gas-source molecular beam epitaxy 165 (1996) 210
Bi, Y.J., J.S. Abell and D. Fort, Crystal growth of iron-based compounds by the cold-crucible Czochralski technique 166 (1996) 298
Biasiol, G., E. Martinet, F. Reinhardt, A. Gustafsson and E. Kapon, Low-pressure OMCVD growth of AlGaAs vertical quantum wells on non-planar substrates 170 (1997) 600
Biasiol, G., see Reinhardt, F. 170 (1997) 689
Bicelli, L.P., see Kozlov 165 (1996) 421
Biderman, S., see Horowitz, A. 167 (1996) 183
Bidnyk, S., see Wong 164 (1996) 159
Biefeld, R.M., H.C. Chui, B.E. Hammons, W.G. Breiland, T.M. Brennan, E.D. Jones, M.H. Kim, P. Grodzinski, K.H. Chang and H.C. Lee, High purity GaAs and AlGaAs grown using tertiarybutylarsine, trimethylalumium, and trimethylgallium 163 (1996) 212
Bieg, B., see Szatkowski 161 (1996) 282
Bieger, W., see Werner 165 (1996) 258
Bignazzi, A., E. Grilli, M. Guzzi, M. Radice, A. Bosacchi, S. Franchi and R. Magnanini, Low temperature photoluminescence of tellurium-doped GaSb grown by molecular beam epitaxy 169 (1996) 450
Bilgram, J.H., see Bisang, U. 166 (1996) 207
Bilgram, J.H., see Bisang, U. 166 (1996) 212
Billia, B., H. Jamgotchian and H. Nguyen Thi, Influence of sample thickness on cellular branches and cell–dendrite transition in directional solidification of binary alloys 167 (1996) 265
Billia, B., see Li, Q. 167 (1996) 277
Bimberg, D., see Dadgar, A. 170 (1997) 173
Bimberg, D., see Heinrichsdorff, F. 170 (1997) 568
Bimberg, D., see Kappelt, M. 170 (1997) 590
Bing, Y.H., see Yuan, D.R. 166 (1996) 545
Birch, J., see Radamson, H.H. 167 (1996) 495
Bisang, U. and J.H. Bilgram, The fractal dimension of xenon dendrites 166 (1996) 207
Bisang, U. and J.H. Bilgram, Dendritic solidification of xenon 166 (1996) 212
Bishop, J.B., see Long, M.M. 168 (1996) 233
Biwa, G., see Yaguchi, H. 170 (1997) 353
Blashenkov, M.N., see Nikolaev, A.E. 166 (1996) 607
Blickle, T., see Farkas, B. 166 (1996) 1064
Bliss, D.F., see Zhang, H. 169 (1996) 250
Blouin, J., see Gerbaud, V. 166 (1996) 172
Blumberg, R., see Kastner, M.J. 170 (1997) 188
Blumberg, R., see Hahn, B. 170 (1997) 472
Bocchi, C., A. Bosacchi, C. Ferrari, S. Franchi, P. Franzosi, R. Magnanini and L. Nasi, Determination of lattice parameters in the epitaxial AlSb/GaSb system by high resolution X-ray diffraction 165 (1996) 8
Bockowski, M., see Leszczynski, M. 169 (1996) 235
Böddeker, N., see Thygesen, J. 168 (1996) 308
Bogatyreva, S.V., see Smolsky, I.L. 166 (1996) 228
Boilot, J.-P., see Ricolleau, C. 166 (1996) 769
Boistelle, R., see Veesler, S. 168 (1996) 124
Boistelle, R., see El Moussaouiti, M. 169 (1996) 118
Boistelle, R., see Seyssiecq, I. 169 (1996) 124
Bolay, H., see Scholz, F. 170 (1997) 321
Bollmann, J., see Wienecke 161 (1996) 82
Bollmann, J., see Hermann 161 (1996) 181
Bolognesi, C.R., see Watkins, S.P. 170 (1997) 788
Bolt, R., M. Heim, J. Almgren and J. Åhman, A high temperature study of $CsTiOAsO_4$ and $RbTiOAsO_4$ 166 (1996) 537
Bongartz, M., see Hartmann, A. 170 (1997) 605
Bongers, M.M.G., Y. Li, J. te Nijenhuis and L.J. Giling, Structural analysis of $In_xGa_{1-x}As$ grown on Ge by low pressure metalorganic chemical vapour deposition 162 (1996) 7
Bongers, M.M.G., see Li 163 (1996) 195
Bongers, M.M.G., see Bastos, P.L. 170 (1997) 710
Bonnet, D., see Loginov 161 (1996) 159

Bonneté, F., O. Vidal, M.C. Robert and A. Tardieu, Gel techniques and small angle X-ray scattering to follow protein crystal growth 168 (1996) 185

Booker, G.R., M. Daly, P.C. Klipstein, M. Lakrimi, T.F. Kuech, Jiang Li, S.G. Lyapin, N.J. Mason, I.J. Murgatroyd, J.C. Portal, R.J. Nicholas, D.M. Symons, P. Vicente and P.J. Walker, Growth of InAs/GaSb strained layer superlattices by MOVPE. III. Use of UV absorption to monitor alkyl stability in the reactor 170 (1997) 777

Borghs, G., see Srnánek 165 (1996) 156

Born, E., see Fischer, R.A. 170 (1997) 139

Bornmann, S., see Dubs, C. 166 (1996) 836

Borodi, Gh., see Darabont, Al. 169 (1996) 89

Borshchevsky, A., see Caillat, T. 166 (1996) 722

Bosacchi, A., see Bocchi 165 (1996) 8

Bosacchi, A., see Bignazzi, A. 169 (1996) 450

Bosshard, Ch., see Pan 165 (1996) 273

Botea, M., see Stănculescu, F. 166 (1996) 183

Botez, D., see Mawst, L.J. 170 (1997) 383

Botha, J.R. and A.W.R. Leitch, Influence of growth interruption on the heterointerface morphology of InGaAs/GaAs strained quantum wells 169 (1996) 629

Böttcher, J., see Schelhase 164 (1996) 339

Boufaden, T., see Beaumont, B. 170 (1997) 316

Bouhaouss, A., see El Moussaouiti, M. 169 (1996) 118

Bouix, J., see Thévenot, V. 170 (1997) 251

Boulliard, J.C., see Zheng 162 (1996) 135

Bousetta, A., see Taferner 164 (1996) 167

Bousetta, A., see Bensaoula 164 (1996) 185

Bovin, J.-O., see Deppert, K. 169 (1996) 13

Boyd, A.R., T.B. Joyce and R. Beanland, An in-situ laser-light scattering study of the development of surface topography during GaAs and $In_xGa_{1-x}As$ chemical beam epitaxy 164 (1996) 51

Boyd, A.R., T.J. Bullough, T. Farrell and T.B. Joyce, Growth mechanisms and morphology of Ar^+ laser assisted CBE of GaAs 164 (1996) 71

Boyer, M., M.-O. Roy and M. Jullien, Dynamic light scattering study of precrystallizing ribonuclease solutions 167 (1996) 212

Brandle, C.D., see Fratello, V.J. 166 (1996) 774

Brandle, C.D., see Fratello, V.J. 166 (1996) 878

Brandon, S., D. Gazit and A. Horowitz, Interface shapes and thermal fields during the gradient solidification method growth of sapphire single crystals 167 (1996) 190

Braunger, D., T.A. Oberacker and H.W. Schock, Flux-enhanced growth of multi-source physical vapor deposited $SrGa_2S_4$:Ce,Cl electroluminescent thin films 167 (1996) 129

Bray, T.L., see Ansari, R.R. 168 (1996) 216

Brebrick, R.F., see Su, C.-H. 166 (1996) 736

Brehmer, D., see Sadwick 164 (1996) 285

Breiland, W.G., see Biefeld 163 (1996) 212

Bremond, G., see Martel 161 (1996) 250

Bremond, G., see Zerrai 161 (1996) 264

Brener, E.A., Three-dimensional dendritic growth 166 (1996) 339

Brennan, S., see Kisker 163 (1996) 54

Brennan, S., see Kamiya 163 (1996) 67

Brennan, T.M., see Biefeld 163 (1996) 212

Breton, R., see Zhou, M. 168 (1996) 142

Bricconi, A., see Bertone, D. 170 (1997) 715

Brinkman, A.W., see Loginov 161 (1996) 159

Brinkmann, M., T. Rex, H. Bach and K. Westerholt, Crystal growth of high-T_C superconductors $Pr_{2-x}Ce_xCuO_{4+\delta}$ with substitutions of Ni and Co for Cu 163 (1996) 369

Brinkmann, M., see Stauche, P. 166 (1996) 390

Brodsky, I., see Burtman, V. 166 (1996) 832

Bromley, P.A., see Wood, A.K. 170 (1997) 132

Brown, M., see Steiner, B. 169 (1996) 1

Brown, P.W., see Graham 165 (1996) 106

Bruchlos, G., see Dubs, C. 166 (1996) 836

Brück, E., H.J. Gelders, B.J. Harrison and A.A. Menovsky, Laser-heated fibre pedestal growth under UHV conditions 166 (1996) 394

Bruinsma, O.S.L., see van Leeuwen, M.L.J. 166 (1996) 1004

Brun, G., see Ferhat, M. 167 (1996) 122

Brunner, F., see Kurpas, P. 170 (1997) 442

Bruno, G., M. Losurdo and P. Capezzuto, On the use of remote RF plasma source to enhance III–V MOCVD technology 170 (1997) 301

Bryce, J.E., see Watkins, S.P. 170 (1997) 788

Bublikova, T.M., see Balitsky 162 (1996) 142

Bugge, F., see Knauer, A. 170 (1997) 281

Bullough, T.J., see Boyd 164 (1996) 71

Bullough, T.J., see Davidson 164 (1996) 383

Bullough, T.J., see Westwater, S.P. 170 (1997) 752

Bulman, G., see Dmitriev, V. 166 (1996) 601

Burak, V.S., see Luginets 162 (1996) 89

Burchard, A., R. Magerle, J. Freidinger, S.G. Jahn and M. Deicher, Defect recovery of ion-implanted CdTe 161 (1996) 128

Burchard, A., see Lindner, A. 170 (1997) 287

Burger, A., see Chen, K.-T. 166 (1996) 731

Burgess, D.R., P.A. Morris Hotsenpiller, T.J. Anderson and J.L. Hohman, Solid precursor MOCVD of heteroepitaxial rutile phase TiO_2 166 (1996) 763

Burghardt, H., see Prösch, G. 170 (1997) 537

Burianek, M., J. Liebertz and M. Mühlberg, Crystal growth and characterization of $LiPbPO_4$ 166 (1996) 361

Burk Jr., A.A. and L.B. Rowland, The role of excess silicon and in situ etching on 4H-SiC and 6H-SiC epitaxial layer morphology 167 (1996) 586

Burlitch, J.M., see Mass 165 (1996) 250
Burtman, V., M. Schieber, I. Brodsky, H. Hermon and Y. Yaroslavsky, Raman and infrared spectroscopy and transport properties of aged organometallic precursors used for the deposition of high-T_c superconducting films 166 (1996) 832
Busch, M.C., see Martel 161 (1996) 250
Buschmann, F., see Valdna 161 (1996) 164
Butler, C., see Capper 161 (1996) 104
Button, C.C., see Chen, Y.H. 170 (1997) 394
Butzke, S., see Werner 164 (1996) 223

Caballero, M.A., see Martínez-López, J. 166 (1996) 325
Cabré, R., see Solé, R. 166 (1996) 402
Cabré, R., see Solé, R. 167 (1996) 681
Čabrić, B., N. Danilović and B. Žižić, A crystallization cooler in a chamber furnace 169 (1996) 199
Cacciatore, C., see Rigo 164 (1996) 430
Cahen, D., see Lyubomirsky 161 (1996) 90
Caillat, T., J.-P. Fleurial and A. Borshchevsky, Bridgman-solution crystal growth and characterization of the skutterudite compounds $CoSb_3$ and $RhSb_3$ 166 (1996) 722
Calixto, E., P.J. Sebastian and A. Fernandez, Electro/electroless deposition and characterization of Cu–In precursors for CIS ($CuInSe_2$) films 169 (1996) 287
Canadell, E., see Figueras, A. 166 (1996) 798
Canselier, J.P., see Lin, C.H. 166 (1996) 104
Cao, J.Y., see Li 163 (1996) 348
Cao, J.Y., see Li, B. 169 (1996) 480
Cao, X., see Katabi, G. 166 (1996) 760
Capasso, S., see Sica, F. 168 (1996) 192
Capelle, B., see Zheng 162 (1996) 135
Capelle, B., see Martínez-López, J. 166 (1996) 325
Capelle, B., see Palmier, D. 166 (1996) 347
Capezzuto, P., see Bruno, G. 170 (1997) 301
Capik, R.J., see Wajid, A. 170 (1997) 237
Capper, P., E.S. O'Keefe, C. Maxey, D. Dutton, P. Mackett, C. Butler and I. Gale, Matrix and impurity element distributions in CdHgTe (CMT) and (Cd,Zn)(Te,Se) compounds by chemical analysis 161 (1996) 104
Caram, R., see Aguiar, M.R. 166 (1996) 398
Cardona, M., see Lin, C.T. 167 (1996) 612
Carlin, J.F., see Amano 164 (1996) 321
Carlin, J.F., A. Rudra and M. Ilegems, Pseudomorphic InGaAs/In(Ga)P bidimensional electron gas grown by chemical beam epitaxy 164 (1996) 470
Carlsson, N., see Seifert, W. 170 (1997) 39
Carlsson, N., S. Anand, S.-B. Carlsson, B. Gustafson, P. Omling, P. Ramvall, L. Samuelson, W. Seifert and Q. Wang, MOVPE growth of InP/GaInAs and GaAs/GaInP heterostructures for electronic transport applications 170 (1997) 127
Carlsson, S.-B., see Carlsson, N. 170 (1997) 127
Caro, J., see Figueras, A. 166 (1996) 798
Carpenter, G., see Van Hove 164 (1996) 154
Carr, N., see Wood, A.K. 170 (1997) 132
Carrà, S., S. Fogliani, M. Masi, L. Zanotti, C. Mucchino and C. Paorici, Melt–solid interface shape in LEC GaAs crystals: comparison between calculated and experimentally observed shapes 166 (1996) 641
Carstanjen, H.-J., see Scholz, U. 169 (1996) 575
Carter, M.J., see Miles 161 (1996) 148
Carter Jr., C.W., see Kuyper, L.F. 168 (1996) 155
Casanove, M.J., see Snoeck, E. 167 (1996) 143
Case, F.C., see Mitra, P. 170 (1997) 542
Cassanto, J.M., see Sygusch 162 (1996) 167
Cavagnat, R., see Oçafrain, A. 166 (1996) 414
Cerva, H., see Kappelt, M. 170 (1997) 590
Chait, A., see Pines, V. 167 (1996) 383
Chait, A., see Pines, V. 167 (1996) 777
Chait, A., see Pines, V. 169 (1996) 798
Chambers, J., see van Gelder, R.N.M.R. 166 (1996) 189
Chaminade, J.P., see Oçafrain, A. 166 (1996) 414
Champagne, M., see Ortion, J.M. 170 (1997) 674
Champness, C.H., see Shukri, Z.A. 166 (1996) 708
Chan, V.A. and H.M. Ang, A laboratory continuous crystallization system for aluminium hydroxide precipitation studies 166 (1996) 1009
Chandrasekhar, S., see Hamm 164 (1996) 362
Chang, K.H., see Biefeld 163 (1996) 212
Chang, R.H., see Rao 162 (1996) 48
Chang, Y.G., see Chen 164 (1996) 460
Chani, V.I., K. Shimamura, S. Endo and T. Fukuda, $K(M_{1/3}Nb_{2/3})OAsO_4$ (M = Mg, Zn) crystals with structure of $KTiOPO_4$ 169 (1996) 604
Charnley, N.R., see Chowdhury, A.J.S. 169 (1996) 405
Chatterjee, T., see Liu, W.K. 167 (1996) 111
Chau, H.F., see Beam III 164 (1996) 389
Chauhan, A.K., see Sabharwal, S.C. 169 (1996) 304
Chelakara, R.V., P.A. Grudowski and R.D. Dupuis, Design and growth of InAlAs/InGaAlAs strained-superlattice-barrier heterostructures for use in light-emitting devices 170 (1997) 595
Chen, B.D. and J. Garside, Crystallization of tetracosane from dodecane solutions with homologous additives 166 (1996) 1094
Chen, C., see Wu, K. 166 (1996) 533
Chen, C., see Chen, S. 170 (1997) 433
Chen, C.T., see Hu 163 (1996) 266
Chen, C.Y. and R.M. Cohen, Zn solubility limit in GaAs: growth versus equilibrium 167 (1996) 17
Chen, Falin, see Lu 165 (1996) 137
Chen, F.R., see Chou, W.C. 169 (1996) 747
Chen, J.-C., Y.-C. Lee and C. Hu, A simple method of examining the propagation of

defects in the floating-zone solidification process of lithium niobate 166 (1996) 151
Chen, J.C., see Huang, Z.C. 170 (1997) 362
Chen, J.C., see Lee, K.-J. 170 (1997) 757
Chen, J.X., see Li 164 (1996) 84
Chen, J.X., A.Z. Li, Y.C. Ren, M. Qi and Y.G. Chang, Parametric study on lattice-matched and pseudomorphic InGaAs/InAlAs/InP modulation-doped heterostructures grown by GSMBE 164 (1996) 460
Chen, K.-T., Y. Zhang, S.U. Egarievwe, M.A. George, A. Burger, C.-H. Su, Y.-G. Sha and S.L. Lehoczky, Post-growth annealing of CdS crystals grown by physical vapor transport 166 (1996) 731
Chen, L., see Wang, Y. 167 (1996) 176
Chen, L., see Chen, S. 170 (1997) 433
Chen, N., H. He, Y. Wang, K. Pan and L. Lin, Dislocations and precipitates in semi-insulating gallium arsenide revealed by ultrasonic Abrahams–Buiocchi etching 167 (1996) 766
Chen, S., B. Liu, B. Wang, M. Huang, L. Chen and C. Chen, GaAs–InP heteroepitaxy and GaAs–InP MESFET fabrication by MOVPE 170 (1997) 433
Chen, W.L., G.O. Munns, X. Wang and G.I. Haddad, Co-integration of high speed InP-based HBTs and RTDs using chemical beam epitaxy 164 (1996) 454
Chen, W.L., see Munns 164 (1996) 476
Chen, X.Q., see Li 163 (1996) 348
Chen, X.Q., see Li, B. 169 (1996) 480
Chen, Y.H., C.I. Wilkinson, J. Woodhead, J.P.R. David, C.C. Button and P.N. Robson, Polarisation characteristics of visible VCSELs 170 (1997) 394
Chen, Y.H., see Roberts, J.S. 170 (1997) 621
Chen, Yufeng, see Hong 165 (1996) 81
Cheng, C.-C., see Liu, W.-C. 170 (1997) 438
Cheng, H., see Li 163 (1996) 339
Cheng, T.S., S.E. Hooper, L.C. Jenkins, C.T. Foxon, D.E. Lacklison, J.D. Dewsnip and J.W. Orton, Optical properties of doped GaN grown by a modified molecular beam epitaxial (MBE) process on GaAs substrates 166 (1996) 597
Chen Zhiwen, see Xie Yi 167 (1996) 656
Cherkashina, N.V., see Volkov 163 (1996) 377
Cherng, Y.T., see Sze, P.W. 169 (1996) 27
Chernov, A.A., see Coriell, S.R. 169 (1996) 773
Chern-Yu, K., see Chou, W.C. 169 (1996) 747
Chiampo, F., see Marmo, L. 166 (1996) 1027
Chianese, A., N. Santilli and O. Söhnel, Influence of admixtures and operating conditions on the crystallization of ammonium chloride 166 (1996) 1099
Chiang, T.Y., see Chou, W.C. 169 (1996) 747
Chibani, L., M. Hage-Ali and P. Siffert, Electrically active defects in detector-grade CdTe:Cl and CdZnTe materials grown by THM and HPBM 161 (1996) 153
Chichibu, S., see Kamata, A. 170 (1997) 518
Choe, K.S., Y.H. Choi and W.S. Yi, Complementary non-destructive optical methods for characterizing $Al_xGa_{1-x}As$ HMESFET heterostructures 169 (1996) 227
Choi, C.K., see Hwang 162 (1996) 182
Choi, In-Hoo, see Son 165 (1996) 222
Choi, J., see Aggarwal, M.D. 166 (1996) 542
Choi, Y.-d., see Lee, C.-h. 167 (1996) 473
Choi, Y.H., see Choe, K.S. 169 (1996) 227
Chong, P.J., see Kuznetsov, A.V. 167 (1996) 458
Chou, W.C., F.R. Chen, T.Y. Chiang, H.Y. Shin, C.Y. Sun, C.M. Lin, K. Chern-Yu, C.T. Tsai and D.S. Chuu, Growth and characterization of $Cd_{1-x-y}Zn_xMn_yTe$ crystals 169 (1996) 747
Chow, P.P., see Van Hove 164 (1996) 154
Chowdhury, A.J.S., B.M.R. Wanklyn, A.V. Volkozub and J.W. Hodby, Growth of doped and undoped BSCCO 2212 crystals in platinum crucibles by repeated remelting and recrystallisation 166 (1996) 863
Chowdhury, A.J.S., N.R. Charnley, F.R. Wondre, A.V. Volkozub, P.A.J. de Groot, B.M.R. Wanklyn and J.W. Hodby, Growth of BSCCO 2212 crystals in flat dish-shaped crucibles 169 (1996) 405
Christen, J., see Heinrichsdorff, F. 170 (1997) 568
Christiansen, J., see Christiansen, S. 166 (1996) 848
Christiansen, S., F. Mücke, J. Markl, W. Dorsch, R. Stark, K. Frank, H.P. Strunk, G. Saemann-Ischenko and J. Christiansen, Structural characterization of superconducting Y–Ba–Cu–O thin films, prepared by pulsed electron beam evaporation 166 (1996) 848
Christiansen, S., see Albrecht, M. 167 (1996) 24
Christmann, P., J. Kreissl, D.M. Hofmann, B.K. Meyer, R. Schwarz and K.W. Benz, Vanadium in CdTe 161 (1996) 259
Christoffersen, J., M.R. Christoffersen and T. Johansen, Kinetics of growth and dissolution of fluorapatite 163 (1996) 295
Christoffersen, J., M.R. Christoffersen and T. Johansen, Some new aspects of surface nucleation applied to the growth and dissolution of fluorapatite and hydroxyapatite 163 (1996) 304
Christoffersen, M.R., see Christoffersen 163 (1996) 295
Christoffersen, M.R., see Christoffersen 163 (1996) 304
Chu, J.H., see Li 163 (1996) 348
Chu, J.H., see Li, B. 169 (1996) 480
Chui, H.C., see Biefeld 163 (1996) 212
Chun, Y.S., H. Murata, I.H. Ho, T.C. Hsu and G.B. Stringfellow, Use of V/III ratio to produce heterostructures in ordered GaInP 170 (1997) 263
Chung, Hyung-Tae, Seung-Cheol Lee and Jong-Kyu Yoon, Numerical prediction of operational parameters in Czochralski growth of large-scale Si 163 (1996) 249
Chung, S.-I., see Togawa 165 (1996) 362

Chunggaze, M., see O'Brien, P. 170 (1997) 23
Chuu, D.S., see Chou, W.C. 169 (1996) 747
Chuvilin, A.L., see Volkov 163 (1996) 377
Ciach, R., M. Faryna, M. Kuźma, M. Pociask and E. Sheregii, Oscillations of the composition of HgCdTe solid solution after laser annealing 161 (1996) 234
Cifré, J., see Figueras, A. 166 (1996) 798
Clark, A., R.J. Egan and C. Jagadish, Design and optimisation of $Al_xGa_{1-x}As/Al_yGa_{1-y}As$ multilayer structures for visible wavelength applications 170 (1997) 424
Clark, R.D., see Aggarwal, M.D. 166 (1996) 542
Clemens, B.M., see Artymowicz, D.M. 169 (1996) 83
Cliffe, K.A., see Skeldon 162 (1996) 95
Cloots, R., see Stassen, S. 166 (1996) 281
Cloots, R., N. Vandewalle and M. Ausloos, Simulations of the kinetic growth of $YBa_2Cu_3O_{7-\delta}$ grains 166 (1996) 816
Cloots, R., see Vandewalle, N. 169 (1996) 79
Clydesdale, G., K.J. Roberts and R. Docherty, HABIT95 – a program for predicting the morphology of molecular crystals as a function of the growth environment 166 (1996) 78
Cohen, R.M., see Chen, C.Y. 167 (1996) 17
Cohen-Adad, M.Th., see Wang, X.L. 167 (1996) 93
Cole-Hamilton, D.J., see Pickett, N.L. 170 (1997) 476
Cole-Hamilton, D.J., see Fan, G.H. 170 (1997) 485
Coleman, C.C., see Urgiles 165 (1996) 245
Colônia, E.J., A.B. Dixit and N.S. Tavare, Separation of *o*- and *p*-chlorobenzoic acids: hydrotropy and precipitation 166 (1996) 976
Colpitts, T., see Venkatasubramanian, R. 170 (1997) 817
Colson, H.G., see Kidd, P. 169 (1996) 649
Corbel, C., see Fischer 161 (1996) 214
Cordier, Y., see Ortion 164 (1996) 97
Cordier, Y., see Ortion, J.M. 170 (1997) 674
Coriell, S.R., see Singh, N.B. 166 (1996) 364
Coriell, S.R., see Singh, N.B. 167 (1996) 107
Coriell, S.R., B.T. Murray, A.A. Chernov and G.B. McFadden, Step bunching on a vicinal face of a crystal growing in a flowing solution 169 (1996) 773
Cork, C., see Earnest, T. 168 (1996) 248
Corre, S., see Garandet 165 (1996) 471
Costa, F.E., see Ranieri, I.M. 166 (1996) 423
Cotta, M.A., M.M.G. de Carvalho, M.A.A. Pudenzi, K.M.I. Landers, C.F. de Souza, R.B. Martins, R. Landers and O. Teschke, Surface morphologies of Be-doped homoepitaxial InP films 164 (1996) 409
Coulas, D., see Maigné, P. 170 (1997) 743
Coulombe, R., see Sygusch 162 (1996) 167
Courrol, L.C., see Ranieri, I.M. 166 (1996) 423
Couto, M.S., see van Enckevort, W.J.P. 166 (1996) 156
Couzi, M., see Oçafrain, A. 166 (1996) 414
Crawley, J.A., see Zhang, X. 170 (1997) 83
Crawley, J.A., see Van der Stricht, W. 170 (1997) 344
Cristiani, G., see Konuma, M. 166 (1996) 234
Cröll, A., M. Schweizer, A. Tegetmeier and K.W. Benz, Floating-zone growth of GaAs 166 (1996) 239
Cröll, A., see Kloess, G. 166 (1996) 319
Cröll, A., see Tegetmeier, A. 166 (1996) 651
Cross, L.E., see Galambos, L. 167 (1996) 660
Cross, L.E., see Erdei, S. 167 (1996) 670
Cui, F.Z., L.F. Zhou, H. Cui, C.L. Ma, H.B. Lu and H.D. Li, Phase diagram for controlled crystallization of calcium phosphate under acidic organic monolayers 169 (1996) 557
Cui, H., see Cui, F.Z. 169 (1996) 557
Cui, J., see Zhang 164 (1996) 28
Cui, Q., see Li 163 (1996) 339
Cui, S.F., see Li 163 (1996) 339
Curtis, A.P., see Islam, M.R. 170 (1997) 413
Czech, E., see Konuma, M. 166 (1996) 234
Czech, E., see Silier, I. 166 (1996) 727

Da, X., see Schwabe, D. 166 (1996) 483
Dabkowska, H.A., Single crystal growth and characterization of frustrated antiferromagnet $Sr_aPb_{1-a}Cr_xGa_{12-x}O_{19}$ 165 (1996) 179
Dabringhaus, H., see Helmrich, R. 169 (1996) 279
Dadgar, A., L. Köhne, J.Y. Hyeon, T. Grundemann, O. Stenzel, M. Strassburg, M. Kuttler, R. Heitz, D. Bimberg and H. Schumann, 4d- and 5d-transition metal acceptor doping of InP 170 (1997) 173
Daguet, C., see Silvestre, L. 170 (1997) 639
Dai, L.R., see Han, J.H. 169 (1996) 129
Dakshina Murthy, S. and I.B. Bhat, In situ monitoring of CdTe nucleation on GaAs (100) using spectroscopic ellipsometry 170 (1997) 193
Daly, M., see Booker, G.R. 170 (1997) 777
Danilewsky, A., see Tegetmeier, A. 166 (1996) 651
Danilović, N., see Čabrić, B. 169 (1996) 199
Dao Thi, M.H., see Lisgarten 163 (1996) 474
Darabont, Al., C. Neamţu, S.I. Fărcaş and Gh. Borodi, Growth of pure and doped $KMgF_3$ single crystals 169 (1996) 89
D'Arcy, A., C. Elmore, M. Stihle and J.E. Johnston, A novel approach to crystallising proteins under oil 168 (1996) 175
Dash, J.G., see Ishizaki 163 (1996) 455
Da Silva, M.F., see Sochinskii 161 (1996) 195
Datta, P.K., see Miles 161 (1996) 148
Dauelsberg, M., see Bergunde, T. 170 (1997) 66
Davey, R.J., J. Garside, A.M. Hilton, D. McEwan and J.W. Morrison, Emulsion solidification of meta-chloronitrobenzene: purification and crystallisation 166 (1996) 971
David, J.P.R., see Chen, Y.H. 170 (1997) 394
David, J.P.R., see Sale, T.E. 170 (1997) 399
David, J.P.R., see Roberts, J.S. 170 (1997) 621

Davidson, B.R., L. Hart, R.C. Newman, T.B. Joyce and T.J. Bullough, Characterization of carbon delta-doping GaAs superlattices grown by chemical beam epitaxy using CBr_4 164 (1996) 383

Davidson, B.R., R.C. Newman, T. Kanedo, O. Naji and K.H. Bachem, The rotation of the alignment by 90° of $(H–(C_{As})_2)$ complexes resulting from metalorganic molecular beam epitaxy or metalorganic vapour phase epitaxy growth on GaAs(001) using trimethylgallium 164 (1996) 396

Davies, G.J., see Foord 164 (1996) 190

Davies, G.J., see Foord 164 (1996) 208

Davis, R.F., S. Tanaka and R.C. Kern, Microstructural evolution and defect formation during the initial stages of the growth of silicon carbide and aluminum nitride on α(6H)-SiC(0001) substrates 163 (1996) 93

Davis, R.F., S. Tanaka, L.B. Rowland, R.S. Kern, Z. Sitar, S.K. Ailey and C. Wang, Growth of SiC and III–V nitride thin films via gas-source molecular beam epitaxy and their characterization 164 (1996) 132

Davis, S.H., see Anderson 163 (1996) 329

Davydova, N., see Garber, M. 168 (1996) 301

De Carvalho, M.M.G., see Cotta 164 (1996) 409

Declémy, A. and P.O. Renault, Characterization by diffuse X-ray scattering of damage in ion-implanted HgCdTe 161 (1996) 139

De Franceschi, R., see Rigo 164 (1996) 327

De Groot, P.A.J., see Chowdhury, A.J.S. 169 (1996) 405

Deicher, M., see Burchard 161 (1996) 128

Deicher, M., see Lindner, A. 170 (1997) 287

Delamarre, C., see Androussi, Y. 169 (1996) 209

De Lange, B., see Werner 164 (1996) 223

Delprat, D., see Silvestre, L. 170 (1997) 639

Delprat, D., see Zimmermann, G. 170 (1997) 645

DeLucas, L.J., see Ansari, R.R. 168 (1996) 216

DeLucas, L.J., see Long, M.M. 168 (1996) 233

De Maeyer, E.A.P., R.M.H. Verbeeck and I.Y. Pieters, Influence of the solution composition on the stoichiometry of Na^+- and of K^+-containing carbonated apatites obtained by the hydrolysis of monetite 169 (1996) 539

Demeester, P., see Zhang, X. 170 (1997) 83

Demeester, P., see Van der Stricht, W. 170 (1997) 344

Demeester, P., see D'Hondt, M. 170 (1997) 616

Demeester, P., see Vanderbauwhede, W. 170 (1997) 738

Demo, P., see Kožíšek, Z. 169 (1996) 413

DenBaars, S.P., see Gaffney, M.S. 167 (1996) 8

DenBaars, S.P., see Kapolnek, D. 170 (1997) 340

DenBaars, S.P., see Keller, S. 170 (1997) 349

Deng, C., see Barbero 165 (1996) 57

Deng, F., see Wong 164 (1996) 159

Deppert, K., J.-O. Bovin, J.-O. Malm and L. Samuelson, A new method to fabricate size-selected compound semiconductor nanocrystals: aerotaxy 169 (1996) 13

Derby, J.J., see Xiao, Q. 167 (1996) 292

Derenzo, S., see Giulietti, M. 166 (1996) 1089

Derksen, A.J., see van Enckevort, W.J.P. 166 (1996) 156

De Rossi, W., see Ranieri, I.M. 166 (1996) 423

Desai, D.G., see Sabharwal, S.C. 169 (1996) 304

DeSisto, W.J. and B.J. Rappoli, In-line UV spectroscopy of $YBa_2Cu_3O_7$ MOCVD precursors 170 (1997) 242

De Souza, C.F., see Cotta 164 (1996) 409

Détaint, J., see Palmier, D. 166 (1996) 347

Detchprohm, T., see Ohuchi, Y. 170 (1997) 325

De Theije, F.K., see Schermer 165 (1996) 387

Deufel, M., see Hahn, B. 170 (1997) 472

Devouard, B., see Baronnet, A. 166 (1996) 952

DeWitt, R., see Singh, N.B. 166 (1996) 364

DeWitt, R., see Singh, N.B. 167 (1996) 107

Dewsnip, J.D., see Cheng, T.S. 166 (1996) 597

De Yoreo, J.J., Z.U. Rek, N.P. Zaitseva and B.W. Woos, Sources of optical distortion in rapidly grown crystals of KH_2PO_4 166 (1996) 291

De Yoreo, J.J., see Land, T.A. 166 (1996) 893

De Yoreo, J.J., see Smolski, I. 169 (1996) 741

Dhanasekaran, R., see Gopalakrishnan 162 (1996) 113

D'Hondt, M., I. Moerman and P. Demeester, Characterisation of 2% mismatched InGaAs and InAsP layers, grown on different buffer layers and at different growth temperatures 170 (1997) 616

Díaz, F., see Solé, R. 166 (1996) 402

Díaz, F., see Solé, R. 167 (1996) 681

Díaz, F., see Solé, R. 169 (1996) 600

Di Cristoforo, A., P. Mengucci, G. Majni, M. Severi, S. Guerri, B.E. Watts, F. Leccabue and D. Seuret, Effect of composition and preparation conditions on the microstructure of lead zirconate titanate films 167 (1996) 644

Dieckmann, R., see Mass 165 (1996) 250

Dieckmann, R., see Tsai, T.-L. 169 (1996) 759

Dieckmann, R., see Tsai, T.-L. 169 (1996) 764

Diéguez, E., see Sochinskii 161 (1996) 195

Diéguez, E., see Martínez-López, J. 166 (1996) 325

Diéguez, E., see Bermúdez, V. 169 (1996) 409

Dieker, Ch., see Hartmann, A. 170 (1997) 605

Dietz, N., U. Rossow, D.E. Aspnes and K.J. Bachmann, Real-time optical monitoring of $Ga_xIn_{1-x}P$ and GaP heteroepitaxy on Si under pulsed chemical beam conditions 164 (1996) 34

Dijkstra, J.W., see Kramer, H.J.M. 166 (1996) 1084

Dimitrov, N., see Obretenov, W. 167 (1996) 253

Dimitrov, R., see Ambacher, O. 167 (1996) 1

Dimitrov, R., see Ambacher, O. 170 (1997) 335

Dixit, A.B., see Colônia, E.J. 166 (1996) 976

Djilali, N., see Kimura, M. 167 (1996) 516

Dmitriev, V.A., K. Irvine, G. Bulman, J. Edmond, A. Zubrilov, A.E. Nikolaev, I.

Nikitina, D. Tsvetkov, A. Babanin, A. Sitnikova, Yu. Musikhin and N. Bert, Growth and characterization of GaN layers on SiC substrates 166 (1996) 601
Dmitriev, V.A., see Nikolaev, A.E. 166 (1996) 607
Docherty, R., see Clydesdale, G. 166 (1996) 78
Domagala, J., see Tomasini 165 (1996) 203
Domagala, J., see Leszczynski, M. 169 (1996) 235
Domingo, C., E.M. Berends and G.M. van Rosmalen, Precipitation of ultrafine benzoic acid by expansion of a supercritical carbon dioxide solution through a porous plate nozzle 166 (1996) 989
Domininguez-Vera, J.M., D. Rondón, A. Moreno and J.M. García-Ruiz, A preliminary study on the interaction of ferritin single crystals with chelating agents 168 (1996) 138
Donecker, J., B. Lux and P. Reiche, Use of optical diffraction effects in crystals for growth characterization 166 (1996) 303
Dong, C., see Li 163 (1996) 339
Dong, H.K., see Tu 163 (1996) 187
Dong, H.K., see Li 164 (1996) 112
Dong, H.K., see Wong 164 (1996) 159
Dong, H.K., see Li 164 (1996) 180
Dornberger, E., W. von Ammon, N. Van den Bogaert and F. Dupret, Transient computer simulation of a CZ crystal growth process 166 (1996) 452
Dörnen, A., see Scholz, F. 170 (1997) 321
Dorren, B.H.P., see Vreeburg 164 (1996) 442
Dorsch, W., see Voigt, A. 166 (1996) 694
Dorsch, W., see Christiansen, S. 166 (1996) 848
Dost, S., see Qin, Z. 167 (1996) 74
Dost, S. and J. Su, A morphological stability analysis of the growth interface during liquid phase electroepitaxy 167 (1996) 305
Dost, S., see Kimura, M. 167 (1996) 516
Dost, S., see Kimura, M. 169 (1996) 697
Drápala, J., see Kuchař 161 (1996) 94
Dravid, V., see Zhang, K. 169 (1996) 73
Drews, D., see Schneider, A. 170 (1997) 767
Dribin, A., see Thygesen, J. 168 (1996) 308
Drigo, A.V., see Mazzer, M. 170 (1997) 553
Driver, R.D., see Salim, S. 169 (1996) 443
Druilhe, R., see Tromson-Carli, A. 170 (1997) 549
Duan, S.-k. and D.-c. Lu, Phase diagrams for the MOVPE growth of ZnTe and ZnSeTe 170 (1997) 514
Duarte, M., see Baldochi, S.L. 166 (1996) 375
Dubon, A., see Androussi, Y. 169 (1996) 209
Dubs, C., S. Bornmann, M. Schmelz, T. Schüler, F. Sandiumenge, G. Bruchlos and P. Görnert, Microstructure and surface morphology of *a*/*b*-axis oriented $YBa_2Cu_3O_{7-x}$ films on (110) $NdGaO_3$ grown by liquid phase epitaxy 166 (1996) 836
Duc, T.-M., see Thévenot, V. 170 (1997) 251
Ducourant, B., see Tomasini 165 (1996) 203
Ducruix, A., J.P. Guilloteau, M. Riès-Kautt and A. Tardieu, Protein interactions as seen by solution X-ray scattering prior to crystallogenesis 168 (1996) 28
Dufour, C., see Oderno 165 (1996) 175
Duke, S., see Miles 161 (1996) 148
Dumesnil, K., see Oderno 165 (1996) 175
Dumont, H., see Thévenot, V. 170 (1997) 251
Duncan, W.M., see Bevan, M.J. 170 (1997) 467
Dunstan, D.J., see Kidd, P. 169 (1996) 649
Dupret, F., see Van den Bogaert, N. 166 (1996) 446
Dupret, F., see Dornberger, E. 166 (1996) 452
Dupuis, R.D., see Islam, M.R. 170 (1997) 413
Dupuis, R.D., see Chelakara, R.V. 170 (1997) 595
Durose, K., see Loginov 161 (1996) 159
Durugkar, P.G. and A.G. Katpatal, Growth and characterization of pure, and doped crystals of potassium niobate 162 (1996) 161
Durygin, A., see Frukacz, Z. 169 (1996) 98
Duschl, R., see Kastner, M.J. 170 (1997) 188
Dutta, P., see Mukherjee, D.K. 169 (1996) 136
Dutta, P.S., see Bermúdez, V. 169 (1996) 409
Dutton, D., see Capper 161 (1996) 104
Duval, W.M.B., see Kim 165 (1996) 429
Duval, W.M.B., see Singh, N.B. 166 (1996) 364
Duval, W.M.B., see Singh, N.B. 167 (1996) 107
Duval, W.M.B., see Zhou, H. 167 (1996) 534
Dwir, B., see Reinhardt, F. 170 (1997) 689
Dziesiaty, J., see Peka 161 (1996) 277

Earnest, T., H. Padmore, C. Cork, R. Behrsing and S.-H. Kim, The macromolecular crystallography facility at the advanced light source 168 (1996) 248
Ebling, D.G., see Eiche, C. 166 (1996) 245
Ebling, D.G., see Fiederle, M. 166 (1996) 256
Eddrief, M., see Zheng 162 (1996) 135
Edmond, J., see Dmitriev, V. 166 (1996) 601
Egami, M., see Yao 165 (1996) 198
Egan, R.J., see Clark, A. 170 (1997) 424
Egarievwe, S.U., see Chen, K.-T. 166 (1996) 731
Egelhaaf, H.-J. and D. Oelkrug, Luminescence and nonradiative deactivation of excited states involving oxygen defect centers in polycrystalline ZnO 161 (1996) 190
Egorov, A.V., see Fiederle, M. 166 (1996) 256
Eguchi, M., see Kakimoto 163 (1996) 238
Eguchi, M., see Yi 165 (1996) 358
Eiche, C., see Laasch 161 (1996) 34
Eiche, C., W. Joerger, R. Schwarz and K.W. Benz, Noncontact characterization of CdTe doped with V or Ti 161 (1996) 271
Eiche, C., W. Joerger, M. Fiederle, D. Ebling, M. Salk, R. Schwarz and K.W. Benz, Characterization of CdTe:Cl crystals grown under microgravity conditions by time dependent charge measurements (TDCM) 166 (1996) 245

Eiche, C., see Fiederle, M. 166 (1996) 256
Einav, Y., see Horowitz, A. 167 (1996) 183
Eisenbach, A., A. Goldhorn, E. Kuphal and K. Mause, MOVPE growth for an integrated InGaAs/InP PIN-HBT receiver using Zn-doped p^+-InGaAs layers 170 (1997) 451
Eisenstein, M., see Thygesen, J. 168 (1996) 308
Ekawa, M., T. Fujii and T. Tanahashi, Effect of incorporation efficiency on dopant behaviors in selective-area metalorganic vapor phase epitaxy 170 (1997) 685
Eliseikina, I., see Garber, M. 168 (1996) 301
El Jani, B., see Beaumont, B. 170 (1997) 316
Elliott, R., see Liu 162 (1996) 107
Ellmer, K., see Thomas, B. 170 (1997) 808
El-Masry, N., see Venkatasubramanian, R. 170 (1997) 817
Elmore, C., see D'Arcy, A. 168 (1996) 175
El Moussaouiti, M., R. Boistelle, A. Bouhaouss and J.P. Klein, Agglomeration kinetics of calcium sulphate hemihydrate crystals in sulpho-phosphoric solutions 169 (1996) 118
Emsellem, V. and P. Tabeling, On the role of convection in free dendritic growth: experimental measurement of the concentration field 166 (1996) 251
Endo, J., see Shigeta, Y. 166 (1996) 617
Endo, S., see Chani, V.I. 169 (1996) 604
Endoh, Y., see Imaizumi, M. 169 (1996) 293
Epler, J., see Moser, M. 170 (1997) 404
Erdei, S., see Galambos, L. 167 (1996) 660
Erdei, S., L. Galambos, I. Tanaka, L. Hesselink, L.E. Cross, R.S. Feigelson, F.W. Ainger and H. Kojima, Inhomogeneities and segregation behavior in strontium–barium niobate fibers grown by laser-heated pedestal growth technique. Part II 167 (1996) 670
Erdt-Böhm, S., see Stauche, P. 166 (1996) 390
Ernst, P., see Geng, C. 170 (1997) 418
Ertel, J., see Tromson-Carli, A. 170 (1997) 549
Esser, N., see Knorr, K. 170 (1997) 230
Evans, D.A., see Gnoth, D.N. 170 (1997) 198
Evrard, R., see Gurskii, A.L. 170 (1997) 533

Fahy, M.R., see Sato 165 (1996) 345
Faivre, G., Morphological instabilities of lamellar eutectic growth fronts: a survey of recent experimental and numerical results 166 (1996) 29
Fan, G.H., N. Maung, T.L. Ng, P.F. Heelis, J.O. Williams, A.C. Wright, D.F. Foster and D.J. Cole-Hamilton, Thermal decomposition of di-tertiarybutyl selenide and dimethylzinc in a metalorganic vapour phase epitaxy reactor 170 (1997) 485
Fang, R., see Su, C.-H. 166 (1996) 736
Fang, R.Y., see Bertone, D. 170 (1997) 715
Fang, X.M., see Liu, W.K. 167 (1996) 111
Fang, Z., see Wang, Y. 167 (1996) 176
Fărcaş, S.I., see Darabont, Al. 169 (1996) 89
Farkas, B., T. Blickle, Zs. Ulbert and M. Hasznos-Nezdei, Characterization of mixing of suspension in a mechanically stirred precipitation system 166 (1996) 1064
Farrell, T., see Boyd 164 (1996) 71
Faryna, M., see Ciach 161 (1996) 234
Fatemi, M., Characterization of semiconductor strained layers grown on (110)-type substrates by high-resolution X-ray diffractometry 169 (1996) 261
Favier, J.J., see Garandet 165 (1996) 471
Fei, X.Y., see Li 162 (1996) 43
Feichouk, P., see Shcherbak 161 (1996) 16
Feichouk, P., see Panchouk 161 (1996) 144
Feichouk, P., see Shcherbak 161 (1996) 219
Feigelson, R.S., Epitaxial growth of lithium niobate thin films by the solid source MOCVD method 166 (1996) 1
Feigelson, R.S., see Galambos, L. 167 (1996) 660
Feigelson, R.S., see Erdei, S. 167 (1996) 670
Feng, Q., see Yanagisawa 163 (1996) 285
Feng, S., see Lu, L. 169 (1996) 637
Feng, S., see Lu, L. 169 (1996) 643
Ferhat, M., B. Liautard, G. Brun, J.C. Tedenac, M. Nouaoura and L. Lassabatere, Comparative studies between the growth characteristics of Bi_2Te_3 thin films deposited on SiO_2, Si(100) and Si(111) 167 (1996) 122
Ferid, T., see Yasuda, K. 166 (1996) 612
Fernandez, A., see Calixto, E. 169 (1996) 287
Fernández, J.M., see Zhang 164 (1996) 40
Fernández, J.M., see Joyce 164 (1996) 214
Fernández, J.M., L. Hart, X.M. Zhang, M.H. Xie, J. Zhang and B.A. Joyce, Silicon/silicon–germanium multiple quantum wells grown by gas-source molecular beam epitaxy: hydrogen coverage and interfacial abruptness 164 (1996) 241
Fernelius, N., see Singh 163 (1996) 398
Ferrari, C., see Bocchi 165 (1996) 8
Fiechter, S., see Thomas, B. 170 (1997) 808
Fiederle, M., see Eiche, C. 166 (1996) 245
Fiederle, M., C. Eiche, W. Joerger, M. Salk, A.S. Senchenkov, A.V. Egorov, D.G. Ebling and K.W. Benz, Radiation detector properties of $CdTe_{0.9}Se_{0.1}$:Cl crystals grown under microgravity in a rotating magnetic field 166 (1996) 256
Figueiredo, J.M.A., A. Vidal and O.N. Mesquita, Planar–cellular instability at a growing nematic–isotropic interface 166 (1996) 222
Figueras, A., S. Garelik, J. Caro, J. Cifré, J. Veciana, C. Rovira, E. Ribera, E. Canadell, A. Seffar and J. Fontcuberta, Preparation and characterization of conducting thin films of molecular organic conductors (TTF–TCNQ) 166 (1996) 798

Filipescu, L., see Isopescu, R. 167 (1996) 260
Fischer, D., see Hastie, G.P. 166 (1996) 67
Fischer, F., see Worschech 161 (1996) 134
Fischer, F., A. Waag, L. Worschech, W. Ossau, S. Scholl, G. Landwehr, J. Mäkinen, P. Hautojärvi and C. Corbel, Self-compensation in halogen doped CdTe grown by molecular beam epitaxy 161 (1996) 214
Fischer, R.A., A. Miehr, O. Ambacher, T. Metzger and E. Born, Novel single source precursors for MOCVD of AlN, GaN and InN 170 (1997) 139
Flavell, W.R., see Yates, H.M. 170 (1997) 611
Flemish, J.R., see Lareau, R.T. 167 (1996) 406
Fleurial, J.-P., see Caillat, T. 166 (1996) 722
Flytzani-Stephanopoulos, M., see Krueger, C.W. 169 (1996) 51
Fochouk, P., see Panchouk 161 (1996) 144
Fochouk, P., see Shcherbak 161 (1996) 219
Fogliani, S., see Carrà, S. 166 (1996) 641
Follonier, S., see Pan 165 (1996) 273
Fomenkova, N., see Garber, M. 168 (1996) 301
Fontcuberta, J., see Figueras, A. 166 (1996) 798
Foord, J.S., C.L. Levoguer and G.J. Davies, An investigation of ZnSe growth by chemical beam epitaxy using modulated beam scattering and related techniques 164 (1996) 190
Foord, J.S., K.P. Loh, N.K. Singh, R.B. Jackman and G.J. Davies, Growth and mechanistic studies of diamond formation by chemical beam epitaxy using methyl and acetylene precursors 164 (1996) 208
Forkel-Wirth, D., see Wienecke 161 (1996) 82
Fornari, R., E. Gilioli, M. Moriglioni, M. Thirumavalavan and A. Zappettini, A study of iron incorporation in LEC-grown indium phosphide 166 (1996) 572
Forsythe, E.L., see Noever, D. 167 (1996) 221
Forsythe, E.L. and M.L. Pusey, The effects of acetate buffer concentration on lysozyme solubility 168 (1996) 112
Fort, D., see Bi, Y.J. 166 (1996) 298
Foster, D.F., see Pickett, N.L. 170 (1997) 476
Foster, D.F., see Fan, G.H. 170 (1997) 485
Fouchet, S., see Legay 164 (1996) 314
Foxon, C.T., see Cheng, T.S. 166 (1996) 597
Franceschi, F., see Thygesen, J. 168 (1996) 308
Franchi, S., see Bocchi 165 (1996) 8
Franchi, S., see Bignazzi, A. 169 (1996) 450
François, P., see Androussi, Y. 169 (1996) 209
Frank, K., see Christiansen, S. 166 (1996) 848
Franke, D. and H. Roehle, Highly reproducible and defect-free MOVPE overgrowth of InGaAsP-based DFB gratings 170 (1997) 113
Franke, W.A., Crystal growth in silicagels in the temperature range 100°C to 250°C 166 (1996) 996
Frankowsky, G., see Ottenwälder, D. 170 (1997) 695
Franzheld, R., see Kirpal, G. 170 (1997) 167
Franzosi, P., see Sochinskii 161 (1996) 195
Franzosi, P., see Bocchi 165 (1996) 8
Franzosi, P., see Zeng, L. 166 (1996) 528
Frasuniak, V.M., see Nikonyuk 161 (1996) 186
Fratello, V.J., H.M. O'Bryan and C.D. Brandle, Search for high thermal expansion substrates for magneto-optic thick film garnets 166 (1996) 774
Fratello, V.J., G.W. Berkstresser, C.D. Brandle and A.J. Ven Graitis, Nickel containing perovskites 166 (1996) 878
Frazier, D.O., see Aggarwal, M.D. 166 (1996) 542
Frechengues, S., see Snoeck, E. 167 (1996) 143
Frediani, C., see Gennari, S. 166 (1996) 309
Freer, R.W., see Whitaker 164 (1996) 296
Freidinger, J., see Burchard 161 (1996) 128
Freitag, S., see Pohl, U.W. 170 (1997) 144
Freitas Jr., J.A., see Wickenden, A.E. 170 (1997) 367
Frenkel, A., see Weiss, E. 166 (1996) 745
Frentrup, W., see Utke 162 (1996) 126
Freundlich, A., see Bensaoula 164 (1996) 271
Freundlich, A., see Vilela 164 (1996) 465
Friedrich, J., J. Baumgartl, H.-J. Leister and G. Müller, Experimental and theoretical analysis of convection and segregation in vertical Bridgman growth under high gravity on a centrifuge 167 (1996) 45
Frukacz, Z., T. Lukasiewicz, A. Matkowskii, I. Pracka, D. Sugak, I. Solskii, L. Vasylechko and A. Durygin, Effects of ionizing radiation on the optical absorption of $LiNbO_3$ and $YAlO_3$ single crystals 169 (1996) 98
Fu, C.K., see Lan, C.W. 166 (1996) 458
Fua, M., see Thygesen, J. 168 (1996) 308
Fujii, K., K. Shimoyama, N. Hosoi, K. Kiyomi, A. Yamauchi and H. Gotoh, Dependence of deposition selectivity for MOVPE of AlGaAs using HCl gas on the orientation of the substrate and the orientation of the stripe of SiN_x masks 170 (1997) 679
Fujii, M., see Takebe 162 (1996) 31
Fujii, M., H. Iwanaga and S. Motojima, CVD growth and morphology of transition-metal phosphides 166 (1996) 99
Fujii, T., see Ando 164 (1996) 1
Fujii, T., see Ekawa, M. 170 (1997) 685
Fujita, K., see Takebe 162 (1996) 31
Fujita, Sg., see Fujita 164 (1996) 196
Fujita, Sg., see Funato, M. 170 (1997) 276
Fujita, Sg., see Ogata, K.-i. 170 (1997) 507
Fujita, Sz., Y. Kawakami and Sg. Fujita, MO(GS)MBE and photo-MO(GS)MBE of II–VI semiconductors 164 (1996) 196
Fujita, Sz., see Funato, M. 170 (1997) 276
Fujita, Sz., see Ogata, K.-i. 170 (1997) 507

Fujiwara, S., K. Matsumoto and T. Shirakawa, In situ transport rate monitor during ZnSe crystal growth by PVT 165 (1996) 169
Fujiwara, S., T. Araki, M. Tatsumi, M. Irikura, K. Matsumoto, S. Murai and T. Shirakawa, The effect of gravity on crystal growth of InGaAs by the Bridgman method 167 (1996) 357
Fujiwara, S., T. Kotani, K. Matsumoto and T. Shirakawa, Crystal growth of ZnSe by PVT using a semi-open ampule 169 (1996) 660
Fujiwara, T., see Igasaki, Y. 167 (1996) 769
Fujiyasu, H., see Tatsuoka, H. 166 (1996) 754
Fukada, T., see Miyazaki 162 (1996) 83
Fukami, T.A., Y. Takasuga, M. Sumi, M. Yohda, M. Yoshida and K. Miki, Crystallization and preliminary X-ray characterization of chaperonin-60 from *Paracoccus denitrificans* 168 (1996) 297
Fuke, S., see Takano, Y. 169 (1996) 621
Fukuchi, F., see Oh 164 (1996) 425
Fukuda, T., see Rudolph 161 (1996) 28
Fukuda, T., K. Umetsu, P. Rudolph, H.J. Koh, S. Iida, H. Uchiki and N. Tsuboi, Growth and characterization of twin-free ZnSe single crystals by the vertical Bridgman method 161 (1996) 45
Fukuda, T., see Shimamura 163 (1996) 388
Fukuda, T., see Kimura 163 (1996) 393
Fukuda, T., see Kawaguchi, T. 166 (1996) 489
Fukuda, T., see Kawaguchi, T. 166 (1996) 493
Fukuda, T., see Rudolph, P. 166 (1996) 578
Fukuda, T., see Schäfer, N. 166 (1996) 675
Fukuda, T., see Matsuoka, M. 166 (1996) 1035
Fukuda, T., see Koh, H.J. 167 (1996) 38
Fukuda, T., see Uda, S. 167 (1996) 64
Fukuda, T., see Terada, Y. 167 (1996) 369
Fukuda, T., see Kawaguchi, T. 169 (1996) 94
Fukuda, T., see Takeda, H. 169 (1996) 503
Fukuda, T., see Chani, V.I. 169 (1996) 604
Fukui, T., see Ishikawa, Y. 167 (1996) 434
Fukui, T., see Hara, S. 170 (1997) 579
Fukui, T., see Kumakura, K. 170 (1997) 700
Funahashi, R., see Matsubara, I. 167 (1996) 570
Funato, M., S. Aoki, Sz. Fujita and Sg. Fujita, Initial growth behavior of GaAs on ZnSe in MOVPE 170 (1997) 276
Funayama, M., see Morita, S. 166 (1996) 370
Fuoss, P.H., see Kisker 163 (1996) 54
Fuoss, P.H., see Kamiya 163 (1996) 67
Füredi-Milhofer, H., see Tunik, L. 167 (1996) 748
Furukawa, Y., see Ishizaki 163 (1996) 455
Furukawa, Y., see Nada, H. 169 (1996) 587

Gabas, N., see Lin, C.H. 166 (1996) 104
Gabas, N., see Gerbaud, V. 166 (1996) 172
Gaborit, F., see Lestra, A. 167 (1996) 446
Gacoin, T., see Ricolleau, C. 166 (1996) 769
Gaffney, M.S., C.M. Reaves, R.S. Smith, A.L. Holmes Jr. and S.P. DenBaars, Control of III–V epitaxy in a metalorganic chemical vapor deposition process: impact of source flow control on composition and thickness 167 (1996) 8
Gahn, C., J. Krey and A. Mersmann, The effect of impact energy and the shape of crystals on their attrition rate 166 (1996) 1058
Galambos, L., S. Erdei, I. Tanaka, L. Hesselink, L.E. Cross, R.S. Feigelson, F.W. Ainger and H. Kojima, Inhomogeneities and segregation behavior in strontium–barium niobate fibers grown by laser-heated pedestal growth technique. Part I 167 (1996) 660
Galambos, L., see Erdei, S. 167 (1996) 670
Gale, I., see Capper 161 (1996) 104
Gallagher, H.G., see Wang 163 (1996) 272
Galloway, S.A., see Loginov 161 (1996) 159
Galstyan, V.G., see Givargizov 162 (1996) 73
Gamblin, S.J., see Xiao, B. 168 (1996) 244
Gandais, M., see Ricolleau, C. 166 (1996) 769
Ganschow, S., see Nitsch 165 (1996) 163
Garandet, J.P., S. Corre, S. Gavoille, J.J. Favier and J.I.D. Alexander, On the effect of gravity perturbations on composition profiles during Bridgman crystal growth in space 165 (1996) 471
Garber, M., N. Davydova, I. Eliseikina, N. Fomenkova, O. Gryaznova, I. Gryshkovskaya, N. Nevskaya, S. Nikonov, A. Rak, S. Sedelnikova, A. Serganov, D. Shcherbakov, S. Tishchenko, V. Vysotskaya, J. Zheltonosova, A. Liljas, A. Aevarsson and S. Al-Karadaghi, Crystallization and structural studies of components of the protein-synthesizing system from *Thermus thermophilus* 168 (1996) 301
Garcia, A., see Prieur, E. 166 (1996) 329
Garcia, J.C., see Ortion, J.M. 170 (1997) 674
Garcia, J.Ch., see Ortion 164 (1996) 97
García, R., see Kidd, P. 169 (1996) 649
García-Ruiz, J.M., see Moreno, A. 166 (1996) 919
García-Ruiz, J.M., see Otálora, F. 168 (1996) 93
García-Ruiz, J.M., see Domininguez-Vera, J.M. 168 (1996) 138
García-Ruiz, J.M., see Otálora, F. 169 (1996) 361
Gardner, N.F., see Islam, M.R. 170 (1997) 413
Garelik, S., see Figueras, A. 166 (1996) 798
Garrett, M.H. and I. Mnushkina, Techniques for top-seeded solution growth of $BaTiO_3$ 166 (1996) 550
Garside, J., see Taguchi 163 (1996) 318
Garside, J., see Davey, R.J. 166 (1996) 971
Garside, J., see Mwangi, S.M. 166 (1996) 1078
Garside, J., see Chen, B.D. 166 (1996) 1094
Garti, N., see Tunik, L. 167 (1996) 748
Gärtner, G., see Müller, M. 166 (1996) 636
Gasparotto, A., see Rigo 164 (1996) 430
Gastaldi, J., see Rossberg, A. 166 (1996) 354
Gastev, S.V., see Sokolov, N.S. 169 (1996) 40

Gaumont-Goarin, E., see Lestra, A. 167 (1996) 446
Gauneau, M., see Martel 161 (1996) 250
Gauneau, M., see Zerrai 161 (1996) 264
Gautam, M., see Gupta 165 (1996) 19
Gauvin, S. and J. Zyss, Growth of organic crystalline thin films, their optical characterization and application to non-linear optics 166 (1996) 507
Gavaldà, Jna., see Solé, R. 167 (1996) 681
Gavaldà, Jna., see Solé, R. 169 (1996) 600
Gavoille, S., see Garandet 165 (1996) 471
Gay, D.H., see Rohl, A.L. 166 (1996) 84
Gazit, D., see Horowitz, A. 167 (1996) 183
Gazit, D., see Brandon, S. 167 (1996) 190
Ge, W., see Lu, L. 169 (1996) 637
Ge, W., see Lu, L. 169 (1996) 643
Gebhardt, W., see Kastner, M.J. 170 (1997) 188
Gebhardt, W., see Hahn, B. 170 (1997) 472
Gedanken, A., see Katabi, G. 166 (1996) 760
Gedridge, R.W., see Sadwick 164 (1996) 285
Gedridge, R.W., see Antonell 164 (1996) 420
Geiger, M., D. Ottenwälder, F. Scholz, M. Glanz, C. Recker, J. Winterfeld and H. Schumann, Bis-phosphino-methane: a new precursor for metalorganic vapor phase epitaxy of phosphides 169 (1996) 625
Geiger, M., A. Bauknecht, F. Adler, H. Schweizer and F. Scholz, Observation of the 2D–3D growth mode transition in the InAs/GaAs system 170 (1997) 558
Gektin, A.V., see Komar, V.K. 160 (1996) 419
Gelders, H.J., see Brück, E. 166 (1996) 394
Geng, C., A. Moritz, S. Heppel, A. Mühe, J. Kuhn, P. Ernst, H. Schweizer, F. Phillipp, A. Hangleiter and F. Scholz, Influence of order-domain size on the optical gain of AlGaInP laser structures 170 (1997) 418
Geng, X., see Wu, X.-B. 169 (1996) 786
Gennari, S., G. Attolini, C. Pelosi, P.P. Lottici, F. Riccò, M. Labardi, M. Allegrini and C. Frediani, Raman scattering study and AFM morphological characterization of MOVPE-grown (111)-strained heterostructures 166 (1996) 309
George, M.A., see Chen, K.-T. 166 (1996) 731
Gerbaud, V., N. Gabas, J. Blouin and C. Laguerie, Nucleation studies of potassium hydrogen tartrate in model solutions and wines 166 (1996) 172
Gerhardt, A., see Abrosimov, N.V. 166 (1996) 657
Gerhardt, M., see Kirpal, G. 170 (1997) 167
Germain, M., see Gurskii, A.L. 170 (1997) 533
Ges, A.P., see Luginets 162 (1996) 89
Geszti, O., see Pfeifer, J. 169 (1996) 727
Geurts, J., see Behet, M. 167 (1996) 415
Geurts, J., see Tümmler, J. 170 (1997) 772
Geva, M., see Hamm 164 (1996) 362
Geva, M., see Thygesen, J. 168 (1996) 308
Gfrörer, O., see Ottenwälder, D. 170 (1997) 695
Ghosh, B., see Miles 161 (1996) 148
Gibart, P., see Nataf 165 (1996) 1
Gibart, P., see Beaumont, B. 170 (1997) 316
Gibis, R., see Schelhase 164 (1996) 339
Gibis, R., see Künzel 164 (1996) 449
Giegé, R., see Ng, J.D. 168 (1996) 50
Giegé, R., see Lorber, B. 168 (1996) 204
Gigase, Y., see Beccard, R. 170 (1997) 97
Gilbert, T.S., see Van Scyoc, J.M. 166 (1996) 384
Giling, L.J., see Bongers 162 (1996) 7
Giling, L.J., see Li 163 (1996) 195
Giling, L.J., see Li 163 (1996) 203
Giling, L.J., see Schermer 165 (1996) 387
Giling, L.J., see Schermer, J.J. 166 (1996) 622
Giling, L.J., see te Nijenhuis, J. 167 (1996) 397
Giling, L.J., see Hageman, P.R. 170 (1997) 270
Giling, L.J., see Bastos, P.L. 170 (1997) 710
Gilioli, E., see Fornari, R. 166 (1996) 572
Gillies, D., see Palosz, W. 169 (1996) 20
Gilmer, G.H., see Jackson 163 (1996) 461
Giulietti, M., M.M. Seckler, S. Derenzo and J.V. Valarelli, Changes in copper sulfate crystal habit during cooling crystallization 166 (1996) 1089
Givargizov, E.I., L.L. Aksenova, V.G. Galstyan, A.N. Kiselev, A.V. Kuznetsov, V.I. Muratova, E.V. Rakova and A.N. Stepanova, Growth of diamond particles on sharpened Si tips 162 (1996) 73
Glantz, W., see Kuznetsov, Yu.G. 168 (1996) 63
Glanz, M., see Geiger, M. 169 (1996) 625
Glass, R.C., see Tuominen 165 (1996) 233
Glicksman, M.E., see Kim 165 (1996) 429
Glicksman, M.E., see Singh, N.B. 166 (1996) 364
Glicksman, M.E., see Singh, N.B. 167 (1996) 107
Gloukhian, A., see Zimmermann, G. 170 (1997) 645
Gnoth, D.N., I.B. Poole, T.L. Ng, D.A. Evans, N. Maung, J.O. Williams and A.C. Wright, Growth process studies by reflectance anisotropy spectroscopy on MOVPE ZnSe 170 (1997) 198
Göbel, A., see Lin, C.T. 167 (1996) 612
Göbel, E.O., see Protzmann, H. 170 (1997) 155
Göbel, E.O., see Spika, Z. 170 (1997) 257
Göbel, E.O., see Rettig, R. 170 (1997) 748
Gogol, C., see Wajid, A. 170 (1997) 237
Goiffon, A., see Palmier, D. 166 (1996) 347
Gokhale, M., see Bao, K.X. 170 (1997) 497
Gokhale, M.R., K.X. Bao, P.D. Healey, F.C. Jain and J.E. Ayers, Factors influencing low-temperature photo-assisted OMVPE growth of ZnSe 165 (1996) 25
Goldhorn, A., see Eisenbach, A. 170 (1997) 451
Goldstein, L., see Lestra, A. 167 (1996) 446
Gomei, Y., see Murooka, K.-i. 169 (1996) 485
Gomes, L., see Ranieri, I.M. 166 (1996) 423
Gómez-Morales, J., see López-Macipe, A. 166 (1996) 1015
Gómez-Morales, J., J. Torrent-Burgués, A. López-Macipe and R. Rodríguez-Clemente,

Precipitation of calcium carbonate from solutions with varying Ca^{2+}/carbonate ratios 166 (1996) 1020
Gómez-Morales, J., J. Torrent-Burgués and R. Rodríguez-Clemente, Nucleation of calcium carbonate at different initial pH conditions 169 (1996) 331
Gómez-Morales, J., see Rodríguez-Clemente, R. 169 (1996) 339
Gonda, S., see Yamamoto 164 (1996) 117
González, D., see Kidd, P. 169 (1996) 649
González, L., see Kidd, P. 169 (1996) 649
González, Y., see Kidd, P. 169 (1996) 649
González-Borrero, P.P., D.I. Lubyshev, E. Marega Jr., E. Petitprez and P. Basmaji, Self-organized InGaAs quantum dots grown by molecular beam epitaxy on (100), (711)A/B, (511)A/B, (311)A/B, (211)A/B, and (111)A/B oriented GaAs 169 (1996) 424
González-Mañas, M., see Martínez-López, J. 166 (1996) 325
González-Muñoz, M.T., N. Ben Omar, M. Martínez-Cañamero, M. Rodríguez-Gallego, A. López Galindo and J.M. Arias, Struvite and calcite crystallization induced by cellular membranes of *Myxococcus xanthus* 163 (1996) 434
González-Sanz, F., see Kidd, P. 169 (1996) 649
Goodhew, P.J., see Joyce 164 (1996) 371
Goodhew, P.J., see Petkos 164 (1996) 415
Goodhew, P.J., see Kidd, P. 169 (1996) 649
Gopalakrishnan, N. and R. Dhanasekaran, On the nucleation and composition analysis of $InAs_{1-x}P_x$ during vapour phase epitaxial growth 162 (1996) 113
Gorbunov, L.A., Experimental study of thermocapillary convection in a germanium melt 165 (1996) 351
Görnert, P., see Dubs, C. 166 (1996) 836
Goronkin, H., see Shiralagi 164 (1996) 334
Gortenmulder, T.J., see Mihalik, M. 167 (1996) 621
Goto, H., M. Takemura and T. Ido, Deep hole trap level of nitrogen-doped ZnSe grown by metalorganic vapor phase epitaxy 170 (1997) 510
Goto, K., see Takiguchi, T. 170 (1997) 705
Gotoda, M., H. Sugimoto, T. Isu and M. Nunoshita, Grown mirrors of InP formed by dry etching and selective CBE regrowth for short cavity lasers 164 (1996) 308
Gotoh, H., see Fujii, K. 170 (1997) 679
Gotoh, S., see Nakamura, K. 170 (1997) 377
Gotoh, Y., see Tanaka, Y. 169 (1996) 299
Gottfriedsen, J., see Pohl, U.W. 170 (1997) 144
Gottschalch, V., see Kirpal, G. 170 (1997) 167
Gough, C.E., see Yang, G. 166 (1996) 820
Graham, S. and P.W. Brown, Reactions of octacalcium phosphate to form hydroxyapatite 165 (1996) 106
Grahn, H.T., see Hatatani, S. 170 (1997) 297
Gramlich, S., see Knauer, A. 170 (1997) 281
Gránásy, L., T. Pusztai and E. Hartmann, Diffuse interface model of nucleation 167 (1996) 756
Grancea, A., see Alexandru, H.V. 166 (1996) 162
Grant, J.T., see Li 164 (1996) 180
Grasza, K., see Laasch 161 (1996) 34
Grasza, K. and A. Jędrzejczak, Growth stability in high temperature vapour growth 162 (1996) 173
Grasza, K., see Palosz, W. 169 (1996) 20
Grattepain, C., see Ortion 164 (1996) 97
Grattepain, C., see Tromson-Carli, A. 170 (1997) 549
Gravey, P., see Martel 161 (1996) 250
Gravey, P., see Zerrai 161 (1996) 264
Greborio, L., see Bertone, D. 170 (1997) 715
Greenberg, J.H., *P–T–X* phase equilibrium and vapor pressure scanning of non-stoichiometry in CdTe 161 (1996) 1
Greenwood, A., see Kuznetsov, Yu.G. 166 (1996) 913
Grietens, B., see Srnánek 165 (1996) 156
Griffiths, C.L., see Stafford, A. 170 (1997) 182
Grilli, E., see Bignazzi, A. 169 (1996) 450
Grodzinski, P., see Biefeld 163 (1996) 212
Gromilov, S., see Isaenko, L. 166 (1996) 502
Grudowski, P.A., see Chelakara, R.V. 170 (1997) 595
Grugel, R.N., see Shen 165 (1996) 438
Grunberg, P., see Amano 164 (1996) 321
Grundemann, T., see Dadgar, A. 170 (1997) 173
Grundmann, M., see Heinrichsdorff, F. 170 (1997) 568
Grundmann, M., see Kappelt, M. 170 (1997) 590
Gryaznova, O., see Garber, M. 168 (1996) 301
Gryshkovskaya, I., see Garber, M. 168 (1996) 301
Grzegory, I., see Leszczynski, M. 169 (1996) 235
Guérin, R., see Le Marec, C. 169 (1996) 147
Guerri, S., see di Cristoforo, A. 167 (1996) 644
Gui, L.-L., see Pan, J.-S. 168 (1996) 227
Guillemoles, J.F., see Lyubomirsky 161 (1996) 90
Guilloteau, J.P., see Ducruix, A. 168 (1996) 28
Gulden, K.H., see Moser, M. 170 (1997) 404
Gumlich, H.-E., see Hermann 161 (1996) 181
Günter, P., see Pan 165 (1996) 273
Guo, J.-K., see Xia, C.-T. 166 (1996) 961
Guo, L.-Q., see Hatatani, S. 170 (1997) 297
Guo, X.L., Z.G. Liu, S.N. Zhu, T. Yu, S.B. Xiong and W.S. Hu, Pulsed laser deposition of *c*-oriented $LiNbO_3$/$LiTaO_3$ optical waveguiding bilayered films on silicon wafers 165 (1996) 187
Guo, X.L., Z.G. Liu, S.N. Zhu, S.B. Xiong, Y.Y. Zhu and J.M. Liu, $Ba_2NaNb_5O_{15}$/MgO optical waveguide structure grown on Si wafer by pulsed laser deposition 167 (1996) 378
Guo, Z.-Y., see Wu, X.-B. 169 (1996) 786
Gupta, S.C., S. Sitharaman, A. Nagpal, M. Gautam and L.E.A. Berlouis, Growth and characterization of $Hg_{1-x}Cd_xTe$ ($0.21 < x < 0.36$) epilayers grown from Te-rich solution by the dipping technique 165 (1996) 19
Guretskii, S.A., see Luginets 162 (1996) 89
Gurskii, A.L., W. Taudt, S. Lampe, H. Hamadeh, F. Sauerländer, M. Germain, M. Basilavecchia, R. Evrard, G.P. Yablonskii and M. Heuken, Optical and electrical prop-

erties of MOVPE-grown ZnSe:N using triallylamine as a nitrogen precursor 170 (1997) 533
Gustafson, B., see Carlsson, N. 170 (1997) 127
Gustafsson, A., see Biasiol, G. 170 (1997) 600
Guthmann, C., see Rolley, E. 166 (1996) 55
Gutjahr, A., see Konuma, M. 166 (1996) 234
Gutjahr, A., see Silier, I. 166 (1996) 727
Gutsche, D., see Kurpas, P. 170 (1997) 442
Guzzi, M., see Bignazzi, A. 169 (1996) 450

Habuka, H., T. Nagoya, M. Mayusumi, M. Katayama, M. Shimada and K. Okuyama, Model on transport phenomena and epitaxial growth of silicon thin film in $SiHCl_3$–H_2 system under atmospheric pressure 169 (1996) 61
Haddad, G.I., see Chen 164 (1996) 454
Haddad, G.I., see Munns 164 (1996) 476
Hadj-Ali, M., see Martel 161 (1996) 250
Hadj-Ali, M., see Zerrai 161 (1996) 264
Hage-Ali, M., see Chibani 161 (1996) 153
Hageman, P.R., see te Nijenhuis, J. 167 (1996) 397
Hageman, P.R., J. te Nijenhuis, M.J. Anders and L.J. Giling, Dependence of impurity incorporation upon substrate misorientation during GaAs growth by metalorganic vapour phase epitaxy 170 (1997) 270
Hageman, P.R., see Bastos, P.L. 170 (1997) 710
Hahn, B., see Kastner, M.J. 170 (1997) 188
Hahn, B., M. Deufel, M. Meier, M.J. Kastner, R. Blumberg and W. Gebhardt, Photoassisted growth and nitrogen doping of ZnSe 170 (1997) 472
Hahn, J.H., see Hwang 162 (1996) 55
Hahn, T.S., see Song, M.H. 167 (1996) 157
Hähnert, I., see Utke 162 (1996) 126
Haidoux, A., see Tomasini 165 (1996) 203
Haidoux, A., see Tomasini, P. 166 (1996) 590
Hajdusianek, A., see Szatkowski 161 (1996) 282
Haldenwang, P., see Le Marec, C. 169 (1996) 147
Hallin, C., see Owman, F. 167 (1996) 391
Halliwell, M.A.G., X-ray diffraction solutions to heteroepitaxial growth problems 170 (1997) 47
Haltakov, I.V., see Mouchovski 162 (1996) 79
Halwax, E., see Wang, X.L. 167 (1996) 93
Hamacher, M., see Künzel 164 (1996) 449
Hamadeh, H., see Taudt, W. 169 (1996) 243
Hamadeh, H., see Heuken, M. 170 (1997) 30
Hamadeh, H., see Taudt, W. 170 (1997) 491
Hamadeh, H., see Gurskii, A.L. 170 (1997) 533
Hamakawa, E., see Hayakawa 163 (1996) 220
Hamm, R.A., S. Chandrasekhar, L. Lunardi, M. Geva, R. Malik, D. Humphrey and R. Ryan, Materials and electrical characteristics of carbon-doped $Ga_{0.47}In_{0.53}As$ using carbontetrabromide by MOMBE for HBT device applications 164 (1996) 362
Hammons, B.E., see Biefeld 163 (1996) 212
Han, J.H., Z.W. Sun, L.R. Dai, J.C. Xie and W.R. Hu, Experiment on the thermocapillary convection of a mercury liquid bridge in a floating half zone 169 (1996) 129
Han, Q. and S.-X. Lin, A microcrystal selection technique in protein crystallization 168 (1996) 181
Han, T.P.J., see Wang 163 (1996) 272
Han, Y., see Hu 163 (1996) 266
Han, Y., see Liu, W.J. 169 (1996) 534
Han, Y.K., see Kim, E.K. 170 (1997) 803
Hanamaki, Y., see Pan, W. 170 (1997) 585
Haneda, S., see Nishida, K. 170 (1997) 312
Hangleiter, A., see Scholz, F. 170 (1997) 321
Hangleiter, A., see Geng, C. 170 (1997) 418
Hangleiter, A., see Ottenwälder, D. 170 (1997) 695
Hansen, H.A.S., see Thygesen, J. 168 (1996) 308
Hansson, G.V., see Radamson, H.H. 167 (1996) 495
Hansson, P.O., see Konuma, M. 166 (1996) 234
Hansson, P.O., see Silier, I. 166 (1996) 727
Hansson, P.O., see Albrecht, M. 167 (1996) 24
Hara, K., see Watanabe, K. 169 (1996) 223
Hara, K., see Nishida, K. 170 (1997) 312
Hara, K., see Honda, T. 170 (1997) 503
Hara, S., J. Motohisa and T. Fukui, Formation and characterization of InGaAs strained quantum wires on GaAs multiatomic steps grown by metalorganic vapor phase epitaxy 170 (1997) 579
Harada, J., I. Takahashi, Y. Itoh, N.S. Sokolov, N.L. Yakovlev, Y. Shusterman and J.C. Alvarez, X-ray scattering from surfaces and interfaces and its application to the characterization of CaF_2/Si(111) interfaces 163 (1996) 31
Harada, J., see Itoh, Y. 166 (1996) 61
Harada, J., see Shimura, T. 166 (1996) 786
Harada, J., see Sokolov, N.S. 169 (1996) 40
Harada, M., see Igasaki, Y. 167 (1996) 769
Harada, S., see Nishida, M. 168 (1996) 284
Harada, S., see Miyawaki, K. 168 (1996) 292
Hardt, A., see Taudt, W. 170 (1997) 491
Hardtdegen, H., see Hollfelder, M. 170 (1997) 103
Hardtdegen, H., see Hartmann, A. 170 (1997) 605
Härle, V., see Scholz, F. 170 (1997) 321
Harmandas, N.G. and P.G. Koutsoukos, The formation of iron(II) sulfides in aqueous solutions 167 (1996) 719
Harms, J., see Thygesen, J. 168 (1996) 308
Harris Jr., J.S., see Hung, C.Y. 169 (1996) 201
Harris Jr., J.S., see Lee, H. 169 (1996) 689
Harrison, B.J., see Brück, E. 166 (1996) 394
Hart, L., see Fernández 164 (1996) 241
Hart, L., see Davidson 164 (1996) 383
Hart, L., see O'Brien, P. 167 (1996) 133
Hartmann, A., M. Bongartz, M. Hollfelder, H. Hardtdegen, Ch. Dieker and H. Lüth, Growth of modulation-doped GaAs/AlGaAs quantum wires on V-groove patterned substrates 170 (1997) 605

Hartmann, E. and E. Beregi, Dissolution forms of rare-earth orthoferrites 166 (1996) 109
Hartmann, E., see Gránásy, L. 167 (1996) 756
Härtwig, J., see Prieur, E. 166 (1996) 329
Hasebe, K., see Shishiguchi, S. 166 (1996) 689
Hasegawa, K., S. Miyashita, H. Komatsu, C. Sano and N. Nagashima, In-situ observation of the concentration gradient layer around a growing crystal of leucine complex 166 (1996) 925
Hasegawa, M., see Zhao, T.-r. 166 (1996) 408
Hasegawa, M., see Suzuki, T. 166 (1996) 872
Hasegawa, T., W. Shimada, H. Tochihara and S. Hosoki, Dynamic observation of Si-island growth on a Si(111)-7 × 7 surface by high-temperature scanning tunneling microscopy 166 (1996) 314
Hashimoto, E., see Mizuno, K. 166 (1996) 146
Hashimoto, K., see Yoshimoto, N. 167 (1996) 574
Hashimoto, M., H. Qiu, T. Ohbuchi, M. Adamik, H. Nakai, A. Barna and P.B. Barna, Characterization of cobalt films grown on MgO(001) by dc-biased-sputter deposition 166 (1996) 792
Hashimoto, S., A. Yamaguchi and S.-i. Oya, Formation of needle-like β-Ca_2SiO_4 crystals by vapor phase reaction 169 (1996) 376
Hashimoto, T., O. Imafuji, M. Ishida, Y. Terakoshi, T. Sugino, A. Yoshikawa, K. Itoh and J. Shirafuji, Inheritance of zinc-blende structure from 3C–SiC/Si(001) substrate in growth of GaN by MOCVD 169 (1996) 185
Hastie, G.P., J. Johnstone, K.J. Roberts and D. Fischer, Application of polarised ultra-soft X-ray absorption near-edge spectroscopy to the characterisation of the structure of molecular interfaces 166 (1996) 67
Hasumi, H., see Sakata, Y. 170 (1997) 456
Hasznos-Nezdei, M., see Liszi, I. 166 (1996) 179
Hasznos-Nezdei, M., see Farkas, B. 166 (1996) 1064
Hatakka, H., see Sha, Z.L. 166 (1996) 1105
Hatano, H., see Yasuda, K. 166 (1996) 612
Hatatani, S., L.-Q. Guo, J.-H. Oh, H.T. Grahn and M. Konagai, Heavily carbon-doped GaAs grown on various oriented GaAs substrates by MOMBE 170 (1997) 297
Hatta, K., M. Higuchi, J. Takahashi and K. Kodaira, Floating zone growth and characterization of aluminum-doped rutile single crystals 163 (1996) 279
Hautojärvi, P., see Fischer 161 (1996) 214
Hayakawa, R., see Tanaka, S. 168 (1996) 44
Hayakawa, Y., E. Hamakawa, T. Koyama and M. Kumagawa, Rapid diffusion of Ga into InSb and precipitation of In 163 (1996) 220
Hayakawa, Y., see Ozawa, T. 166 (1996) 463
Hayakawa, Y., S. Iida, T. Sakurai, H. Yanagida, M. Kikuzawa, T. Koyama and M. Kumagawa, Epitaxial lateral overgrowth of InGaAs on patterned GaAs substrates by liquid phase epitaxy 169 (1996) 613
Hayashi, T., see Yamamoto 164 (1996) 117
Hays, J., see Wong 164 (1996) 159
He, H., see Chen, N. 167 (1996) 766
Healey, P.D., see Gokhale 165 (1996) 25
Heelis, P.F., see Fan, G.H. 170 (1997) 485
Heim, M., see Bolt, R. 166 (1996) 537
Heime, K., see Behet, M. 167 (1996) 415
Heime, K., see Behres, A. 170 (1997) 655
Heime, K., see Lakner, H. 170 (1997) 732
Heime, K., see Tümmler, J. 170 (1997) 772
Heime, K., see von Eichel-Streiber, C. 170 (1997) 783
Heinecke, H., see Marheineke 164 (1996) 16
Heinecke, H., see Wachter 164 (1996) 302
Heinecke, H., see Veuhoff 164 (1996) 402
Heinecke, H., see Ritter, D. 170 (1997) 149
Heinecke, H., see Keidler, M. 170 (1997) 161
Heinrichsdorff, F., A. Krost, M. Grundmann, D. Bimberg, F. Bertram, J. Christen, A. Kosogov and P. Werner, Self organization phenomena of InGaAs/GaAs quantum dots grown by metalorganic chemical vapour deposition 170 (1997) 568
Heitz, R., see Dadgar, A. 170 (1997) 173
Hellig, K., see Prösch, G. 170 (1997) 537
Helmers, L., J. Schilz and G. Bähr, A boundary layer model for macrosegregation of Bridgman grown $Ge_{1-x}Si_x$ mixed crystals 165 (1996) 381
Helmrich, R. and H. Dabringhaus, Investigation of condensation and evaporation of alkali halide crystals by molecular beam methods. XIV. Development of two-dimensional islands on the (100) surface of LiF 169 (1996) 279
Henderson, B., see Wang 163 (1996) 272
Hendrikx, R.W.A., see Mihalik, M. 167 (1996) 621
Henningsen, T., see Singh 163 (1996) 398
Henry, D., see Ben Hadid, H. 166 (1996) 436
Heppel, S., see Geng, C. 170 (1997) 418
Herden, A., see Tanneberger, U. 166 (1996) 1074
Hermann, S., H.-E. Mahnke, D. Schumann, B. Spellmeyer, G. Sulzer, J. Bollmann, B. Reinhold, J. Röhrich, M. Wienecke, R. Yankov and H.-E. Gumlich, Palladium as impurity in ZnTe 161 (1996) 181
Hermans, J., see Behet, M. 167 (1996) 415
Hermans, J., see Tümmler, J. 170 (1997) 772
Hermon, H., see Burtman, V. 166 (1996) 832
Hesselink, L., see Galambos, L. 167 (1996) 660
Hesselink, L., see Erdei, S. 167 (1996) 670
Hetzel, M., see Wajid, A. 170 (1997) 237
Heuken, M., see Taudt, W. 169 (1996) 243
Heuken, M., J. Söllner, W. Taudt, S. Lampe and H. Hamadeh, Metalorganic chemical vapor epitaxy and doping of ZnMgSSe heterostructures for blue emitting devices 170 (1997) 30
Heuken, M., see Taudt, W. 170 (1997) 491

Heuken, M., see Gurskii, A.L. 170 (1997) 533
Heuken, M., see Prösch, G. 170 (1997) 537
Heuken, M., see Schneider, A. 170 (1997) 767
Heuken, M., see von Eichel-Streiber, C. 170 (1997) 783
He Youping, Su Genbo, Yu Xianchun, Li Zhengdong, Huang Bingrong, Jang Rihong and Zhao Qingran, Growth of α-nickel sulphate hexahydrate for ultraviolet filters 169 (1996) 193
He Youping, Zeng Jinbo, Wu Dexang, Su Genbo and Yan Mingshan, New technology of KDP crystal growth 169 (1996) 196
Hibino, M., see Tanaka, S. 166 (1996) 334
Hidaka, J., see Arai, T. 170 (1997) 88
Higashi, I., see Okada, S. 166 (1996) 429
Higashikawa, I., see Murooka, K.-i. 169 (1996) 485
Higuchi, H., see Akane, T. 167 (1996) 32
Higuchi, M., see Hatta 163 (1996) 279
Higuchi, M., see Mass 165 (1996) 250
Higuchi, M., see Tsai, T.-L. 169 (1996) 764
Higuchi, Y., T. Okamoto and N. Yasuoka, The heterogeneity in a protein crystal revealed by synchrotron radiation 168 (1996) 99
Hiie, J., see Valdna 161 (1996) 177
Hill, C.W., G.B. Stringfellow and L.P. Sadwick, Tris-dimethylaminophosphorus reactions at low pressure on GaP, InP and quartz surfaces 162 (1996) 1
Hill, R., see Miles 161 (1996) 148
Hilton, A.M., see Davey, R.J. 166 (1996) 971
Hinks, D.G., see Zhang, K. 169 (1996) 73
Hiquily, N., see Lin, C.H. 166 (1996) 104
Hirabayashi, I., see Kitamura, T. 166 (1996) 854
Hirabayashi, I., see Yamada, Y. 167 (1996) 566
Hiramatsu, K., see Ohuchi, Y. 170 (1997) 325
Hirata, A., see Hu, W.-R. 169 (1996) 380
Hirotani, M., T.E. Sale, J. Woodhead, J.S. Roberts, P.N. Robson, T. Saka and T. Kato, High power, high speed surface emitting LEDs with an InGaAs quantum well 170 (1997) 390
Hirt, G., see Müller, M. 166 (1996) 636
Hiruma, K., H. Murakoshi, M. Yazawa and T. Katsuyama, Self-organized growth of GaAs/InAs heterostructure nanocylinders by organometallic vapor phase epitaxy 163 (1996) 226
Hisa, Y., see Takiguchi, T. 170 (1997) 705
Hjelt, K. and T. Tuomi, Photoluminescence and electrical properties of MOVPE-grown zinc-doped gallium antimonide on gallium arsenide 170 (1997) 794
Ho, I.H., see Murata, H. 170 (1997) 219
Ho, I.H., see Chun, Y.S. 170 (1997) 263
Hodby, J.W., see Chowdhury, A.J.S. 166 (1996) 863
Hodby, J.W., see Chowdhury, A.J.S. 169 (1996) 405
Hoffmann, B., see Amon, J. 166 (1996) 646
Hofmann, D.M., see Christmann 161 (1996) 259
Hofsäss, H., see Restle 161 (1996) 168
Hofsäss, H., see Jahn 161 (1996) 172
Hogyoku, M., see Takahashi, T. 168 (1996) 130
Hohman, J.L., see Burgess, D.R. 166 (1996) 763
Höhnsdorf, F., see Protzmann, H. 170 (1997) 155
Hollfelder, M., S. Hon, B. Setzer, K. Schimpf, M. Horstmann, Th. Schäpers, D. Schmitz, H. Hardtdegen and H. Lüth, Demonstration of the N_2 carrier process for LP-MOVPE of III/V's 170 (1997) 103
Hollfelder, M., see Hartmann, A. 170 (1997) 605
Holmes, A.L., see Islam, M.R. 170 (1997) 413
Holmes Jr., A.L., see Gaffney, M.S. 167 (1996) 8
Holstein, W.L., Methods to improve the P/As compositional uniformity of InGaAsP thin films prepared by MOCVD 167 (1996) 525
Homma, Y., see Inoue 164 (1996) 88
Hon, M.-H., see Leu, I.-C. 167 (1996) 607
Hon, S., see Hollfelder, M. 170 (1997) 103
Honda, T., S.W. Lim, K. Inoue, K. Hara, H. Munekata, H. Kukimoto, F. Koyama and K. Iga, Diode characteristics of Li_3N-diffused ZnSe grown by MOVPE 170 (1997) 503
Hong, S.-K., H.-G. Lee, J.-J. Lee, S.-G. Kim, K.-E. Pyun and H.-M. Park, Molecular beam epitaxy growth of indium-rich $In_xGa_{1-x}As/In_yAl_{1-y}As/InP$ structures towards high channel conductivity for a high electron mobility transistor using a linearly graded buffer layer 169 (1996) 435
Hong, Xinguo and Yufeng Chen, Variation of the viscosity of molten potassium niobate with annealing time 165 (1996) 81
Hooper, S.E., see Cheng, T.S. 166 (1996) 597
Höpfner, C., see Thomas, B. 170 (1997) 808
Hopkins, F.K., see Singh 163 (1996) 398
Horikawa, H., see Nakamura, K. 170 (1997) 377
Horikoshi, Y., see Ando, S. 170 (1997) 719
Horowitz, A., S. Biderman, Y. Einav, G. Ben Amar and D. Gazit, Improved control of sapphire crystal growth 167 (1996) 183
Horowitz, A., see Brandon, S. 167 (1996) 190
Horstmann, M., see Hollfelder, M. 170 (1997) 103
Hosoi, N., see Fujii, K. 170 (1997) 679
Hosoki, S., see Hasegawa, T. 166 (1996) 314
Hotta, Y., see Tsutsui 163 (1996) 440
Hou, W.B., see Yuan, D.R. 166 (1996) 545
Houng, M.P., see Sze, P.W. 169 (1996) 27
Hourai, M., see Miyano, T. 166 (1996) 469
Hourai, M., see Kanda, T. 166 (1996) 663
Hou Xun, see Wang Xiaoliang 164 (1996) 281
Hsieh, Jin-Yuan, see Hwang 165 (1996) 147
Hsieh, W.C. and C.W. Lan, Experimental study on floating-zone tube growth and comparison with computer simulation 165 (1996) 447
Hsu, K.Y.J., see Hwang 161 (1996) 73
Hsu, T.C., see Chun, Y.S. 170 (1997) 263
Hu, C., see Chen, J.-C. 166 (1996) 151
Hu, W.R., see Han, J.H. 169 (1996) 129

Hu, W.-R., A. Hirata and S.-i. Nishizawa, Diffusion dominated process for the crystal growth of a binary alloy 169 (1996) 380
Hu, W.S., see Guo 165 (1996) 187
Hu, X.B., S.S. Jiang, X.R. Huang, W. Zeng, W.J. Liu, C.T. Chen, Q.L. Zhao, J.H. Jiang, Z.G. Wang, Y.L. Tian and Y. Han, The formation mechanisms of dislocations and negative crystals in LiB_3O_5 single crystals 163 (1996) 266
Hu, X.B., see Liu, W.J. 169 (1996) 534
Huang, C., see Wang, Y. 167 (1996) 176
Huang, Helan, see Yang 165 (1996) 70
Huang, J.-W., see Kuech 163 (1996) 171
Huang, M., see Chen, S. 170 (1997) 433
Huang, M.-H., see Huang, Y. 166 (1996) 867
Huang, Xinming, Yaqin Zhao, Kunquan Lu and Dingyuan Tang, Density, surface tension and viscosity of BaB_2O_4 melt 165 (1996) 413
Huang, X.R., see Hu 163 (1996) 266
Huang, X.R., see Liu, W.J. 169 (1996) 534
Huang, Y., M.-H. Huang and J.M. Jian, Primary crystallization field and crystal growth of $Bi_2Sr_2CaCu_2O_x$ 166 (1996) 867
Huang, Z.C., J.C. Chen and D. Wickenden, Characterization of GaN using thermally stimulated current and photocurrent spectroscopies and its application to UV detectors 170 (1997) 362
Huang Bingrong, see He Youping 169 (1996) 193
Huitema, E. and J.P. van der Eerden, Defect formation during crystal growth 166 (1996) 141
Hull, R., see Islam, M.R. 170 (1997) 413
Hultman, L., see Radamson, H.H. 167 (1996) 495
Humphrey, D., see Hamm 164 (1996) 362
Hung, C.Y., M.V. Weckwerth, A.F. Marshall, Y.C. Pao and J.S. Harris Jr., Observation of superstructure in high-quality pseudomorphic films of NiAl grown on GaAs 169 (1996) 201
Hurd, C., see Wajid, A. 170 (1997) 237
Hwang, Chi-Chuan, Jin-Yuan Hsieh and Hsuan-Hao Liu, The effects of an applied electric field on the linear stability in the solidification of a dilute binary alloy 165 (1996) 147
Hwang, H.L., K.Y.J. Hsu and H.Y. Ueng, Fundamental studies of p-type doping of CdTe 161 (1996) 73
Hwang, I.G. and C.K. Choi, An analysis of the onset of compositional convection in a binary melt solidified from below 162 (1996) 182
Hwang, N.M., J.H. Hahn and D.Y. Yoon, Charged cluster model in the low pressure synthesis of diamond 162 (1996) 55
Hwang, S.-M., see Kim, S.-I. 170 (1997) 665
Hwu, R.J., see Sadwick 164 (1996) 285
Hyeon, J.Y., see Dadgar, A. 170 (1997) 173
Hyuga, F., see Nittono, T. 170 (1997) 762

Ichimiya, A., H. Nakahara and Y. Tanaka, Atomic structures of Si(111) surface during silicon epitaxial growth 163 (1996) 39
Ichimiya, A., see Itoh, Y. 166 (1996) 61
Ido, T., see Goto, H. 170 (1997) 510
Iga, K., see Honda, T. 170 (1997) 503
Igasaki, Y., M. Maeda, M. Harada and T. Fujiwara, Preparation of $CuInSe_2$ films by hot-wall evaporation technique 167 (1996) 769
Iguchi, T., see Shibata, T. 167 (1996) 716
Iida, S., see Fukuda 161 (1996) 45
Iida, S., see Hayakawa, Y. 169 (1996) 613
Iizumi, K., see Okada, S. 166 (1996) 429
Ikari, A., K. Izunome, S. Kawanishi, S. Togawa, K. Terashima and S. Kimura, Influence of the thermal history of melts on the formation of grown-in defects in silicon 167 (1996) 361
Ikuhara, Y., see Kitamura, T. 166 (1996) 854
Ilegems, M., see Amano 164 (1996) 321
Ilegems, M., see Carlin 164 (1996) 470
Imaeda, M., see Kawaguchi, T. 166 (1996) 489
Imaeda, M., see Kawaguchi, T. 166 (1996) 493
Imaeda, M., see Kawaguchi, T. 169 (1996) 94
Imafuji, O., see Hashimoto, T. 169 (1996) 185
Imai, M., see Shiraishi, Y. 166 (1996) 685
Imai, S., see Kanaya 165 (1996) 172
Imai, T., see Takano, Y. 169 (1996) 621
Imaizumi, M., Y. Endoh, M. Suita, H. Sugimoto, K.-i. Ohtsuka, T. Isu and T. Ozeki, Gas-source molecular beam epitaxy of MgZnSSe for fabricating blue/green laser diodes 169 (1996) 293
Inami, S.-i., see Miyano, T. 166 (1996) 469
Ingle, N.K., C. Theodoropoulos, T.J. Mountziaris, R.M. Wexler and F.T.J. Smith, Reaction kinetics and transport phenomena underlying the low-pressure metalorganic chemical vapor deposition of GaAs 167 (1996) 543
Ingle, N.K., see Theodoropoulos, C. 170 (1997) 72
Inomoto, Y., see Sakata, Y. 170 (1997) 456
Inoue, H., see Nishida, M. 168 (1996) 284
Inoue, K., see Honda, T. 170 (1997) 503
Inoue, N., Y. Homma, J. Osaka and T. Araki, Behavior of monolayer holes on MBE grown GaAs surfaces during annealing revealed by in situ scanning electron microscopy 164 (1996) 88
Inoue, T., see Takemoto 163 (1996) 100
Instone, T., see van Gelder, R.N.M.R. 166 (1996) 189
Ioku, K., see Yanagisawa 163 (1996) 285
Iov, V., see Alexandru, H.V. 166 (1996) 162
Iov, V., Characterization of garnet laser crystals by cathodoluminescence emission in a scanning electron microscope 167 (1996) 180
Irikura, M., see Fujiwara, S. 167 (1996) 357
Irisawa, T. and Y. Arima, Structural feature of surface in MBE growth Monte Carlo simulation 163 (1996) 22
Irvine, K., see Dmitriev, V. 166 (1996) 601
Irvine, S.J.C., see Stafford, A. 170 (1997) 182
Isaenko, L., A. Merkulov, V. Tyurikov, R. Mashkovtsev and S. Gromilov, Growth and

characterization of $KTi_{1-x}Zr_xAsO_5$ single crystals 166 (1996) 502
Ishibashi, A., see Toda, A. 170 (1997) 461
Ishida, M., see Hashimoto, T. 169 (1996) 185
Ishida, M., see Wado, H. 169 (1996) 457
Ishida, M., see Suda, Y. 169 (1996) 672
Ishikawa, H., see Matsubara, I. 167 (1996) 570
Ishikawa, M., see Pan, W. 170 (1997) 585
Ishikawa, T., see Tanaka, S. 166 (1996) 334
Ishikawa, Y., K. Nakakoshi and T. Fukui, Novel in situ optical monitoring method for selective area metalorganic vapor phase epitaxy 167 (1996) 434
Ishino, M., see Otsuka, N. 170 (1997) 626
Ishiwara, H., see Moon 162 (1996) 154
Ishizaki, T., M. Maruyama, Y. Furukawa and J.G. Dash, Premelting of ice in porous silica glass 163 (1996) 455
Ishizawa, Y., see Otani 165 (1996) 319
Ishizawa, Y., see Louchev, O.A. 167 (1996) 333
Islam, M.R., R.D. Dupuis, A.L. Holmes, A.P. Curtis, N.F. Gardner, G.E. Stillman, J.E. Baker and R. Hull, Luminescence characteristics of InAlP–InGaP heterostructures having native-oxide windows 170 (1997) 413
Isopescu, R., M. Mocioi, F. Zahanagiu and L. Filipescu, Growth rate models and kinetics estimation for $CaCO_3$ precipitated in continuous crystallizers 167 (1996) 260
Isu, T., see Gotoda 164 (1996) 308
Isu, T., see Imaizumi, M. 169 (1996) 293
Itagaki, T., see Takiguchi, T. 170 (1997) 705
Ito, A., S. Nakamura, H. Aoki, M. Akao, K. Teraoka, S. Tsutsumi, K. Onuma and T. Tateishi, Hydrothermal growth of carbonate-containing hydroxyapatite single crystals 163 (1996) 311
Ito, A., see Onuma, K. 167 (1996) 773
Ito, H. and K. Kurishima, Influence of gallium sources on carbon incorporation efficiency into InGaAs grown by metalorganic chemical vapor deposition 165 (1996) 215
Ito, K., see Tanaka, S. 168 (1996) 44
Ito, R., see Yaguchi, H. 170 (1997) 353
Ito, R., see Pan, W. 170 (1997) 585
Ito, S., see Kawaguchi, T. 169 (1996) 94
Itoh, K., see Hashimoto, T. 169 (1996) 185
Itoh, O., see Nugraha 163 (1996) 353
Itoh, O., see Nugraha 165 (1996) 402
Itoh, Y., see Harada 163 (1996) 31
Itoh, Y., I. Takahashi, A. Ichimiya, J. Harada and N.S. Sokolov, Structure of CaF_2/Si(111) long interface 166 (1996) 61
Itoh, Y., see Sokolov, N.S. 169 (1996) 40
Ivanov, M.A., see Terada, Y. 167 (1996) 369
Ivanov, N.P., see Komar, V.K. 160 (1996) 419
Ivanov, Yu.M., Growth and homogeneity region of CdTe 161 (1996) 12
Ivantsov, V.A., see Nikolaev, A.E. 166 (1996) 607
Iwai, S., see Tanaka, S. 170 (1997) 329
Iwami, M., see Mizuno, K. 166 (1996) 146
Iwanaga, H., see Fujii, M. 166 (1996) 99
Izmailov, A.F. and A.S. Myerson, Relationship between solution shear viscosity and density at the saturation point 166 (1996) 261
Izmailov, A.F., see Myerson, A.S. 166 (1996) 981
Izumi, K., S. Sawamura and M. Ataka, X-ray topography of lysozyme crystals 168 (1996) 106
Izumi, K., Growth and lattice defects of hexamethylbenzene crystals 169 (1996) 325
Izunome, K., see Togawa 165 (1996) 362
Izunome, K., see Ikari, A. 167 (1996) 361
Izuta, T., see Kaito, C. 167 (1996) 580

Jackman, R.B., see Foord 164 (1996) 208
Jackson, K.A., G.H. Gilmer, D.E. Temkin and K.M. Beatty, Microsegregation far from equilibrium 163 (1996) 461
Jacobs, K., see Neubert 161 (1996) 229
Jagadish, C., see Li, G. 167 (1996) 421
Jagadish, C., see Clark, A. 170 (1997) 424
Jahn, S.G., see Burchard 161 (1996) 128
Jahn, S.G., see Restle 161 (1996) 168
Jahn, S.G., The ISOLDE Collaboration, H. Hofsäss, M. Restle, C. Ronning, H. Quintel, K. Bharuth-Ram and U. Wahl, Thermal stability of substitutional Ag in CdTe 161 (1996) 172
Jahrling, K. and S. Tait, Measurements of the evolution of porosity in a mushy layer 167 (1996) 285
Jain, F.C., see Gokhale 165 (1996) 25
Jain, F.C., see Bao, K.X. 170 (1997) 497
James, R.B., see Van Scyoc, J.M. 166 (1996) 384
Jamgotchian, H., see Billia, B. 167 (1996) 265
Jang Rihong, see He Youping 169 (1996) 193
Jansen, M., see Mawst, L.J. 170 (1997) 383
Janzén, E., see Tuominen 165 (1996) 233
Janzén, E., see Owman, F. 167 (1996) 391
Jędrzejczak, A., see Grasza 162 (1996) 173
Jenichen, B., see Silier, I. 166 (1996) 727
Jenkins, L.C., see Cheng, T.S. 166 (1996) 597
Jensen, K.F., see Salim, S. 169 (1996) 443
Jensen, K.F., see Wang, C.A. 170 (1997) 55
Jeon, G.-n., see Lee, C.-h. 167 (1996) 473
Jeppesen, S., see Junno 164 (1996) 66
Jeppesen, S., see Miller 164 (1996) 345
Jerman, G., see Palosz, W. 169 (1996) 20
Ji, Z., see Zhang, W. 169 (1996) 598
Jian, J.M., see Huang, Y. 166 (1996) 867
Jiang, H., see Yu, X. 166 (1996) 195
Jiang, J., see Spika, Z. 170 (1997) 257
Jiang, J.H., see Hu 163 (1996) 266
Jiang, J.H., see Liu, W.J. 169 (1996) 534
Jiang, M.H., see Yuan, D.R. 166 (1996) 545
Jiang, S.S., see Hu 163 (1996) 266
Jiang, S.S., see Liu, W.J. 169 (1996) 534

Jiang, Z., see Lu, X. 169 (1996) 665
Jie, W., see Ma, D. 169 (1996) 170
Jimbo, T., see Soga 163 (1996) 165
Jimbo, T., see Soga, T. 170 (1997) 447
Jiménez-González, A. and R. Suárez-Parra, Effect of heat treatment on the properties of ZnO thin films prepared by successive ion layer adsorption and reaction (SILAR) 167 (1996) 649
Jitsukawa, H., see Matsushita, H. 166 (1996) 712
Joelsson, K.B., see Radamson, H.H. 167 (1996) 495
Joerger, W., see Eiche 161 (1996) 271
Joerger, W., see Eiche, C. 166 (1996) 245
Joerger, W., see Fiederle, M. 166 (1996) 256
Johansen, T., see Christoffersen 163 (1996) 295
Johansen, T., see Christoffersen 163 (1996) 304
Johansson, J., see Seifert, W. 170 (1997) 39
Johnson, A.D., see Whitaker 164 (1996) 125
Johnson, N.P., see Yates, H.M. 170 (1997) 611
Johnston, J.E., see D'Arcy, A. 168 (1996) 175
Johnstone, J., see Hastie, G.P. 166 (1996) 67
Jones, A.C., see Taudt, W. 169 (1996) 243
Jones, A.C., see O'Brien, P. 170 (1997) 23
Jones, A.C., see Wang, C.A. 170 (1997) 55
Jones, E.D., see Ahmed 161 (1996) 223
Jones, E.D., see Biefeld 163 (1996) 212
Jones, I.P., see Yang, G. 166 (1996) 820
Jones, K.A., see Lareau, R.T. 167 (1996) 406
Jones, K.S., see Santana 164 (1996) 248
Jones, O.C., see Kim 165 (1996) 429
Jones, R., see Lareau, R.T. 167 (1996) 406
Jones, T.S., see Naji 164 (1996) 58
Joyce, B.A., see Zhang 164 (1996) 40
Joyce, B.A., see Naji 164 (1996) 58
Joyce, B.A., J.M. Fernández, M.H. Xie, A. Matsumura, J. Zhang and A.G. Taylor, Growth and doping of Si and SiGe films by hydride gas-source molecular beam epitaxy 164 (1996) 214
Joyce, B.A., see Fernández 164 (1996) 241
Joyce, B.A., see Sato 165 (1996) 345
Joyce, T.B., see Boyd 164 (1996) 51
Joyce, T.B., see Boyd 164 (1996) 71
Joyce, T.B., S.P. Westwater, P.J. Goodhew and R.E. Pritchard, Growth of carbon-doped GaAs, AlGaAs and InGaAs by chemical beam epitaxy and the application of in-situ monitoring 164 (1996) 371
Joyce, T.B., see Davidson 164 (1996) 383
Joyce, T.B., see Petkos 164 (1996) 415
Juang, W.-S., see Tai, C.Y. 166 (1996) 1040
Jullien, M., see Boyer, M. 167 (1996) 212
Jun, J., see Leszczynski, M. 169 (1996) 235
Jung, T. and G. Müller, Effective segregation coefficients: a comparison of axial solute distributions predicted by analytical boundary layer models and numerical calculations 165 (1996) 463
Junno, B., S. Jeppesen, M.S. Miller and L. Samuelson, A comparison of RHEED reconstruction phases on (100) InAs, GaAs and InP 164 (1996) 66
Juravel, Y., see Weiss, E. 166 (1996) 745
Jürgensen, H., see Bergunde, T. 170 (1997) 66
Jürgensen, H., see Beccard, R. 170 (1997) 97
Jurisch, M., see Müller, M. 166 (1996) 636

Kadinski, L., see Bergunde, T. 170 (1997) 66
Kaigawa, K., see Kawaguchi, T. 169 (1996) 94
Kaiser, R., see Roehle, H. 170 (1997) 109
Kaito, C., T. Sakamoto, D. Ban, T. Izuta, Y. Kitano and Y. Saito, A novel method to prepare carbon-coated quantum dots by an advanced gas evaporation method 167 (1996) 580
Kakimoto, K., K.-W. Yi and M. Eguchi, Oxygen transfer during single silicon crystal growth in Czochralski system with vertical magnetic fields 163 (1996) 238
Kakimoto, K., see Yi 165 (1996) 358
Kaldis, E., see Rossberg, A. 166 (1996) 354
Kalinichev, A.G., see Balitsky 162 (1996) 142
Kalisetty, S., see Bao, K.X. 170 (1997) 497
Kallavus, U., see Valdna 161 (1996) 177
Kamata, A., H. Yoshida, S. Chichibu and H. Nakanishi, Growth and doping characteristics of ZnSeTe epilayers by MOCVD 170 (1997) 518
Kamel, M., see Tanaka, Y. 169 (1996) 299
Kamiko, M., see Mogi, I. 166 (1996) 276
Kamiya, I., L. Mantese, D.E. Aspnes, D.W. Kisker, P.H. Fuoss, G.B. Stephenson and S. Brennan, Optical characterization of surfaces during epitaxial growth using RDS and GIXS 163 (1996) 67
Kamiya, T., M. Kimura, A. Tanaka and T. Sukegawa, Lattice compensation in LPE-grown GaAs crystals by simultaneous Te and Si doping 165 (1996) 482
Kanai, H., see Kimura, M. 167 (1996) 516
Kanaya, H., S. Imai and N. Sugiyama, Examination of pits appearing on selective grown Si film on SiO_2 patterned wafers 165 (1996) 172
Kanaya, M., see Takahashi, J. 167 (1996) 596
Kanda, I., T. Suzuki and K. Kojima, Influence of crucible and crystal rotation on oxygen-concentration distribution in large-diameter silicon single crystals 166 (1996) 669
Kanda, T., see Miyano, T. 166 (1996) 469
Kanda, T., M. Hourai, S. Miki, T. Shigematsu, H. Tomokage, T. Miyano, H. Morita and A. Shintani, Influence of melt-temperature fluctuations on striation formation in large-scale Czochralski Si growth systems 166 (1996) 663
Kaneda, N., see Ohuchi, Y. 170 (1997) 325
Kanedo, T., see Davidson 164 (1996) 396
Kaneko, F., see Kurasawa, M. 167 (1996) 151
Kaneko, T., see Naji 164 (1996) 58
Kaneko, Y., see Pan, W. 170 (1997) 585

Kang, H.-C., see Oh 164 (1996) 425
Kang, I.S., see Oh, H.J. 167 (1996) 345
Kaplun, A.B. and A.B. Meshalkin, Stable and metastable phase equilibrium in system Bi_2O_3–GeO_2 167 (1996) 171
Kapolnek, D., R.D. Underwood, B.P. Keller, S. Keller, S.P. DenBaars and U.K. Mishra, Selective area epitaxy of GaN for electron field emission devices 170 (1997) 340
Kapolnek, D., see Keller, S. 170 (1997) 349
Kapon, E., see Biasiol, G. 170 (1997) 600
Kapon, E., see Reinhardt, F. 170 (1997) 689
Kappelt, M., V. Türck, M. Grundmann, H. Cerva and D. Bimberg, Low pressure metal-organic chemical vapor deposition of InP/InAlAs/InGaAs quantum wires 170 (1997) 590
Karabashev, S.G., see Balbashov, A.M. 167 (1996) 365
Karandikar, S.C., see Sabharwal, S.C. 169 (1996) 304
Karpov, S.Yu., see Alexeev 162 (1996) 15
Karpov, S.Yu., see Alexeev, A.N. 166 (1996) 72
Karpov, S.Yu., see Alexeev, A.N. 166 (1996) 167
Karpov, S.Yu., Yu.N. Makarov and M.S. Ramm, Analytical model of silicon carbide growth under free-molecular transport conditions 169 (1996) 491
Kassemi, M., see Korpela 165 (1996) 455
Kastner, M.J., B. Hahn, R. Blumberg, E. Sossna, R. Duschl and W. Gebhardt, In situ reflectance difference spectroscopy of ZnSe-based semiconductor surfaces 170 (1997) 188
Kastner, M.J., see Hahn, B. 170 (1997) 472
Kasu, M. and N. Kobayashi, Surface diffusion kinetics of GaAs and AlAs metalorganic vapor-phase epitaxy 170 (1997) 246
Katabi, G., Yu. Koltypin, X. Cao and A. Gedanken, Self-assembled monolayer coatings of iron nanoparticles with thiol derivatives 166 (1996) 760
Katanić-Popović, J., see Lazić 165 (1996) 124
Katayama, M., see Habuka, H. 169 (1996) 61
Kato, K., see Okajima 165 (1996) 37
Kato, T., see Hirotani, M. 170 (1997) 390
Kato, T., see Soga, T. 170 (1997) 447
Kato, Takashi, see Kuriyama, K. 166 (1996) 631
Kato, Tomoharu, see Kuriyama, K. 166 (1996) 631
Katpatal, A.G., see Durugkar 162 (1996) 161
Katsura, T., see Kudo, N. 168 (1996) 118
Katsuyama, T., see Hiruma 163 (1996) 226
Kaufmann, B., see Scholz, F. 170 (1997) 321
Kawaguchi, D., see Ogata, K.-i. 170 (1997) 507
Kawaguchi, T., M. Imaeda, M. Minakata, T. Taniuchi and T. Fukuda, Growth of $LiNbO_3/LiNb_{1-x}Ta_xO_3$ multilayered waveguides on $LiNbO_3$ by liquid phase epitaxy 166 (1996) 489
Kawaguchi, T., M. Imaeda, R. Ohuchi, M. Minakata, T. Taniuchi and T. Fukuda, Growth-temperature dependence of the Li/Nb ratio in LPE-grown $LiNbO_3$ films estimated by second-harmonic generation 166 (1996) 493
Kawaguchi, T., H. Kitayama, M. Imaeda, S. Ito, K. Kaigawa, T. Taniuchi and T. Fukuda, Stoichiometry of liquid-phase epitaxial grown $LiNb_{1-x}Ta_xO_3$ films on $LiNbO_3$ substrates 169 (1996) 94
Kawakami, Y., see Fujita 164 (1996) 196
Kawamoto, K., see Yasuda, K. 166 (1996) 612
Kawanaka, T., see Okada 165 (1996) 31
Kawanishi, S., see Togawa 165 (1996) 362
Kawanishi, S., see Ikari, A. 167 (1996) 361
Kawarai, K., see Sugino, T. 166 (1996) 628
Kawasaki, S., see Rudolph 161 (1996) 28
Kawashima, K., see Tanaka, S. 168 (1996) 44
Kayzel, F.E., see Mihalik, M. 167 (1996) 621
Kearley, M.Q., see Wood, A.K. 170 (1997) 132
Kedar, E., see Weiss, E. 166 (1996) 745
Keidler, M., M. Popp, D. Ritter, B. Marheineke, H. Heinecke, H. Baumeister and E. Veuhoff, Growth of 1.55 μm DH laserstructures using TBAs and TBP in MOMBE 170 (1997) 161
Keller, B.P., see Kapolnek, D. 170 (1997) 340
Keller, B.P., see Keller, S. 170 (1997) 349
Keller, S., see Kapolnek, D. 170 (1997) 340
Keller, S., B.P. Keller, D. Kapolnek, U.K. Mishra, S.P. DenBaars, I.K. Shmagin, R.M. Kolbas and S. Krishnankutty, Growth of bulk InGaN films and quantum wells by atmospheric pressure metalorganic chemical vapour deposition 170 (1997) 349
Kera, T., see Ogata, K.-i. 170 (1997) 507
Kern, D., see Ng, J.D. 168 (1996) 50
Kern, R.C., see Davis 163 (1996) 93
Kern, R.S., see Davis 164 (1996) 132
Keshwani, K.S., see Sabharwal, S.C. 169 (1996) 304
Key, D.L., see Lisgarten 163 (1996) 474
Khattak, C.P., see Rao 162 (1996) 48
Khine, Y.Y. and J.S. Walker, Centrifugal pumping during Czochralski silicon growth with a strong, non-uniform, axisymmetric magnetic field 165 (1996) 372
Khusnatdinov, N.N. and V.F. Petrenko, Fast-growth technique for ice single crystals 163 (1996) 420
Kibune, M., see Yaguchi, H. 170 (1997) 353
Kičin, S., see Srnánek 165 (1996) 156
Kidd, P., D.J. Dunstan, H.G. Colson, M.A. Lourenço, A. Sacedón, F. González-Sanz, L. González, Y. González, R. García, D. González, F.J. Pacheco and P.J. Goodhew, Comparison of the crystalline quality of step-graded and continuously graded InGaAs buffer layers 169 (1996) 649
Kikuchi, K., see Tachibana, M. 166 (1996) 883
Kikuma, I. and T. Shiohara, Seeded melt growth of ZnSe crystals under Zn partial pressure 161 (1996) 60

Kikuzawa, M., see Hayakawa, Y. 169 (1996) 613
Kim, C.W., G.B. Stringfellow and L.P. Sadwick, CBE growth of InP using BPE and TBP: a comparative study 164 (1996) 104
Kim, E., see Taferner 164 (1996) 167
Kim, E., see Bensaoula 164 (1996) 185
Kim, E.K., see Kim, S.-I. 170 (1997) 665
Kim, E.K., M.H. Son, S.-K. Min, Y.K. Han and S.S. Yom, Growth of highly oriented TiO_2 thin films on InP(100) substrates by metalorganic chemical vapor deposition 170 (1997) 803
Kim, G.T., J.T. Lin, O.C. Jones, M.E. Glicksman, W.M.B. Duval and N.B. Singh, Effects of convection during the physical vapor transport process: application of laser Doppler velocimetry 165 (1996) 429
Kim, M., H.J. Osten, A. Wolff, C. Quick, H.P. Zeindl, J. Klatt and D. Knoll, The growth of nanometer Si/SiGe/Si quantum well wires with local molecular beam epitaxy in dependence on the shadow mask geometry 167 (1996) 508
Kim, M., H.J. Thieme, G. Lippert and H.J. Osten, Optical in situ measurements of temperature and layer thickness in Si molecular beam epitaxy 169 (1996) 681
Kim, M.H., see Biefeld 163 (1996) 212
Kim, Moo-Sung, see Son 165 (1996) 222
Kim, M.-S., see Kim, S.-I. 170 (1997) 665
Kim, S.-B., J.-R. Ro, S.-J. Park and E.-H. Lee, Selective area epitaxy of GaAs and InGaAs by ultra-high vacuum chemical vapor deposition using triethylgallium, trimethylindium, arsine, and monoethylarsine 169 (1996) 429
Kim, Seong-Il, see Son 165 (1996) 222
Kim, S.-G., see Hong, S.-K. 169 (1996) 435
Kim, S.-H., see Earnest, T. 168 (1996) 248
Kim, S.-I., M.-S. Kim, Y. Kim, S.-M. Hwang, B.-D. Min, C.S. Son, E.K. Kim and S.-K. Min, Lateral growth rate control of GaAs on patterned substrates by CCl_4 and CBr_4 during MOCVD 170 (1997) 665
Kim, Sung-Bock, Seong-Ju Park, Jeong-Rae Ro and El-Hang Lee, Fabrication of InGaAs/GaAs quantum wires on a non-(111) V-grooved GaAs substrate by chemical beam epitaxy 164 (1996) 356
Kim, Sung-Bock, see Ro 164 (1996) 377
Kim, Y., see Kim, S.-I. 170 (1997) 665
Kim, Yong, see Son 165 (1996) 222
Kimura, H., V.V. Kochurikhin, K. Shimamura and T. Fukuda, OH bands in $(Dy_{1-x}Gd_x)_3Ga_5O_{12}$, $Dy_3(Ga_{1-y}Al_y)_5O_{12}$ and related oxides grown by the Czochralski method 163 (1996) 393
Kimura, H., T. Numazawa and M. Sato, Crystal growth of BaB_2O_4 from melt using a Pt tube as a seed 165 (1996) 408
Kimura, M., see Kamiya 165 (1996) 482
Kimura, M., see Qin, Z. 167 (1996) 74
Kimura, M., N. Djilali, S. Dost, H. Kanai, A. Tanaka and T. Sukegawa, Liquid phase epitaxy of silicon: an experimental and numerical parametric study 167 (1996) 516
Kimura, M., see Udono, H. 169 (1996) 181
Kimura, M., S. Dost, H. Udono, A. Tanaka, T. Sukegawa and Z. Qin, A numerical analysis for the conversion phenomenon of GaAs to GaAsP on a GaP substrate in an LPE system 169 (1996) 697
Kimura, S., see Togawa 165 (1996) 362
Kimura, S., see Ikari, A. 167 (1996) 361
Kina, H., Y. Yamada, Y. Maruta and Y. Tamura, ZnS:Mn thin-film electroluminescent devices prepared by metalorganic chemical vapor deposition 169 (1996) 33
Kino, T., see Mizuno, K. 166 (1996) 146
Kinoshita, K. and T. Yamada, Spherical crystals of $Pb_{1-x}Sn_xTe$ grown in microgravity 165 (1996) 75
Kinoshita, K., S. Yoda, T. Nakamura, H. Sameshima, H. Ando, S. Anzawa and Y. Arai, Video imaging of the melting and solidification processes of the $PbBr_2$–$PbCl_2$ system under microgravity 166 (1996) 266
Kirmse, H., see Utke 162 (1996) 126
Kirpal, G., M. Gerhardt, G. Benndorf, R. Schwabe, F. Pietag, I. Pietzonka, G. Lippold, G. Wagner, R. Franzheld and V. Gottschalch, MOVPE growth and characterization of GaInAs(P) on (001) InP using diethyltertiarybutylarsine (DEtBAs) and tertiarybutylphosphine (TBP) as the group-V sources 170 (1997) 167
Kiselev, A.N., see Givargizov 162 (1996) 73
Kishimoto, D., see Nishinaga 163 (1996) 60
Kishimoto, S., see Kishishita, A. 167 (1996) 729
Kishishita, A., S. Kishimoto and N. Nagashima, Characterization of organic crystal products 167 (1996) 729
Kisker, D.W., G.B. Stephenson, J. Tersoff, P.H. Fuoss and S. Brennan, Atomic scale studies of epitaxial growth processes using X-ray techniques 163 (1996) 54
Kisker, D.W., see Kamiya 163 (1996) 67
Kitamura, M., M. Nishioka, R. Schur and Y. Arakawa, Direct observation of the transition from a 2D layer to 3D islands at the initial stage of InGaAs growth on GaAs by AFM 170 (1997) 563
Kitamura, T., Y. Yamada, Y. Shiohara, I. Hirabayashi, S. Tanaka, Y. Sugawara and Y. Ikuhara, Growth mechanism and crystalline orientation of liquid-phase epitaxially grown $YBa_2Cu_3O_{7-y}$ films 166 (1996) 854
Kitano, M., T. Okabe and M. Shiojiri, Morphology and growth mechanism of ZnO particles electro-crystallized on Zn in aqueous solution 166 (1996) 1116
Kitano, Y., see Kaito, C. 167 (1996) 580

Kitatani, T., see Kondow 164 (1996) 175
Kitayama, H., see Kawaguchi, T. 169 (1996) 94
Kito, M., see Otsuka, N. 170 (1997) 626
Kiyomi, K., see Fujii, K. 170 (1997) 679
Klapper, H., see Tanneberger, U. 166 (1996) 1074
Klatt, J., see Kim, M. 167 (1996) 508
Klein, J.P., see El Moussaouiti, M. 169 (1996) 118
Klemenz, C., see Mukaida, M. 169 (1996) 715
Klipstein, P.C., see Booker, G.R. 170 (1997) 777
Kloess, G., see Laasch 161 (1996) 34
Kloess, G., A. Cröll and K.W. Benz, Contactless measurement of dopant distribution using etch roughnesses 166 (1996) 319
Knauer, A., I. Rechenberg, F. Bugge, S. Gramlich, G. Oelgardt, A. Oster and M. Weyers, Influence of the growth temperature and substrate orientation on the layer properties of MOVPE-grown (Ga,In)(As,P)/GaAs 170 (1997) 281
Knight, C.A., see Nelson, J. 169 (1996) 795
Knight, R.W., see Mackowski 165 (1996) 323
Knoll, D., see Kim, M. 167 (1996) 508
Knorr, K., see Kurpas, P. 170 (1997) 203
Knorr, K., M. Pristovsek, U. Resch-Esser, N. Esser, M. Zorn and W. Richter, In situ surface passivation of III–V semiconductors in MOVPE by amorphous As and P layers 170 (1997) 230
Ko, S.-y., see Lee, C.-h. 167 (1996) 473
Kobayashi, K., see Takebe 162 (1996) 31
Kobayashi, N., Y. Kobayashi and K. Uwai, Chemical trend observed in anisotropic surface reflectance spectra of MOVPE by surface photoabsorption 170 (1997) 225
Kobayashi, N., see Kasu, M. 170 (1997) 246
Kobayashi, N., see Saito, H. 170 (1997) 372
Kobayashi, N., see Ando, S. 170 (1997) 719
Kobayashi, S., see Kurasawa, M. 167 (1996) 151
Kobayashi, Y., see Kobayashi, N. 170 (1997) 225
Kochurikhin, V.V., see Kimura 163 (1996) 393
Kochurikhin, V.V., see Terada, Y. 167 (1996) 369
Kodaira, K., see Hatta 163 (1996) 279
Koëbel, A., see Zheng 162 (1996) 135
Koebel, J.M., see Martel 161 (1996) 250
Koebel, J.M., see Zerrai 161 (1996) 264
Kogure, M., see Shibata, T. 167 (1996) 716
Koh, H.J., see Fukuda 161 (1996) 45
Koh, H.J., see Rudolph, P. 166 (1996) 578
Koh, H.J., see Schäfer, N. 166 (1996) 675
Koh, H.J., N. Schäfer, K. Shimamura and T. Fukuda, $Si_{1-x}Ge_x$ fiber crystals with functionally variant composition grown by micro-pulling-down technique 167 (1996) 38
Kohda, H. and K. Wada, The carbon doping mechanism in GaAs using trimethylgallium and trimethylarsenic 167 (1996) 557
Kohl, A., see Behres, A. 170 (1997) 655
Kohl, A., see Lakner, H. 170 (1997) 732
Köhler, A., see Müller, M. 166 (1996) 636
Köhler, R., see Silier, I. 166 (1996) 727
Köhne, L., see Dadgar, A. 170 (1997) 173
Kohno, T., see Shimamura 163 (1996) 388
Kohno, T., see Takeda, H. 169 (1996) 503
Koike, M., see Yan 165 (1996) 183
Kojima, H., see Galambos, L. 167 (1996) 660
Kojima, H., see Erdei, S. 167 (1996) 670
Kojima, H., see Tanaka, I. 169 (1996) 469
Kojima, K., see Kanda, I. 166 (1996) 669
Kojima, K., see Tachibana, M. 166 (1996) 883
Kolbas, R.M., see Keller, S. 170 (1997) 349
Koleske, D.D., see Wickenden, A.E. 170 (1997) 367
Koljonen, T., M. Sopanen, H. Lipsanen and T. Tuomi, Metalorganic vapor phase epitaxial growth of AlGaSb and AlGaAsSb using all-organometallic sources 169 (1996) 417
Koltypin, Yu., see Katabi, G. 166 (1996) 760
Komar, V.K., A.V. Gektin, N.P. Ivanov, Y.A. Nesterenko and N.V. Shiran, Growth and study of properties of pure and rare-earth-doped $KMgF_3$ crystals 160 (1996) 419
Komatsu, H., see Takemoto 163 (1996) 100
Komatsu, H., see Kurihara, K. 166 (1996) 904
Komatsu, H., see Hasegawa, K. 166 (1996) 925
Komatsu, H., see Sazaki, G. 169 (1996) 355
Komori, M., see Suzuki, M. 170 (1997) 661
Komura, T., see Yao 163 (1996) 78
Kon, J., see Uda, S. 167 (1996) 64
Konagai, M., see Oh 164 (1996) 425
Konagai, M., see Hatatani, S. 170 (1997) 297
Konagaya, Y., see Rudolph 161 (1996) 28
Kondow, M., K. Uomi, T. Kitatani, S. Watahiki and Y. Yazawa, Extremely large N content (up to 10%) in GaNAs grown by gas-source molecular beam epitaxy 164 (1996) 175
Kong, D., see Zhang, Y. 167 (1996) 373
Kong Meiying, see Wang Xiaoliang 164 (1996) 281
König, U., see Sobolev, N.A. 167 (1996) 502
Konuma, M., I. Silier, A. Gutjahr, P.O. Hansson, G. Cristiani, E. Czech, E. Bauser and F. Banhart, Centrifugal techniques for solution growth of semiconductor layers 166 (1996) 234
Konuma, M., see Silier, I. 166 (1996) 727
Korostelin, Yu.V., V.I. Kozlovsky, A.S. Nasibov and P.V. Shapkin, Vapour growth and characterization of bulk ZnSe single crystals 161 (1996) 51
Korpela, S.A., J. Ni, A. Chait and M. Kassemi, Radiative heat transfer in fiber drawing and crystal pulling 165 (1996) 455
Korshunov, F.P., see Sobolev, N.A. 167 (1996) 502
Koshimae, T., see Obara, K. 166 (1996) 271
Kosogov, A., see Heinrichsdorff, F. 170 (1997) 568
Kosyakov, V.I., see Kovalevski, S.V. 167 (1996) 208
Koszelak, S., see McPherson, A. 168 (1996) 74
Kotani, T., see Fujiwara, S. 169 (1996) 660
Kou, S., see Tao 165 (1996) 195
Kou, S., see Tao, Y. 169 (1996) 368

Koukitu, A., N. Takahashi and H. Seki, In situ monitoring of the GaAs growth process in halogen transport atomic layer epitaxy 163 (1996) 180
Koukitu, A., see Takahashi, N. 169 (1996) 463
Koukitu, A., N. Takahashi, T. Taki and H. Seki, Thermodynamic analysis of the MOVPE growth of $In_xGa_{1-x}N$ 170 (1997) 306
Kouta, H. and Y. Kuwano, β-BaB_2O_4 phase-matching-direction growth by the Czochralski method 166 (1996) 497
Koutsoukos, P.G., see Sabbides 165 (1996) 268
Koutsoukos, P.G., see Harmandas, N.G. 167 (1996) 719
Kováč, J., see Srnánek 165 (1996) 156
Kovács, T., see Pfeifer, J. 169 (1996) 727
Kovalets, M.O., see Nikonyuk 161 (1996) 186
Kovalevski, S.V., V.I. Kosyakov and I.R. Shelpakova, Cadmium purification by vacuum distillation in the presence of its oxide: thermodynamic modelling and experiment 167 (1996) 208
Kowalski, B., see Miller 164 (1996) 345
Koyama, A., see Asahi 161 (1996) 20
Koyama, F., see Honda, T. 170 (1997) 503
Koyama, T., see Hayakawa 163 (1996) 220
Koyama, T., see Hayakawa, Y. 169 (1996) 613
Koziol, J., see Anselmo 163 (1996) 359
Kožíšek, Z. and P. Demo, Comment on 'Transient kinetics of binary nucleation by Z. Kožíšek and P. Demo' [J. Crystal Growth 132 (1993) 491] 169 (1996) 413
Kozitsky, S.V. and A.N. Krasnov, Formation of "gigantic" crystallites in ZnS obtained by self-propagating high-temperature synthesis 165 (1996) 166
Kozlov, V.M. and L.P. Bicelli, Formation of structural defects during metal electrocrystallization 165 (1996) 421
Kozlovsky, V.I., see Korostelin 161 (1996) 51
Kozyrkov, V.V., see Scriven, G.J. 170 (1997) 813
Krabbes, G., see Werner 165 (1996) 258
Kramer, H.J.M., see Ó Meadhra, R. 166 (1996) 1046
Kramer, H.J.M., J.W. Dijkstra, A.M. Neumann, R. Ó Meadhra and G.M. van Rosmalen, Modelling of industrial crystallizers, a compartmental approach using a dynamic flowsheeting tool 166 (1996) 1084
Krämer, V., see Weise, S. 166 (1996) 718
Krasiński, M.J. and R. Rolandi, Ex situ investigation of surface topography of as-grown potassium dihydrogen phosphate crystals by atomic force microscopy 169 (1996) 548
Krasnov, A.N., see Kozitsky 165 (1996) 166
Krauns, C., see Yamada, Y. 166 (1996) 804
Krauns, C., see Nakamura, M. 166 (1996) 859
Kreissl, J. and H.-J. Schulz, Transition-metal impurities in II–VI semiconductors: characterization and switching of charge states 161 (1996) 239
Kreissl, J., see Christmann 161 (1996) 259
Kreuwel, K.B.G., see van Enckevort, W.J.P. 166 (1996) 156
Krey, J., see Gahn, C. 166 (1996) 1058
Krinke, J., see Voigt, A. 166 (1996) 694
Krishnankutty, S., see Keller, S. 170 (1997) 349
Kroll, W., see Thompson, A.G. 170 (1997) 92
Krost, A., see Heinrichsdorff, F. 170 (1997) 568
Krueger, C.W., S. Patnaik, C.A. Wang and M. Flytzani-Stephanopoulos, CH_3I vapor etching of GaAs in a vertical rotating-disk reactor 169 (1996) 51
Krumbholz, S., see Thygesen, J. 168 (1996) 308
Kubo, Y., see Obara, K. 166 (1996) 271
Kuchař, L., J. Drápala and J. Luňáček, Purification methods of Cd, Te and CdTe and periodicity of segregation coefficients of admixtures 161 (1996) 94
Kuchma, M.I., see Nikonyuk 161 (1996) 186
Kudaka, K., see Okada, S. 166 (1996) 429
Kudo, K., T. Sasaki and M. Yamaguchi, Migration-controlled narrow-stripe selective MOVPE for high-quality InGaAsP/InGaAsP MQWs 170 (1997) 634
Kudo, N., M. Ataka, H. Sasaki, T. Muramatsu, T. Katsura and M. Tanokura, Phase diagram of crystallization of *Aspergillus niger* acid proteinase A, a non-pepsin-type acid proteinase 168 (1996) 118
Kudou, K., see Okada, S. 166 (1996) 429
Kuech, T.F., S. Nayak, J.-W. Huang and J. Li, Chemical and physical effects in oxygen incorporation during the metalorganic vapor phase epitaxial growth of GaAs 163 (1996) 171
Kuech, T.F. and N.R. Perkins, Metalorganic vapor phase epitaxy of II–VI materials for visible light emitters 166 (1996) 558
Kuech, T.F., see Li, J. 170 (1997) 292
Kuech, T.F., see Liu, J. 170 (1997) 357
Kuech, T.F., see Booker, G.R. 170 (1997) 777
Kuhn, J., see Geng, C. 170 (1997) 418
Kühnle, J., R. Bergmann, J.H. Werner and M. Albrecht, Silicon surface passivation by metal layers for low-temperature epitaxy 163 (1996) 470
Kukimoto, H., see Watanabe, K. 169 (1996) 223
Kukimoto, H., see Nishida, K. 170 (1997) 312
Kukimoto, H., see Honda, T. 170 (1997) 503
Kumagawa, M., see Hayakawa 163 (1996) 220
Kumagawa, M., see Ozawa, T. 166 (1996) 463
Kumagawa, M., see Hayakawa, Y. 169 (1996) 613
Kumakura, K., J. Motohisa and T. Fukui, Formation and characterization of coupled quantum dots (CQDs) by selective area metalorganic vapor phase epitaxy 170 (1997) 700
Kumano, H., see Suemune, I. 170 (1997) 480
Kunz, Th., see Laasch 161 (1996) 34
Künzel, H., see Schelhase 164 (1996) 339
Künzel, H., P. Albrecht, R. Gibis, M. Hamacher and S. Schelhase, MOMBE growth of high quality GaInAsP ($\lambda_g = 1.05$ μm) for waveguide applications 164 (1996) 449
Kuo, H.C., see Sato 164 (1996) 47

Kuo, J.M., see Sato 164 (1996) 47
Kuphal, E., see Lindner, A. 170 (1997) 287
Kuphal, E., see Eisenbach, A. 170 (1997) 451
Kuppurao, S., see Xiao, Q. 167 (1996) 292
Kurasawa, M., S. Kobayashi, F. Kaneko, K. Oishi and S.-i. Ohta, Preparation and characterization of $AgGaS_2$ thin films by vacuum evaporation 167 (1996) 151
Kurihara, K., S. Miyashita, G. Sazaki, T. Nakada, Y. Suzuki and H. Komatsu, Interferometric study on the crystal growth of tetragonal lysozyme crystal 166 (1996) 904
Kurihara, K., see Sazaki, G. 169 (1996) 355
Kurishima, K., see Ito 165 (1996) 215
Kuriyama, K., Takashi Kato, Tomoharu Kato and H. Matsuno, Growth and photoluminescence properties of the filled tetrahedral semiconductor LiZnAs 166 (1996) 631
Kurosaka, S., see Shiraishi, Y. 166 (1996) 685
Kurpas, P., A. Rumberg, M. Weyers, K. Knorr, T. Bergunde, M. Sato and W. Richter, Growth monitoring by reflectance anisotropy spectroscopy in MOVPE reactors for device fabrication 170 (1997) 203
Kurpas, P., E. Richter, M. Sato, F. Brunner, D. Gutsche and M. Weyers, MOVPE growth of GaInP/GaAs hetero-bipolar-transistors using CBr_4 as carbon dopant source 170 (1997) 442
Küssel, E., see Althaus, M. 166 (1996) 566
Kusunoki, T., see Nakajima, K. 169 (1996) 217
Kuttler, M., see Dadgar, A. 170 (1997) 173
Kuwabara, H., see Tatsuoka, H. 166 (1996) 754
Kuwahara, K., see Takano, Y. 169 (1996) 621
Kuwano, N. and K. Oki, Ising model analysis of the formation mechanism of ordered structures in III–V alloy semiconductors 163 (1996) 122
Kuwano, Y., see Kouta, H. 166 (1996) 497
Kuwashima, S., see Onuma, K. 167 (1996) 387
Kuyper, L.F. and C.W. Carter Jr., Resolving crystal polymorphisms by finding "stationary points" from quantitative analysis of crystal growth response surfaces 168 (1996) 155
Kuźma, M., see Ciach 161 (1996) 234
Kuznetsov, A.V., see Givargizov 162 (1996) 73
Kuznetsov, A.V., E.V. Rakova, S.S. Lee and P.J. Chong, Influence of moisture and oxygen on the formation of cubic phase GaN in halide vapor phase epitaxial growth 167 (1996) 458
Kuznetsov, Yu.G., see Land, T.A. 166 (1996) 893
Kuznetsov, Yu.G., A.J. Malkin, A. Greenwood and A. McPherson, Michelson interferometric studies of protein and virus crystal growth 166 (1996) 913
Kuznetsov, Yu.G., A.J. Malkin, W. Glantz and A. McPherson, In situ atomic force microscopy studies of protein and virus crystal growth mechanisms 168 (1996) 63
Kuznetsov, Yu.G., see McPherson, A. 168 (1996) 74
Kvit, A.V., see Volkov 163 (1996) 377

Laasch, M., G. Kloess, Th. Kunz, R. Schwarz, K. Grasza, C. Eiche and K.W. Benz, Stress birefringence in vapour-grown CdTe and its correlation to the growth techniques 161 (1996) 34
Labardi, M., see Gennari, S. 166 (1996) 309
Lach, E., see Wiedemann, P. 170 (1997) 117
Lacklison, D.E., see Cheng, T.S. 166 (1996) 597
Lacmann, R., see Tanneberger, U. 166 (1996) 1074
Lafont, S., see Veesler, S. 168 (1996) 124
Laguerie, C., see Gerbaud, V. 166 (1996) 172
Laih, L.-W., see Liu, W.-C. 170 (1997) 438
Lairson, B.M., see Artymowicz, D.M. 169 (1996) 83
Lakner, H., S. Ungerechts, A. Behres, A. Kohl, B. Opitz, K. Heime and J. Woitok, Characterization of MOVPE grown InGaAsP superlattices for modulators by electron diffraction, X-ray diffraction and *Z*-contrast imaging 170 (1997) 732
Lakrimi, M., see Booker, G.R. 170 (1997) 777
Lamare, B., J.L. Benchimol, P. Ossart and G. Le Roux, CBE growth of InGaAs(P) alloys using TDMAAs and TBP 164 (1996) 122
Lambert, B., see Martel 161 (1996) 250
Lambert, B., see Zerrai 161 (1996) 264
Lampe, S., see Taudt, W. 169 (1996) 243
Lampe, S., see Heuken, M. 170 (1997) 30
Lampe, S., see Taudt, W. 170 (1997) 491
Lampe, S., see Gurskii, A.L. 170 (1997) 533
Lamvik, M., see Venkatasubramanian, R. 170 (1997) 817
Lan, C.W., see Hsieh 165 (1996) 447
Lan, C.W., M.C. Liang, C.R. Song and C.K. Fu, Shape control in crystal pulling from a floating die 166 (1996) 458
Lan, C.W., see Liang, M.C. 167 (1996) 320
Lan, C.W., Effect of axisymmetric magnetic fields on radial dopant segregation of floating-zone silicon growth in a mirror furnace 169 (1996) 269
Land, T.A., A.J. Malkin, Yu.G. Kuznetsov, A. McPherson and J.J. De Yoreo, Mechanisms of protein and virus crystal growth: an atomic force microscopy study of canavalin and STMV crystallization 166 (1996) 893
Land, T.A., see Smolski, I. 169 (1996) 741
Landers, K.M.I., see Cotta 164 (1996) 409
Landers, R., see Cotta 164 (1996) 409
Landgren, G., see Silfvenius, C. 170 (1997) 122
Landwehr, G., see Lugauer 161 (1996) 86
Landwehr, G., see Worschech 161 (1996) 134
Landwehr, G., see Fischer 161 (1996) 214
Lareau, R.T., K.A. Jones, T. Monahan, J.R. Flemish, R.L. Pfeffer, R.E. Sherriff, C.W. Litton, R. Jones, C.E. Stutz and D.C. Look, Comparison of OMVPE and MBE grown AlGaAs/InGaAs PHEMT structures 167 (1996) 406

Larson, D., see Steiner, B. 169 (1996) 1
Lassabatere, L., see Ferhat, M. 167 (1996) 122
Lau, S.S., see Wong 164 (1996) 159
Laube, G., see Wiedemann, P. 170 (1997) 117
Laügt, S.M., see Nataf 165 (1996) 1
Laune, F., see Legay 164 (1996) 314
Laval, J.Y., see Androussi, Y. 169 (1996) 209
Law, K.S., see Rao 162 (1996) 48
Lazić, S., J. Katanić-Popović, S. Zec and N. Miljević, Properties of hydroxyapatite crystallized from high temperature alkaline solutions 165 (1996) 124
Lazzarini, L., see Li 163 (1996) 195
Lebbou, K., see Wang, X.L. 167 (1996) 93
Leccabue, F., see di Cristoforo, A. 167 (1996) 644
Lee, C.-h., Y.-d. Choi, G.-n. Jeon, S.-c. Yu and S.-y. Ko, Epitaxial growth of ZnSe/GaAs (100) by hot wall epitaxy 167 (1996) 473
Lee, Ching-Ting, Jih-Hsien Yeh and Yen-Tang Lyu, Characterization of Nd-doped AsGaAs grown by liquid phase epitaxy 163 (1996) 343
Lee, E.-H., see Kim, S.-B. 169 (1996) 429
Lee, El-Hang, see Kim 164 (1996) 356
Lee, El-Hang, see Ro 164 (1996) 377
Lee, H. and J.S. Harris Jr., Vapor phase epitaxy of GaN using $GaCl_3/N_2$ and NH_3/N_2 169 (1996) 689
Lee, H.C., see Biefeld 163 (1996) 212
Lee, H.-G., see Roh, D.-W. 167 (1996) 468
Lee, H.-G., see Hong, S.-K. 169 (1996) 435
Lee, H.P., see Sato 164 (1996) 47
Lee, J.D., see Smolski, I. 169 (1996) 741
Lee, J.-J., see Roh, D.-W. 167 (1996) 468
Lee, J.-J., see Hong, S.-K. 169 (1996) 435
Lee, K.-J. and J.C. Chen, Regrowth of high-quality AlGaAs and AlGaInP layers and quantum well structures on Se-doped AlGaAs by MOVPE 170 (1997) 757
Lee, Min-Suk, see Son 165 (1996) 222
Lee, P.P., see Sadwick 164 (1996) 285
Lee, Seung-Cheol, see Chung 163 (1996) 249
Lee, S.S., see Kuznetsov, A.V. 167 (1996) 458
Lee, S.-T., see Zhang, Y. 169 (1996) 722
Lee, Y.-C., see Chen, J.-C. 166 (1996) 151
Lee, Y.H., see Song, M.H. 167 (1996) 157
Lees, A.K., see Zhang 164 (1996) 40
Lefaucheux, F., Y. Bernard, C. Vennin and M.C. Robert, Gel growth of 2-amino-5-nitropyridinium dihydrogen phosphate crystals followed by holographic interferometry 165 (1996) 90
Lefaucheux, F., see Vidal, O. 168 (1996) 40
Lefebvre, A., see Androussi, Y. 169 (1996) 209
Legay, P., F. Alexandre, J.L. Benchimol, M. Allovon, F. Laune and S. Fouchet, Selective area chemical beam epitaxy for butt-coupling integration 164 (1996) 314
Legrand, P., see Vuillard, L. 168 (1996) 150
Lehmann, M., see Vuillard, L. 168 (1996) 150
Lehoczky, S.L., see Chen, K.-T. 166 (1996) 731
Lehoczky, S.L., see Su, C.-H. 166 (1996) 736
Lehoczky, S.L., see Watring, D.A. 167 (1996) 478
Lehr, M.U., see Peka 161 (1996) 277
Lei, X.-Y., P. Wan, Q.-H. Wei, C.-H. Zhou and N.-B. Ming, Nucleation and growth of drop-like clusters in two-dimensional colloidal systems 166 (1996) 909
Lei, X.-Y., P. Wan, N. Xu, C.-H. Zhou and N.-B. Ming, Coarsening phenomenon in two-dimensional colloidal aggregation and crystallization 169 (1996) 570
Leister, H.-J., see Friedrich, J. 167 (1996) 45
Leitch, A.W.R., see Botha, J.R. 169 (1996) 629
Leitch, A.W.R., see Scriven, G.J. 170 (1997) 813
Le Marec, C., R. Guérin and P. Haldenwang, Radial macrosegregation induced by 3D patterns of solutal convection in upward Bridgman solidification 169 (1996) 147
Lengeling, G., see Beccard, R. 170 (1997) 97
Lentz, D., see Ambacher, O. 167 (1996) 1
Lentz, D., see Ambacher, O. 170 (1997) 335
Lenz, A., see Weise, S. 166 (1996) 718
Leo, G., see Mazzer, M. 170 (1997) 553
Leonyuk, L., G.-J. Babonas, A. Arakcheeva, A. Vetkin and V. Maltsev, Influence of the cation sublattice on the growth, structure and properties of single crystals of 123- and 2212-type high-T_c superconductors 167 (1996) 102
Le Roux, G., see Lamare 164 (1996) 122
Leroux, M., see Nataf 165 (1996) 1
Lesterlin, D., see Lestra, A. 167 (1996) 446
Lestra, A., F. Gaborit, E. Gaumont-Goarin, L. Goldstein, D. Lesterlin and Ph. Pagnod-Rossiaux, Etching of deep V-groove channels on a (001) InP substrate and regrowth by gas source molecular beam epitaxy 167 (1996) 446
Leszczynski, M., I. Grzegory, H. Teisseyre, T. Suski, M. Bockowski, J. Jun, J.M. Baranowski, S. Porowski and J. Domagala, The microstructure of gallium nitride monocrystals grown at high pressure 169 (1996) 235
Leu, I.-C., Y.-M. Lu and M.-H. Hon, Substrate effect on the preparation of silicon carbide whiskers by chemical vapor deposition 167 (1996) 607
Leusen, F.J.J., Ab initio prediction of polymorphs 166 (1996) 900
Levin, I., see Thygesen, J. 168 (1996) 308
Levine, L.E., see Steiner, B. 169 (1996) 1
Levoguer, C.L., see Foord 164 (1996) 190
Lew, A.Y., see Yan 164 (1996) 77
Leys, M.R., see Rongen 164 (1996) 263
Leys, M.R., see Vreeburg 164 (1996) 442
Leys, M.R., see Verschuren, C.A. 170 (1997) 650
Li, A.Z., J.X. Chen, M. Qi and Y.C. Ren, The effect of III–V ratio at the substrate surface on the quality of inP grown by GSMBE 164 (1996) 84

Li, A.Z., see Chen 164 (1996) 460
Li, B., X.B. Xiang, Z.P. You, Y. Xu and X.Y. Fei, Structure and device characteristics of $Al_xGa_{1-x}As$/GaAs solar cells 162 (1996) 43
Li, B., J.H. Chu, J.Q. Zhu, X.Q. Chen, J.Y. Cao and D.Y. Tang, Growth of $Hg_{1-x}Cd_xTe$ liquid phase epitaxial films on vicinal planes 169 (1996) 480
Li, Biao, J.H. Chu, J.Q. Zhu, X.Q. Chen, J.Y. Cao and D.Y. Tang, Morphology investigation of $Hg_{1-x}Cd_xTe$ liquid phase epitaxial films 163 (1996) 348
Li, C.Y. and D.H. Zhang, Effects of As cell temperature on oval defect density and C acceptor concentration of light Si-doped GaAs grown by molecular beam epitaxy 165 (1996) 15
Li, E., see Schall 165 (1996) 299
Li, G. and C. Jagadish, Confinement and concentration of electrons in Si δ-doped $Al_xGa_{1-x}As$ ($x = 0$ and 0.35) grown by metalorganic vapour phase epitaxy 167 (1996) 421
Li, H.D., see Cui, F.Z. 169 (1996) 557
Li, J., see Kuech 163 (1996) 171
Li, J. and T.F. Kuech, Surface morphology of carbon-doped GaAs grown by MOVPE 170 (1997) 292
Li, J., see Booker, G.R. 170 (1997) 777
Li, Ming, S.F. Cui, C. Dong, H. Cheng, F. Wu, Q. Cui and Z.H. Mai, Replication of steps from substrate surface to superlattice interfaces 163 (1996) 339
Li, N.Y., see Tu 163 (1996) 187
Li, N.Y., H.K. Dong, W.S. Wong and C.W. Tu, An evaluation of alternative precursors in chemical beam epitaxy: tris-dimethylaminoarsenic, tris-dimethylaminophosphorus, and tertiarybutylphosphine 164 (1996) 112
Li, N.Y., see Wong 164 (1996) 159
Li, N.Y., W.S. Wong, D.H. Tomich, H.K. Dong, J.S. Solomon, J.T. Grant and C.W. Tu, Growth study of chemical beam epitaxy of GaN_xP_{1-x} using NH_3 and tertiarybutylphosphine 164 (1996) 180
Li, Q., H. Nguyen Thi and B. Billia, Quantitative analysis of the influence of Peltier interface demarcation on directional solidification 167 (1996) 277
Li, S., Q. Xiang, D. Wang and K.L. Wang, Investigation of facet formation and competition in MBE growth 164 (1996) 235
Li, Wenming, see Yang 165 (1996) 70
Li, Y., see Bongers 162 (1996) 7
Li, Y., S. Linzen, P. Seidel, F. Machalett and F. Schmid, Preparation of epitaxial oxide thin films on Si(100) substrates with $CoSi_2$ surface layers 162 (1996) 147
Li, Y., G. Salviati, M.M.G. Bongers, L. Lazzarini, L. Nasi and L.J. Giling, On the formation of antiphase domains in the system of GaAs on Ge 163 (1996) 195
Li, Y. and L.J. Giling, A closer study on the self-annihilation of antiphase boundaries in GaAs epilayers 163 (1996) 203
Li, Z., see Wu, H. 167 (1996) 429
Liang, J., see Lu, L. 169 (1996) 637
Liang, M.C., see Lan, C.W. 166 (1996) 458
Liang, M.C. and C.W. Lan, Three-dimensional convection and solute segregation in vertical Bridgman crystal growth 167 (1996) 320
Liautard, B., see Ferhat, M. 167 (1996) 122
Liebertz, J., see Burianek, M. 166 (1996) 361
Liljas, A., see Garber, M. 168 (1996) 301
Lim, L.C., L.K. Tan and H.C. Zeng, Bubble formation in Czochralski-grown lead molybdate crystals 167 (1996) 686
Lim, S.W., see Honda, T. 170 (1997) 503
Lin, C.H., N. Gabas, J.P. Canselier and N. Hiquily, Influence of additives on the growth morphology of γ-aminobutyric acid 166 (1996) 104
Lin, C.M., see Chou, W.C. 169 (1996) 747
Lin, C.T., E. Schönherr, A. Schmeding, T. Ruf, A. Göbel and M. Cardona, Growth of CuCl single crystals composed of pure isotopes 167 (1996) 612
Lin, J.T., see Kim 165 (1996) 429
Lin, K.-W., see Liu, W.-C. 170 (1997) 438
Lin, L., see Chen, N. 167 (1996) 766
Lin, S.-X., see Zhou, M. 168 (1996) 142
Lin, S.-X., see Han, Q. 168 (1996) 181
Lin, S.-X., see Zhu, D.-W. 168 (1996) 275
Lindner, A., P. Velling, W. Prost, A. Wiersch, E. Kuphal, A. Burchard, R. Magerle, M. Deicher and F.J. Tegude, The role of hydrogen in low-temperature MOVPE growth and carbon doping of $In_{0.53}Ga_{0.47}As$ for InP-based HBT 170 (1997) 287
Linzen, S., see Li 162 (1996) 147
Lippert, G., see Kim, M. 169 (1996) 681
Lippold, G., see Kirpal, G. 170 (1997) 167
Lipsanen, H., see Koljonen, T. 169 (1996) 417
Lisgarten, J.N., D. Maes, M.H. Dao Thi, L. Wyns, D.L. Key and J.A. Marks, Crystal orientation effect under microgravity conditions 163 (1996) 474
Liszi, I. and M. Hasznos-Nezdei, Crystal growth of (E)-2-butenedioic acid from aqueous solution in batch-cooling crystallization 166 (1996) 179
Litton, C.W., see Lareau, R.T. 167 (1996) 406
Liu, B., see Chen, S. 170 (1997) 433
Liu, H.-C., see Su, C.-H. 166 (1996) 736
Liu, Hsuan-Hao, see Hwang 165 (1996) 147
Liu, H.Y., see Bevan, M.J. 170 (1997) 467
Liu, J. and R. Elliott, Lamellar fault formation during eutectic growth 162 (1996) 107
Liu, J. and R.H. Zee, Growth of molybdenum-based alloy single crystals using electron beam zone melting 163 (1996) 259
Liu, J., D. Zhi, J.M. Redwing, M.A. Tischler and T.F. Kuech, GaN films studied by

near-field scanning optical microscopy, atomic force microscopy and high resolution X-ray diffraction 170 (1997) 357
Liu, J.M., see Guo, X.L. 167 (1996) 378
Liu, K., see Lu, X. 169 (1996) 665
Liu, M.G., see Yuan, D.R. 166 (1996) 545
Liu, S., see Ma, D. 169 (1996) 170
Liu, W.-C., L.-W. Laih, J.-H. Tsai, K.-W. Lin and C.-C. Cheng, InGaAs–GaAs pseudomorphic heterostructure transistors prepared by MOVPE 170 (1997) 438
Liu, W.J., see Hu 163 (1996) 266
Liu, W.J., S.S. Jiang, X.R. Huang, X.B. Hu, W. Zeng, J.Q. Wei, J.Y. Wang, J.H. Jiang and Y. Han, Growth defects in Nb:KTP crystals observed by synchrotron radiation topography 169 (1996) 534
Liu, W.K., X.M. Fang, W.-L. Yuan, M.B. Santos, T. Chatterjee, P.J. McCann and E.A. O'Rear, Initial growth of CaF_2 and BaF_2/CaF_2 on Si(110) during molecular beam epitaxy 167 (1996) 111
Liu, Xi, see Meng 163 (1996) 232
Liu, X.Y. and P. Bennema, An inhomogeneous cell model and the growth of crystals 166 (1996) 112
Liu, X.Y. and P. Bennema, Prediction of the growth morphology of crystals 166 (1996) 117
Liu, Y. and G.H. Nancollas, Fluorapatite growth kinetics and the influence of solution composition 165 (1996) 116
Liu, Z.G., see Guo 165 (1996) 187
Liu, Z.G., see Guo, X.L. 167 (1996) 378
Liu Song, and Ma Rongjun, Synthesis and structure of hydrated europium carbonate 169 (1996) 190
Li Zhengdong, see He Youping 169 (1996) 193
Loginov, Y.Y., K. Durose, H.M. Al-Allak, S.A. Galloway, S. Oktik, A.W. Brinkman, H. Richter and D. Bonnet, Transmission electron microscopy of CdTe/CdS based solar cells 161 (1996) 159
Loh, K.P., see Foord 164 (1996) 208
Long, M.M., J.B. Bishop, T.L. Nagabhushan, P. Reichert, G.D. Smith and L.J. DeLucas, Protein crystal growth in microgravity review of large scale temperature induction method: bovine insulin, human insulin and human alpha interferon 168 (1996) 233
Longo, M., see Mazzer, M. 170 (1997) 553
Look, D.C., see Lareau, R.T. 167 (1996) 406
Lopez, J., see Mawst, L.J. 170 (1997) 383
López Galindo, A., see González-Muñoz 163 (1996) 434
López-Macipe, A., J. Gómez-Morales and R. Rodríguez-Clemente, Calcium carbonate precipitation from aqueous solutions containing Aerosol OT 166 (1996) 1015
López-Macipe, A., see Gómez-Morales, J. 166 (1996) 1020
Lorber, B., see Ng, J.D. 168 (1996) 50
Lorber, B. and R. Giegé, Containerless protein crystallization in floating drops: application to crystal growth monitoring under reduced nucleation conditions 168 (1996) 204
Lorberth, J., see Protzmann, H. 170 (1997) 155
Losurdo, M., see Bruno, G. 170 (1997) 301
Lottici, P.P., see Gennari, S. 166 (1996) 309
Louchev, O.A., Thermal effects and kinetics in step-flow crystal growth of α-HgI_2 163 (1996) 411
Louchev, O.A., S. Otani and Y. Ishizawa, The incorporation of convection in 1D models of float zone and traveling solvent techniques 167 (1996) 333
Louhi-Kultanen, M., see Sha, Z.L. 166 (1996) 1105
Lourenço, M.A., see Kidd, P. 169 (1996) 649
Lovergine, N., see Mazzer, M. 170 (1997) 553
Lu, D.-c., see Duan, S.-k. 170 (1997) 514
Lu, H.B., see Cui, F.Z. 169 (1996) 557
Lu, Jay W. and Falin Chen, Stability of double-diffusive convection in a freckle-free solidification system 165 (1996) 137
Lu, Kunquan, see Wen 165 (1996) 191
Lu, Kunquan, see Huang 165 (1996) 413
Lu, L., S. Feng, J. Liang, Z. Wang, J. Wang, Y. Wang and W. Ge, Characterization of deep centers in AlGaAs/InGaAs/GaAs pseudomorphic HEMT structures grown by molecular beam epitaxy and hydrogen treatment 169 (1996) 637
Lu, L., S. Feng, J. Xu, H. Yang, Z. Wang, J. Wang, Y. Wang and W. Ge, Deep centers in AlGaAs/GaAs GRIN-SCH SQW laser structures grown by MBE and MOCVD 169 (1996) 643
Lu, Lei, see Yang 165 (1996) 70
Lu, X., Z. Jiang, K. Liu, H. Zhu, X. Zhang and X. Wang, Co-evaporative Sb doping and crystalline quality in Si molecular beam epitaxy 169 (1996) 665
Lu, Y.-M., see Leu, I.-C. 167 (1996) 607
Lubyshev, D.I., see González-Borrero, P.P. 169 (1996) 424
Lugauer, H.-J., A. Waag, L. Worschech, W. Ossau and G. Landwehr, Generation of atomic group V materials for the p-type doping of wide gap II–VI semiconductors using a novel plasma cracker 161 (1996) 86
Luginets, A.M., S.A. Guretskii, A.P. Ges, A.S. Milovanov, L.V. Markova and V.S. Burak, The influence of growth conditions on the optical properties of barium betaborate single crystals 162 (1996) 89
Lu Haibo, see Wang Siqing 162 (1996) 69
Lukasiewicz, T., see Frukacz, Z. 169 (1996) 98
Lum, R., see Wajid, A. 170 (1997) 237
Luňáček, J., see Kuchař 161 (1996) 94
Lunardi, L., see Hamm 164 (1996) 362
Lundström, T., see Okada, S. 166 (1996) 429
Lunk, H.-J., see Pfeifer, J. 169 (1996) 727
Lusson, A., see Rzepka 161 (1996) 286

Lüth, H., see Hollfelder, M. 170 (1997) 103
Lüth, H., see Hartmann, A. 170 (1997) 605
Lux, B., see Donecker, J. 166 (1996) 303
Lyakhovitskaya, V., see Lyubomirsky 161 (1996) 90
Lyapin, S.G., see Booker, G.R. 170 (1997) 777
Lyu, Yen-Tang, see Lee 163 (1996) 343
Lyubomirsky, I., V. Lyakhovitskaya, J.F. Guillemoles, I. Riess, R. Triboulet and D. Cahen, Evidence for thermodynamically stable p/n junction, formed by Ag doping of (Hg,Cd)Te 161 (1996) 90
Lyutskanov, V.L., see Mouchovski 162 (1996) 79

Ma, C.L., see Cui, F.Z. 169 (1996) 557
Ma, D., W. Jie, S. Liu and W. Xu, Solute redistribution and growth velocity response in directional solidification process 169 (1996) 170
Maass, K., see Wienecke 161 (1996) 82
Machalett, F., see Li 162 (1996) 147
Macicek, J.J., see Nihtianova, D.D. 169 (1996) 527
Mackenzie, J.D., C.R. Abernathy, J.D. Stewart and G.T. Muhr, Growth of Group III nitrides by chemical beam epitaxy 164 (1996) 143
Mackett, P., see Capper 161 (1996) 104
Mackowski, D.W., R. Rammohan Rao and R.W. Knight, Effect of solid phase heat transfer and wall deposition on crystal growth in physical vapor transport ampoules 165 (1996) 323
Madella, M., see Rigo 164 (1996) 430
Madhukar, A., A unified atomistic and kinetic framework for growth front morphology evolution and defect initiation in strained epitaxy 163 (1996) 149
Maeda, M., see Sugino, T. 166 (1996) 628
Maeda, M., see Igasaki, Y. 167 (1996) 769
Maejima, T., see Yasuda, K. 166 (1996) 612
Maes, D., see Lisgarten 163 (1996) 474
Maes, J.W., see Werner 164 (1996) 223
Ma Fukang, see Wang Siqing 162 (1996) 69
Magerl, A., see Rossberg, A. 166 (1996) 354
Magerle, R., see Burchard 161 (1996) 128
Magerle, R., see Lindner, A. 170 (1997) 287
Magnanini, R., see Bocchi 165 (1996) 8
Magnanini, R., see Bignazzi, A. 169 (1996) 450
Magnetti, G., see Bertone, D. 170 (1997) 715
Mahnke, H.-E., see Hermann 161 (1996) 181
Mai, Z.H., see Li 163 (1996) 339
Maigné, P. and D. Coulas, Structural investigation of MOVPE grown InGaAs buffer layers 170 (1997) 743
Maiorov, M.A., see Alexeev, A.N. 166 (1996) 167
Majerfeld, A., see Mao, E. 170 (1997) 428
Majni, G., see di Cristoforo, A. 167 (1996) 644
Makarov, Yu.N., see Karpov, S.Yu. 169 (1996) 491
Makarov, Yu.N., see Bergunde, T. 170 (1997) 66
Maki, K., see Shigeta, Y. 166 (1996) 617
Makimoto, T., see Saito, H. 170 (1997) 372
Mäkinen, J., see Fischer 161 (1996) 214
Makita, K., see Tsuji 162 (1996) 25
Makita, K., see Tsuji, M. 170 (1997) 669
Maksimov, I.L., see Nishioka 163 (1996) 1
Mąlag, A. and W. Strupiński, MOVPE-grown (AlGa)As double-barrier multiquantum well (DBMQW) laser diode with low vertical beam divergence 170 (1997) 408
Malik, M.A., see Taudt, W. 169 (1996) 243
Malik, M.A., see O'Brien, P. 170 (1997) 23
Malik, R., see Hamm 164 (1996) 362
Malkin, A.J., see Land, T.A. 166 (1996) 893
Malkin, A.J., see Kuznetsov, Yu.G. 166 (1996) 913
Malkin, A.J., see Kuznetsov, Yu.G. 168 (1996) 63
Malkin, A.J., see McPherson, A. 168 (1996) 74
Malm, J.-O., see Deppert, K. 169 (1996) 13
Maltsev, V., see Leonyuk, L. 167 (1996) 102
Maltz, E., see Thygesen, J. 168 (1996) 308
Mancini, A.M., see Mazzer, M. 170 (1997) 553
Mandeville, P., see Moore 164 (1996) 485
Mangin, Ph., see Oderno 165 (1996) 175
Mani, S.S., see Singh, N.B. 166 (1996) 364
Manna, L., see Marmo, L. 166 (1996) 1027
Mansurov, L.G. and V.G. Savitsky, Ordered phase in HgCdTe thin films grown by reactive deposition in RF mercury glow discharge 161 (1996) 201
Mantese, L., see Kamiya 163 (1996) 67
Manth, T., D. Mignon and H. Offermann, The role of hydrodynamics in precipitation 166 (1996) 998
Mao, E. and A. Majerfeld, Growth of heavily C-doped GaAs/AlGaAs MQW structures by MOVPE for 2–3 μm normal incidence photodetectors 170 (1997) 428
Marchal, G., see Oderno 165 (1996) 175
Marcq, S., see Veesler, S. 168 (1996) 124
Marega Jr., E., see González-Borrero, P.P. 169 (1996) 424
Marfaing, Y., Fundamental studies on compensation mechanisms in II–VI compounds 161 (1996) 205
Marfaing, Y., see Martel 161 (1996) 250
Marfaing, Y., see Zerrai 161 (1996) 264
Marfaing, Y., see Rzepka 161 (1996) 286
Marheineke, B., M. Popp and H. Heinecke, Growth of GaInAs(P) using a multiwafer MOMBE 164 (1996) 16
Marheineke, B., see Keidler, M. 170 (1997) 161
Markgraf, S.A., see Mass 165 (1996) 250
Markgraf, S.A., see Tsai, T.-L. 169 (1996) 759
Markgraf, S.A., see Tsai, T.-L. 169 (1996) 764
Markl, J., see Christiansen, S. 166 (1996) 848
Markova, L.V., see Luginets 162 (1996) 89
Marks, J.A., see Lisgarten 163 (1996) 474
Marmo, L., L. Manna, F. Chiampo, S. Sicardi and G. Bersano, Influence of mixing on the particle size distribution of an organic precipitate 166 (1996) 1027
Ma Rongjun, see Liu Song 169 (1996) 190

Marrakchi, G., see Martel 161 (1996) 250
Marrakchi, G., see Zerrai 161 (1996) 264
Marschner, T., see Rettig, R. 170 (1997) 748
Marshall, A.F., see Hung, C.Y. 169 (1996) 201
Martel, G., J.Y. Moisan, B. Lambert, M. Gauneau, S. Stephan, N. Wolffer, P. Gravey, A. Aoudia, E. Rzepka, Y. Marfaing, R. Triboulet, M.C. Busch, M. Hadj-Ali, J.M. Koebel, P. Siffert, G. Bremond, A. Zerrai and G. Marrakchi, Influence of zinc on the photorefractivity behaviour of $Cd_{1-x}Zn_xTe$:V 161 (1996) 250
Martel, G., see Zerrai 161 (1996) 264
Marten, R., see Seidl, A. 166 (1996) 680
Mårtensson, P., see Owman, F. 167 (1996) 391
Martin, R.W., see Wood, A.K. 170 (1997) 132
Martin, T., see Whitaker 164 (1996) 125
Martin, T., see Whitaker 164 (1996) 296
Martinet, E., see Biasiol, G. 170 (1997) 600
Martínez-Cañamero, M., see González-Muñoz 163 (1996) 434
Martínez-López, J., M. González-Mañas, M.A. Caballero, E. Diéguez and B. Capelle, Synchrotron X-ray topography of bismuth silicon oxide crystals 166 (1996) 325
Martins, E., see Baldochi, S.L. 166 (1996) 375
Martins, R.B., see Cotta 164 (1996) 409
Maruta, Y., see Kina, H. 169 (1996) 33
Maruyama, M., see Ishizaki 163 (1996) 455
Mashkovtsev, R., see Isaenko, L. 166 (1996) 502
Masi, M., see Carrà, S. 166 (1996) 641
Mason, N.J., see Booker, G.R. 170 (1997) 777
Mass, J.L., J.M. Burlitch, S.A. Markgraf, M. Higuchi, R. Dieckmann, D.B. Barber and C.R. Pollock, Oxygen activity dependence of the chromium (IV) population in chromium-doped forsterite crystals grown by the floating zone technique 165 (1996) 250
Masumoto, K., see Yonenaga, I. 167 (1996) 616
Matada, S., see Rudolph 161 (1996) 28
Matkowskii, A., see Frukacz, Z. 169 (1996) 98
Matsubara, I., R. Funahashi, K. Ueno and H. Ishikawa, In situ observation of $Bi_2Sr_2CaCu_2O_x$ superconducting whisker growth 167 (1996) 570
Matsui, Y., see Otsuka, N. 170 (1997) 626
Matsumoto, K., see Fujiwara 165 (1996) 169
Matsumoto, K., see Fujiwara, S. 167 (1996) 357
Matsumoto, K., see Fujiwara, S. 169 (1996) 660
Matsumoto, K., see Arai, T. 170 (1997) 88
Matsumoto, S., see Akane, T. 167 (1996) 32
Matsumura, A., see Joyce 164 (1996) 214
Matsuno, H., see Kuriyama, K. 166 (1996) 631
Matsuoka, M., T. Fukuda, Y. Takagi and H. Takiyama, Purification of organic solid solutions by melt crystallization: comparison between layer and suspension crystallization 166 (1996) 1035
Matsushita, H., H. Jitsukawa and T. Takizawa, Thermal analysis of the chemical-reaction process for $CuGa_{1-x}In_xSe_2$ crystals 166 (1996) 712
Matsuzaki, T., see Noguchi, S. 168 (1996) 270
Mattocks, P.G., see Peck, J. 170 (1997) 523
Maung, N., see Gnoth, D.N. 170 (1997) 198
Maung, N., see Fan, G.H. 170 (1997) 485
Maung, N., see Poole, I.B. 170 (1997) 528
Maurin, M., see Tomasini 165 (1996) 203
Maurin, M., see Tomasini, P. 166 (1996) 590
Mause, K., see Eisenbach, A. 170 (1997) 451
Mawst, L.J., A. Bhattacharya, M. Nesnidal, J. Lopez, D. Botez, A.V. Syrbu, V.P. Yakovlev, G.I. Suruceanu, A.Z. Mereutza, M. Jansen and R.F. Nabiev, MOVPE-grown high CW power InGaAs/InGaAsP/InGaP diode lasers 170 (1997) 383
Maxey, C., see Capper 161 (1996) 104
Maximov, I., see Miller 164 (1996) 345
Mayer, K. and D. Woermann, Influence of a polycrystalline precipitation zone on the growth of single crystals using a gel method: growth of single crystals of $PbHPO_4$ 169 (1996) 317
Mayusumi, M., see Habuka, H. 169 (1996) 61
Mazuruk, K., see Su, C.-H. 166 (1996) 736
Mazzarella, L., see Sica, F. 168 (1996) 192
Mazzer, M., M. Longo, G. Leo, N. Lovergine, A.M. Mancini, A.V. Drigo, F. Romanato, C. Zanotti Fregonara and G. Salviati, Structural study of (100)CdTe epilayers grown by MOVPE on ZnTe buffered and unbuffered (100)GaAs 170 (1997) 553
McCann, P.J., see Liu, W.K. 167 (1996) 111
McCormick, K., see Sadwick 164 (1996) 285
McDonald, M., see Wajid, A. 170 (1997) 237
McEwan, A., R.I. Ristic, B.Yu. Shekunov and J.N. Sherwood, The growth and perfection of organic non-linear optical crystals: N-methyl urea (NMU) from methanol solution. II. Morphological instability 167 (1996) 701
McEwan, D., see Davey, R.J. 166 (1996) 971
McFadden, G.B., see Coriell, S.R. 169 (1996) 773
McPherson, A., see Land, T.A. 166 (1996) 893
McPherson, A., see Kuznetsov, Yu.G. 166 (1996) 913
McPherson, A., see Kuznetsov, Yu.G. 168 (1996) 63
McPherson, A., A.J. Malkin, Yu.G. Kuznetsov and S. Koszelak, Incorporation of impurities into macromolecular crystals 168 (1996) 74
Medelci, N., see Vilela 164 (1996) 465
Mei, X.B., see Bi 164 (1996) 256
Meier, M., see Hahn, B. 170 (1997) 472
Meliga, M., see Bertone, D. 170 (1997) 715
Mellikov, E., see Valdna 161 (1996) 164
Melo, P., see Urgiles 165 (1996) 245
Meng, Guangyao, Xi Liu, Song Xie and Dingkun Peng, ⟨0001⟩-oriented growth of AlN films on Si(111) by microwave plasma CVD with $AlBr_3$–NH_3–N_2 system 163 (1996) 232
Mengucci, P., see di Cristoforo, A. 167 (1996) 644
Menovsky, A.A., see Brück, E. 166 (1996) 394
Menovsky, A.A., see Mihalik, M. 167 (1996) 621

Mere, A., see Valdna 161 (1996) 177
Mereutza, A.Z., see Mawst, L.J. 170 (1997) 383
Merkulov, A., see Isaenko, L. 166 (1996) 502
Mersmann, A., see Gahn, C. 166 (1996) 1058
Mersmann, A., see Tanneberger, U. 166 (1996) 1074
Meshalkin, A.B., see Kaplun, A.B. 167 (1996) 171
Mesquita, O.N., see Figueiredo, J.M.A. 166 (1996) 222
Metzger, T., see Ambacher, O. 167 (1996) 1
Metzger, T., see Fischer, R.A. 170 (1997) 139
Metzger, T., see Ambacher, O. 170 (1997) 335
Meyer, B.K. and W. Stadler, Native defect identification in II–VI materials 161 (1996) 119
Meyer, B.K., see Christmann 161 (1996) 259
Meyer, S. and A.G. Ostrogorsky, Interface shape in the vertical Bridgman configuration with and without the submerged heater 166 (1996) 700
Michiyama, M., see Tachibana, M. 166 (1996) 883
Michler, J., see Albrecht, M. 167 (1996) 24
Miehr, A., see Fischer, R.A. 170 (1997) 139
Mignon, D., see Manth, T. 166 (1996) 998
Mihalik, M., F.E. Kayzel, A.A. Menovsky, R.W.A. Hendrikx, T.J. Gortenmulder and J.A. Mydosh, Crystal growth and characterisation of $UNi_4{}^{11}B$ ternary compound 167 (1996) 621
Mihashi, Y., see Takiguchi, T. 170 (1997) 705
Miki, K., see Sugahara, M. 168 (1996) 288
Miki, K., see Fukami, T.A. 168 (1996) 297
Miki, S., see Kanda, T. 166 (1996) 663
Miles, R.W., B. Ghosh, S. Duke, J.R. Bates, M.J. Carter, P.K. Datta and R. Hill, Formation of low resistance contacts to p-CdTe by annealing autocatalytically deposited Ni–P alloy coatings 161 (1996) 148
Miljević, N., see Lazić 165 (1996) 124
Miller, M.S., see Junno 164 (1996) 66
Miller, M.S., S. Jeppesen, B. Kowalski, I. Maximov and L. Samuelson, Directional dependence of InAs island formation on patterned GaAs 164 (1996) 345
Mills, V., see Baldock, P. 168 (1996) 170
Milovanov, A.S., see Luginets 162 (1996) 89
Min, B.-D., see Kim, S.-I. 170 (1997) 665
Min, S.-K., see Kim, S.-I. 170 (1997) 665
Min, S.-K., see Kim, E.K. 170 (1997) 803
Min, Suk-Ki, see Son 165 (1996) 222
Minagawa, S., see Suzuki, M. 170 (1997) 661
Minakata, M., see Kawaguchi, T. 166 (1996) 489
Minakata, M., see Kawaguchi, T. 166 (1996) 493
Minamide, M., see Yasuda, K. 166 (1996) 612
Miner, C.J., see Moore 164 (1996) 485
Ming, N.-B., see Lei, X.-Y. 166 (1996) 909
Ming, N.-B., see Lei, X.-Y. 169 (1996) 570
Minoda, H. and K. Yagi, In-situ observations of growths of Si and Ge on metal-adsorbed Si(111) surfaces by REM-RHEED 163 (1996) 48
Mircea, A., see Zimmermann, G. 170 (1997) 645
Misaki, H., see Shimura, T. 166 (1996) 786
Mishra, U.K., see Kapolnek, D. 170 (1997) 340
Mishra, U.K., see Keller, S. 170 (1997) 349
Mitchell, J., see Zhang, K. 169 (1996) 73
Mitra, P., F.C. Case, M.B. Reine, R. Starr and M.H. Weiler, Doping in MOVPE of HgCdTe: orientation effects and growth of high performance IR photodiodes 170 (1997) 542
Miura, K., see Mizutani, R. 168 (1996) 253
Miyano, T., S.-i. Inami, A. Shintani, T. Kanda and M. Hourai, Dynamical behaviour of Czochralski melts and its influence on crystal growth 166 (1996) 469
Miyano, T., see Kanda, T. 166 (1996) 663
Miyashita, S., see Takemoto 163 (1996) 100
Miyashita, S., see Kurihara, K. 166 (1996) 904
Miyashita, S., see Hasegawa, K. 166 (1996) 925
Miyashita, S., see Sazaki, G. 169 (1996) 355
Miyawaki, K., S. Noguchi, S. Harada and Y. Satow, Crystallography of succinimide hen egg-white lysozyme at low temperatures 168 (1996) 292
Miyazaki, N., H. Uchida, T. Tsukada and T. Fukada, Quantitative assessment for cracking in oxide bulk single crystals during Czochralski growth: development of a computer program for thermal stress analysis 162 (1996) 83
Miyazaki, Y., see Takiguchi, T. 170 (1997) 705
Miyazawa, S., see Sasaura, M. 166 (1996) 825
Miyazawa, S., Top-seeded solution growth of $Bi_{12}TiO_{20}$ single crystals doped with P 167 (1996) 638
Miyazawa, S., see Mukaida, M. 169 (1996) 715
Miyazawa, Y., S. Morita and H. Sekiwa, Flow in oxide melts in a high magnetic field 166 (1996) 286
Miyazawa, Y., see Morita, S. 166 (1996) 370
Miyoshi, S., see Yaguchi, H. 170 (1997) 353
Mizukoshi, T., see Yao 165 (1996) 198
Mizuno, K., A. Tamiya, K. Ono, M. Iwami, E. Hashimoto and T. Kino, Vacancy-type dislocation loops observed at fairly high temperatures in nearly perfect Al crystals 166 (1996) 146
Mizuno, Y., S.-i. Uekusa and H. Okabe, Hydrodynamic description of epitaxial film growth in a horizontal reactor 170 (1997) 61
Mizutani, R., K. Miura, T. Nakayama, I. Shimada, Y. Arata and Y. Satow, Crystallization and crystallographic studies on Fab fragments of anti-nitrophenol antibodies from primary and secondary immune responses 168 (1996) 253
Mnushkina, I., see Garrett, M.H. 166 (1996) 550
Mo, R., see Bao, K.X. 170 (1997) 497
Mocioi, M., see Isopescu, R. 167 (1996) 260
Moerman, I., see Zhang, X. 170 (1997) 83
Moerman, I., see Van der Stricht, W. 170 (1997) 344
Moerman, I., see D'Hondt, M. 170 (1997) 616
Moerman, I., see Vanderbauwhede, W. 170 (1997) 738

Mogi, I. and M. Kamiko, Striking effects of magnetic field on the growth morphology of electrochemical deposits 166 (1996) 276
Mogilevsky, R., see Zhang, K. 169 (1996) 73
Moisan, J.Y., see Martel 161 (1996) 250
Moisan, J.Y., see Zerrai 161 (1996) 264
Moiseev, I.I., see Volkov 163 (1996) 377
Moldoveanu, M., see Stănculescu, F. 166 (1996) 183
Momirlan, M., see Badescu, V. 169 (1996) 309
Momonaga, M., J. Stávek and J. Ulrich, Interpretation of dissolution rates by the reaction fractal dimensions 166 (1996) 1053
Momose, M., see Watanabe, K. 169 (1996) 223
Monahan, T., see Lareau, R.T. 167 (1996) 406
Monteil, Y., see Thévenot, V. 170 (1997) 251
Monti, R., see Savino 165 (1996) 308
Moon, B.K. and H. Ishiwara, Epitaxial growth of conductive strontium-vanadate films on Si(100) substrates and their electrical resistivities 162 (1996) 154
Moon, R.L., MOVPE: is there any other technology for optoelectronics? 170 (1997) 1
Moore, W.T., P. Mandeville, R.W. Streater and C.J. Miner, Device quality AlGaAs grown by chemical beam epitaxy 164 (1996) 485
Morato, S.P., see Baldochi, S.L. 166 (1996) 375
Morato, S.P., see Ranieri, I.M. 166 (1996) 423
Moreno, A., D. Rondón and J.M. García-Ruiz, Growth of shaped single crystals of proteins 166 (1996) 919
Moreno, A., see Otálora, F. 168 (1996) 93
Moreno, A., see Dominguez-Vera, J.M. 168 (1996) 138
Moriglioni, M., see Fornari, R. 166 (1996) 572
Morimoto, T., see Sakata, Y. 170 (1997) 456
Morishita, T., see Becht, M. 170 (1997) 799
Morita, H., see Kanda, T. 166 (1996) 663
Morita, S., see Miyazawa, Y. 166 (1996) 286
Morita, S., T. Watanabe, M. Funayama, Y. Miyazawa and M. Sekita, The growth of $(Tb_xGd_{1-x})AlO_3$ single crystals by the Czochralski method 166 (1996) 370
Moritz, A., see Geng, C. 170 (1997) 418
Morlang, S., see Thygesen, J. 168 (1996) 308
Morris Hotsenpiller, P.A., see Burgess, D.R. 166 (1996) 763
Morris Hotsenpiller, P.A., G.A. Wilson, A. Roshko, J.B. Rothman and G.S. Rohrer, Heteroepitaxial growth of TiO_2 films by ion-beam sputter deposition 166 (1996) 779
Morrison, J.W., see Davey, R.J. 166 (1996) 971
Moseley, A.J., see Wood, A.K. 170 (1997) 132
Moser, M., K.H. Gulden, J. Epler and H.P. Schweizer, High performance deep red AlAs/AlGaAs top-emitting VCSELs grown by MOVPE at high growth rates 170 (1997) 404
Motogaito, A., see Udono, H. 169 (1996) 181
Motohisa, J., see Hara, S. 170 (1997) 579
Motohisa, J., see Kumakura, K. 170 (1997) 700
Motojima, S., see Fujii, M. 166 (1996) 99
Mouchovski, J.T., I.V. Haltakov and V.L. Lyutskanov, Growth of ultra-violet grade CaF_2 crystals and their application for excimer laser optics 162 (1996) 79
Moulin, D., see Behet, M. 167 (1996) 415
Moulin, D., see Tümmler, J. 170 (1997) 772
Mountziaris, T.J., see Ingle, N.K. 167 (1996) 543
Mountziaris, T.J., see Theodoropoulos, C. 170 (1997) 72
Mountziaris, T.J., see Peck, J. 170 (1997) 523
Mucchino, C., see Carrà, S. 166 (1996) 641
Mücke, F., see Christiansen, S. 166 (1996) 848
Mücklich, F., see Scholz, U. 169 (1996) 575
Mücklich, F., see Scholz, U. 169 (1996) 578
Mühe, A., see Geng, C. 170 (1997) 418
Mühlberg, M., see Burianek, M. 166 (1996) 361
Muhr, G.T., see Mackenzie 164 (1996) 143
Mukaida, M., S. Miyazawa, C. Klemenz and H.J. Scheel, Structural characterization of *a*-axis oriented $YBa_2Cu_3O_x$ films grown by liquid phase epitaxy 169 (1996) 715
Mukherjee, D.K., V. Prasad, P. Dutta and T. Yuan, Liquid crystal visualization of the effects of crucible and crystal rotation on Cz melt flows 169 (1996) 136
Mukovskiy, Ya.M., see Balbashov, A.M. 167 (1996) 365
Müller, G., see Jung 165 (1996) 463
Müller, G., see Müller, M. 166 (1996) 636
Müller, G., see Amon, J. 166 (1996) 646
Müller, G., see Seidl, A. 166 (1996) 680
Müller, G., see Friedrich, J. 167 (1996) 45
Müller, G., see Baumgartl, J. 169 (1996) 582
Müller, M., G. Gärtner, G. Hirt, M. Jurisch, A. Köhler, G. Müller and B. Weinert, Control of oxygen in undoped liquid encapsulation Czochralski GaAs 166 (1996) 636
Müller, M., see Protzmann, H. 170 (1997) 155
Müller, M., see Thomas, B. 170 (1997) 808
Müller, O., see Utke 162 (1996) 126
Müller, S., see Peka 161 (1996) 277
Müller-Vogt, G., see Weigel 161 (1996) 40
Mullin, J.B., see Ahmed 161 (1996) 223
Munekata, H., see Watanabe, K. 169 (1996) 223
Munekata, H., see Nishida, K. 170 (1997) 312
Munekata, H., see Honda, T. 170 (1997) 503
Munns, G.O., see Chen 164 (1996) 454
Munns, G.O., W.L. Chen and G.I. Haddad, Heterojunction bipolar transistors with low temperature Be-doped base grown by CBE 164 (1996) 476
Murai, S., see Fujiwara, S. 167 (1996) 357
Murakoshi, H., see Hiruma 163 (1996) 226
Muramatsu, T., see Kudo, N. 168 (1996) 118
Murata, H., I.H. Ho and G.B. Stringfellow, Effects of growth temperature and V/III ratio on surface structure and ordering in $Ga_{0.5}In_{0.5}P$ 170 (1997) 219
Murata, H., see Chun, Y.S. 170 (1997) 263
Muratova, V.I., see Givargizov 162 (1996) 73

Murgatroyd, I.J., see Booker, G.R. 170 (1997) 777
Murooka, K.-i., I. Higashikawa and Y. Gomei, Growth rate and deposition process of silicon carbide film by low-pressure chemical vapor deposition 169 (1996) 485
Murray, B.T., see Coriell, S.R. 169 (1996) 773
Muschol, M. and F. Rosenberger, Lack of evidence for prenucleation aggregate formation in lysozyme crystal growth solutions 167 (1996) 738
Muschol, M., see Rosenberger, F. 168 (1996) 1
Musikhin, Yu., see Dmitriev, V. 166 (1996) 601
Mu Yufeng, see Wang Siqing 162 (1996) 69
Mwangi, S.M. and J. Garside, Morphology of 6-aminopenicillanic acid crystals and the effect of phenoxyacetic acid 166 (1996) 1078
Myachin, V.E., see Alexeev, A.N. 166 (1996) 167
Mydosh, J.A., see Mihalik, M. 167 (1996) 621
Myers, T., see Aggarwal, M.D. 166 (1996) 542
Myerson, A.S., see Izmailov, A.F. 166 (1996) 261
Myerson, A.S., A.F. Izmailov and H.-S. Na, Thermodynamic studies of levitated microdroplets of highly supersaturated electrolyte solutions 166 (1996) 981

Na, H.-S., see Myerson, A.S. 166 (1996) 981
Nabiev, R.F., see Mawst, L.J. 170 (1997) 383
Nada, H. and Y. Furukawa, Anisotropic growth kinetics of ice crystals from water studied by molecular dynamics simulation 169 (1996) 587
Naeven, R., see Althaus, M. 166 (1996) 566
Nagabhushan, T.L., see Long, M.M. 168 (1996) 233
Nagaki, Y., see Takano, Y. 169 (1996) 621
Nagashima, N., see Sano, C. 166 (1996) 129
Nagashima, N., see Hasegawa, K. 166 (1996) 925
Nagashima, N., see Kishishita, A. 167 (1996) 729
Nagatomo, T., see Okumura 164 (1996) 149
Nagayama, K., see Takahashi, T. 168 (1996) 130
Nagel, N., see Silier, I. 166 (1996) 727
Nagoya, T., see Habuka, H. 169 (1996) 61
Nagpal, A., see Gupta 165 (1996) 19
Naji, O., J. Zhang, T. Kaneko, T.S. Jones, J.H. Neave and B.A. Joyce, A detailed time of flight study of the cracking pattern trimethylgallium; implications for MOMBE growth 164 (1996) 58
Naji, O., see Davidson 164 (1996) 396
Nakada, T., see Kurihara, K. 166 (1996) 904
Nakada, T., see Sazaki, G. 169 (1996) 355
Nakahara, H., see Ichimiya 163 (1996) 39
Nakahara, J., see Suemune, I. 170 (1997) 480
Nakai, H., see Hashimoto, M. 166 (1996) 792
Nakajima, K. and T. Kusunoki, Constant temperature LEC growth of InGaAs ternary bulk crystals using the double crucible method 169 (1996) 217
Nakajima, M., see Nakamura, K. 170 (1997) 377
Nakakoshi, K., see Ishikawa, Y. 167 (1996) 434
Nakamura, F., see Toda, A. 170 (1997) 461
Nakamura, K., S. Oshiba, M. Nakajima, S. Gotoh and H. Horikawa, Microampere laser threshold at 80°C with InGaAs/GaAs/InGaP buried heterostructre strained quantum well lasers 170 (1997) 377
Nakamura, M., see Yamada, Y. 166 (1996) 804
Nakamura, M., C. Krauns, Y. Yamada and Y. Shiohara, Crystal growth of $SmBa_2Cu_3O_{7-x}$ under low oxygen partial pressure 166 (1996) 859
Nakamura, S., see Ito 163 (1996) 311
Nakamura, S., First III–V-nitride-based violet laser diodes 170 (1997) 11
Nakamura, T., see Kinoshita, K. 166 (1996) 266
Nakamura, T., see Tatsuoka, H. 166 (1996) 754
Nakamura, T., see Onuma, K. 167 (1996) 387
Nakanishi, H., see Kamata, A. 170 (1997) 518
Nakanishi, Y., see Tatsuoka, H. 166 (1996) 754
Nakayama, H., T. Takeguchi and T. Nishino, Atom correlation and configurational ordering in pseudobinary epitaxial semiconductors 163 (1996) 135
Nakayama, H., see Ohuchi, Y. 170 (1997) 325
Nakayama, T., see Mizutani, R. 168 (1996) 253
Namikawa, Y., see Yao 165 (1996) 198
Nancollas, G.H., see Liu 165 (1996) 116
Narui, H., Metalorganic vapor deposition growth of AlGaAs on a ridged GaAs(100) substrate for a low threshold current laser 167 (1996) 452
Nashiki, H., see Suemune, I. 170 (1997) 480
Nasi, L., see Li 163 (1996) 195
Nasi, L., see Rigo 164 (1996) 430
Nasi, L., see Bocchi 165 (1996) 8
Nasibov, A.S., see Korostelin 161 (1996) 51
Nataf, G., M. Leroux, S.M. Laügt and P. Gibart, Selective growth of GaAs and $Al_{0.35}Ga_{0.65}As$ on GaAs patterned substrates by HCl assisted low pressure metalorganic vapour phase epitaxy 165 (1996) 1
Naumann, R.J., Stabilizing/destabilizing effects of axial accelerations in Bridgman growth 165 (1996) 129
Nayak, S., see Kuech 163 (1996) 171
Neamţu, C., see Darabont, Al. 169 (1996) 89
Neave, J.H., see Naji 164 (1996) 58
Neethling, J.H., see Scriven, G.J. 170 (1997) 813
Nelson, E., see Van Hove 164 (1996) 154
Nelson, J., Comment on 'Formation mechanism of side branches of dendritic ice crystals grown from vapor by T. Gonda and H. Nakahara'. [J. Crystal Growth 160 (1996) 162] 167 (1996) 782
Nelson, J. and C.A. Knight, A new technique for growing crystals from the vapor 169 (1996) 795
Németh, Š., see Srnánek 165 (1996) 156
Nenov, A.T., see Shumov, D.P. 169 (1996) 519
Nenov, A.T., see Nihtianova, D.D. 169 (1996) 527
Nesnidal, M., see Mawst, L.J. 170 (1997) 383

Nesterenko, Y.A., see Komar, V.K. 160 (1996) 419
Neubert, M. and K. Jacobs, Diffusivity of mercury vacancies in $Hg_{0.8}Cd_{0.2}Te$ 161 (1996) 229
Neumann, A.M., see Kramer, H.J.M. 166 (1996) 1084
Nevskaya, N., see Garber, M. 168 (1996) 301
Newly, J.P., see Whitaker 164 (1996) 125
Newman, R.C., see Davidson 164 (1996) 383
Newman, R.C., see Davidson 164 (1996) 396
Ng, J.D., B. Lorber, J. Witz, A. Théobald-Dietrich, D. Kern and R. Giegé, The crystallization of biological macromolecules from precipitates: evidence for Ostwald ripening 168 (1996) 50
Ng, T.L., see Gnoth, D.N. 170 (1997) 198
Ng, T.L., see Fan, G.H. 170 (1997) 485
Ng, T.L., see Poole, I.B. 170 (1997) 528
Nguyen Thi, H., see Billia, B. 167 (1996) 265
Nguyen Thi, H., see Li, Q. 167 (1996) 277
Ni, J., see Korpela 165 (1996) 455
Ni, W.-X., see Radamson, H.H. 167 (1996) 495
Nicholas, R.J., see Wood, A.K. 170 (1997) 132
Nicholas, R.J., see Booker, G.R. 170 (1997) 777
Nicoara, D., see Nicoara, I. 169 (1996) 102
Nicoara, D., see Vizman, D. 169 (1996) 161
Nicoara, I., D. Vizman and D. Nicoara, Thermal stresses in shaped semi-transparent crystals 169 (1996) 102
Nicoara, I., see Vizman, D. 169 (1996) 161
Nihtianova, D.D., see Shumov, D.P. 169 (1996) 519
Nihtianova, D.D., D.P. Shumov, J.J. Macicek and A.T. Nenov, Inclusions in LiB_3O_5 crystals, obtained by the top-seeded solution growth method in the Li_2O–B_2O_3 system. Part 2 169 (1996) 527
Niiori, Y., see Yamada, Y. 167 (1996) 566
Nikitina, I., see Dmitriev, V. 166 (1996) 601
Nikl, M., see Nitsch 165 (1996) 163
Nikolaev, A.E., V.A. Ivantsov, S.V. Rendakova, M.N. Blashenkov and V.A. Dmitriev, SiC liquid-phase epitaxy on patterned substrates 166 (1996) 607
Nikolaev, V., see Dmitriev, V. 166 (1996) 601
Nikolic, Z.S., see Scholz, U. 169 (1996) 578
Nikolov, V., see Solé, R. 166 (1996) 402
Nikolov, V., see Solé, R. 167 (1996) 681
Nikolov, V., see Solé, R. 169 (1996) 600
Nikols, M., see Sadwick 164 (1996) 285
Nikonov, S., see Garber, M. 168 (1996) 301
Nikonyuk, E.S., V.Z. Shlyakhovuy, M.O. Kovalets, M.I. Kuchma, Z.I. Zakharuk and V.M. Frasuniak, A-centers modifying in CdTe–Yb crystals 161 (1996) 186
Ninomiya, T., see Ohkubo, M. 170 (1997) 177
Nishida, K., S. Haneda, K. Hara, H. Munekata and H. Kukimoto, MOVPE of GaN using a specially designed two-flow horizontal reactor 170 (1997) 312
Nishida, M., S. Harada, Y. Satow, H. Inoue and K. Takahashi, Crystallization and X-ray diffraction studies of glutathione *S*-transferase from *Escherichia coli* 168 (1996) 284
Nishijima, Y., see Nishino 165 (1996) 227
Nishijima, Y., see Nishino, H. 167 (1996) 488
Nishinaga, T., X.Q. Shen and D. Kishimoto, Surface diffusion length of cation incorporation studies by microprobe-RHEED/SEM MBE 163 (1996) 60
Nishinaga, T., see Ren, H.-W. 166 (1996) 217
Nishinaga, T., see Shen, X.Q. 169 (1996) 607
Nishino, H., T. Saito and Y. Nishijima, VI/II ratio dependence of surface macrodefects in CdTe/ZnTe/GaAs(100) growth by metalorganic vapor phase epitaxy 165 (1996) 227
Nishino, H. and Y. Nishijima, CdTe(111)B/Si (100) structure grown by metalorganic vapor phase epitaxy with Te adsorption and annealing 167 (1996) 488
Nishino, T., see Nakayama 163 (1996) 135
Nishioka, K. and I.L. Maksimov, Reconsideration of the concept of critical nucleus and the Gibbs–Thomson equation 163 (1996) 1
Nishioka, M., see Kitamura, M. 170 (1997) 563
Nishizawa, J., see Nugraha 163 (1996) 353
Nishizawa, J., see Nugraha 165 (1996) 402
Nishizawa, S.-i., see Hu, W.-R. 169 (1996) 380
Nitanai, Y., Y. Satow, H. Adachi and M. Tsujimoto, Crystallization and preliminary X-ray investigation of a glycoprotein, human renal dipeptidase 168 (1996) 280
Nitsch, K., M. Nikl, S. Ganschow, P. Reiche and R. Uecker, Growth of lead tungstate single crystal scintillators 165 (1996) 163
Nittono, T. and F. Hyuga, Reduction of unintentional impurities at the interface between epitaxial layers and GaAs substrates 170 (1997) 762
Niu, X.-T., see Pan, J.-S. 168 (1996) 227
Niwa, E., see Yonenaga, I. 167 (1996) 616
Noever, D., M.L. Pusey, E.L. Forsythe and S. Baskaran, Artificial neural network prediction of tetragonal lysozyme face growth rates 167 (1996) 221
Noguchi, H., see Yi 165 (1996) 358
Noguchi, S., Y. Satow, T. Uchida, C. Sasaki and T. Matsuzaki, Crystallization and preliminary X-ray investigation of six new crystal forms of ribonuclease U_2 from *Ustilago sphaerogena* 168 (1996) 270
Noguchi, S., see Miyawaki, K. 168 (1996) 292
Nogueira, G.E.C., see Ranieri, I.M. 166 (1996) 423
Nonaka, H., see Shimizu, T. 166 (1996) 841
Nørager, S., see Vuillard, L. 168 (1996) 150
Nouaoura, M., see Ferhat, M. 167 (1996) 122
Novák, J., see Srnánek 165 (1996) 156
Novotortsev, V.M., see Volkov 163 (1996) 377

Nowak, E., see Weise, S. 166 (1996) 718
Nugraha, O. Itoh, K. Suto and J. Nishizawa, Growth and electrical properties of PbTe epitaxial layers grown by temperature difference method under controlled vapor pressure liquid phase epitaxy 163 (1996) 353
Nugraha, K. Suto, O. Itoh, J. Nishizawa and Y. Yokota, Growth and electrical properties of PbTe bulk crystals grown by the Bridgman method under controlled tellurium or lead vapor pressure 165 (1996) 402
Numazawa, T., see Kimura 165 (1996) 408
Nunoshita, M., see Gotoda 164 (1996) 308

Obara, K., Collective behaviour of metastable liquid particles layer on liquid surface 166 (1996) 124
Obara, K., Y. Ohtera and Y. Suemoto, Two-dimensional metastable macro-crystals of liquid particles on a liquid surface 166 (1996) 136
Obara, K., T. Koshimae, Y. Kubo and Y. Suemoto, Kinetics of microclusters in nonequilibrium plasma magnetron sputtering 166 (1996) 271
Oberacker, T.A., see Braunger, D. 167 (1996) 129
Obinata, T., see Suemune, I. 170 (1997) 480
Obretenov, W., N. Dimitrov and A. Popov, Monte Carlo simulation of underpotential deposition in the $Ag^{+}(111)/Pb^{2+}$ system 167 (1996) 253
O'Brien, P., J.R. Walsh, I.M. Watson, L. Hart and S.R.P. Silva, Properties of cadmium sulphide films grown by single-source metalorganic chemical vapour deposition with dithiocarbamate precursors 167 (1996) 133
O'Brien, P., see Taudt, W. 169 (1996) 243
O'Brien, P., M.A. Malik, M. Chunggaze, T. Trindade, J.R. Walsh and A.C. Jones, Precursor chemistry: remaining challenges and some novel approaches 170 (1997) 23
O'Bryan, H.M., see Fratello, V.J. 166 (1996) 774
Oçafrain, A., J.P. Chaminade, O. Viraphong, R. Cavagnat, M. Couzi and M. Pouchard, Growth by the heat exchanger method and characterization of neighborite, $NaMgF_3$ 166 (1996) 414
Oda, O., see Asahi 161 (1996) 20
Oderno, V., C. Dufour, K. Dumesnil, Ph. Mangin and G. Marchal, Epitaxial growth of (110) $DyFe_2$, $TbFe_2$ and $Dy_{0.7}Tb_{0.3}Fe_2$ thin films by molecular beam epitaxy 165 (1996) 175
Oei, Y.S., see Rongen 164 (1996) 263
Oei, Y.S., see Vreeburg 164 (1996) 442
Oei, Y.S., see Verschuren, C.A. 170 (1997) 650
Oelgardt, G., see Knauer, A. 170 (1997) 281
Oelkrug, D., see Egelhaaf 161 (1996) 190
Offermann, H., see Manth, T. 166 (1996) 998
Ogata, K.-i., T. Kera, D. Kawaguchi, Sz. Fujita and Sg. Fujita, Characterization of p-type ZnSe grown by MOVPE; excitonic emission lifetime measurements 170 (1997) 507
Ogawa, T., see Shibata, T. 167 (1996) 716
Ogle, W., see Tong 164 (1996) 202
Oh, H.J. and I.S. Kang, Effect of crucible geometry on the flow pattern in the magnetic field applied Czochralski process 167 (1996) 345
Oh, J.-H., F. Fukuchi, H.-C. Kang and M. Konagai, Influence of H_2 on electrical and optical properties of carbon-doped InP grown by MOMBE using tertiarybutylphosphine (TBP) 164 (1996) 425
Oh, J.-H., see Hatatani, S. 170 (1997) 297
Oh, M.H., see Song, M.H. 167 (1996) 157
Ohbuchi, T., see Hashimoto, M. 166 (1996) 792
Ohde, Y., see Tanzawa 165 (1996) 284
Ohkohchi, M., see Ando, Y. 166 (1996) 888
Ohkubo, M., J. Osabe, T. Shiojima, T. Yamaguchi and T. Ninomiya, Magnesium-doped InGaAs using $(C_2H_5C_5H_4)_2Mg$: application to InP-based HBTs 170 (1997) 177
Ohler, M., see Prieur, E. 166 (1996) 329
Ohmoto, S., see Okada 165 (1996) 31
Ohno-Iwashita, Y., see Sugahara, M. 168 (1996) 288
Ohta, K., see Okumura 164 (1996) 149
Ohta, S.-i., see Kurasawa, M. 167 (1996) 151
Ohtani, K., see Wado, H. 169 (1996) 457
Ohtani, N., see Takahashi, J. 167 (1996) 596
Ohtera, Y., see Obara, K. 166 (1996) 136
Ohtsuka, K.-i., see Imaizumi, M. 169 (1996) 293
Ohuchi, R., see Kawaguchi, T. 166 (1996) 493
Ohuchi, Y., K. Tadatomo, H. Nakayama, N. Kaneda, T. Detchprohm, K. Hiramatsu and N. Sawaki, New dopant precursors for n-type and p-type GaN 170 (1997) 325
Oishi, K., see Kurasawa, M. 167 (1996) 151
O'Keefe, E.S., see Capper 161 (1996) 104
Oka, K., H. Unoki, H. Yamaguchi and H. Takahashi, Crystal growth of $PbTiO_3$ by the top-seeded solution-growth method 166 (1996) 380
Okabe, H., see Mizuno, Y. 170 (1997) 61
Okabe, T., see Kitano, M. 166 (1996) 1116
Okada, H., T. Kawanaka and S. Ohmoto, Study on the ZnSe phase diagram by differential thermal analysis 165 (1996) 31
Okada, S., K. Kudou, K. Iizumi, K. Kudaka, I. Higashi and T. Lundström, Single-crystal growth and properties of CrB, Cr_3B_4, Cr_2B_3 and CrB_2 from high-temperature aluminum solutions 166 (1996) 429
Okajima, Y., M. Amemiya, K. Kato and S. Asai, VLS growth of silicon whiskers on a patterned silicon-on-insulator (SOI) wafer 165 (1996) 37
Okamoto, T., see Shishiguchi, S. 166 (1996) 689
Okamoto, T., see Higuchi, Y. 168 (1996) 99
Oki, K., see Kuwano 163 (1996) 122
Oktik, S., see Loginov 161 (1996) 159

Okui, N., see Yase, K. 166 (1996) 942
Okumura, H. and S. Yoshida, Compositional micro-area modification of GaAs surfaces by an electron beam under phosphorus flux 164 (1996) 92
Okumura, H., K. Ohta, T. Nagatomo and S. Yoshida, Observation of MBE-grown cubic-GaN/GaAs and cubic-GaN/3C–SiC interfaces by high resolution transmission electron microscope 164 (1996) 149
Okuyama, K., see Habuka, H. 169 (1996) 61
Ó Meadhra, R., H.J.M. Kramer and G.M. van Rosmalen, Crystallization kinetics of pentaerythritol 166 (1996) 1046
Ó Meadhra, R., see Kramer, H.J.M. 166 (1996) 1084
Omling, P., see Carlsson, N. 170 (1997) 127
Onabe, K., see Yaguchi, H. 170 (1997) 353
Onabe, K., see Pan, W. 170 (1997) 585
Ono, K., see Mizuno, K. 166 (1996) 146
Onuma, K., see Ito 163 (1996) 311
Onuma, K., T. Nakamura and S. Kuwashima, Development of new real-time phase-shift interferometry for the investigation of crystal growth kinetics 167 (1996) 387
Onuma, K., A. Ito and T. Tateishi, Investigation of a growth unit of hydroxyapatite crystal from the measurements of step kinetics 167 (1996) 773
Opitz, B., see Lakner, H. 170 (1997) 732
O'Rear, E.A., see Liu, W.K. 167 (1996) 111
Ortion, J.M., Y. Cordier, J.Ch. Garcia and C. Grattepain, Temperature dependence of of GaAs chemical etching using $AsCl_3$ 164 (1996) 97
Ortion, J.M., Y. Cordier, J.C. Garcia, D. Adam and M. Champagne, Selective area etching of AlGaAs/GaAs heterostructures using $AsCl_3$ 170 (1997) 674
Orton, J.W., see Cheng, T.S. 166 (1996) 597
Osabe, J., see Ohkubo, M. 170 (1997) 177
Osaka, J., see Inoue 164 (1996) 88
Oshiba, S., see Nakamura, K. 170 (1997) 377
Oshita, M., see Tatsuoka, H. 166 (1996) 754
Ossart, P., see Lamare 164 (1996) 122
Ossau, W., see Lugauer 161 (1996) 86
Ossau, W., see Worschech 161 (1996) 134
Ossau, W., see Fischer 161 (1996) 214
Osten, H.J., see Kim, M. 167 (1996) 508
Osten, H.J., see Kim, M. 169 (1996) 681
Oster, A., see Knauer, A. 170 (1997) 281
Ostrogorsky, A.G., see Meyer, S. 166 (1996) 700
Otálora, F., J.M. García-Ruiz and A. Moreno, Protein crystal quality studies using rod-shaped crystals 168 (1996) 93
Otálora, F. and J.M. García-Ruiz, Computer model of the diffusion/reaction interplay in the gel acupuncture method 169 (1996) 361
Otani, S. and Y. Ishizawa, Preparation of ZrB_2 single crystals by the floating zone method 165 (1996) 319
Otani, S., see Louchev, O.A. 167 (1996) 333
Otsuka, N., M. Kito, Y. Yabuuchi, M. Ishino and Y. Matsui, Anomalous temperature dependence of PL characteristics in ordered InGaAsP strained layer multi-quantum well structure 170 (1997) 626
Ottenwälder, D., see Geiger, M. 169 (1996) 625
Ottenwälder, D., G. Frankowsky, O. Gfrörer, A. Hangleiter and F. Scholz, Control of monolayer terrace formation in selective epitaxy 170 (1997) 695
Ougazzaden, A., see Silvestre, L. 170 (1997) 639
Ougazzaden, A., see Zimmermann, G. 170 (1997) 645
Overney, R.M., see Sokolov, N.S. 169 (1996) 40
Owman, F., C. Hallin, P. Mårtensson and E. Janzén, Removal of polishing-induced damage from 6H-SiC(0001) substrates by hydrogen etching 167 (1996) 391
Oya, S.-i., see Hashimoto, S. 169 (1996) 376
Ozawa, T., M. Ando, Y. Hayakawa and M. Kumagawa, InGaAs mixed crystals grown by the temperature-difference method and the numerical analysis of solution convection 166 (1996) 463
Ozeki, T., see Imaizumi, M. 169 (1996) 293

Pacheco, F.J., see Kidd, P. 169 (1996) 649
Padmore, H., see Earnest, T. 168 (1996) 248
Pagnod-Rossiaux, Ph., see Lestra, A. 167 (1996) 446
Palmier, D., A. Goiffon, B. Capelle, J. Détaint and E. Philippot, Crystal growth and characterizations of quartz-like material: gallium phosphate ($GaPO_4$) 166 (1996) 347
Palosaari, S., see Sha, Z.L. 166 (1996) 1105
Palosz, W., K. Grasza, D. Gillies and G. Jerman, Growth of cadmium–zinc telluride crystals by controlled seeding "contactless" physical vapor transport 169 (1996) 20
Pan, F., Ch. Bosshard, M.S. Wong, C. Serbutoviez, S. Follonier, P. Günter and K. Schenk, Polymorphism, growth and characterization of a new organic nonlinear optical crystal: 4-dimethylaminobenzaldehyde-4-nitrophenylhydrazone (DANPH) 165 (1996) 273
Pan, J.-S., X.-T. Niu, L.-L. Gui, Y.-C. Zhou and R.-C. Bi, Crystallization under microgravity of acidic phospholipase A_2 from venom of *Agkistrodon halys* Pallas 168 (1996) 227
Pan, K., see Chen, N. 167 (1996) 766
Pan, S., see Zhang, Y. 167 (1996) 373
Pan, W., H. Yaguchi, Y. Hanamaki, M. Ishikawa, Y. Kaneko, K. Onabe, R. Ito and Y. Shiraki, A highly luminescent crescent-shaped tensile-strained GaAsP/AlGaAs quantum wire laser structure 170 (1997) 585
Panchouk, O., see Shcherbak 161 (1996) 16
Panchouk, O., P. Fochouk and P. Feichouk, Point defects in Te-rich CdTe 161 (1996) 144

Panchouk, O., see Shcherbak 161 (1996) 219
Pao, Y.C., see Hung, C.Y. 169 (1996) 201
Paoletti, R., see Bertone, D. 170 (1997) 715
Paorici, C., see Zeng, L. 166 (1996) 528
Paorici, C., see Carrà, S. 166 (1996) 641
Papuzza, C., see Rigo 164 (1996) 430
Paraskevopoulos, A., see Schelhase 164 (1996) 339
Park, H.-M., see Hong, S.-K. 169 (1996) 435
Park, Seong-Ju, see Kim 164 (1996) 356
Park, Seong-Ju, see Ro 164 (1996) 377
Park, S.-J., see Kim, S.-B. 169 (1996) 429
Park, W., see Tong 164 (1996) 202
Parkinson, G.M., see Reyhani, M.M. 166 (1996) 1068
Pashley, D.W., A simple method for determining the restrictive conditions for the formation of stacking faults for the relief of pseudomorphic strain in face centered cubic epilayers 162 (1996) 178
Patel, M., see Sadwick 164 (1996) 285
Patnaik, S., see Krueger, C.W. 169 (1996) 51
Patriarche, G., see Silvestre, L. 170 (1997) 639
Patrikarakos, D.G., N. Shukla and M.E. Pemble, Reflectance anisotropy as an in situ monitor for the growth of InP on (001) InP by pseudo-atmospheric pressure atomic layer epitaxy 170 (1997) 215
Pearton, S.J., see Santana 164 (1996) 248
Peck, J., T.J. Mountziaris, S. Stoltz, A. Petrou and P.G. Mattocks, Metalorganic vapor phase epitaxy of $Zn_{1-x}Fe_xSe$ films 170 (1997) 523
Peka, P., M.U. Lehr, H.-J. Schulz, J. Dziesiaty and S. Müller, Identification of titanium dopants in CdS, CdSe and Cd(S,Se) crystals by luminescence and EPR methods 161 (1996) 277
Pekárek, L., see Srnánek 165 (1996) 156
Pelosi, C., see Gennari, S. 166 (1996) 309
Pemble, M.E., see Zhang 164 (1996) 40
Pemble, M.E., see Patrikarakos, D.G. 170 (1997) 215
Pemble, M.E., see Yates, H.M. 170 (1997) 611
Peng, Dingkun, see Meng 163 (1996) 232
Penn, B.G., see Aggarwal, M.D. 166 (1996) 542
Peretz, M., see Thygesen, J. 168 (1996) 308
Pérez, L.V., A.B. Trigubó and N.E. Walsöe de Reca, Validation of models for subgrain growth in $Hg_{1-x}Cd_xTe$ (MCT) by thermal annealing 167 (1996) 87
Perkins, N.R., see Kuech, T.F. 166 (1996) 558
Perlov, D., see Roth, M. 169 (1996) 734
Petitprez, E., see González-Borrero, P.P. 169 (1996) 424
Petkos, G.M., P.J. Goodhew and T.B. Joyce, Sulphur doping of InGaAs using diethylsulphide 164 (1996) 415
Petrenko, V.F., see Khusnatdinov 163 (1996) 420
Pétroff, J.F., see Zheng 162 (1996) 135
Petrou, A., see Peck, J. 170 (1997) 523
Petzow, G., see Scholz, U. 169 (1996) 575
Petzow, G., see Scholz, U. 169 (1996) 578
Pfeffer, R.L., see Lareau, R.T. 167 (1996) 406
Pfeifer, J., E. Badaljan, P. Tekula-Buxbaum, T. Kovács, O. Geszti, A.L. Tóth and H.-J. Lunk, Growth and morphology of $W_{18}O_{49}$ crystals produced by microwave decomposition of ammonium paratungstate 169 (1996) 727
Philippot, E., see Palmier, D. 166 (1996) 347
Phillipp, F., see Geng, C. 170 (1997) 418
Pickett, N.L., D.F. Foster and D.J. Cole-Hamilton, Studies of prereactions during MOVPE growth of wide band-gap II/VI semiconductors: the effect of pyridine upon the gas-phase reactions between H_2S and Me_2Zn 170 (1997) 476
Pidduck, A.J., see Whitaker 164 (1996) 125
Piechotka, M., see Rossberg, A. 166 (1996) 354
Pietag, F., see Kirpal, G. 170 (1997) 167
Pieters, I.Y., see De Maeyer, E.A.P. 169 (1996) 539
Pietzonka, I., see Kirpal, G. 170 (1997) 167
Piibe, T., see Valdna 161 (1996) 177
Pines, V., A. Chait and M. Zlatkowski, Thermal diffusion dominated dendritic growth – an analysis of the wall proximity effect 167 (1996) 383
Pines, V., A. Chait and M. Zlatkowski, Dynamic scaling in dendritic growth 167 (1996) 777
Pines, V., A. Chait and M. Zlatkowski, Anomaly in dendritic growth data – effect of density change upon solidification 169 (1996) 798
Pistol, M.-E., see Seifert, W. 170 (1997) 39
Plachke, D., see Scholz, U. 169 (1996) 575
Płaczek-Popko, E., see Szatkowski 161 (1996) 282
Ploog, K.H., see Behrend, J. 167 (1996) 440
Pociask, M., see Ciach 161 (1996) 234
Pogorelsky, Yu.V., see Alexeev, A.N. 166 (1996) 72
Pogorelsky, Yu.V., see Alexeev, A.N. 166 (1996) 167
Pohl, U.W., S. Freitag, J. Gottfriedsen, W. Richter and H. Schumann, Synthesis and properties of zinc–nitrogen compounds for the MOVPE of p-type ZnSe 170 (1997) 144
Pollock, C.R., see Mass 165 (1996) 250
Poole, I.B., see Gnoth, D.N. 170 (1997) 198
Poole, I.B., T.L. Ng, N. Maung, J.O. Williams and A.C. Wright, MOVPE growth of magnesium cadmium sulphide: rocksalt or sphalerite? 170 (1997) 528
Popov, A., see Obretenov, W. 167 (1996) 253
Popp, M., see Marheineke 164 (1996) 16
Popp, M., see Veuhoff 164 (1996) 402
Popp, M., see Keidler, M. 170 (1997) 161
Porowski, S., High pressure growth of GaN – new prospects for blue lasers 166 (1996) 583
Porowski, S., see Leszczynski, M. 169 (1996) 235
Portal, J.C., see Booker, G.R. 170 (1997) 777
Poschmann, M. and J. Ulrich, Fractional suspension crystallization with additional purification steps 167 (1996) 248
Pouchard, M., see Oçafrain, A. 166 (1996) 414

Pracka, I., see Frukacz, Z. 169 (1996) 98
Prasad, V., see Anselmo 163 (1996) 359
Prasad, V., see Zou, Y.F. 166 (1996) 476
Prasad, V., see Mukherjee, D.K. 169 (1996) 136
Prasad, V., see Zhang, H. 169 (1996) 250
Presting, H., see Sobolev, N.A. 167 (1996) 502
Prieur, E., see Tuominen 165 (1996) 233
Prieur, E., J. Härtwig, A. Garcia, M. Ohler, J. Baruchel, B. Aspar and G. Rolland, Synchrotron white beam topographic investigation of crystalline defects in silicon on insulator materials 166 (1996) 329
Pristovsek, M., see Knorr, K. 170 (1997) 230
Pritchard, R.E., see Joyce 164 (1996) 371
Prösch, G., K. Hellig, R. Beyer, A. Schneider, H. Burghardt, W. Taudt, M. Heuken and D.R.T. Zahn, Defects in MOVPE grown ZnSe on GaAs studied by deep level transient spectroscopy 170 (1997) 537
Prost, W., see Lindner, A. 170 (1997) 287
Protzmann, H., F. Höhnsdorf, Z. Spika, W. Stolz, E.O. Göbel, M. Müller and J. Lorberth, Properties of $(Ga_{0.47}In_{0.53})As$ epitaxial layers grown by metalorganic vapor phase epitaxy (MOVPE) using alternative arsenic precursors 170 (1997) 155
Prywer, J., Three-dimensional model of the disappearance of triangular faces in the ctystal habit 165 (1996) 335
Pudenzi, M.A.A., see Cotta 164 (1996) 409
Pusey, M.L., see Noever, D. 167 (1996) 221
Pusey, M.L., see Forsythe, E.L. 168 (1996) 112
Pusztai, T., see Gránásy, L. 167 (1996) 756
Pyun, K.-E., see Hong, S.-K. 169 (1996) 435

Qi, M., see Li 164 (1996) 84
Qi, M., see Chen 164 (1996) 460
Qian Yitai, see Xie Yi 167 (1996) 656
Qin, Z., M. Kimura and S. Dost, Convection model for growth and dissolution of ternary alloys by liquid phase epitaxy 167 (1996) 74
Qin, Z., see Kimura, M. 169 (1996) 697
Qiu, H., see Hashimoto, M. 166 (1996) 792
Quick, C., see Kim, M. 167 (1996) 508
Quintel, H., see Restle 161 (1996) 168
Quintel, H., see Jahn 161 (1996) 172

Radamson, H.H., K.B. Joelsson, W.-X. Ni, J. Birch, J.-E. Sundgren, L. Hultman and G.V. Hansson, Strain characterization of $Ge_{1-x}Si_x$ and heavily B-doped Ge layers on Ge(001) by two-dimensional reciprocal space mapping 167 (1996) 495
Radelaar, S., see Werner 164 (1996) 223
Radice, M., see Bignazzi, A. 169 (1996) 450
Rai, R.N., see Rai, U.S. 169 (1996) 563
Rai, U.S. and R.N. Rai, Studies on physicochemical properties of the eutectic and monotectic in the urea–p. chloronitrobenzene system 169 (1996) 563
Raidt, H., see Silier, I. 166 (1996) 727
Raisbeck, D., see Zhang 164 (1996) 40
Rak, A., see Garber, M. 168 (1996) 301
Rakova, E.V., see Givargizov 162 (1996) 73
Rakova, E.V., see Kuznetsov, A.V. 167 (1996) 458
Raman, R., see Saghir, M.Z. 169 (1996) 110
Ramdane, A., see Silvestre, L. 170 (1997) 639
Ramdane, A., see Zimmermann, G. 170 (1997) 645
Ramm, M.S., see Karpov, S.Yu. 169 (1996) 491
Rammohan Rao, R., see Mackowski 165 (1996) 323
Ramvall, P., see Carlsson, N. 170 (1997) 127
Ranieri, I.M., S.L. Baldochi, A.M.E. Santo, L. Gomes, L.C. Courrol, L.V.G. Tarelho, W. de Rossi, J.R. Berretta, F.E. Costa, G.E.C. Nogueira, N.U. Wetter, D.M. Zezell, N.D. Vieira, Jr. and S.P. Morato, Growth of $LiYF_4$ crystals doped with holmium, erbium and thulium 166 (1996) 423
Rao, E.V.K., see Zimmermann, G. 170 (1997) 645
Rao, S.M., R.H. Chang, K.S. Law, M.K. Wu and C.P. Khattak , Influence of KCl on the growth of $YBa_2Cu_3O_{6+\delta}$ from high temperature solutions 162 (1996) 48
Rappoli, B.J., see DeSisto, W.J. 170 (1997) 242
Reaves, C.M., see Gaffney, M.S. 167 (1996) 8
Rechenberg, I., see Knauer, A. 170 (1997) 281
Recker, C., see Geiger, M. 169 (1996) 625
Redwing, J.M., see Liu, J. 170 (1997) 357
Regreny, P., see Thévenot, V. 170 (1997) 251
Rehse, P., see Zhu, D.-W. 168 (1996) 275
Reiche, P., see Nitsch 165 (1996) 163
Reiche, P., see Donecker, J. 166 (1996) 303
Reichert, P., see Long, M.M. 168 (1996) 233
Reine, M.B., see Mitra, P. 170 (1997) 542
Reinhardt, F., see Biasiol, G. 170 (1997) 600
Reinhardt, F., B. Dwir, G. Biasiol and E. Kapon, Step ordering during OMCVD growth on non-planar substrates 170 (1997) 689
Reinhold, B., see Wienecke 161 (1996) 82
Reinhold, B., see Hermann 161 (1996) 181
Rek, Z.U., see De Yoreo, J.J. 166 (1996) 291
Ren, H.-W., X.-Q. Shen and T. Nishinaga, In situ observation of macrostep formation on misoriented GaAs(111)B by molecular beam epitaxy 166 (1996) 217
Ren, H.W., see Shen, X.Q. 169 (1996) 607
Ren, Y.C., see Li 164 (1996) 84
Ren, Y.C., see Chen 164 (1996) 460
Renaud, P., see Vilela 164 (1996) 465
Renault, P.O., see Declémy 161 (1996) 139
Rendakova, S.V., see Nikolaev, A.E. 166 (1996) 607
Resch-Esser, U., see Knorr, K. 170 (1997) 230

Restle, M., K. Bharuth-Ram, H. Quintel, C. Ronning, H. Hofsäss, U. Wahl, S.G. Jahn and The ISOLDE Collaboration, Lattice sites of Li in CdTe 161 (1996) 168
Restle, M., see Jahn 161 (1996) 172
Rettig, R., T. Marschner, L. Tapfer, W. Stolz and E.O. Göbel, Growth and structural properties of (GaIn)As/GaP(As) intentionally disordered superlattice structures grown by metalorganic vapor phase epitaxy 170 (1997) 748
Rex, T., see Brinkmann 163 (1996) 369
Reyhani, M.M. and G.M. Parkinson, A comparison of secondary nuclei produced by contact of different growth faces of potash alum crystals under supersaturated solutions 166 (1996) 1068
Ribera, E., see Figueras, A. 166 (1996) 798
Riccò, F., see Gennari, S. 166 (1996) 309
Richter, E., see Kurpas, P. 170 (1997) 442
Richter, H., see Loginov 161 (1996) 159
Richter, W., see Pohl, U.W. 170 (1997) 144
Richter, W., see Kurpas, P. 170 (1997) 203
Richter, W., see Steimetz, E. 170 (1997) 208
Richter, W., see Knorr, K. 170 (1997) 230
Ricolleau, C., M. Gandais, T. Gacoin and J.-P. Boilot, Correlation between structural and optical properties of PbS nanocrystals 166 (1996) 769
Rieger, W., see Ambacher, O. 167 (1996) 1
Rieger, W., see Ambacher, O. 170 (1997) 335
Riès-Kautt, M., see Ducruix, A. 168 (1996) 28
Riess, I., see Lyubomirsky 161 (1996) 90
Rigo, C., R. Vincenzoni, A. Stano and R. De Franceschi, Chemical beam epitaxy on patterned substrates of InGaAs/InP heterostructures for optoelectronics and nanostructures applications 164 (1996) 327
Rigo, C., M. Madella, C. Papuzza, C. Cacciatore, A. Stano, A. Gasparotto, G. Salviati and L. Nasi, InP:Fe semi-insulating layers by chemical beam epitaxy 164 (1996) 430
Riley, D.S., see Skeldon 162 (1996) 95
Riley, J.S., see Schall 165 (1996) 299
Ristic, R.I., B.Yu. Shekunov and J.N. Sherwood, The growth and perfection of organic non-linear optical crystals: N-methyl urea (NMU) from methanol solution. I. Kinetics and growth anisotropy 167 (1996) 693
Ristic, R.I., see McEwan, A. 167 (1996) 701
Ritter, D. and H. Heinecke, Evaluation of cracking efficiency of As and P precursors 170 (1997) 149
Ritter, D., see Keidler, M. 170 (1997) 161
Riviere, A., see Rzepka 161 (1996) 286
Ro, Jeong-Rae, see Kim 164 (1996) 356
Ro, Jeong-Rae, Seong-Ju Park, Sung-Bock Kim and El-Hang Lee, CBE growth of carbon-doped p-type InGaAs using trimethylindium and unprecracked monoethylarsine as carbon auto-doping precursor 164 (1996) 377
Ro, J.-R., see Kim, S.-B. 169 (1996) 429
Robert, M.C., see Lefaucheux 165 (1996) 90
Robert, M.C., see Vidal, O. 168 (1996) 40
Robert, M.C., see Bonneté, F. 168 (1996) 185
Roberts, J.S., see Hirotani, M. 170 (1997) 390
Roberts, J.S., see Sale, T.E. 170 (1997) 399
Roberts, J.S., J.P.R. David, Y.H. Chen and T.E. Sale, Optical properties of MOVPE grown $Al_xGa_{1-x}As$ quantum wells 170 (1997) 621
Roberts, K.J., see Hastie, G.P. 166 (1996) 67
Roberts, K.J., see Clydesdale, G. 166 (1996) 78
Roberts, K.J., see van Gelder, R.N.M.R. 166 (1996) 189
Robinson, J., see Bao, K.X. 170 (1997) 497
Robson, P.N., see Hirotani, M. 170 (1997) 390
Robson, P.N., see Chen, Y.H. 170 (1997) 394
Robson, P.N., see Sale, T.E. 170 (1997) 399
Rodewald, M., see Schäffer 165 (1996) 61
Rodríguez-Clemente, R., see López-Macipe, A. 166 (1996) 1015
Rodríguez-Clemente, R., see Gómez-Morales, J. 166 (1996) 1020
Rodríguez-Clemente, R., see Gómez-Morales, J. 169 (1996) 331
Rodríguez-Clemente, R. and J. Gómez-Morales, Microwave precipitation of $CaCO_3$ from homogeneous solutions 169 (1996) 339
Rodríguez-Gallego, M., see González-Muñoz 163 (1996) 434
Roehle, H., H. Schroeter-Janssen and R. Kaiser, Large- and selective-area LP-MOVPE growth of InGaAsP-based bulk and QW layers under nitrogen atmosphere 170 (1997) 109
Roehle, H., see Franke, D. 170 (1997) 113
Roh, D.-W., H.-G. Lee and J.-J. Lee, Electron mobility characteristics of $In_xGa_{1-x}As$/InAlAs/InP high electron mobility transistor (HEMT) structures grown by molecular beam epitaxy 167 (1996) 468
Rohl, A.L. and D.H. Gay, Calculating the effects of surface relaxation on morphology 166 (1996) 84
Rohrer, G.S., see Morris Hotsenpiller, P.A. 166 (1996) 779
Röhrich, J., see Wienecke 161 (1996) 82
Röhrich, J., see Hermann 161 (1996) 181
Rolandi, R., see Krasiński, M.J. 169 (1996) 548
Rolland, G., see Prieur, E. 166 (1996) 329
Rolley, E., C. Guthmann and S. Balibar, Vicinal surfaces of helium 4 crystals 166 (1996) 55
Romanato, F., see Mazzer, M. 170 (1997) 553
Romanov, S.G., see Yates, H.M. 170 (1997) 611
Rondón, D., see Moreno, A. 166 (1996) 919
Rondón, D., see Domininguez-Vera, J.M. 168 (1996) 138
Rongen, R.T.H., M.R. Leys, H. Vonk, J.H. Wolter and Y.S. Oei, Substitution of InP layers to InAs for strain compensation in $Ga_xIn_{1-x}As$/InP superlattices 164 (1996) 263
Rongen, R.T.H., see Vreeburg 164 (1996) 442
Rongen, R.T.H., see Verschuren, C.A. 170 (1997) 650
Ronning, C., see Restle 161 (1996) 168
Ronning, C., see Jahn 161 (1996) 172

Rosenbaum, D.F. and C.F. Zukoski, Protein interactions and crystallization 169 (1996) 752
Rosenberger, F., Protein crystallization 166 (1996) 40
Rosenberger, F., see Muschol, M. 167 (1996) 738
Rosenberger, F., P.G. Vekilov, M. Muschol and B.R. Thomas, Nucleation and crystallization of globular proteins – what we know and what is missing 168 (1996) 1
Roshko, A., see Morris Hotsenpiller, P.A. 166 (1996) 779
Rossberg, A., M. Piechotka, G. Wetzel, J. Gastaldi, A. Magerl and E. Kaldis, Structural non-uniformities in mercuric iodide crystals grown by two different vapour growth techniques 166 (1996) 354
Rossolenko, S.N., see Abrosimov, N.V. 166 (1996) 657
Rossow, U., see Dietz 164 (1996) 34
Roth, M., see Vuillard, L. 168 (1996) 150
Roth, M. and D. Perlov, Growth of barium borate crystals from sodium fluoride solutions 169 (1996) 734
Rothman, J.B., see Morris Hotsenpiller, P.A. 166 (1996) 779
Roucau, C., see Snoeck, E. 167 (1996) 143
Rovira, C., see Figueras, A. 166 (1996) 798
Rowland, L.B., see Davis 164 (1996) 132
Rowland, L.B., see Burk Jr., A.A. 167 (1996) 586
Roy, M.-O., see Boyer, M. 167 (1996) 212
Rudneva, E.B., see Smolsky, I.L. 166 (1996) 228
Rudneva, E.B., see Smolski, I. 169 (1996) 741
Rudolph, P., S. Kawasaki, S. Yamashita, S. Yamamoto, Y. Usuki, Y. Konagaya, S. Matada and T. Fukuda, Attempts to growth of undoped CdTe single crystals with high electrical resistivity 161 (1996) 28
Rudolph, P., see Fukuda 161 (1996) 45
Rudolph, P., H.J. Koh, N. Schäfer and T. Fukuda, The crystal perfection depends on the superheating of the mother phase too – experimental facts and speculations on the "melt structure" of semiconductor compounds 166 (1996) 578
Rudra, A., see Amano 164 (1996) 321
Rudra, A., see Carlin 164 (1996) 470
Ruf, T., see Lin, C.T. 167 (1996) 612
Ruf, W., see Stura, E.A. 168 (1996) 260
Ruiz, X., see Solé, R. 166 (1996) 402
Ruiz, X., see Solé, R. 167 (1996) 681
Ruiz, X., see Solé, R. 169 (1996) 600
Rulmont, A., see Stassen, S. 166 (1996) 281
Rumberg, A., see Kurpas, P. 170 (1997) 203
Rushworth, S., see Taudt, W. 169 (1996) 243
Russell, G.J., see Zhou 165 (1996) 42
Russell, S.W., see Barbero 165 (1996) 57
Ryan, R., see Hamm 164 (1996) 362
Rzepka, E., see Martel 161 (1996) 250
Rzepka, E., A. Lusson, A. Riviere, A. Aoudia, Y. Marfaing and R. Triboulet, Defects study by photoluminescence and cathodoluminescence in vanadium doped CdZnTe 161 (1996) 286

Sabbides, Th.G. and P.G. Koutsoukos, The effect of surface treatment with inorganic orthophosphate on the dissolution of calcium carbonate 165 (1996) 268
Sabharwal, S.C., Sangeeta, D.G. Desai, S.C. Karandikar, A.K. Chauhan, A.K. Sangiri, K.S. Keshwani and M.N. Ahuja, Effect of non-stoichiometry on some properties of lead tungstate single crystals 169 (1996) 304
Sacedón, A., see Kidd, P. 169 (1996) 649
Sadra, K., Techniques for molecular beam epitaxy of multiple-wavelength vertical-cavity laser arrays 169 (1996) 175
Sadwick, L.P., see Hill 162 (1996) 1
Sadwick, L.P., see Kim 164 (1996) 104
Sadwick, L.P., P.P. Lee, M. Patel, M. Nikols, R.J. Hwu, J.E. Shield, D.C. Streit, D. Brehmer, K. McCormick, S.J. Allen and R.W. Gedridge, Epitaxial dysprosium phosphide grown by gas-source and solid-source MBE on gallium arsenide substrates 164 (1996) 285
Saemann-Ischenko, G., see Christiansen, S. 166 (1996) 848
Saghir, M.Z., R. Abbaschian and R. Raman, Numerical analysis of thermocapillary convection in axisymmetric liquid encapsulated InBi 169 (1996) 110
Sagi, I., see Thygesen, J. 168 (1996) 308
Saijo, H. and M. Shiojiri, J-aggregates of cyanine dye molecules adsorbed on AgBr emulsion crystal surfaces 166 (1996) 930
Saito, H., T. Makimoto and N. Kobayashi, Photoluminescence characteristics of nitrogen atomic-layer-doped GaAs grown by MOVPE 170 (1997) 372
Saito, T., see Nishino 165 (1996) 227
Saito, Y., see Kaito, C. 167 (1996) 580
Saka, T., see Hirotani, M. 170 (1997) 390
Sakamoto, T., see Kaito, C. 167 (1996) 580
Sakata, Y., T. Morimoto, Y. Inomoto and H. Hasumi, Low-threshold strained multiquantum well lasers fabricated by selective metalorganic vapor phase epitaxy without a semiconductor etching process 170 (1997) 456
Sakaue, K., see Yoneda 165 (1996) 50
Sakuma, H., see Tachibana, M. 166 (1996) 883
Sakurai, T., see Hayakawa, Y. 169 (1996) 613
Sale, T.E., see Hirotani, M. 170 (1997) 390
Sale, T.E., J.S. Roberts, J. Woodhead, J.P.R. David and P.N. Robson, Visible (683 to 713 nm) room-temperature AlGaAs vertical cavity surface emitting lasers (VCSELs) 170 (1997) 399
Sale, T.E., see Roberts, J.S. 170 (1997) 621

Salim, S., C.A. Wang, R.D. Driver and K.F. Jensen, In situ concentration monitoring in a vertical OMVPE reactor by fiber-optics-based Fourier transform infrared spectroscopy 169 (1996) 443
Salim, S., see Wang, C.A. 170 (1997) 55
Salk, M., see Eiche, C. 166 (1996) 245
Salk, M., see Fiederle, M. 166 (1996) 256
Salviati, G., see Li 163 (1996) 195
Salviati, G., see Rigo 164 (1996) 430
Salviati, G., see Mazzer, M. 170 (1997) 553
Sameshima, H., see Kinoshita, K. 166 (1996) 266
Sammelselg, V., see Aarik, J. 169 (1996) 496
Samuelson, L., see Junno 164 (1996) 66
Samuelson, L., see Miller 164 (1996) 345
Samuelson, L., see Deppert, K. 169 (1996) 13
Samuelson, L., see Seifert, W. 170 (1997) 39
Samuelson, L., see Carlsson, N. 170 (1997) 127
Sandiumenge, F., see Dubs, C. 166 (1996) 836
Sangeeta, see Sabharwal, S.C. 169 (1996) 304
Sanghadasa, M., see Aggarwal, M.D. 166 (1996) 542
Sangiri, A.K., see Sabharwal, S.C. 169 (1996) 304
Sano, C. and N. Nagashima, Effects of L-glutamyl peptides on the growth of L-glutamic acid crystals (α-form) 166 (1996) 129
Sano, C., see Hasegawa, K. 166 (1996) 925
Santana, C.J., C.R. Abernathy, S.J. Pearton and K.S. Jones, Initial growth stages of $Al_xGa_{1-x}P$ on epitaxial silicon 164 (1996) 248
Santilli, N., see Chianese, A. 166 (1996) 1099
Santo, A.M.E., see Baldochi, S.L. 166 (1996) 375
Santo, A.M.E., see Ranieri, I.M. 166 (1996) 423
Santoro, G.J., see Singh, N.B. 166 (1996) 364
Santoro, G.J., see Singh, N.B. 167 (1996) 107
Santos, M.B., see Liu, W.K. 167 (1996) 111
Sasaki, A., Atomic scale study of InAs/GaAs heteroepitaxy 163 (1996) 143
Sasaki, C., see Noguchi, S. 168 (1996) 270
Sasaki, H., see Kudo, N. 168 (1996) 118
Sasaki, M., see Yoshida 164 (1996) 291
Sasaki, T., see Takano, Y. 169 (1996) 621
Sasaki, T., see Kudo, K. 170 (1997) 634
Sasaura, M. and S. Miyazawa, Growth instability in $LnSrGaO_4$ (Ln: Pr,Nd) crystal pulling 166 (1996) 825
Sato, D.L., H.P. Lee, J.M. Kuo and H.C. Kuo, In-situ pyrometric interferometry monitoring of $In_{0.5}Ga_{0.5}P/In_{0.5}Al_{0.5}P$ material systems during gas-source molecular beam epitaxy growth 164 (1996) 47
Sato, H., see Suzuki, M. 170 (1997) 661
Sato, K., see Tsutsui 163 (1996) 440
Sato, K., M.R. Fahy, M.J. Ashwin and B.A. Joyce, Silicon incorporation behaviour in GaAs grown on GaAs(111)A by molecular beam epitaxy 165 (1996) 345
Sato, M., see Kimura 165 (1996) 408
Sato, M., see Kurpas, P. 170 (1997) 203
Sato, M., see Kurpas, P. 170 (1997) 442
Satow, Y., see Mizutani, R. 168 (1996) 253
Satow, Y., see Noguchi, S. 168 (1996) 270
Satow, Y., see Nitanai, Y. 168 (1996) 280
Satow, Y., see Nishida, M. 168 (1996) 284
Satow, Y., see Miyawaki, K. 168 (1996) 292
Sauer, R., see Sobolev, N.A. 167 (1996) 502
Sauerländer, F., see Taudt, W. 169 (1996) 243
Sauerländer, F., see Gurskii, A.L. 170 (1997) 533
Savino, R. and R. Monti, Buoyancy and surface-tension-driven convection in hanging-drop protein crystallizer 165 (1996) 308
Savitsky, V.G., see Mansurov 161 (1996) 201
Sawaki, N., see Ohuchi, Y. 170 (1997) 325
Sawamura, S., see Izumi, K. 168 (1996) 106
Sazaki, G., see Kurihara, K. 166 (1996) 904
Sazaki, G., K. Kurihara, T. Nakada, S. Miyashita and H. Komatsu, A novel approach to the solubility measurement of protein crystals by two-beam interferometry 169 (1996) 355
Schäfer, N., see Rudolph, P. 166 (1996) 578
Schäfer, N., T. Yamada, K. Shimamura, H.J. Koh and T. Fukuda, Growth of Si_xGe_{1-x} crystals by the micro-pulling-down method 166 (1996) 675
Schäfer, N., see Koh, H.J. 167 (1996) 38
Schäffer, C. and M. Rodewald, Growth of epitaxial $CoSi_2$ films on strained $Si_{1-x}Ge_x$/Si(001) heterostructures 165 (1996) 61
Schall, C.A., E. Arnold and J.M. Wiencek, Enthalpy of crystallization of hen egg-white lysozyme 165 (1996) 293
Schall, C.A., J.S. Riley, E. Li, E. Arnold and J.M. Wiencek, Application of temperature control stategies to the growth of hen egg-white lysozyme crystals 165 (1996) 299
Schaper, A., see Spika, Z. 170 (1997) 257
Schäpers, Th., see Hollfelder, M. 170 (1997) 103
Scharmann, A., see Schwabe, D. 166 (1996) 483
Scheel, H.J., see Mukaida, M. 169 (1996) 715
Schelhase, S., J. Böttcher, R. Gibis, H. Künzel and A. Paraskevopoulos, MOMBE selective infill growth of InP:Si and InGaAs:Si and large area MOMBE regrowth 164 (1996) 339
Schelhase, S., see Künzel 164 (1996) 449
Schenk, K., see Pan 165 (1996) 273
Schenk, M., see Utke 162 (1996) 126
Schermer, J.J., F.K. de Theije and L.J. Giling, Mosaic growth of diamond: a study of homoepitaxial flame deposition and etching of {001}-oriented diamond layers 165 (1996) 387
Schermer, J.J., W.J.P. van Enckevort and L.J. Giling, Surface stabilization phenomena on flame-deposited diamond single crystals 166 (1996) 622
Schieber, M., see Van Scyoc, J.M. 166 (1996) 384
Schieber, M., see Burtman, V. 166 (1996) 832
Schienle, F., see Steimetz, E. 170 (1997) 208
Schilz, J., see Helmers 165 (1996) 381

Schimpf, K., see Hollfelder, M. 170 (1997) 103
Schlesinger, T.E., see Van Scyoc, J.M. 166 (1996) 384
Schlünzen, F., see Thygesen, J. 168 (1996) 308
Schmeding, A., see Lin, C.T. 167 (1996) 612
Schmelz, M., see Dubs, C. 166 (1996) 836
Schmid, F., see Li 162 (1996) 147
Schmid, H., see Ye, Z.-G. 167 (1996) 628
Schmiemann, D., see Tanneberger, U. 166 (1996) 1074
Schmitz, D., see Bergunde, T. 170 (1997) 66
Schmitz, D., see Beccard, R. 170 (1997) 97
Schmitz, D., see Hollfelder, M. 170 (1997) 103
Schneider, A., see Prösch, G. 170 (1997) 537
Schneider, A., D. Drews, J. Söllner, M. Heuken and D.R.T. Zahn, Temperature induced resonant Raman scattering of MOVPE grown ZnS_xSe_{1-x}/GaAs(100) heterostructures 170 (1997) 767
Schneider, P., see Behet, M. 167 (1996) 415
Schneider, P., see Tümmler, J. 170 (1997) 772
Schock, H.W., see Braunger, D. 167 (1996) 129
Scholl, S., see Fischer 161 (1996) 214
Scholz, F., see Geiger, M. 169 (1996) 625
Scholz, F., V. Härle, F. Steuber, H. Bolay, A. Dörnen, B. Kaufmann, V. Syganow and A. Hangleiter, Low pressure MOVPE of GaN and GaInN/GaN heterostructures 170 (1997) 321
Scholz, F., see Geng, C. 170 (1997) 418
Scholz, F., see Geiger, M. 170 (1997) 558
Scholz, F., see Ottenwälder, D. 170 (1997) 695
Scholz, U., D. Plachke, W. Yuan, H.-J. Carstanjen, F. Mücklich and G. Petzow, On the influence of impurities in beryllium single crystal growth 169 (1996) 575
Scholz, U., Z.S. Nikolic, F. Mücklich and G. Petzow, Determination and modification of the thermal conditions in a double ellipsoid mirror furnace 169 (1996) 578
Schönherr, E., see Lin, C.T. 167 (1996) 612
Schröder, W., see Wollweber 163 (1996) 243
Schröder, W., see Abrosimov, N.V. 166 (1996) 657
Schroeter-Janssen, H., see Roehle, H. 170 (1997) 109
Schüler, T., see Dubs, C. 166 (1996) 836
Schultz, A.J., see Zhang, K. 169 (1996) 73
Schulz, D., see Wollweber 163 (1996) 243
Schulz, H.-J., see Kreissl 161 (1996) 239
Schulz, H.-J., see Peka 161 (1996) 277
Schumann, B., see Weise, S. 166 (1996) 718
Schumann, D., see Hermann 161 (1996) 181
Schumann, H., see Geiger, M. 169 (1996) 625
Schumann, H., see Pohl, U.W. 170 (1997) 144
Schumann, H., see Dadgar, A. 170 (1997) 173
Schur, R., see Kitamura, M. 170 (1997) 563
Schwabe, D., X. Da and A. Scharmann, Unstable flow and solidification speed due to the interaction of thermocapillary and solutocapillary forces in directional solidification 166 (1996) 483
Schwabe, R., see Kirpal, G. 170 (1997) 167
Schwarz, R., see Laasch 161 (1996) 34
Schwarz, R., see Christmann 161 (1996) 259
Schwarz, R., see Eiche 161 (1996) 271
Schwarz, R., see Eiche, C. 166 (1996) 245
Schweizer, H., see Geng, C. 170 (1997) 418
Schweizer, H., see Geiger, M. 170 (1997) 558
Schweizer, H.P., see Moser, M. 170 (1997) 404
Schweizer, M., see Cröll, A. 166 (1996) 239
Scriven, G.J., A.W.R. Leitch, J.H. Neethling, V.V. Kozyrkov and V.J. Watters, The growth of Zn_3As_2 on InP by atmospheric pressure MOVPE 170 (1997) 813
Sebastian, P.J., see Calixto, E. 169 (1996) 287
Seckler, M.M., see Giulietti, M. 166 (1996) 1089
Sedelnikova, S., see Garber, M. 168 (1996) 301
Seeger, A., see Zwanger 163 (1996) 445
Seffar, A., see Figueras, A. 166 (1996) 798
Seibt, M., see Tromson-Carli, A. 170 (1997) 549
Seidel, P., see Li 162 (1996) 147
Seidl, A., R. Marten and G. Müller, In situ investigation of oxygen distribution and transport in Czochralski silicon melts by electrochemical solid ionic sensors 166 (1996) 680
Seifert, W., N. Carlsson, J. Johansson, M.-E. Pistol and L. Samuelson, In situ growth of nano-structures by metal-organic vapour phase epitaxy 170 (1997) 39
Seifert, W., see Carlsson, N. 170 (1997) 127
Seki, H., see Koukitu 163 (1996) 180
Seki, H., see Takahashi, N. 169 (1996) 463
Seki, H., see Koukitu, A. 170 (1997) 306
Sekino-Suzuki, N., see Sugahara, M. 168 (1996) 288
Sekita, M., see Morita, S. 166 (1996) 370
Sekiwa, H., see Miyazawa, Y. 166 (1996) 286
Senchenkov, A.S., see Fiederle, M. 166 (1996) 256
Serbutoviez, C., see Pan 165 (1996) 273
Serganov, A., see Garber, M. 168 (1996) 301
Serrano, M.D., see Bermúdez, V. 169 (1996) 409
Serrano, M.L., see Barata 163 (1996) 426
Šesták, J., see Šestáková 165 (1996) 159
Šestáková, V., see Srnánek 165 (1996) 156
Šestáková, V., B. Štěpánek and J. Šesták, Various methods for the growth of GaSb single crystals 165 (1996) 159
Setzer, B., see Hollfelder, M. 170 (1997) 103
Seuret, D., see di Cristoforo, A. 167 (1996) 644
Severi, M., see di Cristoforo, A. 167 (1996) 644
Seyssiecq, I., S. Veesler and R. Boistelle, A non-immersed induction conductivity system for controlling supersaturation in corrosive media: the case of gibbsite crystals agglomeration in Bayer liquors 169 (1996) 124
Sha, Y.-G., see Chen, K.-T. 166 (1996) 731
Sha, Y.-G., see Su, C.-H. 166 (1996) 736
Sha, Z.L., H. Hatakka, M. Louhi-Kultanen and S. Palosaari, Crystallization kinetics of potassium sulfate in an MSMPR stirred crystallizer 166 (1996) 1105

Shang, P., see Yang, G. 166 (1996) 820
Shang, S.X., see Zeng, J.M. 169 (1996) 474
Shao, C.L., see Soga, T. 170 (1997) 447
Shao, Z., see Zhang, Y. 167 (1996) 373
Shapkin, P.V., see Korostelin 161 (1996) 51
Sharon, R., see Thygesen, J. 168 (1996) 308
Shcherbak, L., P. Feichouk and O. Panchouk, Effect of CdTe "postmelting" 161 (1996) 16
Shcherbak, L., P. Feichouk, P. Fochouk and O. Panchouk, Self-compensation studies in Cd-saturated In-doped CdTe 161 (1996) 219
Shcherbakov, D., see Garber, M. 168 (1996) 301
Shekunov, B.Yu., see Ristic, R.I. 167 (1996) 693
Shekunov, B.Yu., see McEwan, A. 167 (1996) 701
Shelpakova, I.R., see Kovalevski, S.V. 167 (1996) 208
Shen, J., see Tsui 164 (1996) 491
Shen, X.F., A.V. Anilkumar, R.N. Grugel and T.G. Wang, Utilizing vibration to promote microstructural homogeneity during floating-zone crystal growth processing 165 (1996) 438
Shen, X.Q., see Nishinaga 163 (1996) 60
Shen, X.-Q., see Ren, H.-W. 166 (1996) 217
Shen, X.Q., H.W. Ren, M. Tanaka and T. Nishinaga, Real-time observations of faceting and shrinkage processes of disk-shaped mesas in GaAs molecular beam epitaxy on GaAs(111)B substrates 169 (1996) 607
Shepherd, E.E.A., J.N. Sherwood and G.S. Simpson, The growth and perfection of organic non-linear optical crystals: N-methyl urea (NMU) from methanol solution. III. The growth of large single crystals for optical examination 167 (1996) 709
Sheregii, E., see Ciach 161 (1996) 234
Sherriff, R.E., see Lareau, R.T. 167 (1996) 406
Sherwood, J.N., see Ristic, R.I. 167 (1996) 693
Sherwood, J.N., see McEwan, A. 167 (1996) 701
Sherwood, J.N., see Shepherd, E.E.A. 167 (1996) 709
Shi, E.-W., see Xia, C.-T. 166 (1996) 961
Shibata, K., see Takiguchi, T. 170 (1997) 705
Shibata, T., Y. Takakuwa, A. Tanaka, T. Iguchi, M. Kogure and T. Ogawa, Doping effect of human blood on surface microstructure of cupric chloride dendrites grown from aqueous solutions 167 (1996) 716
Shibuya, Y., see Tanaka, I. 169 (1996) 469
Shield, J.E., see Sadwick 164 (1996) 285
Shigematsu, N., see Shishiguchi, S. 166 (1996) 689
Shigematsu, T., see Kanda, T. 166 (1996) 663
Shigeta, Y., J. Endo and K. Maki, A characteristic feature of crystalline thin-film growth of Si on a 7×7 superlattice surface of Si(111) 166 (1996) 617
Shih, C.-Y., see Tai, C.Y. 166 (1996) 1040
Shih, H.D., see Bevan, M.J. 170 (1997) 467
Shimada, I., see Mizutani, R. 168 (1996) 253
Shimada, M., see Habuka, H. 169 (1996) 61
Shimada, W., see Hasegawa, T. 166 (1996) 314
Shimamura, K., H. Takeda, T. Kohno and T. Fukuda, Growth and characterization of lanthanum gallium silicate $La_3Ga_5SiO_{14}$ single crystals for piezoelectric applications 163 (1996) 388
Shimamura, K., see Kimura 163 (1996) 393
Shimamura, K., see Schäfer, N. 166 (1996) 675
Shimamura, K., see Koh, H.J. 167 (1996) 38
Shimamura, K., see Uda, S. 167 (1996) 64
Shimamura, K., see Terada, Y. 167 (1996) 369
Shimamura, K., see Takeda, H. 169 (1996) 503
Shimamura, K., see Chani, V.I. 169 (1996) 604
Shimizu, T., H. Nonaka and K. Arai, Growth of homoepitaxial $YBa_2Cu_3O_{7-x}$ films by molecular beam epitaxy 166 (1996) 841
Shimomura, H., T. Anan and S. Sugou, Growth of AlPSb and GaPSb on InP by gas-source molecular beam epitaxy 162 (1996) 121
Shimoyama, K., see Fujii, K. 170 (1997) 679
Shimura, T., H. Misaki, M. Umeno, I. Takahashi and J. Harada, X-ray diffraction evidence for the existence of epitaxial microcrystallites in thermally oxidized SiO_2 thin films on Si(111) surfaces 166 (1996) 786
Shin, H.Y., see Chou, W.C. 169 (1996) 747
Shintani, A., see Miyano, T. 166 (1996) 469
Shintani, A., see Kanda, T. 166 (1996) 663
Shiohara, T., see Kikuma 161 (1996) 60
Shiohara, Y., see Yao 165 (1996) 198
Shiohara, Y., see Yamada, Y. 166 (1996) 804
Shiohara, Y., see Kitamura, T. 166 (1996) 854
Shiohara, Y., see Nakamura, M. 166 (1996) 859
Shiojima, T., see Ohkubo, M. 170 (1997) 177
Shiojiri, M., see Saijo, H. 166 (1996) 930
Shiojiri, M., see Tanabe, K. 166 (1996) 935
Shiojiri, M., see Kitano, M. 166 (1996) 1116
Shirafuji, J., see Sugino, T. 166 (1996) 628
Shirafuji, J., see Hashimoto, T. 169 (1996) 185
Shiraishi, Y., S. Kurosaka and M. Imai, Silicon crystal growth using a liquid-feeding Czochralski method 166 (1996) 685
Shirakawa, T., see Fujiwara 165 (1996) 169
Shirakawa, T., see Fujiwara, S. 167 (1996) 357
Shirakawa, T., see Fujiwara, S. 169 (1996) 660
Shiraki, Y., see Yaguchi, H. 170 (1997) 353
Shiraki, Y., see Pan, W. 170 (1997) 585
Shiralagi, K., M. Walther, R. Tsui and H. Goronkin, Selective InAs growth by chemical beam epitaxy 164 (1996) 334
Shiralagi, K., see Tsui 164 (1996) 491
Shiran, N.V., see Komar, V.K. 160 (1996) 419
Shishiguchi, S., T. Okamoto, K. Arai, K. Hasebe and N. Shigematsu, The reduction of grain size in LPCVD poly-Si by in situ oxygen and phosphorus doping 166 (1996) 689
Shlyakhovuy, V.Z., see Nikonyuk 161 (1996) 186
Shmagin, I.K., see Keller, S. 170 (1997) 349

Shukla, N., see Zhang 164 (1996) 40
Shukla, N., see Patrikarakos, D.G. 170 (1997) 215
Shukri, Z.A. and C.H. Champness, Identification of oxygen in the copper as the source of adhesion in Bridgman-grown $CuInSe_2$ crystals 166 (1996) 708
Shumov, D.P., A.T. Nenov and D.D. Nihtianova, Inclusions in LiB_3O_5 crystals obtained by the top-seeded solution growth method in the Li_2O–B_2O_3 system. Part 1 169 (1996) 519
Shumov, D.P., see Nihtianova, D.D. 169 (1996) 527
Shusterman, Y., see Harada 163 (1996) 31
Shusterman, Yu.V., see Sokolov, N.S. 169 (1996) 40
Sica, F., S. Adinolfi, L. Vitagliano, A. Zagari, S. Capasso and L. Mazzarella, Cosolute effect on crystallization of two dinucleotide complexes of bovine seminal ribonuclease from concentrated salt solutions 168 (1996) 192
Sicardi, S., see Marmo, L. 166 (1996) 1027
Siepel, K., see Thompson, A.G. 170 (1997) 92
Siffert, P., see Chibani 161 (1996) 153
Siffert, P., see Martel 161 (1996) 250
Siffert, P., see Zerrai 161 (1996) 264
Sigmon, T.W., see Barbero 165 (1996) 57
Siimon, H., see Aarik, J. 169 (1996) 496
Silfvenius, C., B. Stålnacke and G. Landgren, MOVPE growth of strain-compensated 1300 nm $In_{1-x}Ga_xAs_yP_{1-y}$ quantum well structures 170 (1997) 122
Silier, I., see Konuma, M. 166 (1996) 234
Silier, I., A. Gutjahr, N. Nagel, P.O. Hansson, E. Czech, M. Konuma, E. Bauser, F. Banhart, R. Köhler, H. Raidt and B. Jenichen, Solution growth of epitaxial semiconductor-on-insulator layers 166 (1996) 727
Silva, S.R.P., see O'Brien, P. 167 (1996) 133
Silvestre, L., A. Ougazzaden, D. Delprat, A. Ramdane, C. Daguet and G. Patriarche, Study of growth rate and composition variations in metalorganic vapour phase selective area epitaxy at atmospheric pressure and application to the growth of strained layer DBR lasers 170 (1997) 639
Simpson, G.S., see Shepherd, E.E.A. 167 (1996) 709
Singh, N.B., T. Henningsen, V. Balakrishna, D.R. Suhre, N. Fernelius, F.K. Hopkins and D.E. Zelmon, Growth and characterization of gallium selenide crystals for far-infrared conversion applications 163 (1996) 398
Singh, N.B., see Kim 165 (1996) 429
Singh, N.B., S.S. Mani, J.D. Adam, S.R. Coriell, M.E. Glicksman, W.M.B. Duval, G.J. Santoro and R. DeWitt, Direct observations of interface instabilities 166 (1996) 364
Singh, N.B., M.E. Glicksman, S.R. Coriell, W.M.B. Duval, G.J. Santoro and R. DeWitt, Measurement of diffusion coefficient using a diaphragm cell: $PbBr_2$–AgBr system 167 (1996) 107
Singh, N.K., see Foord 164 (1996) 208
Sitar, Z., see Davis 164 (1996) 132
Sitharaman, S., see Gupta 165 (1996) 19
Sitnikova, A., see Dmitriev, V. 166 (1996) 601
Skeldon, A.C., D.S. Riley and K.A. Cliffe, Convection in a low Prandtl number fluid 162 (1996) 95
Smith, F.T.J., see Ingle, N.K. 167 (1996) 543
Smith, G.D., see Long, M.M. 168 (1996) 233
Smith, R.S., see Gaffney, M.S. 167 (1996) 8
Smolski, I., J.J. De Yoreo, N.P. Zaitseva, J.D. Lee, T.A. Land and E.B. Rudneva, Oriented liquid inclusions in KDP crystals 169 (1996) 741
Smolsky, I.L., N.P. Zaitseva, E.B. Rudneva and S.V. Bogatyreva, Formation of "hair" inclusions in rapidly grown potassium dihydrogen phosphate crystals 166 (1996) 228
Snoeck, E., S. Frechengues, M.J. Casanove, C. Roucau and S. Andrieu, HREM study of the epitaxial growth of Fe on Ir(001) 167 (1996) 143
Soares, J.C., see Sochinskii 161 (1996) 195
Sobolev, N.A., F.P. Korshunov, R. Sauer, K. Thonke, U. König and H. Presting, Influence of electron irradiation and annealing on the photoluminescence of Si/Ge superlattices and Si/Ge quantum wells 167 (1996) 502
Sochinskii, N.V., J.C. Soares, E. Alves, M.F. da Silva, P. Franzosi, S. Bernardi and E. Diéguez, Structural properties of CdTe and $Hg_{1-x}Cd_xTe$ epitaxial layers grown on sapphire substrates 161 (1996) 195
Soerensen, G., see Watkins, S.P. 170 (1997) 788
Soga, T., T. Jimbo and M. Umeno, Initial stage of GaP/Si heteroepitaxial growth by metalorganic chemical vapor deposition 163 (1996) 165
Soga, T., T. Kato, K. Baskar, C.L. Shao, T. Jimbo and M. Umeno, MOCVD growth of high-quality AlGaAs on Si substrates for high-efficiency solar cells 170 (1997) 447
Söhnel, O., see Chianese, A. 166 (1996) 1099
Sokolov, I.A., see Alexeev, A.N. 166 (1996) 72
Sokolov, I.A., see Alexeev, A.N. 166 (1996) 167
Sokolov, N.S., see Harada 163 (1996) 31
Sokolov, N.S., see Itoh, Y. 166 (1996) 61
Sokolov, N.S., J.C. Alvarez, S.V. Gastev, Yu.V. Shusterman, I. Takahashi, Y. Itoh, J. Harada and R.M. Overney, High quality CaF_2 layers on Si(111) with type-A epitaxial relation at the interface 169 (1996) 40
Solans, X., see Solé, R. 167 (1996) 681
Solans, X., see Solé, R. 169 (1996) 600
Solé, R., X. Ruiz, R. Cabré, M. Aguiló, F. Díaz and V. Nikolov, Co and Sn substituted barium M-hexaferrites: single crystal growth and magnetic characterization 166 (1996) 402

Solé, R., X. Ruiz, R. Cabré, Jna. Gavaldà, M. Aguiló, F. Díaz, V. Nikolov and X. Solans, $KTiOPO_4$ single crystals grown from neodymium modified fluxes 167 (1996) 681

Solé, R., V. Nikolov, X. Ruiz, Jna. Gavaldà, X. Solans, M. Aguiló and F. Díaz, Growth of β-$KGd_{1-x}Nd_x(WO_4)_2$ single crystals in $K_2W_2O_7$ solvents 169 (1996) 600

Söllner, J., see Taudt, W. 169 (1996) 243

Söllner, J., see Heuken, M. 170 (1997) 30

Söllner, J., see Schneider, A. 170 (1997) 767

Solomon, J.S., see Li 164 (1996) 180

Solskii, I., see Frukacz, Z. 169 (1996) 98

Somers, M., see Werner 164 (1996) 223

Son, Chang-Sik, Seong-Il Kim, Yong Kim, Min-Suk Lee, Moo-Sung Kim, Suk-Ki Min and In-Hoo Choi, Properties of carbon-doped InGaAs grown by atmospheric pressure metalorganic chemical vapor deposition using CCl_4 165 (1996) 222

Son, C.S., see Kim, S.-I. 170 (1997) 665

Son, M.H., see Kim, E.K. 170 (1997) 803

Song, C.R., see Lan, C.W. 166 (1996) 458

Song, J.J., see Wong 164 (1996) 159

Song, M.H., Y.H. Lee, T.S. Hahn, M.H. Oh and K.H. Yoon, Thickness effects of SiO_xN_y interlayer inserted between $BaTiO_3$ insulating layer and ZnS:Mn phosphor layer in thin film electroluminescent devices 167 (1996) 157

Sonnenberg, K., see Althaus, M. 166 (1996) 566

Sopanen, M., see Koljonen, T. 169 (1996) 417

Sossna, E., see Kastner, M.J. 170 (1997) 188

Sotomayor-Torres, C.M., see Yates, H.M. 170 (1997) 611

Souliere, V., see Thévenot, V. 170 (1997) 251

Sousa, R., Group I metal ions of increasing atomic weight suppress the growth of crystalline aggregates and enhance the growth of large, single crystals of T7 RNA polymerase 167 (1996) 734

Spellmeyer, B., see Hermann 161 (1996) 181

Spika, Z., see Protzmann, H. 170 (1997) 155

Spika, Z., C. Zimprich, W. Stolz, E.O. Göbel, J. Jiang, A. Schaper and P. Werner, Correlation of ordering formation and surface structure in (GaIn)P using modulated MOVPE 170 (1997) 257

Spina, A., see Wajid, A. 170 (1997) 237

Sportiello, M.G., see Sygusch 162 (1996) 167

Srnánek, R., Š. Németh, J. Kováč, S. Kičin, B. Grietens, G. Borghs, J. Novák, V. Šestáková and L. Pekárek, Classification of morphological defects on GaAs/AlAsSb/GaSb structures prepared by MBE 165 (1996) 156

Stadler, W., see Meyer 161 (1996) 119

Stafford, A., S.J.C. Irvine and C.L. Griffiths, In situ measurement of the thermal and photo-assisted MOVPE of ZnTe using laser reflectometry 170 (1997) 182

Stall, R.A., see Thompson, A.G. 170 (1997) 92

Stålnacke, B., see Silfvenius, C. 170 (1997) 122

Stănculescu, F., M. Moldoveanu and M. Botea, Analysis of the mechanism of diffusion limited oxygen precipitation in Cz-silicon 166 (1996) 183

Stankus, S.V. and P.V. Tyagel'sky, Crystallization and thermal properties of Al_2O_3–Y_2O_3 melts 167 (1996) 165

Stano, A., see Rigo 164 (1996) 327

Stano, A., see Rigo 164 (1996) 430

Stark, R., see Christiansen, S. 166 (1996) 848

Starr, R., see Mitra, P. 170 (1997) 542

Stassen, S., A. Vanderschueren, R. Cloots, A. Rulmont and M. Ausloos, Texturation of Bi-based 2212 superconducting bulk ceramics 166 (1996) 281

Stauche, P., S. Erdt-Böhm, M. Brinkmann and H. Bach, Crystal growth and characterization of $Fe_{2+x}Ti_{1-x}$ 166 (1996) 390

Stávek, J., see Momonaga, M. 166 (1996) 1053

Steimetz, E., F. Schienle, J.-T. Zettler and W. Richter, Stranski–Krastanov formation of InAs quantum dots monitored during growth by reflectance anisotropy spectroscopy and spectroscopic ellipsometry 170 (1997) 208

Steiner, B., see Voigt, A. 166 (1996) 694

Steiner, B., L.E. Levine, M. Brown and D. Larson, Residual disorder in low pressure, low thermal gradient liquid encapsulated Czochralski gallium arsenide observed in high resolution synchrotron diffraction imaging 169 (1996) 1

Stenzel, O., see Dadgar, A. 170 (1997) 173

Štěpánek, B., see Šestáková 165 (1996) 159

Stepanova, A.N., see Givargizov 162 (1996) 73

Stephan, S., see Martel 161 (1996) 250

Stephenson, G.B., see Kisker 163 (1996) 54

Stephenson, G.B., see Kamiya 163 (1996) 67

Steuber, F., see Scholz, F. 170 (1997) 321

Stewart, J.D., see Mackenzie 164 (1996) 143

Stewart, N.M., see Ahmed 161 (1996) 223

Stewart, P.S., see Baldock, P. 168 (1996) 170

Stihle, M., see D'Arcy, A. 168 (1996) 175

Stillman, G.E., see Islam, M.R. 170 (1997) 413

Stoltz, S., see Peck, J. 170 (1997) 523

Stolz, W., see Protzmann, H. 170 (1997) 155

Stolz, W., see Spika, Z. 170 (1997) 257

Stolz, W., see Rettig, R. 170 (1997) 748

Storm, A., see Werner 164 (1996) 223

Strassburg, M., see Dadgar, A. 170 (1997) 173

Strauch, G., see Bergunde, T. 170 (1997) 66

Streater, R.W., see Moore 164 (1996) 485

Streit, D.C., see Sadwick 164 (1996) 285

Stringfellow, G.B., see Hill 162 (1996) 1

Stringfellow, G.B. and L.C. Su, Step structure during OMVPE growth of ordered GaInP 163 (1996) 128

Stringfellow, G.B., see Kim 164 (1996) 104

Stringfellow, G.B., see Murata, H. 170 (1997) 219
Stringfellow, G.B., see Chun, Y.S. 170 (1997) 263
Strunk, H.P., see Voigt, A. 166 (1996) 694
Strunk, H.P., see Christiansen, S. 166 (1996) 848
Strunk, H.P., see Albrecht, M. 167 (1996) 24
Strupiński, W., see Małąg, A. 170 (1997) 408
Stura, E.A., W. Ruf and I.A. Wilson, Crystallization and preliminary crystallographic data for a ternary complex between tissue factor, factor VIIa and a BPTI-derived inhibitor 168 (1996) 260
Stutz, C.E., see Lareau, R.T. 167 (1996) 406
Stutzmann, M., see Ambacher, O. 167 (1996) 1
Stutzmann, M., see Ambacher, O. 170 (1997) 335
Su, C.-H., see Chen, K.-T. 166 (1996) 731
Su, C.-H., Y.-G. Sha, K. Mazuruk, S.L. Lehoczky, H.-C. Liu, R. Fang and R.F. Brebrick, Mass flux and partial pressures of ZnSe by physical vapor transport 166 (1996) 736
Su, J., see Dost, S. 167 (1996) 305
Su, L.C., see Stringfellow 163 (1996) 128
Suárez-Parra, R., see Jiménez-González, A. 167 (1996) 649
Suda, Y., M. Ishida and M. Yamashita, Ar^+-laser-assisted subatomic-layer epitaxy of Si 169 (1996) 672
Suemoto, Y., see Obara, K. 166 (1996) 136
Suemoto, Y., see Obara, K. 166 (1996) 271
Suemune, I., T. Obinata, K. Uesugi, H. Suzuki, H. Kumano, H. Nashiki and J. Nakahara, Growth of zincblende MgS/ZnSe superlattices and their heterointerface properties 170 (1997) 480
Sugahara, M., N. Sekino-Suzuki, Y. Ohno-Iwashita and K. Miki, Crystallization and preliminary X-ray diffraction studies of θ-toxin (perfringolysin O), a pore-forming cytolysin of *Clostridium perfringens* 168 (1996) 288
Sugak, D., see Frukacz, Z. 169 (1996) 98
Sugawara, Y., see Kitamura, T. 166 (1996) 854
Su Genbo, see He Youping 169 (1996) 193
Su Genbo, see He Youping 169 (1996) 196
Sugimoto, H., see Gotoda 164 (1996) 308
Sugimoto, H., see Imaizumi, M. 169 (1996) 293
Sugino, T., M. Maeda, K. Kawarai and J. Shirafuji, Low-temperature epitaxial growth of InP by remote plasma-assisted metalorganic chemical vapour deposition 166 (1996) 628
Sugino, T., see Hashimoto, T. 169 (1996) 185
Sugiura, H., MOMBE growth of InAsP laser materials 164 (1996) 434
Sugiyama, N., see Kanaya 165 (1996) 172
Sugou, S., see Shimomura 162 (1996) 121
Suh, K.I., see Ansari, R.R. 168 (1996) 216
Suhre, D.R., see Singh 163 (1996) 398
Suita, M., see Imaizumi, M. 169 (1996) 293
Sukegawa, T., see Kamiya 165 (1996) 482
Sukegawa, T., see Kimura, M. 167 (1996) 516
Sukegawa, T., see Udono, H. 169 (1996) 181
Sukegawa, T., see Kimura, M. 169 (1996) 697
Sulzer, G., see Hermann 161 (1996) 181
Sumi, M., see Fukami, T.A. 168 (1996) 297
Sumino, K., see Yonenaga, I. 167 (1996) 616
Summers, C.J., see Tong 164 (1996) 202
Sun, C.Y., see Chou, W.C. 169 (1996) 747
Sun, J., see Zhang, Y. 169 (1996) 722
Sun, Y., see Yu, X. 166 (1996) 195
Sun, Z.W., see Han, J.H. 169 (1996) 129
Sundgren, J.-E., see Radamson, H.H. 167 (1996) 495
Sun Dianzhao, see Wang Xiaoliang 164 (1996) 281
Suruceanu, G.I., see Mawst, L.J. 170 (1997) 383
Suski, T., see Leszczynski, M. 169 (1996) 235
Suto, K., see Nugraha 163 (1996) 353
Suto, K., see Nugraha 165 (1996) 402
Suzuki, H., see Suemune, I. 170 (1997) 480
Suzuki, M., M. Aoki, M. Komori, H. Sato and S. Minagawa, Silicon shadow mask MOVPE for in-plane thickness control of InGaAsP/InP structures 170 (1997) 661
Suzuki, T., Oxygen partial pressure dependence of optical absorption in lithium niobate 163 (1996) 403
Suzuki, T., see Kanda, I. 166 (1996) 669
Suzuki, T., K.-I. Yumoto, M. Hasegawa and H. Takei, In situ observation of phase changes by X-ray diffraction in the Bi–Sr–Ca–Cu–O system 166 (1996) 872
Suzuki, Y., see Kurihara, K. 166 (1996) 904
Syganow, V., see Scholz, F. 170 (1997) 321
Sygusch, J., R. Coulombe, J.M. Cassanto, M.G. Sportiello and P. Todd, Protein crystallization in low gravity by step gradient diffusion method 162 (1996) 167
Syllaios, A.J., see Bevan, M.J. 170 (1997) 467
Symons, D.M., see Booker, G.R. 170 (1997) 777
Syrbu, A.V., see Mawst, L.J. 170 (1997) 383
Sys, C., see Zhang, X. 170 (1997) 83
Szatkowski, J., E. Płaczek-Popko, A. Hajdusianek and B. Bieg, Deep electron states in gallium-doped CdMnTe mixed crystals 161 (1996) 282
Sze, P.W., N.F. Wang, M.P. Houng, Y.H. Wang, Y.T. Cherng and C.H. Wang, Characteristics of ZnCdTe grown on (100) GaAs substrate by MOCVD 169 (1996) 27

Tabarrok, B., see Ye, X. 169 (1996) 704
Tabeling, P., see Emsellem, V. 166 (1996) 251
Tachibana, M., M. Michiyama, H. Sakuma, K. Kikuchi, Y. Achiba and K. Kojima, Growth, perfection, and mechanical properties of C_{60} single crystals 166 (1996) 883
Tadano, A., M. Asanuma and R. Aogaki, Electrochemical nucleation induced by nonequilibrium fluctuations 166 (1996) 1111
Tadatomo, K., see Ohuchi, Y. 170 (1997) 325
Taferner, W.T., A. Bensaoula, E. Kim and A. Bousetta, The investigation of GaN growth on silicon and sapphire using in-situ time-

of-flight low energy ion scattering and RHEED 164 (1996) 167
Taferner, W.T., see Bensaoula 164 (1996) 185
Tagami, M., see Yamada, Y. 166 (1996) 804
Taguchi, K., see Tsuji 162 (1996) 25
Taguchi, K., J. Garside and N.S. Tavare, Nucleation and growth kinetics of barium sulphate in batch precipitation 163 (1996) 318
Taguchi, K., see Tsuji, M. 170 (1997) 669
Tai, C.Y., C.-Y. Shih and W.-S. Juang, Suspension crystallization of p-dichlorobenzene from the melt 166 (1996) 1040
Tait, S., see Jahrling, K. 167 (1996) 285
Takagi, Y., see Matsuoka, M. 166 (1996) 1035
Takahashi, H., see Oka, K. 166 (1996) 380
Takahashi, I., see Harada 163 (1996) 31
Takahashi, I., see Itoh, Y. 166 (1996) 61
Takahashi, I., see Shimura, T. 166 (1996) 786
Takahashi, I., see Sokolov, N.S. 169 (1996) 40
Takahashi, J., see Hatta 163 (1996) 279
Takahashi, J., N. Ohtani and M. Kanaya, Structural defects in α-SiC single crystals grown by the modified-Lely method 167 (1996) 596
Takahashi, K., see Nishida, M. 168 (1996) 284
Takahashi, N., see Koukitu 163 (1996) 180
Takahashi, N., A. Koukitu and H. Seki, Effect of Ag addition on $YBa_2Cu_3O_{7-\delta}$ superconducting thin films prepared by mist microwave-plasma chemical vapor deposition 169 (1996) 463
Takahashi, N., see Koukitu, A. 170 (1997) 306
Takahashi, T., M. Hogyoku and K. Nagayama, Inter-subunit electrostatic interactions in ferritin molecule: comparison with intermolecular interactions in crystals 168 (1996) 130
Takakuwa, Y., see Shibata, T. 167 (1996) 716
Takamiya, S., see Takiguchi, T. 170 (1997) 705
Takano, Y., T. Sasaki, Y. Nagaki, K. Kuwahara, S. Fuke and T. Imai, Two-step growth of InP on GaAs substrates by metalorganic vapor phase epitaxy 169 (1996) 621
Takasuga, Y., see Fukami, T.A. 168 (1996) 297
Takebe, T., M. Fujii, T. Yamamoto, K. Fujita, K. Kobayashi and T. Watanabe, Facet generation during molecular beam epitaxy of GaAs/AlGaAs multilayers on GaAs(111)A patterned substrates 162 (1996) 31
Takeda, H., see Shimamura 163 (1996) 388
Takeda, H., K. Shimamura, T. Kohno and T. Fukuda, Growth and characterization of $La_3Nb_{0.5}Ga_{5.5}O_{14}$ single crystals 169 (1996) 503
Takeguchi, T., see Nakayama 163 (1996) 135
Takei, H., see Yan 165 (1996) 183
Takei, H., see Zhao, T.-r. 166 (1996) 408
Takei, H., see Suzuki, T. 166 (1996) 872
Takemi, M., see Takiguchi, T. 170 (1997) 705
Takemoto, A., see Takiguchi, T. 170 (1997) 705
Takemoto, J., S. Miyashita, T. Inoue and H. Komatsu, Liquid phase epitaxial growth of bismuth based superconductors 163 (1996) 100
Takemura, M., see Goto, H. 170 (1997) 510
Takeuchi, T., see Tsuji 162 (1996) 25
Takeuchi, T., see Tsuji, M. 170 (1997) 669
Taki, T., see Koukitu, A. 170 (1997) 306
Takiguchi, T., T. Itagaki, M. Takemi, A. Takemoto, Y. Miyazaki, K. Shibata, Y. Hisa, K. Goto, Y. Mihashi, S. Takamiya and M. Aiga, Selective-area MOCVD growth for 1.3 μm laser diodes with a monolithically integrated waveguide lens 170 (1997) 705
Takiyama, H., see Matsuoka, M. 166 (1996) 1035
Takizawa, T., see Matsushita, H. 166 (1996) 712
Tamiya, A., see Mizuno, K. 166 (1996) 146
Tamura, Y., see Kina, H. 169 (1996) 33
Tan, L.K., see Lim, L.C. 167 (1996) 686
Tanabe, K. and M. Shiojiri, Epitaxial growth of indigoid dyes on oriented polyethylene films 166 (1996) 935
Tanahashi, T., see Ekawa, M. 170 (1997) 685
Tanaka, A., see Kamiya 165 (1996) 482
Tanaka, A., see Kimura, M. 167 (1996) 516
Tanaka, A., see Shibata, T. 167 (1996) 716
Tanaka, A., see Udono, H. 169 (1996) 181
Tanaka, A., see Kimura, M. 169 (1996) 697
Tanaka, I., see Galambos, L. 167 (1996) 660
Tanaka, I., see Erdei, S. 167 (1996) 670
Tanaka, I., Y. Shibuya and H. Kojima, Crystal growth of pure and Zn-doped $CuGeO_3$ by the floating zone (FZ) method 169 (1996) 469
Tanaka, M., see Shen, X.Q. 169 (1996) 607
Tanaka, S., see Davis 163 (1996) 93
Tanaka, S., see Davis 164 (1996) 132
Tanaka, S., see Yao 165 (1996) 198
Tanaka, S., T. Ishikawa and M. Hibino, Transmission electron microscopy study of InGaAsP/InGaP thin-layer structure grown by liquid phase epitaxy 166 (1996) 334
Tanaka, S., see Yamada, Y. 166 (1996) 804
Tanaka, S., see Kitamura, T. 166 (1996) 854
Tanaka, S., see Yamada, Y. 167 (1996) 566
Tanaka, S., M. Yamamoto, K. Kawashima, K. Ito, R. Hayakawa and M. Ataka, Kinetic study on the early stage of the crystallization process of two forms of lysozyme crystals by photon correlation spectroscopy 168 (1996) 44
Tanaka, S., S. Iwai and Y. Aoyagi, Reduction of the defect density in GaN films using ultra-thin AlN buffer layers on 6H-SiC 170 (1997) 329
Tanaka, Y., see Ichimiya 163 (1996) 39
Tanaka, Y., M. Kamel and Y. Gotoh, Growth of Ce thin film on a Mo(110) surface 169 (1996) 299
Tang, D., see Zhong, W. 166 (1996) 91
Tang, Dingyuan, see Huang 165 (1996) 413
Tang, D.Y., see Li 163 (1996) 348

Tang, D.Y., see Li, B. 169 (1996) 480
Taniguchi, Y., see Asahi 161 (1996) 20
Taniuchi, T., see Kawaguchi, T. 166 (1996) 489
Taniuchi, T., see Kawaguchi, T. 166 (1996) 493
Taniuchi, T., see Kawaguchi, T. 169 (1996) 94
Tanneberger, U., R. Lacmann, A. Herden, H. Klapper, D. Schmiemann, R.A. Becker, A. Mersmann and U. Zacher, The dispersion of growth rate as a result of different crystal perfection 166 (1996) 1074
Tanokura, M., see Kudo, N. 168 (1996) 118
Tanzawa, Y. and Y. Ohde, Simulational approach to crystallization of finite polymer chains at high supercoolings 165 (1996) 284
Tao, X.T., see Yuan, D.R. 166 (1996) 545
Tao, Y. and S. Kou, Segregation control in horizontal Bridgman crystal growth 165 (1996) 195
Tao, Y. and S. Kou, Segregation control in vertical Bridgman crystal growth 169 (1996) 368
Tapfer, L., see Rettig, R. 170 (1997) 748
Tardieu, A., see Ducruix, A. 168 (1996) 28
Tardieu, A., see Bonneté, F. 168 (1996) 185
Tarelho, L.V.G., see Ranieri, I.M. 166 (1996) 423
Tateishi, T., see Ito 163 (1996) 311
Tateishi, T., see Onuma, K. 167 (1996) 773
Tatsumi, M., see Fujiwara, S. 167 (1996) 357
Tatsuoka, H., H. Kuwabara, M. Oshita, T. Nakamura, H. Fujiyasu and Y. Nakanishi, Epitaxial ferromagnetic MnSb layers on GaAs substrates grown by hot-wall epitaxy 166 (1996) 754
Taudt, W., S. Lampe, F. Sauerländer, J. Söllner, H. Hamadeh, M. Heuken, A.C. Jones, S. Rushworth, P. O'Brien and M.A. Malik, Nitrogen doping of ZnSe with trimethylsilylazide, triallylamine or bisditrimethylsilylamidozinc during metalorganic vapour phase epitaxy 169 (1996) 243
Taudt, W., see Heuken, M. 170 (1997) 30
Taudt, W., A. Hardt, S. Lampe, H. Hamadeh and M. Heuken, Nitrogen as carrier gas for the growth of ZnSe and ZnSe:N in plasma enhanced metalorganic vapor phase epitaxy 170 (1997) 491
Taudt, W., see Gurskii, A.L. 170 (1997) 533
Taudt, W., see Prösch, G. 170 (1997) 537
Tavare, N.S., see Taguchi 163 (1996) 318
Tavare, N.S., see Colônia, E.J. 166 (1996) 976
Taylor, A.G., see Zhang 164 (1996) 40
Taylor, A.G., see Joyce 164 (1996) 214
Tedenac, J.C., see Tomasini 165 (1996) 203
Tedenac, J.C., see Tomasini, P. 166 (1996) 590
Tedenac, J.C., see Ferhat, M. 167 (1996) 122
Tegetmeier, A., see Cröll, A. 166 (1996) 239
Tegetmeier, A., A. Cröll, A. Danilewsky and K.W. Benz, GaSb: surface tension and floating-zone growth 166 (1996) 651
Tegude, F.J., see Lindner, A. 170 (1997) 287
Teisseyre, H., see Leszczynski, M. 169 (1996) 235
Tekula-Buxbaum, P., see Pfeifer, J. 169 (1996) 727
Temkin, D.E., see Jackson 163 (1996) 461
Te Nijenhuis, J., see Bongers 162 (1996) 7
Te Nijenhuis, J., P.R. Hageman and L.J. Giling, Dependence of indium incorporation upon the substrate misorientation during growth of $In_xGa_{1-x}As$ by metalorganic vapour phase epitaxy 167 (1996) 397
Te Nijenhuis, J., see Hageman, P.R. 170 (1997) 270
Terada, Y., K. Shimamura, V.V. Kochurikhin, L.V. Barashov, M.A. Ivanov and T. Fukuda, Growth and optical properties of $ErVO_4$ and $LuVO_4$ single crystals 167 (1996) 369
Terakoshi, Y., see Hashimoto, T. 169 (1996) 185
Teraoka, K., see Ito 163 (1996) 311
Terashima, K., see Togawa 165 (1996) 362
Terashima, K., see Ikari, A. 167 (1996) 361
Terauchi, H., see Yoneda 165 (1996) 50
Tersoff, J., see Kisker 163 (1996) 54
Teschke, O., see Cotta 164 (1996) 409
The ISOLDE Collaboration, see Wienecke 161 (1996) 82
The ISOLDE Collaboration, see Restle 161 (1996) 168
The ISOLDE Collaboration, see Jahn 161 (1996) 172
Théobald-Dietrich, A., see Ng, J.D. 168 (1996) 50
Theodoropoulos, C., see Ingle, N.K. 167 (1996) 543
Theodoropoulos, C., N.K. Ingle and T.J. Mountziaris, Computational studies of the transient behavior of horizontal MOVPE reactors 170 (1997) 72
Thévenot, V., V. Souliere, H. Dumont, Y. Monteil, J. Bouix, P. Regreny and T.-M. Duc, Behaviour of vicinal InP surfaces grown by MOVPE: exploitation of AFM images 170 (1997) 251
Thieme, H.J., see Kim, M. 169 (1996) 681
Thirumavalavan, M., see Fornari, R. 166 (1996) 572
Thomas, B., K. Ellmer, M. Müller, C. Höpfner, S. Fiechter and H. Tributsch, Structural and photoelectrical properties of FeS_2 (pyrite) thin films grown by MOCVD 170 (1997) 808
Thomas, B.R., see Rosenberger, F. 168 (1996) 1
Thompson, A.G., R.A. Stall, W. Kroll, E. Armour, C. Beckham, P. Zawadzki, L. Aina and K. Siepel, Large scale manufacturing of compound semiconductors by MOVPE 170 (1997) 92
Thompson, J., see Wood, A.K. 170 (1997) 132
Thonke, K., see Sobolev, N.A. 167 (1996) 502
Thrush, E.J., see Zhang, X. 170 (1997) 83
Thrush, E.J., see Van der Stricht, W. 170 (1997) 344
Thygesen, J., S. Krumbholz, I. Levin, A. Zaytzev-Bashan, J. Harms, H. Bartels, F. Schlünzen, H.A.S. Hansen, W.S. Bennett, N. Volkmann, I. Agmon, M. Eisenstein, A. Dribin, E. Maltz, I. Sagi, S. Morlang, M. Fua, F. Franceschi, S. Weinstein, N. Böddeker, R. Sharon, K. Anagnostopoulos,

M. Peretz, M. Geva, Z. Berkovitch-Yellin and A. Yonath, Ribosomal crystallography: from crystal growth to initial phasing 168 (1996) 308
Tian, Y.L., see Hu 163 (1996) 266
Tischler, M.A., see Liu, J. 170 (1997) 357
Tishchenko, S., see Garber, M. 168 (1996) 301
Tochihara, H., see Hasegawa, T. 166 (1996) 314
Toda, A., F. Nakamura, K. Yanashima and A. Ishibashi, Blue-green laser diode grown by photo-assisted MOCVD 170 (1997) 461
Todd, P., see Sygusch 162 (1996) 167
Togawa, S., K. Izunome, S. Kawanishi, S.-I. Chung, K. Terashima and S. Kimura, Oxygen transport from a silica crucible in Czochralski silicon growth 165 (1996) 362
Togawa, S., see Ikari, A. 167 (1996) 361
Tokunaga, H., see Arai, T. 170 (1997) 88
Tomasini, P., A. Haidoux, J. Domagala, J.C. Tedenac, M. Maurin and B. Ducourant, Growth by atmospheric pressure OMVPE and X-ray analysis of ZnTe epilayers on III–V substrates 165 (1996) 203
Tomasini, P., A. Haidoux, M. Maurin and J.C. Tedenac, Growth by OMVPE and X-ray analysis of ZnTe and ZnTe/ZnSe epilayers on III–V substrates 166 (1996) 590
Tomich, D.H., see Li 164 (1996) 180
Tomokage, H., see Kanda, T. 166 (1996) 663
Tong, W., B.K. Wagner, T.K. Tran, W. Ogle, W. Park and C.J. Summers, Kinetics of chemical beam epitaxy for high quality ZnS film growth 164 (1996) 202
Torrent-Burgués, J., see Gómez-Morales, J. 166 (1996) 1020
Torrent-Burgués, J., see Gómez-Morales, J. 169 (1996) 331
Tóth, A.L., see Pfeifer, J. 169 (1996) 727
Tran, C.A., see Arès, R. 170 (1997) 574
Tran, C.A., see Watkins, S.P. 170 (1997) 788
Tran, T.K., see Tong 164 (1996) 202
Treichler, R., see Veuhoff 164 (1996) 402
Triboulet, R., see Lyubomirsky 161 (1996) 90
Triboulet, R., see Martel 161 (1996) 250
Triboulet, R., see Zerrai 161 (1996) 264
Triboulet, R., see Rzepka 161 (1996) 286
Triboulet, R., see Tromson-Carli, A. 170 (1997) 549
Tributsch, H., see Thomas, B. 170 (1997) 808
Trigubó, A.B., see Pérez, L.V. 167 (1996) 87
Trindade, T., see O'Brien, P. 170 (1997) 23
Trivedi, S., see Zhou, H. 167 (1996) 534
Tromson-Carli, A., A. Zozime, J. Ertel, M. Seibt, R. Druilhe, C. Grattepain and R. Triboulet, Influence of a ZnMnTe nucleation layer on the structural quality of (111) ZnTe grown by MOVPE on (100) GaAs 170 (1997) 549
Tsai, C.T., see Chou, W.C. 169 (1996) 747
Tsai, J.-H., see Liu, W.-C. 170 (1997) 438
Tsai, T.-L., S.A. Markgraf and R. Dieckmann, Floating-zone growth and characterization of Fe_2SiO_4 single crystals 169 (1996) 759
Tsai, T.-L., S.A. Markgraf, M. Higuchi and R. Dieckmann, Growth of $(Fe_xMg_{1-x})_2SiO_4$ single crystals by the double pass floating zone method 169 (1996) 764
Tsirkov, G.A., see Volkov 163 (1996) 377
Tsuboi, N., see Fukuda 161 (1996) 45
Tsui, R., see Shiralagi 164 (1996) 334
Tsui, R., K. Shiralagi and J. Shen, Growth of resonant interband tunneling diodes using trimethylamine alane 164 (1996) 491
Tsuji, M., K. Makita, T. Takeuchi and K. Taguchi, Selective growth of InAlAs by low pressure metalorganic vapor phase epitaxy 162 (1996) 25
Tsuji, M., K. Makita, T. Takeuchi and K. Taguchi, Large bandgap energy control of InAlAs/InGaAs multiple quantum wells selectively grown by low-pressure MOVPE 170 (1997) 669
Tsujimoto, M., see Nitanai, Y. 168 (1996) 280
Tsukada, T., see Miyazaki 162 (1996) 83
Tsutsui, K., Y. Hotta and K. Sato, Melt crystallization of behenic acid in microspheres dispersed in polymer 163 (1996) 440
Tsutsumi, S., see Ito 163 (1996) 311
Tsvetkov, D., see Dmitriev, V. 166 (1996) 601
Tu, C.W., H.K. Dong and N.Y. Li, Growth, etching, doping and effects of Ar^+ laser irradiation in chemical beam epitaxy of GaAs with novel precursors 163 (1996) 187
Tu, C.W., see Yan 164 (1996) 77
Tu, C.W., see Li 164 (1996) 112
Tu, C.W., see Wong 164 (1996) 159
Tu, C.W., see Li 164 (1996) 180
Tu, C.W., see Bi 164 (1996) 256
Tu, C.W., see Yan 164 (1996) 276
Tu, C.W., see Bi 165 (1996) 210
Tümmler, J., see Behet, M. 167 (1996) 415
Tümmler, J., J. Woitok, J. Hermans, J. Geurts, P. Schneider, D. Moulin, M. Behet and K. Heime, Growth and characterization of Sb-based heterostructures grown by LP-MOVPE 170 (1997) 772
Tunik, L., L. Addadi, N. Garti and H. Füredi-Milhofer, Morphological and phase changes in calcium oxalate crystals grown in the presence of sodium diisooctyl sulfosuccinate 167 (1996) 748
Tuomi, T., see Tuominen 165 (1996) 233
Tuomi, T., see Koljonen, T. 169 (1996) 417
Tuomi, T., see Hjelt, K. 170 (1997) 794
Tuominen, M., E. Prieur, R. Yakimova, R.C. Glass, T. Tuomi and E. Janzén, Defect analysis in Lely-grown 6H SiC 165 (1996) 233
Türck, V., see Kappelt, M. 170 (1997) 590
Tyagel'sky, P.V., see Stankus, S.V. 167 (1996) 165
Tyurikov, V., see Isaenko, L. 166 (1996) 502

Uchida, H., see Miyazaki 162 (1996) 83
Uchida, T., see Noguchi, S. 168 (1996) 270

Uchiki, H., see Fukuda 161 (1996) 45
Uda, S., J. Kon, K. Shimamura and T. Fukuda, Analysis of Ge distribution in $Si_{1-x}Ge_x$ single crystal fibers by the micro-pulling down method 167 (1996) 64
Udaka, T., see Yase, K. 166 (1996) 946
Udono, H., A. Motogaito, M. Kimura, A. Tanaka and T. Sukegawa, Suppression of twins in GaAs layers grown on a GaP(111)B substrate by liquid phase epitaxy 169 (1996) 181
Udono, H., see Kimura, M. 169 (1996) 697
Uecker, R., see Nitsch 165 (1996) 163
Uekusa, S.-i., see Mizuno, Y. 170 (1997) 61
Ueng, H.Y., see Hwang 161 (1996) 73
Ueno, K., see Matsubara, I. 167 (1996) 570
Uesugi, K., see Yao 163 (1996) 78
Uesugi, K., see Suemune, I. 170 (1997) 480
Ulbert, Zs., see Farkas, B. 166 (1996) 1064
Ulrich, J., see Momonaga, M. 166 (1996) 1053
Ulrich, J., see Poschmann, M. 167 (1996) 248
Umekawa, M., see Akane, T. 167 (1996) 32
Umeno, M., see Soga 163 (1996) 165
Umeno, M., see Shimura, T. 166 (1996) 786
Umeno, M., see Soga, T. 170 (1997) 447
Umetsu, K., see Fukuda 161 (1996) 45
Underwood, R.D., see Kapolnek, D. 170 (1997) 340
Ungerechts, S., see Lakner, H. 170 (1997) 732
Uno, T., see Yase, K. 166 (1996) 942
Unoki, H., see Oka, K. 166 (1996) 380
Uomi, K., see Kondow 164 (1996) 175
Urgiles, E., P. Melo and C.C. Coleman, Vapor reaction growth of single crystal GeI_2 165 (1996) 245
Usuki, Y., see Rudolph 161 (1996) 28
Utke, I., W. Frentrup, I. Hähnert, H. Kirmse, O. Müller, M. Schenk and M. Winkler, Non-abruptness of heterointerfaces during LPE growth of (Hg,Cd)Te on (Cd,Zn)Te and Cd(Te,Se) substrates 162 (1996) 126
Uusi-Penttilä, M. and K.A. Berglund, Spectroscopic monitoring of environmentally benign anti-solvent crystallization 166 (1996) 967
Uustare, T., see Aarik, J. 169 (1996) 496
Uwai, K., see Kobayashi, N. 170 (1997) 225

Vaille, M., see Beaumont, B. 170 (1997) 316
Valarelli, J.V., see Giulietti, M. 166 (1996) 1089
Valdna, V., F. Buschmann and E. Mellikov, Conductivity conversion in CdTe layers 161 (1996) 164
Valdna, V., J. Hiie, U. Kallavus, A. Mere and T. Piibe, $ZnSe_{1-x}Te_x$ solid solutions 161 (1996) 177
Van den Bogaert, N. and F. Dupret, Simulation of back-melting in Czochralski growth 166 (1996) 446
Van den Bogaert, N., see Dornberger, E. 166 (1996) 452
Vanderbauwhede, W., X. Zhang, I. Moerman and P. Demeester, Growth and characterization of InAlGaAs(P)/InGaAs(P) MQW structures 170 (1997) 738
Van der Berg, A.C.J.F., see van Enckevort, W.J.P. 166 (1996) 156
Van der Drift, E., see Werner 164 (1996) 223
Van der Eerden, J.P., see Huitema, E. 166 (1996) 141
Vanderschueren, A., see Stassen, S. 166 (1996) 281
Van der Stricht, W., I. Moerman, P. Demeester, J.A. Crawley and E.J. Thrush, Study of GaN and InGaN films grown by metalorganic chemical vapour deposition 170 (1997) 344
Van der Tol, J.J.G.M., see Vreeburg 164 (1996) 442
Vandewalle, N., see Cloots, R. 166 (1996) 816
Vandewalle, N., M. Ausloos and R. Cloots, Fractal grain boundaries in growth competition 169 (1996) 79
Van Enckevort, W.J.P., A.C.J.F. van der Berg, K.B.G. Kreuwel, A.J. Derksen and M.S. Couto, Impurity blocking of growth steps: experiments and theory 166 (1996) 156
Van Enckevort, W.J.P., see Schermer, J.J. 166 (1996) 622
Van Gelder, R.N.M.R., K.J. Roberts, J. Chambers and T. Instone, Nucleation of single and mixed straight chain surfactants from dilute aqueous solutions 166 (1996) 189
Van Hove, J.M., G. Carpenter, E. Nelson, A. Wowchak and P.P. Chow, III–N light emitting diodes fabricated using RF nitrogen gas source MBE 164 (1996) 154
Van Leeuwen, M.L.J., O.S.L. Bruinsma and G.M. van Rosmalen, Three-zone approach for precipitation of barium sulphate 166 (1996) 1004
Van Rooy, M., see Werner 164 (1996) 223
Van Rosmalen, G.M., see Domingo, C. 166 (1996) 989
Van Rosmalen, G.M., see van Leeuwen, M.L.J. 166 (1996) 1004
Van Rosmalen, G.M., see Ó Meadhra, R. 166 (1996) 1046
Van Rosmalen, G.M., see Kramer, H.J.M. 166 (1996) 1084
Van Scyoc, J.M., R.B. James, T.E. Schlesinger, T.S. Gilbert and M. Schieber, Characterization of silver impurities in mercuric iodide and their relationship to γ-ray-detector performance 166 (1996) 384
Van Tendeloo, G., see Volkov 163 (1996) 377
Vargaftik, M.N., see Volkov 163 (1996) 377
Vasylechko, L., see Frukacz, Z. 169 (1996) 98
Veciana, J., see Figueras, A. 166 (1996) 798
Veesler, S., S. Lafont, S. Marcq, J.P. Astier and R. Boistelle, Prenucleation, crystal growth and polymorphism of some proteins 168 (1996) 124
Veesler, S., see Seyssiecq, I. 169 (1996) 124
Vekilov, P.G., see Rosenberger, F. 168 (1996) 1
Velling, P., see Lindner, A. 170 (1997) 287
Ven Graitis, A.J., see Fratello, V.J. 166 (1996) 878
Venkatasubramanian, R., T. Colpitts, E. Watko, M. Lamvik and N. El-Masry, MOCVD of Bi_2Te_3, Sb_2Te_3 and their superlattice structures for thin-film thermoelectric applications 170 (1997) 817
Vennin, C., see Lefaucheux 165 (1996) 90

Verbeeck, R.M.H., see De Maeyer, E.A.P. 169 (1996) 539
Verbeek, B.H., see Vreeburg 164 (1996) 442
Verschuren, C.A., M.R. Leys, Y.S. Oei, C.G.M. Vreeburg, H. Vonk, R.T.H. Rongen and J.H. Wolter, Surface morphology of InP/InGaAs in selective area growth by chemical beam epitaxy 170 (1997) 650
Vesselinov, I., Dendritic growth of lead molybdate in aqueous solutions 167 (1996) 725
Vetkin, A., see Leonyuk, L. 167 (1996) 102
Veuhoff, E., H. Baumeister, R. Treichler, M. Popp and H. Heinecke, Zn doping of InP/GaInAsP device structures in metalorganic molecular beam epitaxy using diethylzinc 164 (1996) 402
Veuhoff, E., see Keidler, M. 170 (1997) 161
Vicente, P., see Booker, G.R. 170 (1997) 777
Vidal, A., see Figueiredo, J.M.A. 166 (1996) 222
Vidal, O., Y. Bernard, M.C. Robert and F. Lefaucheux, Time evolution of refractive index of gelled and gel-free supersaturated lysozyme solutions 168 (1996) 40
Vidal, O., see Bonneté, F. 168 (1996) 185
Vieira, Jr., N.D., see Baldochi, S.L. 166 (1996) 375
Vieira, Jr., N.D., see Ranieri, I.M. 166 (1996) 423
Vieira, M.M.F., see Baldochi, S.L. 166 (1996) 375
Vilela, M.F., N. Medelci, A. Bensaoula, A. Freundlich and P. Renaud, First epitaxial InP tunnel junctions grown by chemical beam epitaxy 164 (1996) 465
Vincenzoni, R., see Rigo 164 (1996) 327
Viraphong, O., see Oçafrain, A. 166 (1996) 414
Vitagliano, L., see Sica, F. 168 (1996) 192
Vizman, D., see Nicoara, I. 169 (1996) 102
Vizman, D., I. Nicoara and D. Nicoara, On the factors affecting the isotherm shape during Bridgman growth of semi-transparent crystals 169 (1996) 161
Voigt, A., B. Steiner, W. Dorsch, J. Krinke, M. Albrecht, H.P. Strunk and G. Wagner, Solution growth of silicon on multicrystalline Si substrate: growth velocity, defect structure and electrical activity 166 (1996) 694
Volkmann, N., see Thygesen, J. 168 (1996) 308
Volkov, V.V., G. Van Tendeloo, G.A. Tsirkov, N.V. Cherkashina, M.N. Vargaftik, I.I. Moiseev, V.M. Novotortsev, A.V. Kvit and A.L. Chuvilin, Long- and short-distance ordering of the metal cores of giant Pd clusters 163 (1996) 377
Volkozub, A.V., see Chowdhury, A.J.S. 166 (1996) 863
Volkozub, A.V., see Chowdhury, A.J.S. 169 (1996) 405
Von Ammon, W., see Dornberger, E. 166 (1996) 452
Von Eichel-Streiber, C., M. Behet, M. Heuken and K. Heime, Doping of InAs, GaSb and InPSb by low pressure MOVPE 170 (1997) 783
Vonk, H., see Rongen 164 (1996) 263
Vonk, H., see Vreeburg 164 (1996) 442
Vonk, H., see Verschuren, C.A. 170 (1997) 650
Vreeburg, C.G.M., Y.S. Oei, B.H. Verbeek, J.J.G.M. van der Tol, R.T.H. Rongen, H. Vonk, M.R. Leys, B.H.P. Dorren and J.H. Wolter, Strained GaInAs/InP MQW layers grown by CBE for optical components 164 (1996) 442
Vreeburg, C.G.M., see Verschuren, C.A. 170 (1997) 650
Vuillard, L., B. Baalbaki, M. Lehmann, S. Nørager, P. Legrand and M. Roth, Protein crystallography with non-detergent sulfobetaines 168 (1996) 150
Vydyanath, H.R., Incorporation of dopants and native defects in bulk $Hg_{1-x}Cd_xTe$ crystals and epitaxial layers 161 (1996) 64
Vysotskaya, V., see Garber, M. 168 (1996) 301

Waag, A., see Lugauer 161 (1996) 86
Waag, A., see Worschech 161 (1996) 134
Waag, A., see Fischer 161 (1996) 214
Wachter, M. and H. Heinecke, Beam geometrical effects on planar selective area epitaxy of InP/GaInAs heterostructures 164 (1996) 302
Wada, K., see Kohda, H. 167 (1996) 557
Wado, H., K. Ohtani and M. Ishida, Epitaxial growth of SiGe on Al_2O_3 using Si_2H_6 gas and Ge solid source molecular beam epitaxy 169 (1996) 457
Wagner, B.K., see Tong 164 (1996) 202
Wagner, G., see Voigt, A. 166 (1996) 694
Wagner, G., see Kirpal, G. 170 (1997) 167
Wahl, U., see Restle 161 (1996) 168
Wahl, U., see Jahn 161 (1996) 172
Wajid, A., C. Gogol, C. Hurd, M. Hetzel, A. Spina, R. Lum, M. McDonald and R.J. Capik, A high-speed high-sensitivity acoustic cell for in-line continuous monitoring of MOCVD precursor gases 170 (1997) 237
Walker, J.S., see Khine 165 (1996) 372
Walker, P.J., see Booker, G.R. 170 (1997) 777
Walsh, D., see Ye, X. 169 (1996) 704
Walsh, J.R., see O'Brien, P. 167 (1996) 133
Walsh, J.R., see O'Brien, P. 170 (1997) 23
Walsöe de Reca, N.E., see Pérez, L.V. 167 (1996) 87
Walther, M., see Shiralagi 164 (1996) 334
Wan, P., see Lei, X.-Y. 166 (1996) 909
Wan, P., see Lei, X.-Y. 169 (1996) 570
Wang, B., see Chen, S. 170 (1997) 433
Wang, C., see Davis 164 (1996) 132
Wang, C.A., see Krueger, C.W. 169 (1996) 51
Wang, C.A., see Salim, S. 169 (1996) 443
Wang, C.A., S. Salim, K.F. Jensen and A.C. Jones, Characteristics of GaSb growth using various gallium and antimony precursors 170 (1997) 55
Wang, C.A., Organometallic vapor phase epitaxial growth of AlSb-based alloys 170 (1997) 725
Wang, C.H., see Sze, P.W. 169 (1996) 27
Wang, D., see Li 164 (1996) 235

Wang, F., see Becht, M. 170 (1997) 799
Wang, G., H.G. Gallagher, T.P.J. Han and B. Henderson, The growth and optical assessment of Cr^{3+}-doped $RX(BO_3)_4$ crystals with R = Y, Gd; X = Al, Sc 163 (1996) 272
Wang, H., see Zeng, J.M. 169 (1996) 474
Wang, J., see Lu, L. 169 (1996) 637
Wang, J., see Lu, L. 169 (1996) 643
Wang, J.Y., see Liu, W.J. 169 (1996) 534
Wang, K.L., see Li 164 (1996) 235
Wang, M., see Ando, Y. 166 (1996) 888
Wang, M., see Zeng, J.M. 169 (1996) 474
Wang, N.F., see Sze, P.W. 169 (1996) 27
Wang, Q., see Carlsson, N. 170 (1997) 127
Wang, Shanli, see Yang 165 (1996) 70
Wang, T.G., see Shen 165 (1996) 438
Wang, W.S., see Aggarwal, M.D. 166 (1996) 542
Wang, X., see Chen 164 (1996) 454
Wang, X., see Lu, X. 169 (1996) 665
Wang, X.L., X.M. Yang, H.W. Weber, R. Abraham, K. Lebbou, M.Th. Cohen-Adad, E. Halwax and P. Wiede, Growth and characterization of $(Tl,Pb)(Sr,Ba)_2Ca_2Cu_3O_y$ single crystals 167 (1996) 93
Wang, Y., C. Huang, L. Chen and Z. Fang, Crystal growth of Cr^{3+}:$LiCaAlF_6$ by Bridgman technique 167 (1996) 176
Wang, Y., see Chen, N. 167 (1996) 766
Wang, Y., see Zhang, K. 169 (1996) 73
Wang, Y., see Lu, L. 169 (1996) 637
Wang, Y., see Lu, L. 169 (1996) 643
Wang, Y.H., see Sze, P.W. 169 (1996) 27
Wang, Z., see Zeng, J.M. 169 (1996) 474
Wang, Z., see Lu, L. 169 (1996) 637
Wang, Z., see Lu, L. 169 (1996) 643
Wang, Z.G., see Hu 163 (1996) 266
Wang Siqing, Lu Haibo, Ma Fukang and Mu Yufeng, Heterogeneous nucleation of diamond under high static pressure and high temperature 162 (1996) 69
Wang Wenzhong, see Xie Yi 167 (1996) 656
Wang Xiaoliang, Sun Dianzhao, Kong Meiying, Hou Xun and Zeng Yiping, GSMBE growth and PL investigation of lattice-matched InGaAs/InP quantum wells 164 (1996) 281
Wanklyn, B.M.R., see Chowdhury, A.J.S. 166 (1996) 863
Wanklyn, B.M.R., see Chowdhury, A.J.S. 169 (1996) 405
Wassermeier, M., see Behrend, J. 167 (1996) 440
Watahiki, S., see Kondow 164 (1996) 175
Watanabe, K., M. Momose, K. Hara, H. Munekata and H. Kukimoto, Selective area chemical beam epitaxy of GaAs using Ga_2O_3 as a mask layer 169 (1996) 223
Watanabe, K., Growth of minute barium ferrite single crystals from a Na_2O–B_2O_3 flux system 169 (1996) 509
Watanabe, T., see Takebe 162 (1996) 31
Watanabe, T., see Morita, S. 166 (1996) 370
Watkins, S.P., see Arès, R. 170 (1997) 574
Watkins, S.P., R. Arès, G. Soerensen, W. Zhong, C.A. Tran, J.E. Bryce and C.R. Bolognesi, Atomic force microscopy study of morphology and dislocation structure of InAs and GaSb grown on highly mismatched substrates 170 (1997) 788
Watko, E., see Venkatasubramanian, R. 170 (1997) 817
Watring, D.A. and S.L. Lehoczky, Magneto-hydrodynamic damping of convection during vertical Bridgman–Stockbarger growth of HgCdTe 167 (1996) 478
Watson, I.M., see O'Brien, P. 167 (1996) 133
Watters, V.J., see Scriven, G.J. 170 (1997) 813
Watts, B.E., see di Cristoforo, A. 167 (1996) 644
Weber, H.W., see Wang, X.L. 167 (1996) 93
Weber, J., see Wiedemann, P. 170 (1997) 117
Weckwerth, M.V., see Hung, C.Y. 169 (1996) 201
Wei, J.Q., see Liu, W.J. 169 (1996) 534
Wei, Q.-H., see Lei, X.-Y. 166 (1996) 909
Weigel, E. and G. Müller-Vogt, Comparison of Bridgman and THM method regarding the effect of In doping and distribution of Zn in CdTe 161 (1996) 40
Weiler, M.H., see Mitra, P. 170 (1997) 542
Weinert, B., see Müller, M. 166 (1996) 636
Weinstein, S., see Thygesen, J. 168 (1996) 308
Weise, S., E. Nowak, A. Lenz, B. Schumann and V. Krämer, Investigations of the system $LiInSe_2$–$CuInSe_2$ 166 (1996) 718
Weiss, E., E. Benory, E. Kedar, Y. Juravel and A. Frenkel, Is $Hg_{1-x}Cd_xTe$ grown epitaxially by the travelling heater method? Does it matter? 166 (1996) 745
Wen, J.G., see Becht, M. 170 (1997) 799
Wen, Weijia and Kunquan Lu, A simple and low cost method for fabricating single crystal microspheres 165 (1996) 191
Werner, H., see Behres, A. 170 (1997) 655
Werner, J., G. Behr, W. Bieger and G. Krabbes, Chemical transport of restricted solid solutions of In_2O_3 and SnO_2: experiments and thermodynamic process analysis 165 (1996) 258
Werner, K., A. Storm, S. Butzke, J.W. Maes, M. van Rooy, P. Alkemade, E. Algra, M. Somers, B. de Lange, E. van der Drift, T. Zijlstra and S. Radelaar, Gas source MBE growth of Si/SiGe device materials 164 (1996) 223
Werner, P., see Spika, Z. 170 (1997) 257
Werner, P., see Heinrichsdorff, F. 170 (1997) 568
Westerholt, K., see Brinkmann 163 (1996) 369
Westwater, S.P., see Joyce 164 (1996) 371
Westwater, S.P. and T.J. Bullough, The microstructure and thermal stability of CBE grown heavily carbon doped GaAs 170 (1997) 752
Wetter, N.U., see Ranieri, I.M. 166 (1996) 423

Wetzel, G., see Rossberg, A. 166 (1996) 354
Wexler, R.M., see Ingle, N.K. 167 (1996) 543
Weyburne, D.W. and B.S. Ahern, Design and operating considerations for a water-cooled close-spaced reactant injector in a production scale MOCVD reactor 170 (1997) 77
Weyers, M., see Bergunde, T. 170 (1997) 66
Weyers, M., see Kurpas, P. 170 (1997) 203
Weyers, M., see Knauer, A. 170 (1997) 281
Weyers, M., see Kurpas, P. 170 (1997) 442
Whitaker, T.J., T. Martin, A.D. Johnson, A.J. Pidduck and J.P. Newly, Atomic force microscopy studies of substrate cleaning using tris(dimethylamino)arsenic and tris(dimethylamino)antimony and investigations of surface decomposition mechanisms 164 (1996) 125
Whitaker, T.J., T. Martin and R.W. Freer, Increasing the range of growth temperatures available for GaAs selective area growth using triisopropylgallium and arsine 164 (1996) 296
Wickenden, A.E., W.B. Alexander, D.D. Koleske and J.A. Freitas Jr., The influence of strain and mosaic structure on electrical and optical properties of GaN films on sapphire substrates 170 (1997) 367
Wickenden, D., see Huang, Z.C. 170 (1997) 362
Wiede, P., see Wang, X.L. 167 (1996) 93
Wiedemann, P., G. Laube, J. Weber and E. Lach, MOVPE growth of ternary and quaternary tensile strained MQW structures for polarization insensitive devices 170 (1997) 117
Wiencek, J.M., see Schall 165 (1996) 293
Wiencek, J.M., see Schall 165 (1996) 299
Wienecke, M., J. Bollmann, J. Röhrich, K. Maass, B. Reinhold, D. Forkel-Wirth and The ISOLDE Collaboration, Transmutation doping of wide-bandgap II–VI compounds 161 (1996) 82
Wienecke, M., see Hermann 161 (1996) 181
Wiersch, A., see Lindner, A. 170 (1997) 287
Wilkinson, C.I., see Chen, Y.H. 170 (1997) 394
Williams, J.O., see Gnoth, D.N. 170 (1997) 198
Williams, J.O., see Fan, G.H. 170 (1997) 485
Williams, J.O., see Poole, I.B. 170 (1997) 528
Wilson, G.A., see Morris Hotsenpiller, P.A. 166 (1996) 779
Wilson, I.A., see Stura, E.A. 168 (1996) 260
Wilson, W.W., see Ansari, R.R. 168 (1996) 216
Winkler, M., see Utke 162 (1996) 126
Winterfeld, J., see Geiger, M. 169 (1996) 625
Witz, J., see Ng, J.D. 168 (1996) 50
Woermann, D., see Mayer, K. 169 (1996) 317
Woitok, J., see Behet, M. 167 (1996) 415
Woitok, J., see Lakner, H. 170 (1997) 732
Woitok, J., see Tümmler, J. 170 (1997) 772
Wolf, Th., Crystal growth mechanisms and growth anisotropy of $YBa_2Cu_3O_x$ crystals 166 (1996) 810
Wolff, A., see Kim, M. 167 (1996) 508
Wolffer, N., see Martel 161 (1996) 250
Wolffer, N., see Zerrai 161 (1996) 264
Wollweber, J., D. Schulz and W. Schröder, Si_xGe_{1-x} single crystals grown by the RF-heated float zone technique 163 (1996) 243
Wolter, J.H., see Rongen 164 (1996) 263
Wolter, J.H., see Vreeburg 164 (1996) 442
Wolter, J.H., see Verschuren, C.A. 170 (1997) 650
Wondre, F.R., see Chowdhury, A.J.S. 169 (1996) 405
Wong, M.S., see Pan 165 (1996) 273
Wong, W.S., see Li 164 (1996) 112
Wong, W.S., N.Y. Li, H.K. Dong, F. Deng, S.S. Lau, C.W. Tu, J. Hays, S. Bidnyk and J.J. Song, Growth of GaN by gas-source molecular beam epitaxy by ammonia and by plasma generated nitrogen radicals 164 (1996) 159
Wong, W.S., see Li 164 (1996) 180
Wood, A.K., J. Thompson, N. Carr, A.J. Moseley, P.A. Bromley, M.Q. Kearley, R.W. Martin and R.J. Nicholas, Influence of substrate dopant type on the optical properties of GaInAs/InP multiquantum well structures grown by low pressure MOVPE 170 (1997) 132
Woodhead, J., see Hirotani, M. 170 (1997) 390
Woodhead, J., see Chen, Y.H. 170 (1997) 394
Woodhead, J., see Sale, T.E. 170 (1997) 399
Woos, B.W., see De Yoreo, J.J. 166 (1996) 291
Worschech, L., see Lugauer 161 (1996) 86
Worschech, L., W. Ossau, F. Fischer, A. Waag and G. Landwehr, Cadmium vacancy related defects in MBE grown CdTe 161 (1996) 134
Worschech, L., see Fischer 161 (1996) 214
Worster, M.G., see Anderson 163 (1996) 329
Wowchak, A., see Van Hove 164 (1996) 154
Wright, A.C., see Gnoth, D.N. 170 (1997) 198
Wright, A.C., see Fan, G.H. 170 (1997) 485
Wright, A.C., see Poole, I.B. 170 (1997) 528
Wu, F., see Li 163 (1996) 339
Wu, H. and Z. Li, Electrical and structural characterisation of carbon-doped GaAs grown by MOVPE using carbon tetrabromide 167 (1996) 429
Wu, K. and C. Chen, Theoretical studies for novel non-linear optical crystals 166 (1996) 533
Wu, M.K., see Rao 162 (1996) 48
Wu, X.-B., X. Geng and Z.-Y. Guo, Fundamental study of crystal/melt interface shape change in Czochralski crystal growth 169 (1996) 786
Wu Dexang, see He Youping 169 (1996) 196
Wyns, L., see Lisgarten 163 (1996) 474

Xia, C.-T., E.-W. Shi, W.-Z. Zhong and J.-K. Guo, Hydrothermal synthesis of $BaTiO_3$ nano/microcrystals 166 (1996) 961
Xiang, Q., see Li 164 (1996) 235
Xiang, X.B., see Li 162 (1996) 43
Xiao, B. and S.J. Gamblin, The effects of cryoprotectant on crystal stability 168 (1996) 244

Xiao, Q., S. Kuppurao, A. Yeckel and J.J. Derby, On the effects of ampoule tilting during vertical Bridgman growth: three-dimensional computations via a massively parallel, finite element method 167 (1996) 292
Xie, J.C., see Han, J.H. 169 (1996) 129
Xie, L., see Zhang, Y. 169 (1996) 722
Xie, M.H., see Joyce 164 (1996) 214
Xie, M.H., see Fernández 164 (1996) 241
Xie, Song, see Meng 163 (1996) 232
Xie Yi, Wang Wenzhong, Qian Yitai, Yang Li and Chen Zhiwen, Deposition and microstructural characterization of NiO thin films by a spray pyrolysis method 167 (1996) 656
Xiong, S.B., see Guo 165 (1996) 187
Xiong, S.B., see Guo, X.L. 167 (1996) 378
Xiong, Xin, see Yang 165 (1996) 70
Xu, D., see Yuan, D.R. 166 (1996) 545
Xu, J., see Lu, L. 169 (1996) 643
Xu, J.-j., Global interfacial instabilities and selection of dendrite growth 166 (1996) 201
Xu, Lixing, see Yang 165 (1996) 70
Xu, N., see Lei, X.-Y. 169 (1996) 570
Xu, W., see Ma, D. 169 (1996) 170
Xu, Y., see Li 162 (1996) 43

Yablonskii, G.P., see Gurskii, A.L. 170 (1997) 533
Yabuuchi, Y., see Otsuka, N. 170 (1997) 626
Yagi, K., see Minoda 163 (1996) 48
Yaguchi, H., S. Miyoshi, G. Biwa, M. Kibune, K. Onabe, Y. Shiraki and R. Ito, Photoluminescence excitation spectroscopy of $GaP_{1-x}N_x$ alloys: conduction-band-edge formation by nitrogen incorporation 170 (1997) 353
Yaguchi, H., see Pan, W. 170 (1997) 585
Yakimova, R., see Tuominen 165 (1996) 233
Yakovlev, N.L., see Harada 163 (1996) 31
Yakovlev, V.P., see Mawst, L.J. 170 (1997) 383
Yamada, T., see Kinoshita 165 (1996) 75
Yamada, T., see Schäfer, N. 166 (1996) 675
Yamada, Y., M. Nakamura, C. Krauns, M. Tagami, Y. Shiohara and S. Tanaka, Top-seeded solution growth of $YBa_2Cu_3O_{6+d}$ superconductive crystals 166 (1996) 804
Yamada, Y., see Kitamura, T. 166 (1996) 854
Yamada, Y., see Nakamura, M. 166 (1996) 859
Yamada, Y., Y. Niiori, Y. Yoshida, I. Hirabayashi and S. Tanaka, Low temperature growth of $YBa_2Cu_3O_{6+\delta}$ single crystalline films from fluoride/oxide solvents 167 (1996) 566
Yamada, Y., see Kina, H. 169 (1996) 33
Yamaguchi, A., see Hashimoto, S. 169 (1996) 376
Yamaguchi, H., see Oka, K. 166 (1996) 380
Yamaguchi, M., see Kudo, K. 170 (1997) 634
Yamaguchi, T., see Ohkubo, M. 170 (1997) 177
Yamamoto, K., H. Asahi, T. Hayashi, K. Asami and S. Gonda, Metalorganic molecular beam epitaxy growth and etching of GaSb on flat and high-index surfaces uusing trisdimethylaminoantimony 164 (1996) 117
Yamamoto, M., see Tanaka, S. 168 (1996) 44
Yamamoto, S., see Rudolph 161 (1996) 28
Yamamoto, T., see Takebe 162 (1996) 31
Yamasaki, N., see Yanagisawa 163 (1996) 285
Yamashita, M., see Suda, Y. 169 (1996) 672
Yamashita, S., see Rudolph 161 (1996) 28
Yamauchi, A., see Fujii, K. 170 (1997) 679
Yamaura, S., see Ando 164 (1996) 1
Yan, C.H., A.Y. Lew, E.T. Yu and C.W. Tu, P_2-induced P/As exchange on GaAs during gas-source molecular beam epitaxy growth interruptions 164 (1996) 77
Yan, C.H. and C.W. Tu, Synthesis of highly strained $In_yGa_{1-y}P/In_xGa_{1-x}As/In_yGa_{1-y}P$ quantum well structures with strain compensation 164 (1996) 276
Yan, S., see Zhang, W. 169 (1996) 598
Yan, Z., M. Koike and H. Takei, Preparation of spinel $ZnGa_2O_4$ films on MgO substrates by the solvent evaporation epitaxy method 165 (1996) 183
Yanagida, H., see Hayakawa, Y. 169 (1996) 613
Yanagisawa, K., Q. Feng, K. Ioku and N. Yamasaki, Hydrothermal single crystal growth of calcite in ammonium acetate solution 163 (1996) 285
Yanashima, K., see Toda, A. 170 (1997) 461
Yang, G., J.S. Abell, P. Shang, I.P. Jones and C.E. Gough, Growth and microstructure in $Bi_2Sr_2CaCu_2O_y$ single crystals 166 (1996) 820
Yang, H., see Lu, L. 169 (1996) 643
Yang, X.M., see Wang, X.L. 167 (1996) 93
Yang, Yi, see Yang 165 (1996) 70
Yang, Yukan, Wenming Li, Lei Lu, Yi Yang, Lixing Xu, Xin Xiong, Shanli Wang and Helan Huang, Hot wall epitaxy grown n-PtTe(100)/p-Si(100) heterojunction 165 (1996) 70
Yang Li, see Xie Yi 167 (1996) 656
Yankov, R., see Hermann 161 (1996) 181
Yan Mingshan, see He Youping 169 (1996) 196
Yao, T., K. Uesugi, T. Komura and M. Yoshimura, Atomistic study on solid phase epitaxy processes on Si(100) surfaces by the scanning tunneling microscope 163 (1996) 78
Yao, X., M. Egami, Y. Namikawa, T. Mizukoshi, Y. Shiohara and S. Tanaka, Improved growth of large YBCO single crystals 165 (1996) 198
Yaroslavsky, Y., see Burtman, V. 166 (1996) 832
Yase, K., Y. Yoshida, T. Uno and N. Okui, Direct analysis of an organic molecular beam by quadrupole mass spectrometry 166 (1996) 942
Yase, K. and T. Udaka, Two-dimensional crystallization of ferritin molecules at the air–water interface 166 (1996) 946
Yasuda, K., H. Hatano, T. Ferid, M. Minamide, T. Maejima and K. Kawamoto, Growth

characteristics of (100)HgCdTe layers in low-temperature MOVPE with ditertiarybutyltelluride 166 (1996) 612
Yasuda, Y., see Zaima 163 (1996) 105
Yasuoka, N., see Higuchi, Y. 168 (1996) 99
Yates, H.M., W.R. Flavell, M.E. Pemble, N.P. Johnson, S.G. Romanov and C.M. Sotomayor-Torres, Novel quantum confined structures via atmospheric pressure MOCVD growth in asbestos and opals 170 (1997) 611
Yazawa, M., see Hiruma 163 (1996) 226
Yazawa, Y., see Kondow 164 (1996) 175
Ye, X., B. Tabarrok and D. Walsh, The influence of thermosolutal convection on CdTe growth by the traveling heater method 169 (1996) 704
Ye, Z.-G. and H. Schmid, Growth from high temperature solution and characterization of $Pb(Fe_{2/3}W_{1/3})O_3$ single crystals 167 (1996) 628
Yeckel, A., see Xiao, Q. 167 (1996) 292
Yeh, Jih-Hsien, see Lee 163 (1996) 343
Yi, K.-W., see Kakimoto 163 (1996) 238
Yi, K.-W., K. Kakimoto, M. Eguchi and H. Noguchi, Oxygen transport mechanism in Si melt during single crystal growth in the Czochralski system 165 (1996) 358
Yi, W.S., see Choe, K.S. 169 (1996) 227
Yoda, S., see Kinoshita, K. 166 (1996) 266
Yohda, M., see Fukami, T.A. 168 (1996) 297
Yokota, Y., see Nugraha 165 (1996) 402
Yom, S.S., see Kim, E.K. 170 (1997) 803
Yonath, A., see Thygesen, J. 168 (1996) 308
Yoneda, Y., K. Sakaue and H. Terauchi, Growth and phase transition of $[(C_{60})_5(Cu)_5]_{52}$ multilayer film 165 (1996) 50
Yonenaga, I., K. Sumino, E. Niwa and K. Masumoto, Characterization of native dislocations in chalcopyrite $AgGaS_2$ by X-ray topography 167 (1996) 616
Yoon, D.Y., see Hwang 162 (1996) 55
Yoon, Jong-Kyu, see Chung 163 (1996) 249
Yoon, K.H., see Song, M.H. 167 (1996) 157
Yoshida, H., see Kamata, A. 170 (1997) 518
Yoshida, M., see Fukami, T.A. 168 (1996) 297
Yoshida, S., see Okumura 164 (1996) 92
Yoshida, S., see Okumura 164 (1996) 149
Yoshida, S. and M. Sasaki, In situ selective area growth of GaAs, AlAs, and AlGaAs using MOMBE 164 (1996) 291
Yoshida, Y., see Yase, K. 166 (1996) 942
Yoshida, Y., see Yamada, Y. 167 (1996) 566
Yoshikawa, A., see Hashimoto, T. 169 (1996) 185
Yoshimoto, N., K. Hashimoto and M. Yoshizawa, In situ observation of crystal growth of β-(BEDT-TTF)$_2$I$_3$ by electrochemical oxidation method 167 (1996) 574
Yoshimura, M., see Yao 163 (1996) 78
Yoshizawa, M., see Yoshimoto, N. 167 (1996) 574
You, Z.P., see Li 162 (1996) 43
Yu, E.T., see Yan 164 (1996) 77
Yu, S.-c., see Lee, C.-h. 167 (1996) 473
Yu, T., see Guo 165 (1996) 187
Yu, X., Y. Sun, H. Jiang and S. Zhang, Growth kinetics of the metastable tetragonal phase of potassium dideuterium phosphate (DKDP) crystals 166 (1996) 195
Yuan, D.R., N. Zhang, X.T. Tao, D. Xu, M.G. Liu, W.B. Hou, Y.H. Bing and M.H. Jiang, Growth of a new highly efficient organic nonlinear optical crystal: 3-methoxy-4-hydroxy-benzaldehyde (MHBA) 166 (1996) 545
Yuan, T., see Mukherjee, D.K. 169 (1996) 136
Yuan, W., see Scholz, U. 169 (1996) 575
Yuan, W.-L., see Liu, W.K. 167 (1996) 111
Yumoto, K.-I., see Suzuki, T. 166 (1996) 872
Yushkin, N.P., Natural polymer crystals of hydrocarbons as models of prebiological organisms 167 (1996) 237
Yu Xianchun, see He Youping 169 (1996) 193

Zacher, U., see Tanneberger, U. 166 (1996) 1074
Zagari, A., see Sica, F. 168 (1996) 192
Zahanagiu, F., see Isopescu, R. 167 (1996) 260
Zahn, D.R.T., see Prösch, G. 170 (1997) 537
Zahn, D.R.T., see Schneider, A. 170 (1997) 767
Zaima, S. and Y. Yasuda, Studies on the suppression of Ge segregation during Si overgrowth on Ge(n ML)/Si(100) substrates by gas-source MBE 163 (1996) 105
Zaitseva, N.P., see Smolsky, I.L. 166 (1996) 228
Zaitseva, N.P., see De Yoreo, J.J. 166 (1996) 291
Zaitseva, N.P., see Smolski, I. 169 (1996) 741
Zakharuk, Z.I., see Nikonyuk 161 (1996) 186
Zangwill, A., Some causes and a consequence of epitaxial roughening 163 (1996) 8
Zanotti, L., see Zeng, L. 166 (1996) 528
Zanotti, L., see Carrà, S. 166 (1996) 641
Zanotti Fregonara, C., see Mazzer, M. 170 (1997) 553
Zappettini, A., see Fornari, R. 166 (1996) 572
Zawadzki, P., see Thompson, A.G. 170 (1997) 92
Zaytzev-Bashan, A., see Thygesen, J. 168 (1996) 308
Zebib, A., see Zhou, H. 167 (1996) 534
Zec, S., see Lazić 165 (1996) 124
Zee, R.H., see Liu 163 (1996) 259
Zeindl, H.P., see Kim, M. 167 (1996) 508
Zelmon, D.E., see Singh 163 (1996) 398
Zemke, D., see Amon, J. 166 (1996) 646
Zeng, H.C., see Lim, L.C. 167 (1996) 686
Zeng, J.M., H. Wang, S.X. Shang, Z. Wang and M. Wang, Preparation and characterization of epitaxial MgO thin film by atmospheric-pressure metalorganic chemical vapor deposition 169 (1996) 474
Zeng, L., M. Zha, M. Ardoino, P. Franzosi, L. Zanotti, G. Zuccalli and C. Paorici, Solution

crystal growth of urea and derivatives for nonlinear optical applications 166 (1996) 528
Zeng, W., see Hu 163 (1996) 266
Zeng, W., see Liu, W.J. 169 (1996) 534
Zeng Jinbo, see He Youping 169 (1996) 196
Zeng Yiping, see Wang Xiaoliang 164 (1996) 281
Zerrai, A., see Martel 161 (1996) 250
Zerrai, A., G. Marrakchi, G. Bremond, J.Y. Moisan, G. Martel, M. Gauneau, B. Lambert, P. Gravey, N. Wolffer, A. Aoudia, Y. Marfaing, R. Triboulet, J.M. Koebel, M. Hadj-Ali and P. Siffert, Relationship between deep levels in vanadium-doped CdTe and photorefractive effect 161 (1996) 264
Zettler, J.-T., see Steimetz, E. 170 (1997) 208
Zezell, D.M., see Ranieri, I.M. 166 (1996) 423
Zha, M., see Zeng, L. 166 (1996) 528
Zhang, D.H., see Li 165 (1996) 15
Zhang, H., see Zou, Y.F. 166 (1996) 476
Zhang, H., V. Prasad and D.F. Bliss, Modeling of high pressure, liquid-encapsulated Czochralski growth of InP crystals 169 (1996) 250
Zhang, J., A.K. Lees, A.G. Taylor, D. Raisbeck, N. Shukla, J.M. Fernández, B.A. Joyce and M.E. Pemble, In-situ monitoring of Si and SiGe growth on Si(001) surfaces during gas-source molecular beam epitaxy using reflectance anisotropy 164 (1996) 40
Zhang, J., see Naji 164 (1996) 58
Zhang, J., see Joyce 164 (1996) 214
Zhang, J., see Fernández 164 (1996) 241
Zhang, K., R. Mogilevsky, D.G. Hinks, J. Mitchell, A.J. Schultz, Y. Wang and V. Dravid, Crystal growth of $(La,Sr)_2CuO_4$ by float zone melting 169 (1996) 73
Zhang, N., see Yuan, D.R. 166 (1996) 545
Zhang, S., J. Cui and Y. Aoyagi, Growth control of GaAs using short-pulse supersonic beam epitaxy 164 (1996) 28
Zhang, S., see Yu, X. 166 (1996) 195
Zhang, S.B. and A. Zunger, Predicted structures and stabilities of the surface A grooves and double bilayer height steps on the GaAs(001)-2 × 4 surface 163 (1996) 113
Zhang, W., S. Yan and Z. Ji, Effective segregation coefficient and steady state segregation coefficient of germanium in Czochralski silicon 169 (1996) 598
Zhang, X., see Lu, X. 169 (1996) 665
Zhang, X., I. Moerman, C. Sys, P. Demeester, J.A. Crawley and E.J. Thrush, Highly uniform AlGaAs/GaAs and InGaAs(P)/InP structures grown in a multiwafer vertical rotating susceptor MOVPE reactor 170 (1997) 83
Zhang, X., see Vanderbauwhede, W. 170 (1997) 738
Zhang, X.G., see Bao, K.X. 170 (1997) 497
Zhang, X.M., see Fernández 164 (1996) 241
Zhang, Y., see Chen, K.-T. 166 (1996) 731
Zhang, Y., S. Pan, Z. Shao and D. Kong, Properties of MNBA-Et (4′-nitrobenzylidene, 3-ethylcarbonylamino, 4-methoxyaniline) melt 167 (1996) 373
Zhang, Y., L. Xie, Z. Zhou, J. Sun and S.-T. Lee, Characteristics of diamond crystals deposited on quartz substrates by chemical vapor deposition 169 (1996) 722
Zhao, G., see Bao, K.X. 170 (1997) 497
Zhao, Q.L., see Hu 163 (1996) 266
Zhao, T.-r., M. Hasegawa and H. Takei, Crystal growth and characterization of cuprous ferrite ($CuFeO_2$) 166 (1996) 408
Zhao, Yaqin, see Huang 165 (1996) 413
Zhao Qingran, see He Youping 169 (1996) 193
Zheltonosova, J., see Garber, M. 168 (1996) 301
Zheng, Y., A. Koëbel, J.F. Pétroff, J.C. Boulliard, B. Capelle and M. Eddrief, GaSe/Si(111) heteroepitaxy: the early stages of growth 162 (1996) 135
Zhi, D., see Liu, J. 170 (1997) 357
Zhong, W. and D. Tang, Growth units and morphology of lithium triborate (LBO) crystals 166 (1996) 91
Zhong, W., see Watkins, S.P. 170 (1997) 788
Zhong, W.-Z., see Xia, C.-T. 166 (1996) 961
Zhou, B. and G.J. Russell, Growth mechanisms of $YBa_2Cu_3O_{7-\delta}$ single crystals grown by the flux method using alumina crucibles 165 (1996) 42
Zhou, C.-H., see Lei, X.-Y. 166 (1996) 909
Zhou, C.-H., see Lei, X.-Y. 169 (1996) 570
Zhou, H., A. Zebib, S. Trivedi and W.M.B. Duval, Physical vapor transport of zinc-telluride by dissociative sublimation 167 (1996) 534
Zhou, L.F., see Cui, F.Z. 169 (1996) 557
Zhou, M., R. Breton, A. Azzi and S.-X. Lin, Rapid purification of the over-expressed membrane 3β-hydroxysteroid dehydrogenase in the presence of detergents 168 (1996) 142
Zhou, Y.-C., see Pan, J.-S. 168 (1996) 227
Zhou, Z., see Zhang, Y. 169 (1996) 722
Zhu, D.-W., A. Azzi, P. Rehse and S.-X. Lin, The crystallogenesis of a human estradiol dehydrogenase–substrate complex 168 (1996) 275
Zhu, H., see Lu, X. 169 (1996) 665
Zhu, J.Q., see Li 163 (1996) 348
Zhu, J.Q., see Li, B. 169 (1996) 480
Zhu, S.N., see Guo 165 (1996) 187
Zhu, S.N., see Guo, X.L. 167 (1996) 378
Zhu, Y.Y., see Guo, X.L. 167 (1996) 378
Zijlstra, T., see Werner 164 (1996) 223
Zimmermann, G., A. Ougazzaden, A. Gloukhian, E.V.K. Rao, D. Delprat, A. Ramdane and A. Mircea, Selective area MOVPE

growth of InP, InGaAs and InGaAsP using TBAs and TBP at different growth conditions 170 (1997) 645
Zimprich, C., see Spika, Z. 170 (1997) 257
Žižić, B., see Čabrić, B. 169 (1996) 199
Zlatkowski, M., see Pines, V. 167 (1996) 383
Zlatkowski, M., see Pines, V. 167 (1996) 777
Zlatkowski, M., see Pines, V. 169 (1996) 798
Zorn, M., see Knorr, K. 170 (1997) 230
Zou, Y.F., H. Zhang and V. Prasad, Dynamics of melt–crystal interface and coupled convection–stress predictions for Czochralski crystal growth processes 166 (1996) 476
Zozime, A., see Tromson-Carli, A. 170 (1997) 549
Zubrilov, A., see Dmitriev, V. 166 (1996) 601
Zuccalli, G., see Zeng, L. 166 (1996) 528
Zukoski, C.F., see Rosenbaum, D.F. 169 (1996) 752
Zunger, A., see Zhang 163 (1996) 113
Zverkov, S.A., see Balbashov, A.M. 167 (1996) 365
Zwanger, M.S., F. Banhart and A. Seeger, Formation and delay of spherical concentric-shell carbon clusters 163 (1996) 445
Zyss, J., see Gauvin, S. 166 (1996) 507

ELSEVIER

Journal of Crystal Growth 170 (1997) 896–909

JOURNAL OF CRYSTAL GROWTH

Subject index to volumes 161–170

Aluminum
– antimonide **164** (1996) 491
– arsenide **164** (1996) 291, 454
– gallium arsenide **163** (1996) 343
– nitride **163** (1996) 93, 232; **164** (1996) 132, 143, 159
– phosphide antimonide **162** (1996) 121
Apparatus
– for agglomeration
– – of gibbsite **169** (1996) 124
– for beryllium growth
– – by mirror furnace **169** (1996) 578
– for bulk organic film **165** (1996) 273
– for chemical beam epitaxy
– – of multiwafers **170** (1997) 16
– – of III–V compounds **164** (1996) 1
– for containerless crystal growth
– – of proteins **168** (1996) 204
– for fast growth of ice **163** (1996) 420
– for growth and crystallographic monitoring by fiber optics
– – of proteins **168** (1996) 216
– for growth kinetics probing
– – by real time phase shift interferometry **167** (1996) 387
– for high T_c crystals **163** (1996) 369
– for highly reactive intermetalics
– – of uranium nickel oxide **167** (1996) 621
– for indium gallium arsenide growth
– – by double crucible **169** (1996) 217
– for large single crystals of bone and tooth mineral **163** (1996) 311
– for laser assisted chemical beam epitaxy
– – of gallium arsenide **164** (1996) 71
– for laser Doppler velocimetry **165** (1996) 429
– for macromolecular crystallography
– – by synchrotron radiation **168** (1996) 245
– for melt growth
– – by Bridgman–Stockbarger method
– – – of gallium arsenide **166** (1996) 566
– – by Czochralski method
– – – of gallium antimonide **165** (1996) 159
– – by fractional suspension **167** (1996) 248
– for microsphere growth
– – of potassium niobate **165** (1996) 191
– for organic crystalline thin films **166** (1996) 507
– for production scale metalorganic chemical vapor deposition reactor **170** (1997) 77
– for protein crystallization
– – by step gradient diffusion **162** (1996) 167
– for pure crystals
– – of potassium magnesium ferrite **169** (1996) 89
– for surface tension determination **165** (1996) 413
– for thin film growth
– – by molecular beam epitaxy, electron beam assisted
– – – of gallium arsenide **164** (1996) 92
– – by rotating susceptor **170** (1997) 83
– for vapor growth
– – of ice **169** (1996) 795
– for miscellaneous purposes
– – fibre growth of uranium under ultrahigh vacuum **166** (1996) 394
– – in situ X-ray and microscopic observation **166** (1996) 872
– – quadrupole analysis of organic molecular beams **166** (1996) 942
– – ultrasoft X-ray absorption **166** (1996) 67
– – viscosity of molten potassium niobate **165** (1996) 81

Barium
– sulphide **163** (1996) 318
Beryllium **169** (1996) 575, 578

Cadmium **167** (1996) 208
– manganese telluride **161** (1996) 282
– selenide **161** (1996) 277
– sulphide **161** (1996) 159, 277; **166** (1996) 731; **167** (1996) 133
– sulphide selenide **161** (1996) 277
– telluride **161** (1996) 1, 12, 16, 28, 34, 73, 82, 86, 94, 104, 119, 128, 134, 144, 148, 159, 164, 168, 172, 186, 195, 214, 219, 223, 239, 259, 286; **165** (1996) 227; **166** (1996) 245
– telluride selenide **161** (1996) 104; **166** (1996) 256
– zinc telluride **161** (1996) 20, 40, 104, 153, 250, 286
Calcium
– fluoride **163** (1996) 31; **166** (1996) 61
Cellular growth
– of binary alloys **167** (1996) 265
– of gamma-aminobutyric acid **166** (1996) 104
– of nematic isotropic interface **166** (1996) 222

Characterization
– by atomic force microscopy
– – of III–V compounds **170** (1997) 357, 566, 788
– by deep level transient spectroscopy
– – of II–VI compounds **170** (1997) 537
– by Michelson interferometry
– – of canavalin **166** (1996) 913
– by photoluminescence
– – of III–V compounds **170** (1997) 372
– by Raman scattering
– – of II–VI compounds **170** (1997) 767
– by thermally stimulated currents
– – of III–V compounds **170** (1997) 362
– by X-ray diffraction
– – of organic crystals **167** (1996) 729
– by X-ray diffusion
– – of III–V compounds **170** (1997) 47, 357
Cobalt **166** (1996) 792
Computer simulation
– of composition **162** (1996) 113
– of convection **162** (1996) 95; **165** (1996) 308; **167** (1996) 45
– of conversion phenomenon **169** (1996) 697
– of crystallization of finite polymer chains **165** (1996) 284
– of electron distribution **161** (1996) 172
– of epitaxial growth **169** (1996) 61
– of flow patterns **165** (1996) 447
– of front growth morphology **163** (1996) 149
– of heat convection **166** (1996) 463
– of heat flow **169** (1996) 269
– of heat transfer in metalorganic chemical vapor deposition **170** (1997) 66
– of impurity blocking **166** (1996) 156
– of industrial crystallizer **166** (1996) 1084
– of melt crystal interface **166** (1996) 476
– of melt flow **165** (1996) 362
– of moving boundaries **169** (1996) 161
– of protein crystal growth **168** (1996) 93, 130; **169** (1996) 361
– of resistivity distribution **161** (1996) 271
– of segregation **163** (1996) 461
– of solid distribution **165** (1996) 308, 463
– of solid melt interface **165** (1996) 147
– of solute segregation **167** (1996) 320
– of stress field **169** (1996) 102
– of supercooling of melts **166** (1996) 578
– of surface relaxation on morphology **166** (1996) 84
– of surface roughening **166** (1996) 17
– of temperature distribution **163** (1996) 238
– of ternary compounds distribution **167** (1996) 74
– of thermal capillary problem **166** (1996) 458
– of thermal stress in oxides **162** (1996) 83
– of transient behavior of horizontal metalorganic vapor phase epitaxy **170** (1997) 72
– of transient thermal dynamics **166** (1996) 452
– of underpotential deposition **167** (1996) 253
– of YBCO **169** (1996) 79
Constitutional supercooling
– of binary alloys **167** (1996) 265
– of cadmium telluride **161** (1996) 16
– of lithium lead phosphate **166** (1996) 361
– of proteins **168** (1996) 244
Constitutional supersaturation
– of vapor growth **162** (1996) 173
Convection **162** (1996) 95, 182; **163** (1996) 420; **165** (1996) 323, 351, 362, 447, 463; **166** (1996) 124, 136, 239, 261, 266, 303, 700, 825; **167** (1996) 45, 74, 190, 320, 333, 516, 686; **168** (1996) 1; **169** (1996) 110, 147, 582, 773
Copper
– indium selenide **166** (1996) 708
– II oxalate **163** (1996) 474
Crystal growth, special
– of nanostructures **169** (1996) 13
Crystalline form, special
– nanostructure **170** (1997) 476
– quantum dots **170** (1997) 568, 700

Defects
– in aluminum **166** (1996) 146
– in cadmium telluride **161** (1996) 73, 82, 119, 128, 134, 144
– in lithium niobate **166** (1996) 151
– in mercury cadmium telluride **161** (1996) 139
– in potassium dihydrogen phosphate of hair-like inclusion **166** (1996) 228
– in zinc selenide **161** (1996) 45, 119
– in zinc telluride **161** (1996) 82, 119
– theory of formation **166** (1996) 141
Dendritic growth
– of ammonium bromide **166** (1996) 251
– of binary alloys **167** (1996) 265
– of cupric chloride **167** (1996) 716
– of ferroelectric potassium niobate **162** (1996) 161
– of germanium iodide **165** (1996) 245
– of lead molybdate **167** (1996) 725
– of xenon **166** (1996) 207, 212
– theory
– – of density change upon solidification **169** (1996) 798
– – of global interfacial instability **166** (1996) 201
– – of three-dimensional model **166** (1996) 339
Device characterization
– caustic cell **170** (1997) 237
– diodes **161** (1996) 64, 90, 264; **164** (1996) 334, 465, 491; **166** (1996) 601, 745; **170** (1997) 503
– electroluminescent **167** (1996) 157; **169** (1996) 33
– electron field emission **170** (1997) 340
– electronic devices **169** (1996) 201, 227, 637, 649
– electronic materials **161** (1996) 90, 119, 139, 148, 164, 168, 181, 190, 239, 259, 264, 271, 277, 282; **163** (1996) 212; **164** (1996) 285, 383, 415, 485; **166** (1996) 245, 325, 329, 572, 745; **167** (1996) 107, 406, 429, 616; **170** (1997) 92, 103, 173, 287, 725, 803
– heterojunction **161** (1996) 64, 168; **162** (1996) 25, 31; **164** (1996) 389; **165** (1996) 61, 70; **166** (1996) 309, 334; **169** (1996) 201, 227, 629; **170** (1997) 30, 177, 263, 329, 377, 383,408, 413, 424, 442, 574, 595, 725, 732
– induced conductivity **169** (1996) 124
– infrared detectors **166** (1996) 745

– lasers **163** (1996) 272, 398; **164** (1996) 308, 434, 485; **167** (1996) 176, 180; **169** (1996) 293, 643; **170** (1997) 11, 109, 161, 281, 377, 383, 394, 399, 404, 408, 418, 456, 585, 621, 639, 705, 715, 719, 725
– light emitting diodes **164** (1996) 154
– optical crystals **166** (1996) 291
– optoelectronic materials **164** (1996) 396
– piezoelectric **166** (1996) 347
– piezoelectric bulk acoustic wave **163** (1996) 388
– quantum wells or dots **162** (1996) 25; **164** (1996) 241, 263, 276, 281, 434, 442, 485, 491; **165** (1996) 210; **167** (1996) 502; **169** (1996) 424, 629; **170** (1997) 30, 117, 122, 127, 132, 281, 349, 377, 383, 390, 399, 408, 456, 595, 611, 621, 626, 634, 639, 669, 695, 732, 738, 748
– quantum wires **164** (1996) 356; **170** (1997) 585, 590, 595, 605
– radiation sensors **166** (1996) 256, 384
– resistivity by noncontact method **161** (1996) 271
– scintillators **166** (1996) 419
– solar cells **161** (1996) 159; **170** (1997) 447
– transistors **164** (1996) 223, 362, 389, 454, 460, 476; **169** (1996) 435, 637; **170** (1997) 428, 433, 451, 456
– wave guides **164** (1996) 449; **166** (1996) 489
Diamond **162** (1996) 55, 69, 73; **164** (1996) 208; **165** (1996) 387; **166** (1996) 675; **169** (1996) 722
Diffusional control **169** (1996) 380
– of cadmium telluride **161** (1996) 28
– of cadmium zinc telluride in mercury cadmium telluride **162** (1996) 126
– of cation incorporation **163** (1996) 60
– of cluster growth **168** (1996) 44
– of composition **165** (1996) 129, 137
– of faceting **169** (1996) 607
– of lithium nitrate in zinc selenide **170** (1997) 503
– of mercury in cadmium telluride **161** (1996) 223
– of native point defects **161** (1996) 229
– of oxygen in silicon **166** (1996) 183
– of phosphorus in cadmium telluride **161** (1996) 148
– of protein crystal growth **168** (1996) 93, 175; **169** (1996) 361
– of solidification **162** (1996) 182
– of solute redistribution **169** (1996) 170
– of zinc **164** (1996) 402
Diodes, see Device characterization
Dissolution
– of calcium carbonate **165** (1996) 268
– of gamma-aminobutyric acid **166** (1996) 104
– of nitrogen in gallium **166** (1996) 583
– of organic solvents **165** (1996) 273
– of rare earth ortho-ferrites **166** (1996) 109
Doping
– in gallium arsenide **170** (1997) 270, 292, 297, 372, 752
– in indium phosphide **170** (1997) 685
– in zinc selenide **170** (1997) 472, 491, 533
– of antimony
– – in silicon **169** (1996) 665
– of chlorine
– – in cadmium telluride **161** (1996) 134, 164
– – in zinc selenide telluride **161** (1996) 177
– of copper
– – in zinc selenide telluride **161** (1996) 177
– of gallium
– – in cadmium manganese telluride **161** (1996) 282
– of germanium
– – in silicon **169** (1996) 598
– of halogens
– – in cadmium telluride **161** (1996) 214
– of indium
– – in cadmium telluride **161** (1996) 219
– of lithium
– – in cadmium telluride **161** (1996) 168
– of nitrogen
– – in cadmium telluride by plasma activation **161** (1996) 86
– – in zinc selenide **169** (1996) 243
– of palladium
– – in zinc telluride **161** (1996) 181
– of silver
– – in YBCO **169** (1996) 463
– of tellurium
– – in gallium antimonide **169** (1996) 450
– of III–V compounds
– – by carbon **164** (1996) 362, 371, 377, 383, 389, 425
– – by sulphur **164** (1996) 415
– of titanium
– – in cadmium telluride **161** (1996) 271
– of transition metals
– – in II–VI compounds **161** (1996) 239
– of vanadium
– – in cadmium telluride **161** (1996) 259, 264, 271, 286
– – in cadmium zinc telluride **161** (1996) 250, 264, 286
– of ytterbium
– – in cadmium telluride **161** (1996) 186
– of zinc
– – in copper germanate **169** (1996) 469

Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Etching
– chemical **164** (1996) 97; **165** (1996) 156, 387; **166** (1996) 319, 641, 883; **167** (1996) 508, 586, 766; **169** (1996) 51, 409; **170** (1997) 616, 674
– hydrogen **167** (1996) 391
– photolithographic **167** (1996) 508
– reactive ion **164** (1996) 308
– thermal **161** (1996) 164; **166** (1996) 167
Eutectic growth
– of sodium nitrate, 18% barium nitrate **165** (1996) 438
– of tin selenide **166** (1996) 398
– of urea–p. chloronitrobenzene **169** (1996) 563

Fullerene **163** (1996) 445

Gallium
– aluminum arsenide **162** (1996) 31, 43; **164** (1996) 1, 22, 28, 291, 371, 485; **167** (1996) 421, 452; **170** (1997) 88
– aluminum nitride **164** (1996) 154

– aluminum phosphide **164** (1996) 248
– antimonide **164** (1996) 117, 491; **165** (1996) 8, 15, 156, 159; **166** (1996) 651; **167** (1996) 415; **170** (1997) 1, 55
– arsenide **162** (1996) 31; **163** (1996) 54, 60, 149, 171, 180, 187, 195, 203, 212, 226; **164** (1996) 1, 51, 58, 66, 71, 77, 88, 112, 125, 185, 271, 291, 296, 356, 371, 383, 396, 485; **165** (1996) 1, 156, 345, 482; **166** (1996) 72, 217, 239, 309, 636, 641, 646; **167** (1996) 17, 421, 434, 543, 557; **169** (1996) 1, 13; **170** (1997) 83
– arsenide nitride **164** (1996) 175
– arsenide phosphide **164** (1996) 77, 92
– indium arsenide **163** (1996) 149; **164** (1996) 51, 122, 263, 276, 281, 362, 371, 442, 454, 460, 485; **170** (1997) 83, 88
– indium arsenide phosphide **164** (1996) 16, 122, 314, 402, 449
– indium phosphide **163** (1996) 128; **164** (1996) 1, 34, 47, 276, 302, 470; **167** (1996) 8
– nitride **164** (1996) 143, 149, 154, 159, 167, 185; **166** (1996) 597, 601; **167** (1996) 1, 458
– nitride phosphide **164** (1996) 180
– ortho-phosphate **166** (1996) 347
– phosphide **162** (1996) 1; **163** (1996) 165; **164** (1996) 34, 92, 112, 256, 271; **165** (1996) 210; **166** (1996) 309
– phosphide antimonide **162** (1996) 121
– selenide **162** (1996) 135; **163** (1996) 398
Germanium **163** (1996) 48, 105
– iodide **165** (1996) 245
– silicon **165** (1996) 381
Growth theory
– of dissolution rates by reaction fractal dimensions **166** (1996) 1053
– of growth rate by dispersion **166** (1996) 107
– of Hartman–Perdok **166** (1996) 17
– of lamellar eutectics **166** (1996) 29
– of levitated microdroplets **166** (1996) 981
– of polymorphs by ab initio prediction **166** (1996) 900
– of solute distribution **166** (1996) 483
– of suspension mixing **166** (1996) 1064

Heat flow control **165** (1996) 129, 323, 351, 447
– of protein crystallization **168** (1996) 244
– of vapor growth **162** (1996) 173
Heterojunction, see Device characterization
Hydrodynamics, see Convection

Ice **163** (1996) 420, 455
Indium
– aluminum arsenide **162** (1996) 25; **164** (1996) 460; **167** (1996) 468
– aluminum phosphide **164** (1996) 47
– arsenide **163** (1996) 60, 143, 226; **164** (1996) 66, 125, 334, 345; **167** (1996) 440
– arsenide phosphide **162** (1996) 113; **164** (1996) 434
– gallium antimonide **163** (1996) 220
– gallium arsenide **164** (1996) 327, 339, 356, 377, 389, 415, 470, 476; **165** (1996) 215; **166** (1996) 463; **167** (1996) 74, 357, 397, 406, 468
– gallium arsenide phosphide **164** (1996) 321; **166** (1996) 334; **167** (1996) 446, 525
– gallium nitride **170** (1997) 11
– gallium phosphide **165** (1996) 210
– nitride **164** (1996) 143
– phosphide **162** (1996) 1; **164** (1996) 66, 84, 112, 263, 271, 281, 302, 308, 314, 321, 327, 339, 362, 389, 402, 409, 420, 425, 430, 442, 454, 460, 465, 470, 476; **166** (1996) 309, 628, 646; **167** (1996) 468; **170** (1997) 77
Industrial crystallization
– of ammonium chloride **166** (1996) 1099
– of potassium sulphate **166** (1996) 1105
Infrared detectors, see Device characterization

Kinetics
– of aggregation **167** (1996) 738
– of defects **161** (1996) 139
– of diffusion **164** (1996) 302; **170** (1997) 177
– of dissolution **163** (1996) 295, 304; **165** (1996) 268
– of formation **169** (1996) 83
– of growth **161** (1996) 148, 164; **162** (1996) 113, 142, 167; **163** (1996) 54, 60, 143, 149, 232, 295, 304, 318, 411, 420, 445, 461; **164** (1996) 34, 58, 112, 167, 190, 202, 208, 214, 248, 302, 327; **165** (1996) 90, 106, 116, 215, 273, 335, 341; **166** (1996) 91, 104, 112, 117, 124, 129, 136, 156, 162, 179, 195, 271, 303, 347, 469, 578, 763, 810, 893, 904, 946, 976, 1004, 1020, 1040, 1046, 1094, 1099; **167** (1996) 17, 87, 221, 260, 440, 508, 543, 570, 693, 701, 719, 773; **168** (1996) 1, 44, 63, 124, 185, 204, 292; **169** (1996) 79, 279, 309, 347, 393, 429, 491, 496, 548, 570, 587, 607, 629, 697, 773; **170** (1997) 39, 61, 149, 161, 182, 188, 208, 219, 276, 590, 650, 655, 689
– of impurity incorporation **161** (1996) 172; **165** (1996) 215
– of in situ formation of nanostructures **170** (1997) 39
– of interface control **161** (1996) 164; **163** (1996) 86, 149; **164** (1996) 214, 409; **166** (1996) 61, 67, 222, 303, 854; **168** (1996) 1; **169** (1996) 170, 201, 557, 629; **170** (1997) 188, 281, 689
– of melt structure **166** (1996) 578
– of nucleation **162** (1996) 113, 161, 167; **163** (1996) 54, 67, 426, 440; **164** (1996) 167, 190, 248, 302; **166** (1996) 179, 271, 841, 961, 976, 1020, 1046, 1058, 1094, 1099, 1111; **168** (1996) 1, 44, 50, 99, 260; **169** (1996) 181, 331, 413; **170** (1997) 39, 193, 208, 246, 558
– of purification **166** (1996) 998; **169** (1996) 339
– of pyrolysis **162** (1996) 1

Lasers, see Device characterization
Lasers, crystals for
– barium beta-borate **162** (1996) 89
– barium lithium fluoride **166** (1996) 375
– blue emission **170** (1997) 30
– excimer **162** (1996) 79
– garnets **167** (1996) 180
– lithium yttrium fluoride **166** (1996) 423
– nonlinear optics **165** (1996) 273; **166** (1996) 533
– photorefractivity **161** (1996) 250
Lead
– bromide **166** (1996) 266, 364

– telluride **163** (1996) 353; **165** (1996) 70, 402
– tin telluride **162** (1996) 173
– tungstate **165** (1996) 163
Light emitting diodes, see Device characterization
Lysozyme **165** (1996) 293, 299; **166** (1996) 40, 904, 919; **167** (1996) 221, 738; **168** (1996) 1, 28, 40, 93, 112, 181, 292; **169** (1996) 355, 752

Material analysis
– by atomic force microscopy
– – of potassium dihydrogen phosphate **169** (1996) 548
– by optical absorption
– – of lithium niobate **169** (1996) 98
– – of yttrium ortho-aluminate **169** (1996) 98
– by X-ray
– – of silicon germanium **169** (1996) 681
Melt growth technique
– by Bridgman–Stockbarger method **165** (1996) 129
– – of bismuth antimonide **167** (1996) 277
– – of cadmium manganese telluride **161** (1996) 282
– – of cadmium telluride **161** (1996) 28, 104, 144, 186, 219, 259, 264, 271, 286
– – of cadmium telluride selenide **161** (1996) 104
– – of cadmium zinc telluride **161** (1996) 40, 104, 264, 286
– – of calcium fluoride **162** (1996) 79
– – of cobalt triantimonide **166** (1996) 722
– – of copper indium selenide **166** (1996) 708
– – of gallium selenide **163** (1996) 398
– – of germanium **166** (1996) 700
– – of indium gallium antimonide **163** (1996) 220
– – of indium gallium arsenide **167** (1996) 357
– – of lead bromide **166** (1996) 364; **167** (1996) 107
– – of lead telluride **165** (1996) 402
– – of lead–thallium **169** (1996) 147
– – of lithium calcium aluminum fluoride **167** (1996) 176
– – of mercury cadmium telluride **161** (1996) 104; **167** (1996) 87
– – of potassium magnesium fluoride **166** (1996) 419; **169** (1996) 89
– – of rhodium triantimonide **166** (1996) 722
– – of semitransparent fluorides **169** (1996) 161
– – of silicon germanium mixed crystals **165** (1996) 381
– – of silver bromide **167** (1996) 107
– – of sodium nitrate **165** (1996) 195; **169** (1996) 368
– – of tin selenide **166** (1996) 398
– – of 2-dicyanovinylanisole **166** (1996) 542
– – of zinc selenide **161** (1996) 45, 60
– – theory
– – – of ampoule tilting effects **167** (1996) 292
– – – of convention **166** (1996) 436
– – – of *g*-jitter **169** (1996) 582
– – – of gravity perturbation **165** (1996) 471
– – – of solute segregation **167** (1996) 45, 320
– by Czochralski method
– – of barium lithium fluoride **166** (1996) 375
– – of barium meta-borate **166** (1996) 497
– – of bismuth silicon oxide **166** (1996) 325
– – of dysprosium gadolinium gallium garnet **163** (1996) 393
– – of dysprosium gallium aluminum garnet **163** (1996) 393
– – of europium vanadate, lutetium vanadate **167** (1996) 369
– – of gallium antimonide **165** (1996) 159
– – of gallium arsenide **166** (1996) 636, 641; **169** (1996) 1
– – of garnets **166** (1996) 774
– – of germanium **165** (1996) 351
– – of indium phosphide **166** (1996) 303, 572; **169** (1996) 250
– – of iron based compound by cold crucible **166** (1996) 298
– – of iron titanium **166** (1996) 390
– – of lanthanum gallium silicate **163** (1996) 388
– – of lanthanum niobium gallate **169** (1996) 503
– – of lead molybdate **167** (1996) 686
– – of lead tungstate **165** (1996) 163; **169** (1996) 304
– – of liquid crystals **169** (1996) 136
– – of lithium lead phosphate **166** (1996) 361
– – of lithium niobate **163** (1996) 403; **169** (1996) 409
– – of lithium niobate in high magnetic field **166** (1996) 286
– – of neodymium strontium gallate **166** (1996) 825
– – of nickel perovskites **166** (1996) 878
– – of oxides **162** (1996) 83
– – of perovskite rare earth aluminate **166** (1996) 370
– – of praseodymium strontium gallate **166** (1996) 825
– – of rare earth tantalates **166** (1996) 303
– – of rutile in high magnetic field **166** (1996) 286
– – of silicon **163** (1996) 238, 359; **165** (1996) 362, 362, 372; **166** (1996) 183, 469, 663, 669, 680; **167** (1996) 361; **169** (1996) 598
– – of silicon germanium **166** (1996) 657
– – of uranium nickel borate **167** (1996) 621
– – of yttrium lithium fluoride **166** (1996) 423
– – theory
– – – of back melting **166** (1996) 446
– – – of convection **165** (1996) 372
– – – of large scale growth **163** (1996) 249
– – – of melt/crystal interface **169** (1996) 786
– by edge-defined film-fed growth
– – of sapphire **169** (1996) 102
– by eutectic composition
– – of aluminum copper alloy **162** (1996) 107
– by excimer laser melt mixing
– – of silicon germanium **167** (1996) 32
– by floating zone method
– – of aluminum doped rutile **163** (1996) 279
– – of chromium doped magnesium silicate **165** (1996) 250
– – of copper germanate **169** (1996) 469
– – of cuprous ferrite **166** (1996) 408
– – of gallium antimonide **166** (1996) 319
– – of gallium arsenide **166** (1996) 239
– – of iron magnesium sulphate (olivine) **169** (1996) 764
– – of iron sulphate **169** (1996) 759
– – of lanthanum borate **167** (1996) 333
– – of lanthanum calcium manganese oxide **167** (1996) 365
– – of lanthanum strontium cuprate **169** (1996) 73
– – of lanthanum strontium manganese oxide **167** (1996) 365
– – of lithium niobate **166** (1996) 151
– – of molybdenum alloys **163** (1996) 259
– – of silicon **166** (1996) 319; **169** (1996) 269

– – of sodium barium nitrate **165** (1996) 438
– – of sodium nitrate **165** (1996) 447
– – of zirconium borane **165** (1996) 319
– by fluidized bed
– – of epsilon-caprolactam **167** (1996) 248
– – of mercury cadmium telluride **167** (1996) 478
– by gradient solidification method
– – of sapphire **167** (1996) 183, 190
– by high pressure Bridgman
– – of cadmium zinc telluride **161** (1996) 153
– by inverted bell temperature profile
– – of organic crystalline films **166** (1996) 507
– by laser heated pedestal
– – of strontium barium titanate **167** (1996) 660, 670
– by liquid feeding Czochralski method
– – of silicon **166** (1996) 685
– by micro-pulling down method
– – of silicon germanium **166** (1996) 675; **167** (1996) 38, 64
– by self propagating high temperature synthesis
– – of zinc sulphate **165** (1996) 166
– by Stephanov method
– – of tin **166** (1996) 458
– by suspensive crystallization
– – of p-dichlorobenzene **166** (1996) 1040
– by top seeded method
– – of barium titanate **166** (1996) 550
– by traveling heater method
– – of cadmium telluride **161** (1996) 153; **169** (1996) 704
– – of cadmium zinc telluride **161** (1996) 40, 153
– – of mercury cadmium telluride **161** (1996) 229
– – theory of
– – – diffusional dominated process **169** (1996) 380
– – – heat transport **169** (1996) 704
– by uniaxial solidification **165** (1996) 137, 147
– – of binary alloys **167** (1996) 265
– – of bismuth antimonide **167** (1996) 277
– – of 4′-nitrobenzylidene, 3-ethylcarbonylamino, 4-methoxyaniline **167** (1996) 373
– – of lead tin telluride **165** (1996) 75
– – of lithium zinc arsenide **166** (1996) 631
– – of potassium niobate **162** (1996) 161
– – of silver gallium sulphide **167** (1996) 616
– – of sodium magnesium fluoride **166** (1996) 414
– – of sodium nitrate **166** (1996) 483
– – of xenon dendrites **166** (1996) 212
– – theory of convection and radiation heat transfer **165** (1996) 455
– by vertical gradient freeze
– – of cadmium zinc telluride **161** (1996) 20
– – of gallium arsenide **166** (1996) 646
– – of indium phosphide **166** (1996) 646
– by zone melting
– – of indium bismuth **169** (1996) 110
– – of indium gallium arsenide **169** (1996) 217
– – of lanthanum calcium manganese oxide **167** (1996) 365
– – of lanthanum strontium manganese oxide **167** (1996) 365
– – of mercury **169** (1996) 129
– – of silicon germanium **163** (1996) 243
– theory
– – of dynamic contact angle **163** (1996) 329
– – of microsegregation **163** (1996) 461
Mercury
– cadmium telluride **161** (1996) 64, 90, 104, 195, 201, 229, 234; **162** (1996) 126; **163** (1996) 348; **165** (1996) 19, 227; **167** (1996) 87, 493
– iodide **163** (1996) 411; **166** (1996) 354
Microgravity, growth under **165** (1996) 129
– of acidic phospholipase A2 **168** (1996) 227
– of cadmium telluride **166** (1996) 245
– of cadmium telluride selenide **166** (1996) 256
– of copper II oxalate **163** (1996) 474
– of dendritic growth **167** (1996) 777
– of gallium antimonide **166** (1996) 651
– of gallium arsenide **166** (1996) 239
– of germanium **165** (1996) 351
– of indium bismuth **169** (1996) 110
– of indium gallium arsenide **167** (1996) 357
– of iron magnesium sulphate (olivine) **169** (1996) 764
– of lead bromide **166** (1996) 266
– of lead chloride **166** (1996) 266
– of lead tin telluride **165** (1996) 75
– of lysozyme **168** (1996) 40
– of proteins **162** (1996) 167; **165** (1996) 308; **168** (1996) 1, 227, 233
– of silicon **166** (1996) 319
– theory
– – of composition profiles **165** (1996) 471
– – of dynamic contact angle **163** (1996) 329
– – of fluctuation of *g*-jitter **169** (1996) 582
– – of fluid dynamics **165** (1996) 308
– – of mass transfer **165** (1996) 323
Monte Carlo simulation
– of Lennard-Jones potential **166** (1996) 141
– of ordered structure **163** (1996) 122
Morphological stability
– of bismuth titanium oxide **167** (1996) 638
– of calcium oxalate dihydrate **167** (1996) 748
– of calcium oxalate monohydrate **167** (1996) 748
– of copper sulphate pentahydrate **166** (1996) 1089
– of dilute binary alloy **165** (1996) 147
– of electrodeposition of metal and organic polymers **166** (1996) 276
– of fullerene **163** (1996) 445
– of gallium arsenide **167** (1996) 440
– of gallium nitride tips **170** (1997) 335
– of growth interface **167** (1996) 305
– of indium arsenide **167** (1996) 440
– of indium phosphide/indium gallium arsenide **170** (1997) 650
– of lithium triborate **166** (1996) 91
– of mercury cadmium telluride **163** (1996) 348
– of n-methyl urea **167** (1996) 701
– of potassium dihydrogen phosphate **169** (1996) 741

– of protein crystals **168** (1996) 175
– of silicon carbide **167** (1996) 586, 596
– of silicon germanium **167** (1996) 24
– of 6-amino penicilanic acid **166** (1996) 1078

Nickel
– silicate **165** (1996) 57
Nucleation
– of barium sulphide **163** (1996) 318
– of behenic acid **163** (1996) 440
– of binary vapor **169** (1996) 413
– of calcite **163** (1996) 434
– of calcium carbonate **166** (1996) 1015; **169** (1996) 331
– of calcium hydroxy orthophosphate **165** (1996) 98
– of crystalline silicon **165** (1996) 341
– of diamond **162** (1996) 69
– of dislocations **169** (1996) 209
– of drop-like clusters **166** (1996) 909
– of electrodeposits **165** (1996) 421
– of excess vacancies **166** (1996) 146
– of indium arsenide on gallium arsenide **170** (1997) 208
– of indium gallium arsenide **170** (1997) 568
– of inoxide glasses **167** (1996) 756
– of J-aggregates **166** (1996) 930
– of lysozyme **167** (1996) 738; **168** (1996) 40, 150, 185
– of potash alum **166** (1996) 1068
– of potassium dihydrogen phosphate **163** (1996) 426
– of proteins **162** (1996) 167; **168** (1996) 63, 185, 216
– of ribonuclease **167** (1996) 212
– of silicon carbide **167** (1996) 607
– of stacking faults **162** (1996) 178
– of Stranski–Krastanov islands **170** (1997) 39
– of struvite **163** (1996) 434
– theory
– – of cadmium telluride **170** (1997) 193
– – of critical nucleus **163** (1996) 1
Numbers
– fractal dimension **166** (1996) 207
– Grashof **162** (1996) 95; **165** (1996) 129, 351, 463, 471; **166** (1996) 476, 669, 700
– Marangoni **165** (1996) 351;i **167** (1996) 64, 190
– Peclet **165** (1996) 129, 351, 429, 471; **166** (1996) 251; **167** (1996) 777; **170** (1997) 72
– Prandtl **162** (1996) 95; **165** (1996) 351
– Rayleigh **162** (1996) 182; **165** (1996) 129, 351, 429; **167** (1996) 190, 320; **169** (1996) 147
– Reynolds **165** (1996) 463; **166** (1996) 669
– Schmidt **162** (1996) 182; **165** (1996) 471
– Stefan **162** (1996) 182
– Tylor **167** (1996) 45

Optical crystals, see Device characterization
Optoelectronic materials, see Device characterization

Phase diagram
– of alumina yttria **167** (1996) 165
– of aluminum nitride **166** (1996) 583
– of aspergilus niger proteinase A **168** (1996) 118
– of barium beta-borate **162** (1996) 89
– of barium ferrite **169** (1996) 509
– of bismuth oxide–germanium oxide **167** (1996) 171
– of cadmium telluride **161** (1996) 1, 12, 28, 94, 219
– of calcium phosphate **169** (1996) 557
– of copper gallium indium selenide **166** (1996) 712
– of copper indium selenide **166** (1996) 718
– of cytidine deaminase **168** (1996) 155
– of gallium nitride **166** (1996) 583
– of germanium iodide **165** (1996) 245
– of hydroxyapatite **169** (1996) 557
– of indium arsenide **164** (1996) 334
– of indium gallium antimonide **163** (1996) 220
– of indium gallium arsenide **169** (1996) 217
– of indium nitride **166** (1996) 583
– of iron titanate **166** (1996) 390
– of lanthanum strontium gallate **166** (1996) 825
– of lead iron tungstate **167** (1996) 628
– of lead titanate **166** (1996) 380
– of lithium indium selenide **166** (1996) 718
– of lysozyme **165** (1996) 293; **168** (1996) 28, 44
– of proteins **168** (1996) 50, 124; **169** (1996) 355
– of PrYBCO **166** (1996) 804
– of samarium barium cobalt **166** (1996) 859
– of strontium lead gallium hexachromate **165** (1996) 179
– of ternary borates **163** (1996) 272
– of tin selenide **166** (1996) 398
– of urea–p. chloronitrobenzene **169** (1996) 563
– of YBCO **166** (1996) 804
– of zinc selenide **165** (1996) 31
Polymers
– of hydrocarbons **167** (1996) 237
Precursor
– for aluminum gallium indium phosphide **170** (1997) 97
– for aluminum nitride **167** (1996) 1; **170** (1997) 139, 335
– for arsenic **170** (1997) 149
– for cadmium sulphide **167** (1996) 133
– for calcium carbonate **169** (1996) 339
– for calcium hydroxy orthophosphate **165** (1996) 98
– for carbon **170** (1997) 665
– for copper indium selenide **166** (1996) 708
– for doping **164** (1996) 389; **170** (1997) 173
– for fullerene formation **163** (1996) 445
– for gallium aluminum arsenide **163** (1996) 212
– for gallium antimonide **164** (1996) 117; **170** (1997) 55
– for gallium arsenide **163** (1996) 187, 212
– for gallium indium arsenide **170** (1997) 167
– for gallium indium arsenide phosphate **170** (1997) 97, 167
– for gallium indium phosphide **170** (1997) 97
– for gallium nitride **167** (1996) 1; **170** (1997) 139, 325, 335
– for indium nitride **170** (1997) 139
– for indium phosphide **164** (1996) 104, 420; **170** (1997) 97
– for lysozyme crystallization **168** (1996) 28
– for metalorganic chemical vapor deposition **166** (1996) 832
– for nonlinear optical organics **166** (1996) 507
– for phosphides **169** (1996) 625

– for phosphor **170** (1997) 149
– for rutile **166** (1996) 763
– for zinc manganese sulphide selenide **170** (1997) 30
Proteins **168** (1996) 1, 28, 44, 63, 93, 99, 130, 138, 142, 170, 175, 181, 185, 192, 198, 204, 216, 227, 233, 244, 248, 253, 260, 270, 275, 284, 288, 297, 301, 308; **169** (1996) 355
Purification of materials
– of cadmium **161** (1996) 94; **167** (1996) 208
– of cadmium telluride **161** (1996) 94
– of copper **166** (1996) 708
– of isomers **166** (1996) 976
– of lead iodide **166** (1996) 384
– of lysozyme **168** (1996) 1
– of macromolecules **168** (1996) 74
– of mercury iodide **166** (1996) 384
– of organic solution **166** (1996) 1035
– of proteins **166** (1996) 40; **168** (1996) 50, 142, 253, 260, 280, 292
– of tellurium **161** (1996) 94

Quantum dots, see Device characterization
Quantum wells, see Device characterization
Quantum wires, see Device characterization
Quartz **162** (1996) 142

Silicon **163** (1996) 39, 48, 78, 105, 238, 359; **164** (1996) 40, 214, 223, 235, 241; **165** (1996) 37, 61, 172, 341, 362, 362, 372; **166** (1996) 183, 314, 319, 469, 617, 663, 669, 680, 685, 727; **167** (1996) 361, 516; **169** (1996) 61, 598, 665, 672
– carbide **164** (1996) 132; **165** (1996) 233; **166** (1996) 607; **167** (1996) 586, 596, 607; **169** (1996) 485, 491
– dioxide **166** (1996) 727, 786
– germanium **163** (1996) 243; **164** (1996) 40, 214, 223, 241; **165** (1996) 61; **166** (1996) 657, 675, 727; **167** (1996) 24, 32, 38, 64, 495, 508
Solar cells, see Device characterization
Solid growth technique
– by annealing
– – of mercury cadmium telluride **167** (1996) 87
– by hydrolysis
– – of carbonated apatite **169** (1996) 539
– by ion irradiation
– – of silicon **163** (1996) 78
– by polymorphic transformation
– – of L-glutamic acid **166** (1996) 129
– by recrystallization
– – of aluminum **166** (1996) 146
– – of amorphous silicon **165** (1996) 341
– – of BSCCO **166** (1996) 863
– – of cadmium telluride **161** (1996) 164
– – of carbonated apatite **169** (1996) 539
Solution growth technique
– by antisolvent crystallization
– – of lysine monohydrochloride **166** (1996) 967
– by aqueous solution
– – of amorphous iron sulphide **167** (1996) 719
– – of barium sulphate **166** (1996) 1004
– – of calcium carbonate **166** (1996) 1015, 1020
– – of chlorobenzoic **166** (1996) 976
– – of ferritin molecules **166** (1996) 946
– – of lead molybdate **167** (1996) 725
– – of pentaerythritol **166** (1996) 1046
– – of potassium chromate **166** (1996) 156
– – of potassium dideuterium phosphate **166** (1996) 195
– – of potassium dihydrogen phosphate **166** (1996) 228, 291
– – of sodium laurate **166** (1996) 189
– – of sodium myristate **166** (1996) 189
– – of strontium sulphate **166** (1996) 998
– – of tetracosane **166** (1996) 1094
– by bacterial membranes
– – of struvite **163** (1996) 434
– by batch method
– – of proteinase A **168** (1996) 118
– – of proteins **168** (1996) 170, 192, 204
– by centrifugal techniques
– – of gallium arsenide **166** (1996) 234
– – of germanium **166** (1996) 234
– – of silicon germanium **166** (1996) 234
– by colloidal chemistry
– – of lead sulphide **166** (1996) 769
– by electrochemical deposition
– – of copper indium diselenide **169** (1996) 287
– by electrocrystallization
– – of zinc oxide **166** (1996) 1116
– by electrodeposition
– – of copper **165** (1996) 421
– – of iron **165** (1996) 421
– – of nickel **165** (1996) 421
– – of zinc **165** (1996) 421
– by flux method
– – of barium beta-borate **162** (1996) 89
– – of barium borate **165** (1996) 408; **169** (1996) 734
– – of barium ferrite **169** (1996) 509
– – of beta-potassium gadolinium tungstate **169** (1996) 600
– – of BSCCO **166** (1996) 820; **169** (1996) 405
– – of cadmium telluride **161** (1996) 164
– – of cesium titryl arsenate **166** (1996) 537
– – of chromium borides **166** (1996) 429
– – of cobalt substituted M-hexaferrite **166** (1996) 402
– – of gadolinium aluminum borate **163** (1996) 272
– – of gadolinium scandium borate **163** (1996) 272
– – of gel acupuncture **169** (1996) 361
– – of HTSC **167** (1996) 102
– – of lead iron tungstate **167** (1996) 628
– – of lithium triborate **163** (1996) 266
– – of lysozyme **165** (1996) 299
– – of potassium magnesium niobate arsenate **169** (1996) 604
– – of potassium titanyl phosphate **167** (1996) 681; **169** (1996) 534
– – of potassium zinc niobate arsenate **169** (1996) 604
– – of rubidium titryl arsenate **166** (1996) 537
– – of strontium lead gallium hexachromate **165** (1996) 179
– – of tin substituted M-hexaferrite **166** (1996) 402
– – of ytterbium aluminum borate **163** (1996) 272

– – of ytterbium scandium borate **163** (1996) 272
– – of YBCO **162** (1996) 48; **166** (1996) 810
– – theory of growth mechanism **165** (1996) 42
– by gel acupuncture method
– – of proteins **168** (1996) 93, 185, 260
– by gel method
– – of ammonium bromide **166** (1996) 251
– – of barium titanate **166** (1996) 550
– – of 4-dimethylaminobenzaldehyde-4-nitrophenylhydrazone **165** (1996) 273
– – of lead hydrogen phosphate **169** (1996) 317
– – of silica **166** (1996) 996
– – of 2-amino-5-nitropyridium dihydrogen phosphate **165** (1996) 90
– by hanging drop vapor diffusion
– – of chaperonin-60 **168** (1996) 297
– – of ribonuclease U2 **168** (1996) 270
– – of Thermus thermophilus **168** (1996) 301
– by high pressure nitrogen
– – of gallium nitride **166** (1996) 583
– – theory of solute diffusivity **166** (1996) 261
– by high temperature alkaline solution
– – of hydroxyapatite **165** (1996) 124
– – theory of nucleation **165** (1996) 116
– by Holden technique
– – of potassium dihydrate **169** (1996) 196
– by hydrothermal growth
– – of barium titanate **166** (1996) 961
– – of beta-quartz **162** (1996) 142
– – of calcite **163** (1996) 285
– – of gallium ortho-phosphate **166** (1996) 347
– – of hydroxyapatite **163** (1996) 311
– – of lithium triborate **169** (1996) 519, 527
– by low temperature method
– – of ammonium dihydrogen phosphate **169** (1996) 325
– – of behenic acid **163** (1996) 440
– – of cadmium zinc manganese telluride **169** (1996) 747
– – of calcium sulphate hemihydrate **169** (1996) 118
– – of E-2-butenedeioce acid **166** (1996) 179
– – of ferritin **168** (1996) 138
– – of fluorapatite **165** (1996) 116
– – of 4-dimethylaminobenzaldehyde-4-nitrophenylhydrazone **165** (1996) 273
– – of hexahydrate nickel sulphate **169** (1996) 193
– – of hexamethylbenzene **169** (1996) 325
– – of hydroxyapatite **165** (1996) 106
– – of lansine complex **166** (1996) 925
– – of macromolecules **168** (1996) 34
– – of meta-chloronitrobenzene **166** (1996) 971
– – of monomethyl urea **166** (1996) 528
– – of n-methyl urea **167** (1996) 693, 701, 709
– – of palladium clusters **163** (1996) 377
– – of potassium hydrogen tartrate **166** (1996) 172
– – of proteins **166** (1996) 40
– – of ribonuclease A **167** (1996) 212
– – of RNA polymerase **167** (1996) 734
– – of silicon **163** (1996) 470
– – of 3-methoxy-4-hydroxy-benzaldehyde **166** (1996) 545
– – of thyroxyaptite **167** (1996) 773
– – of urea **166** (1996) 528
– – of zinc oxide **167** (1996) 649
– – theory of step bouncing **169** (1996) 773
– by microwave activation
– – of calcium carbonate **169** (1996) 339
– by mixing
– – of oxazolin compounds **166** (1996) 1027
– by rapid expansion of supercritical solution
– – of benzoic acid **166** (1996) 989
– by seeding system
– – of alumina trihydrate **166** (1996) 1009
– – of aluminum hydroxide **166** (1996) 1009
– by sol–gel method
– – of lead zirconate tantalate **167** (1996) 644
– – of lysozyme **168** (1996) 40
– by solvent evaporation
– – of zinc gallium oxide **165** (1996) 183
– – theory of facet formation **165** (1996) 335
– by temperature difference method
– – of indium gallium arsenide **166** (1996) 463
– by top seeded method
– – of lead titanate **166** (1996) 380
– – of lithium lead phosphate **166** (1996) 380
– – of PrYBCO **166** (1996) 804
– – of YBCO **166** (1996) 804
– by top seeded solution
– – of bismuth titanium oxide **167** (1996) 638
– by traveling heater method
– – of cadmium telluride **166** (1996) 245
– – of mercury cadmium telluride **166** (1996) 745
– by vapor diffusion
– – of biological macromolecules **168** (1996) 50
– – of proteins **168** (1996) 170
– – of ribosomes **168** (1996) 308
– theory of supersaturation **163** (1996) 318
Statistical mechanics, molecular theory
– of ice **169** (1996) 393, 587
– of inhomogeneous cell model **166** (1996) 112, 117
– of YBCO **169** (1996) 79
Stefan problem or moving boundary problem
– of binary melt **162** (1996) 182
– of crystal pulling **166** (1996) 458
– of dendritic growth **167** (1996) 383, 777
– of dynamic contact angle **163** (1996) 329
– of fluorides **169** (1996) 161
– of nematic-isotropic interface **166** (1996) 222
– of silicon **169** (1996) 269
Superconductivity materials, high T_c
– bulk
– – of BSCCO **166** (1996) 281, 820, 863, 867; **169** (1996) 405
– – of praseodymium cerium copper oxide **163** (1996) 369
– – of PrYBCO **166** (1996) 804
– – of TLSBCCO **167** (1996) 93

– – of 2212 type **167** (1996) 102
– – of YBCO **162** (1996) 48; **165** (1996) 42, 198; **166** (1996) 804, 810, 816; **167** (1996) 102, 566; **169** (1996) 79
– film
– – of BSCCO **163** (1996) 100; **167** (1996) 570
– – of BSCO **163** (1996) 100
– – of YBCO **166** (1996) 832, 836, 841, 848, 854; **169** (1996) 463, 715; **170** (1997) 242
Superlattices, multilayers
– of HTSC **167** (1996) 93
– of iron/iridium **167** (1996) 143
– of oxides **162** (1996) 147
– of platinum/cobalt **169** (1996) 83
– of silicon germanium/silicon **167** (1996) 502
– of III–V compounds **163** (1996) 226; **164** (1996) 34, 263, 271, 302, 327, 442; **170** (1997) 621, 665, 732, 748
– of II–VI compounds **161** (1996) 234; **170** (1997) 480
Surface energy, determination
– of barium borate melt **165** (1996) 413
– of fluorapatite **163** (1996) 295, 304
– of hydroxyapatite **163** (1996) 304
– of microsphere **165** (1996) 191
– of potassium dihydrogen phosphate **166** (1996) 162
Surface morphology
– of aluminum nitride **170** (1997) 329
– of calcium fluoride **163** (1996) 31
– of gallium arsenide **163** (1996) 171; **164** (1996) 51, 71, 88, 125
– of gallium nitride **170** (1997) 312, 316, 329
– of germanium **163** (1996) 48
– of helium 4 crystals **166** (1996) 55
– of indium antimonide **164** (1996) 125
– of indium arsenide **164** (1996) 125
– of indium gallium arsenide **164** (1996) 51; **170** (1997) 566
– of indium phosphide **164** (1996) 84, 409
– of lithium niobate **166** (1996) 1
– of mercury cadmium telluride **165** (1996) 19
– of proteins by liquid phase epitaxy **168** (1996) 198
– of silicon germanium **164** (1996) 40
– of silicon observed by high temperature **166** (1996) 314
– of Thaumatin **168** (1996) 63
– of YBCO **165** (1996) 42
Surface structure
– of cadmium telluride **161** (1996) 12, 195
– of calcium fluoride **166** (1996) 61
– of canavalin protein **166** (1996) 893
– of carbon nanotubes **166** (1996) 888
– of gallium arsenide **163** (1996) 54, 67, 113, 180; **166** (1996) 72; **170** (1997) 127, 225
– of gallium indium phosphide **170** (1997) 127, 225, 257
– of gallium nitride **164** (1996) 149
– of gallium nitride phosphide **164** (1996) 180
– of gallium phosphide **170** (1997) 225
– of ice **163** (1996) 455
– of ice–vapor interface **169** (1996) 393
– of indium arsenide **164** (1996) 125; **170** (1997) 225
– of indium gallium arsenide **162** (1996) 7; **170** (1997) 225
– of indium phosphide **170** (1997) 225
– of mercury cadmium telluride **161** (1996) 195
– of molecular beam epitaxy **163** (1996) 22
– of n-alkanes **166** (1996) 67
– of replicated substrate surface **163** (1996) 339
– of rutile **166** (1996) 763; **169** (1996) 309; **170** (1997) 803
– of silicon **163** (1996) 78; **166** (1996) 617
– of III–V surfaces **170** (1997) 230
– of zinc selenide **161** (1996) 45
– theory of roughening **163** (1996) 8
Synthesis
– of hydrated europium cuprate **169** (1996) 190

Thin film growth, epitaxy
– by atomic layer epitaxy
– – of calcium fluoride **163** (1996) 31
– – of gallium arsenide **163** (1996) 180; **164** (1996) 28; **170** (1997) 574
– – of indium arsenide **170** (1997) 574
– – of indium phosphide **170** (1997) 215
– – of silicon **169** (1996) 672
– – of titanium oxide **169** (1996) 496
– by chemical beam epitaxy
– – of aluminum antimonide **164** (1996) 491
– – of aluminum arsenide **164** (1996) 454
– – of aluminum nitride **164** (1996) 143
– – of diamond **164** (1996) 208
– – of gallium aluminum arsenide **164** (1996) 1, 371, 485
– – of gallium antimonide **164** (1996) 491
– – of gallium arsenide **163** (1996) 187; **164** (1996) 1, 22, 51, 66, 71, 112, 125, 271, 356, 371, 383, 485; **170** (1997) 752
– – of gallium nitride **164** (1996) 143
– – of gallium phosphide **164** (1996) 112, 271
– – of indium arsenide **164** (1996) 66, 125, 345
– – of indium gallium arsenide **164** (1996) 51, 122, 263, 327, 356, 371, 377, 415, 442, 454, 470, 476, 485; **170** (1997) 650
– – of indium gallium arsenide phosphide **164** (1996) 122
– – of indium gallium phosphide **164** (1996) 1, 470; **170** (1997) 16
– – of indium nitride **164** (1996) 143
– – of indium phosphide **164** (1996) 66, 104, 112, 263, 271, 308, 327, 430, 442, 454, 465, 470, 476; **170** (1997) 16, 650
– – of zinc selenide **164** (1996) 190
– – of zinc sulphide **164** (1996) 202
– by direct current biased sputter deposition
– – of cobalt **166** (1996) 792
– by gas source molecular beam epitaxy
– – of aluminum nitride **164** (1996) 132, 154, 159
– – of aluminum phosphide antimonide **162** (1996) 121
– – of dysprosium phosphide **164** (1996) 285
– – of gallium aluminum nitride **164** (1996) 154
– – of gallium arsenide **164** (1996) 77
– – of gallium arsenide phosphide **164** (1996) 77
– – of gallium indium arsenide **164** (1996) 281, 460
– – of gallium nitride **164** (1996) 154, 159
– – of gallium phosphide **164** (1996) 256; **165** (1996) 210
– – of gallium phosphide antimonide **162** (1996) 121
– – of germanium **163** (1996) 105

– – of indium aluminum arsenide **164** (1996) 460
– – of indium aluminum phosphide **164** (1996) 47
– – of indium gallium phosphide **164** (1996) 47; **165** (1996) 210
– – of indium phosphide **164** (1996) 84, 281, 460
– – of silicon **163** (1996) 105; **164** (1996) 40, 214, 223, 241
– – of silicon carbide **164** (1996) 132
– – of silicon germanium **164** (1996) 40, 214, 223, 241
– – of zinc cadmium selenide **164** (1996) 196
– – of zinc cadmium sulphide selenide **164** (1996) 196
– – of zinc selenide **164** (1996) 196
– by hot wall epitaxy
– – of bismuth telluride **167** (1996) 122
– – of copper indium selenide **167** (1996) 769
– – of zinc selenide **167** (1996) 473
– by ion beam sputter deposition
– – of rutile **166** (1996) 779
– by liquid phase electroepitaxy
– – of III–V compounds **167** (1996) 305
– by liquid phase epitaxy
– – of BSCCO **163** (1996) 100; **166** (1996) 867
– – of BSCO **163** (1996) 100
– – of cyamine dye **166** (1996) 930
– – of gallium aluminum arsenide **162** (1996) 43
– – of gallium arsenide **165** (1996) 482; **169** (1996) 181
– – of garnets **166** (1996) 774
– – of indium gallium arsenide **169** (1996) 613
– – of indium gallium arsenide phosphide **166** (1996) 334
– – of lead telluride **163** (1996) 353
– – of lithium niobate **166** (1996) 489, 493; **169** (1996) 94
– – of lithium tantalate **166** (1996) 489
– – of mercury cadmium telluride **161** (1996) 64; **162** (1996) 126; **163** (1996) 348; **165** (1996) 19; **169** (1996) 480
– – of neodymium doped aluminum gallium arsenide **163** (1996) 343
– – of silicon **163** (1996) 470; **166** (1996) 694, 727; **167** (1996) 516
– – of silicon carbide **166** (1996) 607
– – of silicon dioxide **166** (1996) 727
– – of silicon germanium **166** (1996) 727
– – of III–V compounds **167** (1996) 74
– – of YBCO **166** (1996) 836, 854; **167** (1996) 566; **169** (1996) 715
– by magnetron sputtering
– – of barium titanate **167** (1996) 157
– – of zinc sulphide **167** (1996) 157
– by metalorganic molecular beam epitaxy
– – of aluminum gallium arsenide **164** (1996) 291
– – of aluminum gallium phosphide **164** (1996) 248
– – of gallium aluminum arsenide **170** (1997) 674
– – of gallium antimonide **164** (1996) 117
– – of gallium arsenide **164** (1996) 58, 291, 296, 396; **170** (1997) 297, 674
– – of gallium indium arsenide **170** (1997) 161, 456
– – of gallium indium arsenide phosphide **164** (1996) 16, 314, 321, 362, 389, 402, 449
– – of gallium indium phosphide **164** (1996) 34, 339
– – of gallium nitride phosphide **164** (1996) 180; **170** (1997) 161
– – of gallium phosphide **164** (1996) 34, 314, 321, 420
– – of indium arsenide **164** (1996) 334
– – of indium arsenide phosphide **164** (1996) 434
– – of indium gallium arsenide **170** (1997) 177, 287
– – of indium phosphide **164** (1996) 339, 362, 389, 402, 409, 425; **170** (1997) 161
– – of zinc cadmium selenide **164** (1996) 196
– – of zinc cadmium sulphide selenide **164** (1996) 196
– – of zinc selenide **164** (1996) 196
– – theory
– – – of selective growth **164** (1996) 302
– – – of thermodynamics **170** (1997) 306
– by molecular beam epitaxy
– – of aluminum antimonide **165** (1996) 8
– – of aluminum arsenide antimonide **165** (1996) 156
– – of aluminum gallium arsenide **163** (1996) 149; **167** (1996) 406; **169** (1996) 637
– – of aluminum nitride **163** (1996) 93
– – of barium fluoride **167** (1996) 111
– – of cadmium telluride **161** (1996) 86, 128, 134, 214
– – of calcium chloride **169** (1996) 40
– – of calcium fluoride **163** (1996) 31; **166** (1996) 61; **167** (1996) 111
– – of cerium **169** (1996) 299
– – of cobalt silicate **165** (1996) 61
– – of gallium aluminum arsenide **162** (1996) 31
– – of gallium antimonide **165** (1996) 8, 156; **169** (1996) 450
– – of gallium arsenide **162** (1996) 31; **163** (1996) 60, 149; **164** (1996) 88, 185; **165** (1996) 15, 156, 345; **166** (1996) 72, 217; **167** (1996) 440; **169** (1996) 223, 607, 649
– – of gallium arsenide nitride **164** (1996) 175
– – of gallium arsenide phosphide **164** (1996) 92
– – of gallium indium arsenide **164** (1996) 276
– – of gallium indium phosphide **164** (1996) 276
– – of gallium nitride **164** (1996) 149, 167, 175, 185; **166** (1996) 597, 601
– – of gallium phosphide **162** (1996) 1; **164** (1996) 92
– – of gallium selenide **162** (1996) 135
– – of indium aluminum arsenide **167** (1996) 468; **169** (1996) 435
– – of indium arsenide **163** (1996) 60, 143, 149; **167** (1996) 440
– – of indium gallium arsenide **163** (1996) 149; **167** (1996) 406, 468; **169** (1996) 209, 424, 435, 637, 649
– – of indium gallium arsenide phosphide **167** (1996) 446
– – of indium phosphide **162** (1996) 1; **167** (1996) 446, 468; **169** (1996) 435
– – of mercury cadmium telluride **161** (1996) 64
– – of nickel aluminium **169** (1996) 201
– – of silicon **163** (1996) 39; **164** (1996) 235; **165** (1996) 61; **166** (1996) 314; **169** (1996) 665, 681
– – of silicon carbide **163** (1996) 93
– – of silicon germanium **165** (1996) 61; **167** (1996) 495, 502, 508
– – theory
– – – of binary growth **163** (1996) 135
– – – of excess liquid phase formation **162** (1996) 15
– – – of facet formation **164** (1996) 235

– – – of lateral thickness **169** (1996) 175
– – – of silicon carbide growth **169** (1996) 491
– – – of thermal etching of III–V compounds **166** (1996) 167
– by molecular layer epitaxy
– – theory of dopant and defect incorporation in
– – – mercury cadmium telluride **161** (1996) 64
– by pulsed electron-beam evaporation
– – of TBCO **166** (1996) 848
– by radio frequency sputtering
– – of mercury cadmium telluride **161** (1996) 201
– by solid source molecular beam epitaxy
– – of dysprosium phosphide **164** (1996) 285
– by spray pyrolysis
– – of nickel oxide **167** (1996) 656
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of aluminum gallium antimonide **169** (1996) 417
– – – of aluminum gallium arsenide **169** (1996) 227
– – – of aluminum gallium arsenide antimonide **169** (1996) 417
– – – of cadmium sulphide **170** (1997) 23
– – – of cadmium telluride **161** (1996) 195
– – – of diamond **165** (1996) 387; **166** (1996) 622; **169** (1996) 722
– – – of gallium antimonide **169** (1996) 417
– – – of gallium arsenide **169** (1996) 227, 429, 629
– – – of gallium nitride **169** (1996) 185
– – – of in situ monitoring **169** (1996) 443
– – – of indium gallium arsenide **169** (1996) 429
– – – of indium phosphide **169** (1996) 621, 625
– – – of lead sulphide **170** (1997) 23
– – – of magnesium oxide **169** (1996) 474
– – – of magnesium zinc selenide sulphide **169** (1996) 293
– – – of mercury cadmium telluride **161** (1996) 195
– – – of poly-silicon **166** (1996) 689
– – – of silicon **166** (1996) 329; **169** (1996) 61
– – – of silicon carbide **167** (1996) 607
– – – of silicon germanium **169** (1996) 261
– – – of tetrathiafulvalene–tetracyanoquinodimethane **166** (1996) 798
– – – of zinc cadmium telluride **169** (1996) 27
– – – of zinc sulphide **169** (1996) 33
– – – of zirconium selenide **169** (1996) 243
– – – theory
– – – – of flow fields in epitaxial growth **170** (1997) 61
– – – – of nucleation **162** (1996) 113
– – through evaporation and condensation
– – – of germanium **163** (1996) 48
– – – of oxides **162** (1996) 147
– – – of silicon **163** (1996) 48
– – – of strontium vanadate **162** (1996) 154
– – through metalorganic chemical vapor deposition
– – – of aluminum antimonide **170** (1997) 772
– – – of aluminum arsenide **170** (1997) 246, 404, 719
– – – of aluminum gallium antimonide **167** (1996) 415; **170** (1997) 725
– – – of aluminum gallium arsenide **163** (1996) 212; **165** (1996) 1; **167** (1996) 406, 421, 434, 452; **170** (1997) 83, 88, 92, 390, 394, 404, 408, 447, 585, 600, 605, 621, 665, 679, 689, 700, 757
– – – of aluminum gallium arsenide antimonide **170** (1997) 725
– – – of aluminum nitride **167** (1996) 1; **170** (1997) 139, 329, 335
– – – of antimony telluride **170** (1997) 187
– – – of bismuth telluride **170** (1997) 187
– – – of cadmium selenide **166** (1996) 558
– – – of cadmium sulphide **167** (1996) 133; **170** (1997) 23, 528
– – – of cadmium telluride **165** (1996) 227; **167** (1996) 488; **170** (1997) 193, 553
– – – of cadmium zinc selenide **170** (1997) 497
– – – of cerium oxide **170** (1997) 799
– – – of gallium aluminum nitride **163** (1996) 86
– – – of gallium antimonide **166** (1996) 590; **167** (1996) 415; **170** (1997) 55, 777, 783, 788, 794
– – – of gallium arsenide **163** (1996) 54, 67, 171, 195, 203, 212; **164** (1996) 396; **165** (1996) 1; **166** (1996) 309; **167** (1996) 17, 421, 429, 434, 543, 557; **170** (1997) 1, 39, 83, 88, 92, 97, 127, 203, 246, 270, 292, 372, 377, 390, 408, 424, 428, 433, 438, 442, 574, 579, 600, 605, 665, 689, 700, 719, 762, 772
– – – of gallium arsenide phosphide **170** (1997) 585, 748
– – – of gallium indium arsenide **162** (1996) 7; **167** (1996) 8, 406; **170** (1997) 88, 103, 155
– – – of gallium indium arsenide phosphide **170** (1997) 97
– – – of gallium indium nitride **163** (1996) 86; **170** (1997) 321, 344, 349
– – – of gallium indium phosphide **163** (1996) 128; **165** (1996) 215, 222; **170** (1997) 88, 97, 127, 203, 219
– – – of gallium nitride **163** (1996) 86; **166** (1996) 601; **167** (1996) 1; **170** (1997) 11, 139, 312, 316, 321, 325, 329, 335, 340, 344, 367
– – – of gallium phosphide **163** (1996) 165; **166** (1996) 309
– – – of gallium phosphide nitride **170** (1997) 353
– – – of germanium **170** (1997) 1
– – – of indium aluminum arsenide **162** (1996) 25; **170** (1997) 590, 595, 669
– – – of indium arsenide **170** (1997) 203, 558, 574, 772, 783, 788
– – – of indium arsenide phosphide **170** (1997) 122, 616
– – – of indium gallium aluminum arsenide **170** (1997) 399, 738
– – – of indium gallium aluminum phosphide **170** (1997) 92, 103, 394, 399, 418, 595
– – – of indium gallium arsenide **167** (1996) 397; **170** (1997) 83, 92, 117, 127, 132, 167, 377, 390, 394, 438, 451, 568, 579, 590, 616, 639, 645, 661, 669, 695, 700, 705, 743, 748
– – – of indium gallium arsenide phosphide **167** (1996) 525; **170** (1997) 109, 113, 117, 122, 167, 237, 281, 383, 626, 634, 645, 661, 732, 738, 757
– – – of indium gallium phosphide **170** (1997) 39, 122, 257, 263, 377, 383, 413, 428, 442, 710
– – – of indium nitride **170** (1997) 139, 301
– – – of indium phosphide **166** (1996) 309, 590, 628; **167** (1996) 8;**170** (1997) 39, 83, 92, 97, 103, 109, 113, 127, 132, 173, 215, 251, 301, 424, 433, 451, 590, 611, 626, 639, 645, 655, 661, 685, 695, 715
– – – of indium phosphide antimonide **170** (1997) 772, 783

– – – of iron sulphide **170** (1997) 808
– – – of lead sulphide **170** (1997) 23
– – – of lithium niobate **166** (1996) 1
– – – of magnesium sulphide **170** (1997) 480, 528
– – – of mercury cadmium telluride **165** (1996) 227; **166** (1996) 612; **170** (1997) 542
– – – of rutile **166** (1996) 763; **170** (1997) 803
– – – of silicon **166** (1996) 1
– – – of yttrium barium cuprates **166** (1996) 841; **170** (1997) 224
– – – of zinc arsenide **170** (1997) 813
– – – of zinc cadmium selenide **170** (1997) 461
– – – of zinc iron selenide **170** (1997) 523
– – – of zinc magnesium sulphide selenide **170** (1997) 30, 461
– – – of zinc manganese telluride **170** (1997) 549
– – – of zinc selenide **165** (1996) 25; **166** (1996) 558, 590; **170** (1997) 144, 188, 461, 467, 472, 480, 485, 491, 503, 507, 510, 518, 533, 537
– – – of zinc selenide telluride **170** (1997) 514, 518
– – – of zinc sulphide **166** (1996) 558; **170** (1997) 476
– – – of zinc sulphide selenide **170** (1997) 461, 767
– – – of zinc telluride **165** (1996) 203, 227; **166** (1996) 590; **170** (1997) 549
– – – theory **163** (1996) 54
– – – – of compositional uniformity **167** (1996) 525
– – – – of convection **170** (1997) 72
– – – – of gas flow **170** (1997) 77
– – – – of heat transfer **170** (1997) 66
– – – – of thermal decomposition **170** (1997) 485
– – through microwave plasma chemical vapor deposition
– – – of aluminum nitride **163** (1996) 232
– – through pulsed laser deposition
– – – of barium sodium niobate **167** (1996) 378
Transistors, see Device characterization

Vapor growth technique
– by aerosol formation and reaction
– – of gallium arsenide **169** (1996) 13
– by chemical transport
– – of beta-quartz **162** (1996) 142
– – of cadmium telluride **161** (1996) 164
– – of copper indium diselenide **169** (1996) 287
– – of diamond **162** (1996) 73
– – of gallium nitride **169** (1996) 689
– – of indium oxide **165** (1996) 258
– – of silicon **169** (1996) 61
– – of silicon carbide **169** (1996) 485
– – of tin oxide **165** (1996) 258
– by chemical vapor deposition
– – of transition metal phosphide **166** (1996) 99
– by close space sublimation
– – of cadmium sulphide **161** (1996) 159
– – of cadmium telluride **161** (1996) 159
– by evaporation and condensation
– – of alpha-mercuric iodide **163** (1996) 411
– – of beta-Ca_2SiO_4 **169** (1996) 376
– – of cadmium selenide **161** (1996) 277
– – of cadmium sulphide **161** (1996) 277
– – of cadmium sulphide selenide **161** (1996) 277
– – of cadmium telluride **161** (1996) 34
– – of cadmium zinc telluride **169** (1996) 20
– – of calcium carbonate **167** (1996) 260
– – of carbon **167** (1996) 580
– – of cerium dioxide **162** (1996) 147
– – of copper chloride **167** (1996) 612
– – of fullerene **166** (1996) 883
– – of ice **169** (1996) 795
– – of lead telluride **165** (1996) 70
– – of lithium fluoride **169** (1996) 279
– – of manganese antimonide **166** (1996) 754
– – of mercuric iodide **166** (1996) 354
– – of niobium **166** (1996) 271
– – of silicon carbide **165** (1996) 233; **167** (1996) 586, 596
– – of silicon germanium **169** (1996) 261
– – of silver gallium sulphide **167** (1996) 151
– – of strontium gallium sulphide **167** (1996) 129
– – of yttrium stabilized zirconia **162** (1996) 147
– – of zinc selenide **161** (1996) 51; **165** (1996) 169; **169** (1996) 660
– – of zinc telluride **167** (1996) 534
– – theory
– – – of heat and mass transfer **165** (1996) 323
– – – of coupled step flow **163** (1996) 411
– by halide transport
– – of gallium nitride **167** (1996) 458
– by laser fabrication
– – of nickel chromium silicide **165** (1996) 57
– by physical vapor transport
– – of cadmium sulphide **166** (1996) 731
– – of zinc selenide **166** (1996) 736
– by pulsed laser deposition
– – of lithium niobate/lithium tantalate waveguides **165** (1996) 187
– by sitting drop vapor diffusion method
– – of human estradiol dehydrogenase **168** (1996) 275
– – of proteins **168** (1996) 99
– by vapor reaction
– – of germanium iodide **165** (1996) 245
– theory **169** (1996) 393
– – of diffusion **166** (1996) 739
– – of synthesis from charged clusters **162** (1996) 55
Vapor–liquid–solid growth
– of ice **163** (1996) 420
– of silicon on patterned silicon on insulator **165** (1996) 37
– of water **166** (1996) 124

Wave guides, see Device characterization
Whisker growth
– of alpha-zinc phosphide **166** (1996) 99
– of beta-titanium phosphide **166** (1996) 99
– of BSCCO **167** (1996) 570
– of gallium arsenide **163** (1996) 226
– of indium arsenide **163** (1996) 226
– of silicon **162** (1996) 73

– of silicon carbide **167** (1996) 607
– of tungsten oxide **169** (1996) 727

Yttrium
– stabilized zirconia **162** (1996) 147

Zinc
– cadmium selenide **164** (1996) 196
– magnesium sulphide **164** (1996) 196
– oxide **161** (1996) 190
– selenide **161** (1996) 45, 51, 60, 205; **164** (1996) 190, 196; **165** (1996) 25, 31, 169; **167** (1996) 473
– selenide telluride **161** (1996) 177
– sulphide **164** (1996) 202; **165** (1996) 166
– telluride **161** (1996) 82, 181, 205, 239; **165** (1996) 203; **167** (1996) 534

Zirconium
– borane **165** (1996) 319

Cohesion and Structure, Volume 4

Cohesion and Structure of Surfaces

By **K. Binder, N. Bowker, J.E. Inglesfield and P.J. Rous**

Distributed in Japan by Maruzen Co., Ltd.

During the past fifteen years there has been a dramatic increase in the number of different surfaces whose structures have been determined experimentally. For example, whereas in 1979 there were only 25 recorded adsorption structures, to date there are more than 250. This volume is therefore a timely review of the state-of-the-art in this dynamic field.

Chapter one contains a compilation of the structural data base on surfaces within a series of tables that allows direct comparison of structural parameters for related systems. Experimental structural trends amongst both clean surfaces and adsorbate systems are highlighted and discussed.

The next chapter outlines the successes of local density functional theory in predicting the relaxations and reconstructions of clean metal and semiconductor surfaces, and the behaviour of adsorbates such as hydrogen, oxygen and alkali elements on metal surfaces, thereby explaining some of the experimental trends observed within the database. These *ab initio* density functional calculations are of ground state properties at the absolute zero of temperature.

Chapter three provides an introduction to finite temperature effects in a pedagogical review of current statistical mechanical treatments of phase transitions at surfaces, many of which display the prominent role of fluctuations or non-mean field behaviour.

The final chapter discusses the relationship of the reactivity of a surface to its morphology and composition, which is particularly relevant to a fundamental understanding of catalysis.

Contents: Preface. **Surface Crystallography: The Experimental Data Base** (P.J. Rous). Abstract. Introduction. Metals. Semiconductors. Graphite and diamond surfaces. Compounds. Selected bibliography. Acknowledgements. References. **Theory of Surface Structure and Bonding** (J.E. Inglesfield). Abstract. Introduction. Solving the Schrödinger equation at the surface. Forces and optimization. Clean metal surfaces. Adsorbates on metals. Semiconductor surfaces. Conclusions. Acknowledgements. References. **Phase Transitions at Surfaces** (K. Binder). Abstract. Introduction: surface phase transitions versus transitions in the bulk. Phenomenological theory of phase transitions: a brief review. Surface effects on bulk phase transitions. Discussion. Acknowledgements. References. **Surface Structure and Reactivity** (M. Bowker). Abstract. Introduction. Thermodynamic considerations. Adsorption. Desorption. Surface diffusion. Surface reactions. Structure dependence of reactivity. Modification of surface reactivity: poisoning and promotion. Conclusions. References. **Author index. Subject index.**

©1995 396 pages Hardbound
Price: NLG 285.00 (US$178.25)
ISBN 0-444-89829-8

NORTH-HOLLAND
An imprint of Elsevier Science

TO ORDER
Contact your regular supplier or:

ELSEVIER SCIENCE
Customer Service Department
P.O. Box 945
New York, NY 10159-0945, USA
Fax: +1 212-633-3680
e-mail: usinfo-f@elsevier.com

ELSEVIER SCIENCE
Customer Service Department
P.O. Box 211
1000 AE Amsterdam
The Netherlands
Fax: +31 20 485-3432
e-mail: nlinfo-f@elsevier.nl

ELSEVIER SCIENCE
Customer Service Department
9-15, Higashi-Azabu 1-chome
Minato-ku, Tokyo 106
Japan
Fax: +81 3-5561-5047
e-mail:
fororders-kyf04035@niftyserve.or.jp

No postage will be added to prepaid book orders. Dutch Guilder price(s) quoted applies worldwide US Dollar price(s) quoted may be subject to exchange rate fluctuations. Customers in the European Union should add the appropriate VAT rate applicable in their country to the price(s). In New York State please add applicable sales tax. All prices are subject to change without prior notice.

Dynamical Properties of Solids, Volume 7

Phonon Physics: The Cutting Edge

Edited by **G.K. Horton** and **A.A. Maradudin**

The first two volumes in this series published twenty years ago contained chapters devoted to anharmonic properties of solids, *ab initio* calculations of phonons in metals and insulators, and surface phonons. In the intervening years each of these important areas of lattice dynamics has undergone significant developments. This volume is therefore concerned with reviewing the current status of these areas.

Chapter one deals with the path-integral quantum Monte-Carlo method as a numerical simulation approach and looks at how this has been applied successfully to the determination of low temperature thermodynamic properties of anharmonic crystals and to certain dynamical properties as well. Chapter two is concerned with the calculation of static and dynamic properties of anharmonic crystals in the quantum regime. Chapter three discusses intrinsic anharmonic localized modes that have been intensively studied recently. Two topics, *ab initio* calculations of phonons in metals, and surface phonons are dealt with in the next chapter. The remaining two chapters are devoted to topics that have not been treated in previous volumes. One is phonon transport and the second is phonons in disordered crystals.

The work described in the six chapters of this volume testifies to the continuing vitality of the field of dynamical properties of solids nearly a century after its founding.

Contents: Preface.
1. Path-integral quantum Monte Carlo studies of the vibrational properties of crystals *(A.R. McGurn)*. 2. Lattice dynamical applications of variational effective potentials in the Feynman path-integral formulation of statistical mechanics *(E.R. Cowley, G.K. Horton)*. 3. Unusual anharmonic local mode systems *(A.J. Sievers, J.B. Page)*.
4. Influence of isotopic and substitutional atoms on the propagation of phonons in anisotropic media *(T. Paszkiewicz, M. Wilczyski)*.
5. Phonons in semiconductor alloys *(J.D. Dow et al.)*.
6. Electronic screening in metals: from phonons to plasmons *(A.G. Eguiluz, A.A. Quong)*.
Author index. Subject index.

NORTH-HOLLAND
An imprint of Elsevier Science

1995 544 pages Hardbound
Price: NLG 415.00 (US$259.50)
ISBN 0-444-82262-3

TO ORDER
Contact your regular supplier or:

ELSEVIER SCIENCE
Customer Service Department
P.O. Box 945
New York, NY 10159-0945, USA
Fax: +1 212-633-3680
e-mail: usinfo-f@elsevier.com

ELSEVIER SCIENCE
Customer Service Department
P.O. Box 211
1000 AE Amsterdam
The Netherlands
Fax: +31 20 485-3432
e-mail: nlinfo-f@elsevier.nl

ELSEVIER SCIENCE
Customer Service Department
9-15, Higashi-Azabu 1-chome
Minato-ku, Tokyo 106
Japan
Fax: +81 3-5561-5047
e-mail:
fororders-kyf04035@niftyserve.or.jp

No postage will be added to prepaid book orders. Dutch Guilder price(s) quoted applies worldwide US Dollar price(s) quoted may be subject to exchange rate fluctuations. Customers in the European Union should add the appropriate VAT rate applicable in their country to the price(s). In New York State please add applicable sales tax. All prices are subject to change without prior notice.

LE6

Journal of Crystal Growth

Instructions to Authors (short version)

Submission of papers
Manuscripts (one original + two copies), should be sent to a member of the Editorial Board or preferably to an appropriate subject Associate Editor. News or announcements should be submitted through the Principal Editor; a duplicate should be sent directly to Elsevier Science B.V., address given below.
Original material. Submission of a manuscript implies it is not being simultaneously considered for publication elsewhere and that the authors have obtained the necessary authority for publication.

Types of contributions
Original research papers, Letters to the Editors and Priority communications are welcome. They should contain an Abstract (of up to 200 words) and a Conclusions section, which particularly in the case of theoretical papers translates the results into terms readily accessible to most readers.
As a guideline: *experimental papers* should not be longer than 16 double-spaced typed pages, and 8 figures + tables; for *theoretical papers* a maximum of 20 pages and 10 figures + tables is suggested.
Letters and *Priority communications* should not be longer than 5 double-spaced typed pages, and 3 figures + tables. They will be given priority in both the refereeing and production processes. The faster production schedule may preclude sending proofs of Letters and Priority communcations to authors.

Manuscript preparation
Contributions may be written in English, French or German. They should have an abstract in English. The paper copies of the text should be prepared with double line spacing and wide margins, on numbered sheets.
Structure. Please adhere to the following order of presentation: Article title, Author(s), Affiliation(s), Abstract, PACS codes and keywords, Main text, Acknowledgements, Appendices, References, Figure captions, Tables.
Corresponding author. The name, complete postal address, telephone and fax numbers and the e-mail address of the corresponding author should be given on the first page of the manuscript.
Classification codes/keywords. Please supply one to four classification codes (PACS and/or MSC) and up to six keywords of your own choice that descibe the content of your article in more detail.
References. References to other work should be consecutively numbered in the text using square brackets and listed by number in the Reference list. Please refer to the more detailed instructions for examples.

Illustrations
Illustrations should also be submitted in triplicate: one master set and two sets of copies. The *line drawings* in the master set should be original laser printer or plotter output or drawn in black india ink, with careful lettering, large enough (3–5 mm) to remain legible after reduction for printing. The *photographs* should be originals, with somewhat more contrast than is required in the printed version. They should be unmounted unless part of a composite figure. Any scale markers should be inserted on the photograph itself, not drawn below it.
Colour plates. Figures may be published in colour, if this is judged essential by the Editor. The Publisher and the author will each bear part of the extra costs involved. Further information is available from the Publisher.

After acceptance
Important. When page proofs of the accepted manuscripts are made and sent out to authors, this is in order to check that no undetected errors have arisen in the typesetting (or file conversion) process. At the proof stage only printer's errors may be corrected. No changes in, or additions to, the edited manuscript will be accepted.
Notification. The authors will receive the final answer of acceptance or rejection from the Office of the Principal Editor and will be invited to supply an electronic version of the accepted text, if this is not already available.
Copyright transfer. In the course of the production process you will be asked to transfer the copyright of the article to the Publisher. This transfer will ensure the widest possible dissemination of information.

Electronic manuscripts
The Publisher welcomes the receipt of an electronic version of your accepted manuscript. If there is not already a copy of this (on diskette) with the journal editor at the time the manuscript is being refereed, you will be asked to send a file with the text of the accepted manuscript directly to the Publisher by e-mail or on diskette (allowed formats 3.5″ or 5.25″ MS-DOS, or 3.5″ Macintosh) to the address given below. (When e-mailing a non-ASCII word-processor file, you should encode it, e.g. with UUENCODE or BinHex, so as to retain all formatting codes.) The name and version of the word-processing program and the type of operating system should always be indicated. Please note that no deviations from the version accepted by the Editor of the journal are permissible without the prior and explicit approval by the Editor. Such changes should be clearly indicated on an accompanying printout of the file.

Author benefits
No page charges. Publishing in Journal of Crystal Growth is free.
Free offprints. The corresponding author will receive 50 offprints free of charge. An offprint order form will be supplied by the Publisher for ordering any additional paid offprints.
Discount. Contributors to Elsevier Science journals are entitled to a 30% discount on all Elsevier Science books.

Further information (after acceptance)

Elsevier Science B.V., J. Crystal Growth
Issue Management Physics
and Materials Science
P.O. Box 2759, 1000 CT Amsterdam
The Netherlands
Fax: +31 20 485 2319/+31 20 485 2704
E-mail: matsci-de-f@elsevier.nl

North-Holland, an imprint of Elsevier Science

JOURNAL OF
CRYSTAL GROWTH

Abstracted/Indexed in: Aluminium Industry Abstracts; Chemical Abstracts; Current Contents: Physical, Chemical and Earth Sciences; EI Compendex Plus; Engineered Materials Abstracts; Engineering Index; INSPEC; Metals Abstracts

CONTENTS

Author index to volumes 161–170 837

Subject index to volumes 161–170 896

0022-0248(1997)161/170;1-X